

FIG._4-1

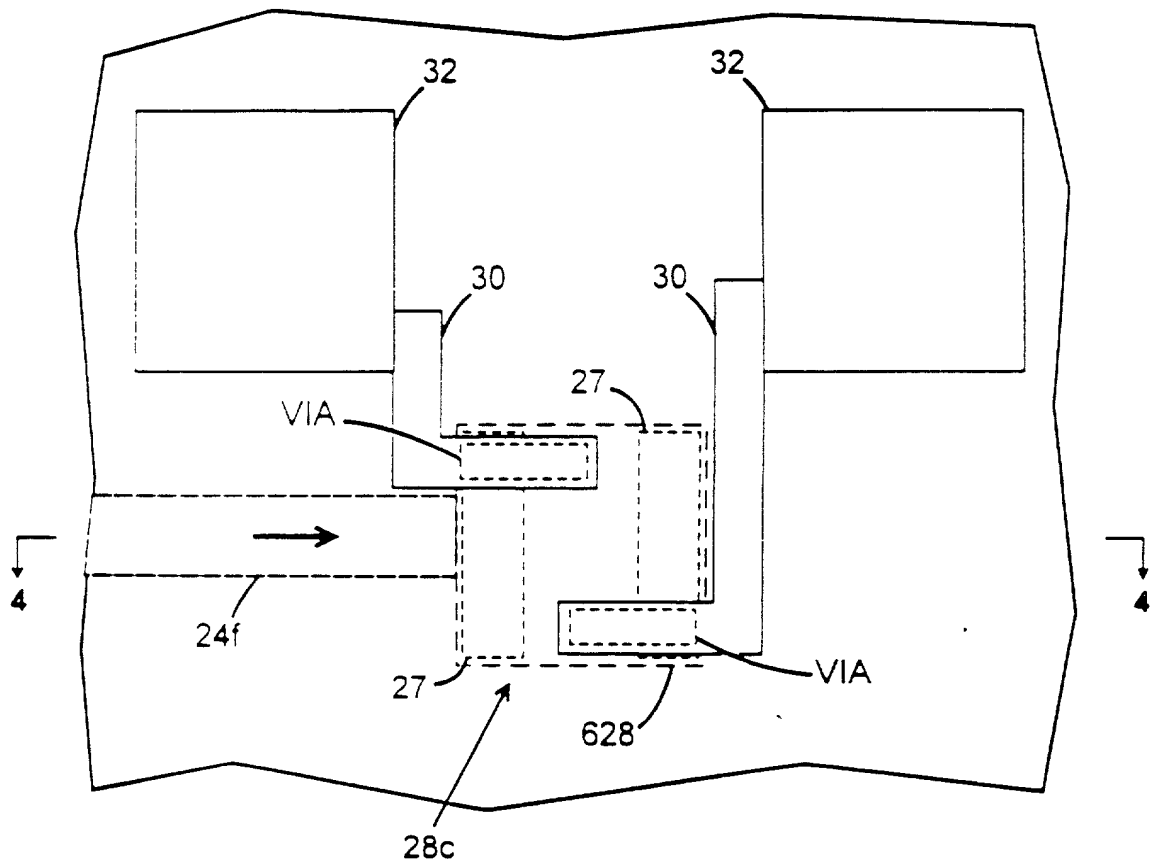
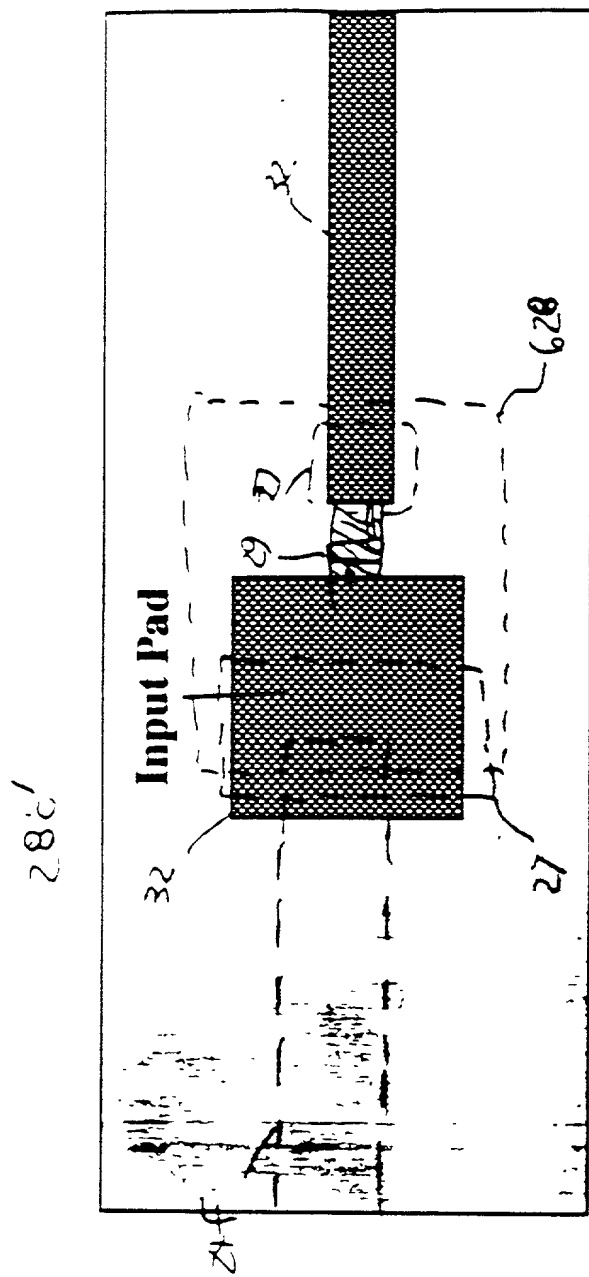
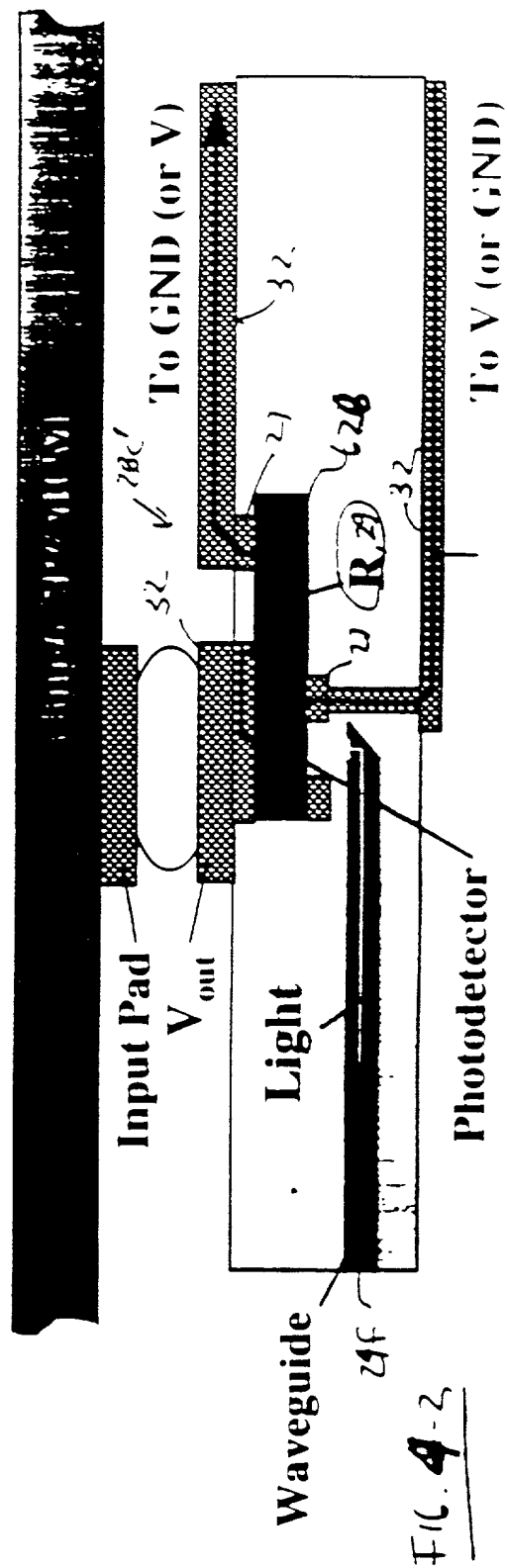


FIG._5-1



F16.5-2



File 4-2

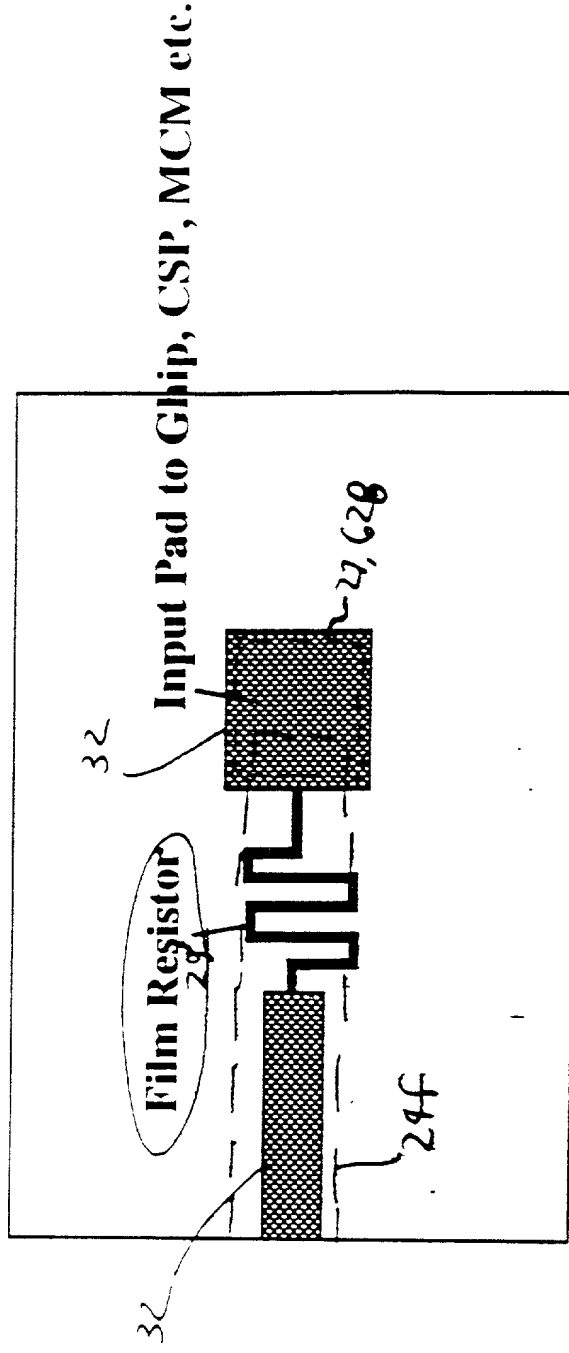


FIG. 5-3

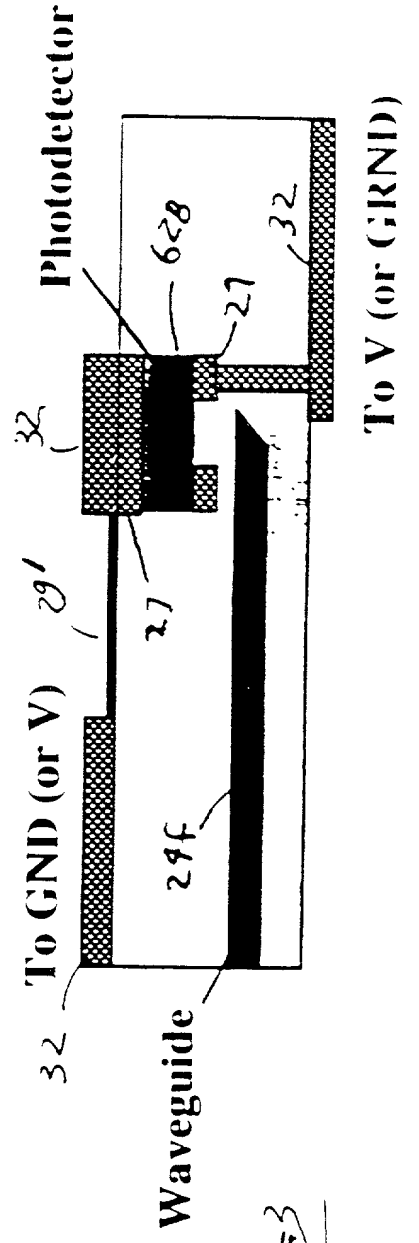


FIG. 4-3

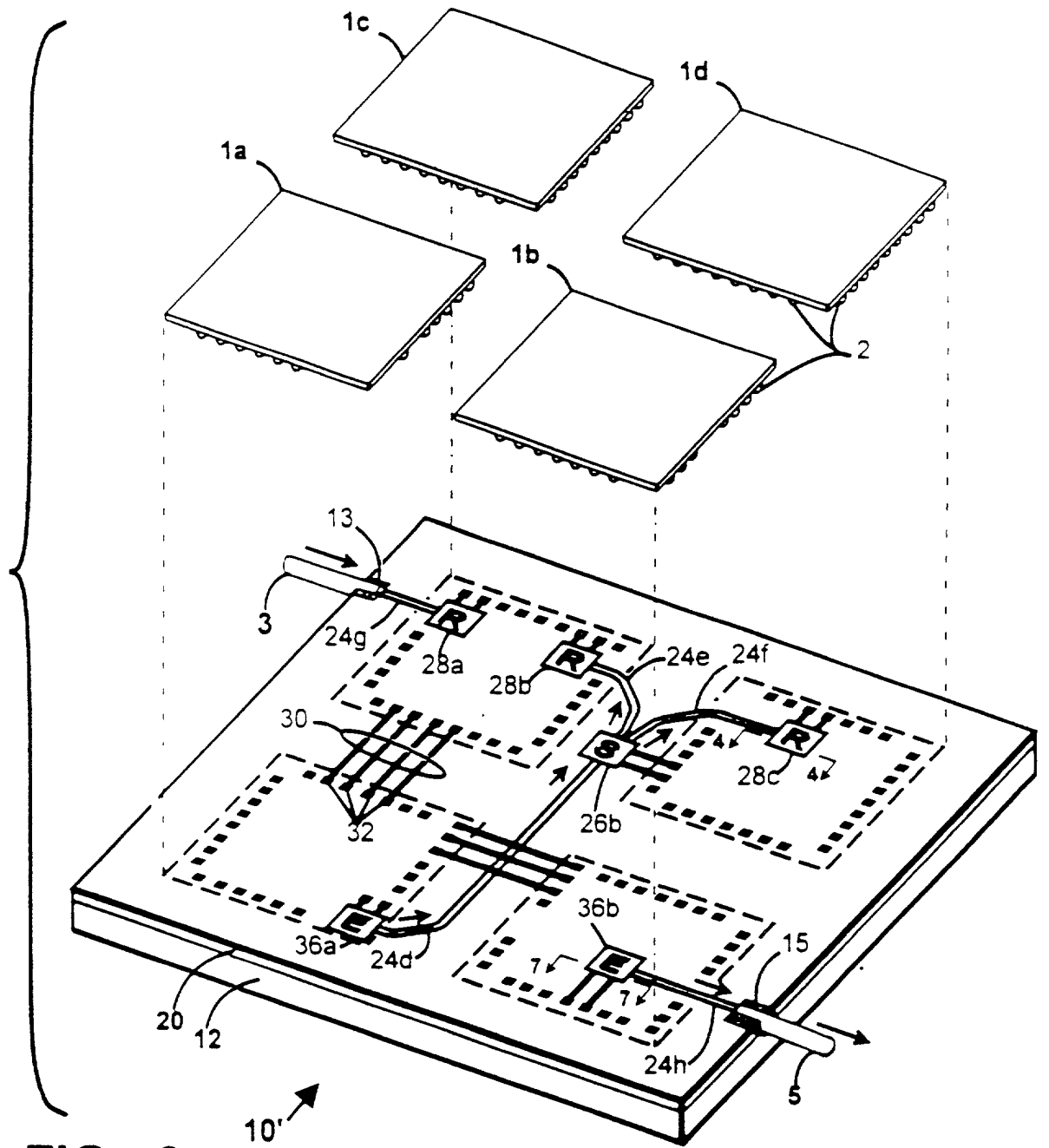


FIG. 6

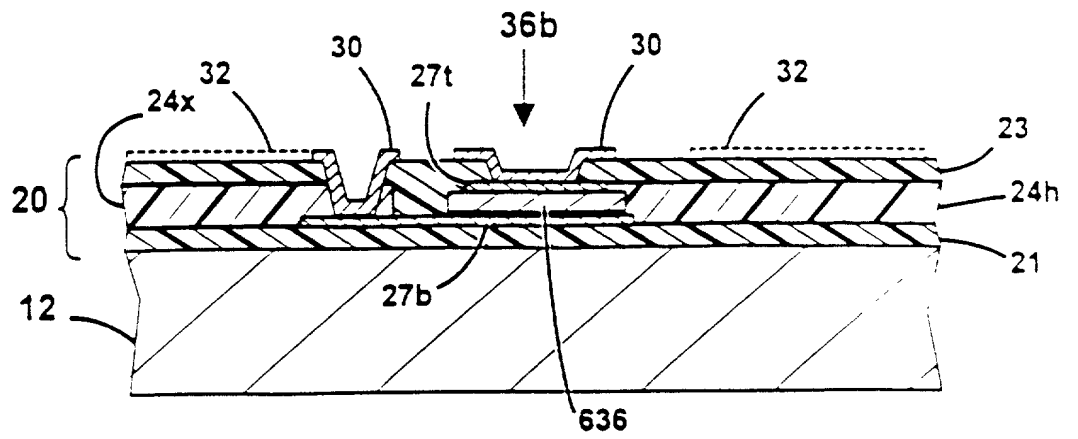


FIG. 7

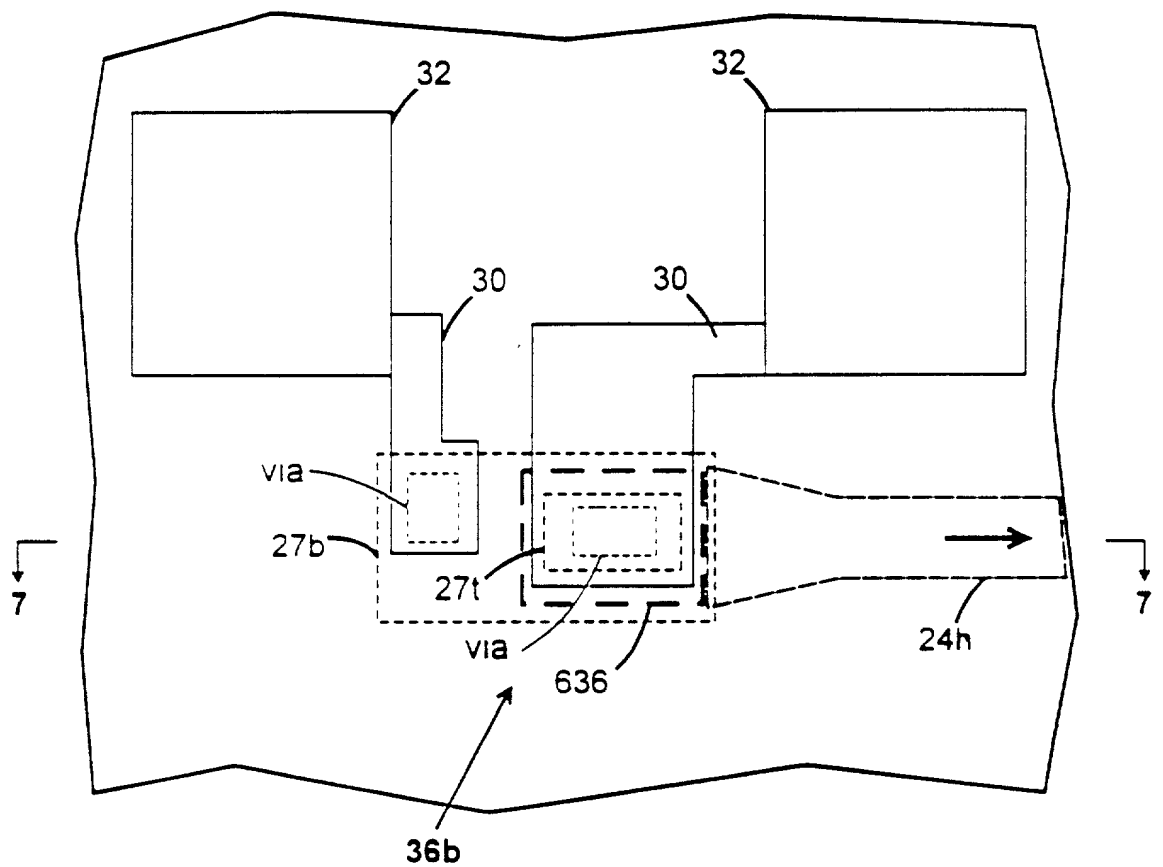


FIG. 8

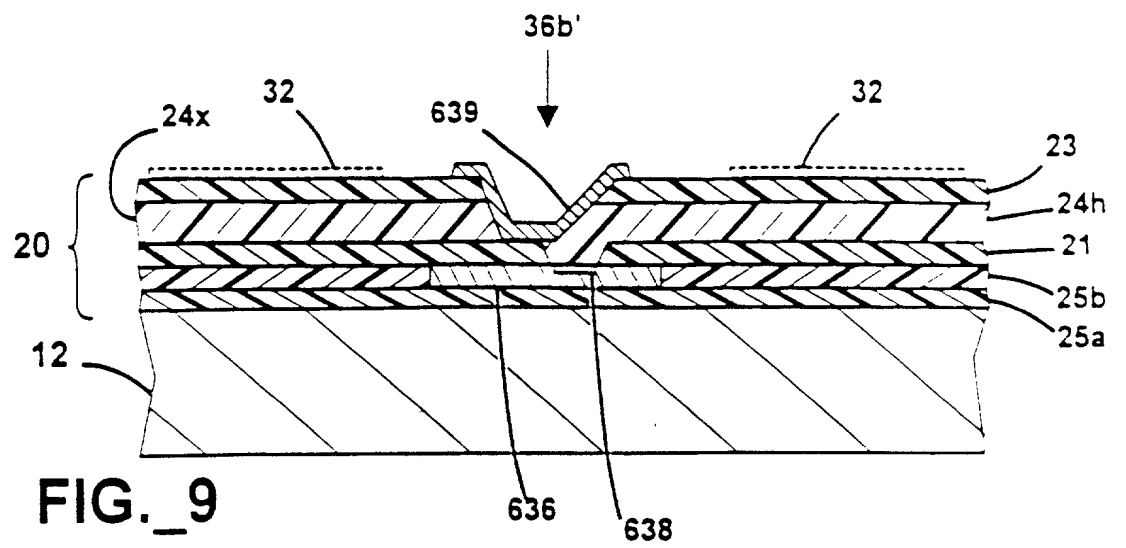


FIG. 9

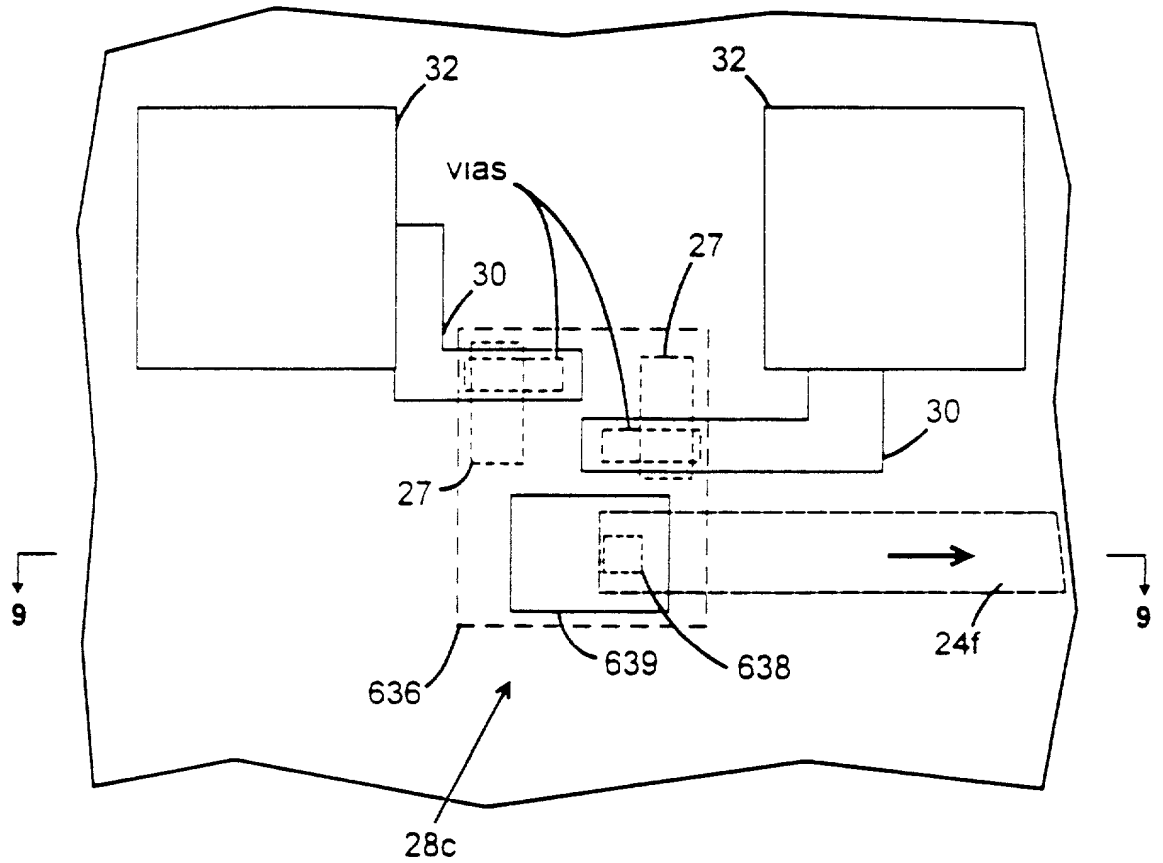


FIG. 10

FIG._11

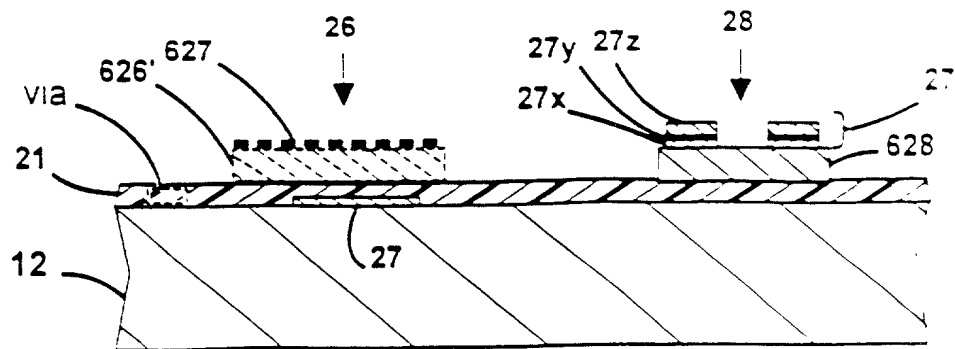


FIG._12

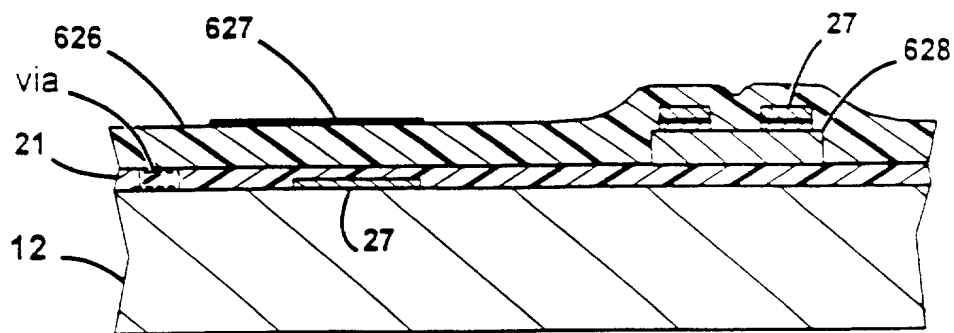


FIG._13

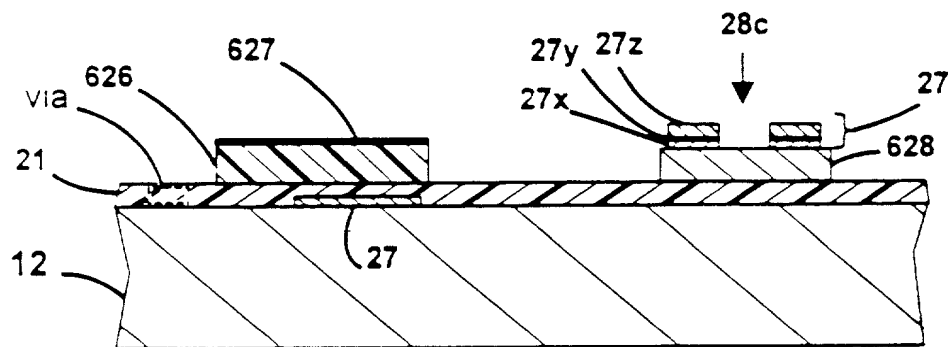
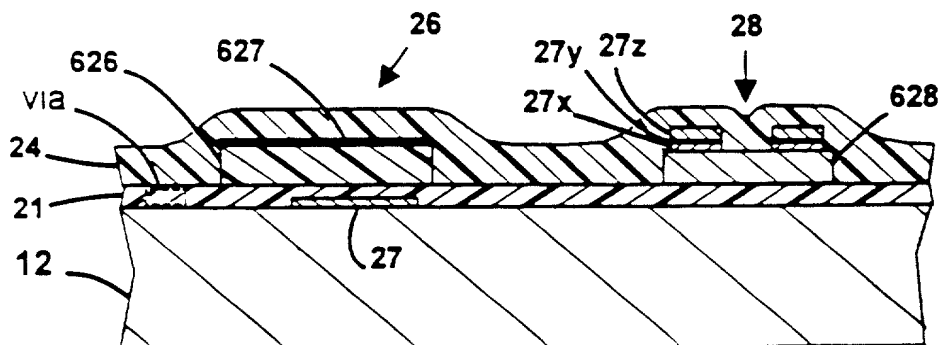


FIG._14



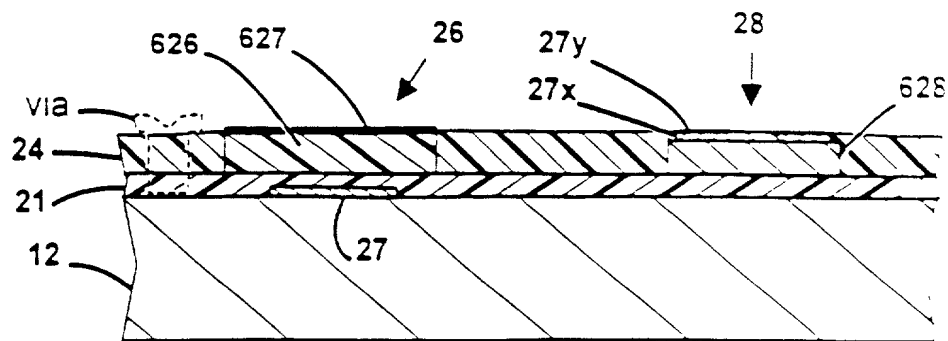


FIG._15

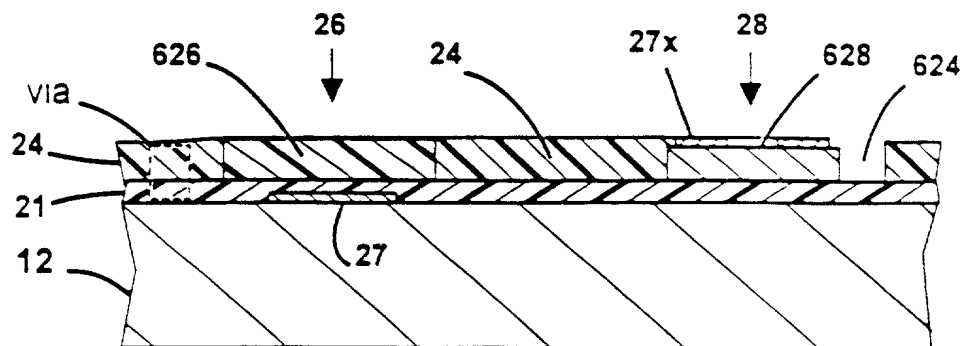


FIG._16

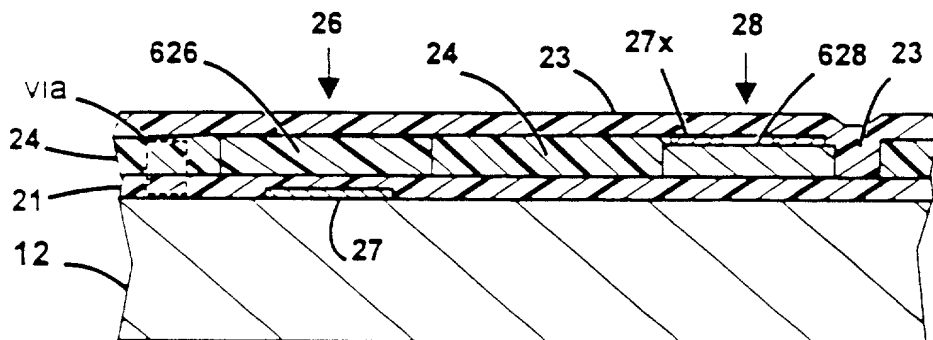


FIG._17

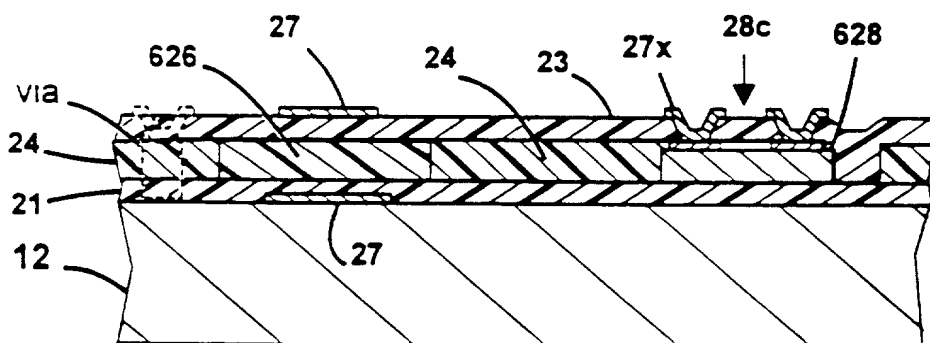


FIG._18

FIG. 20

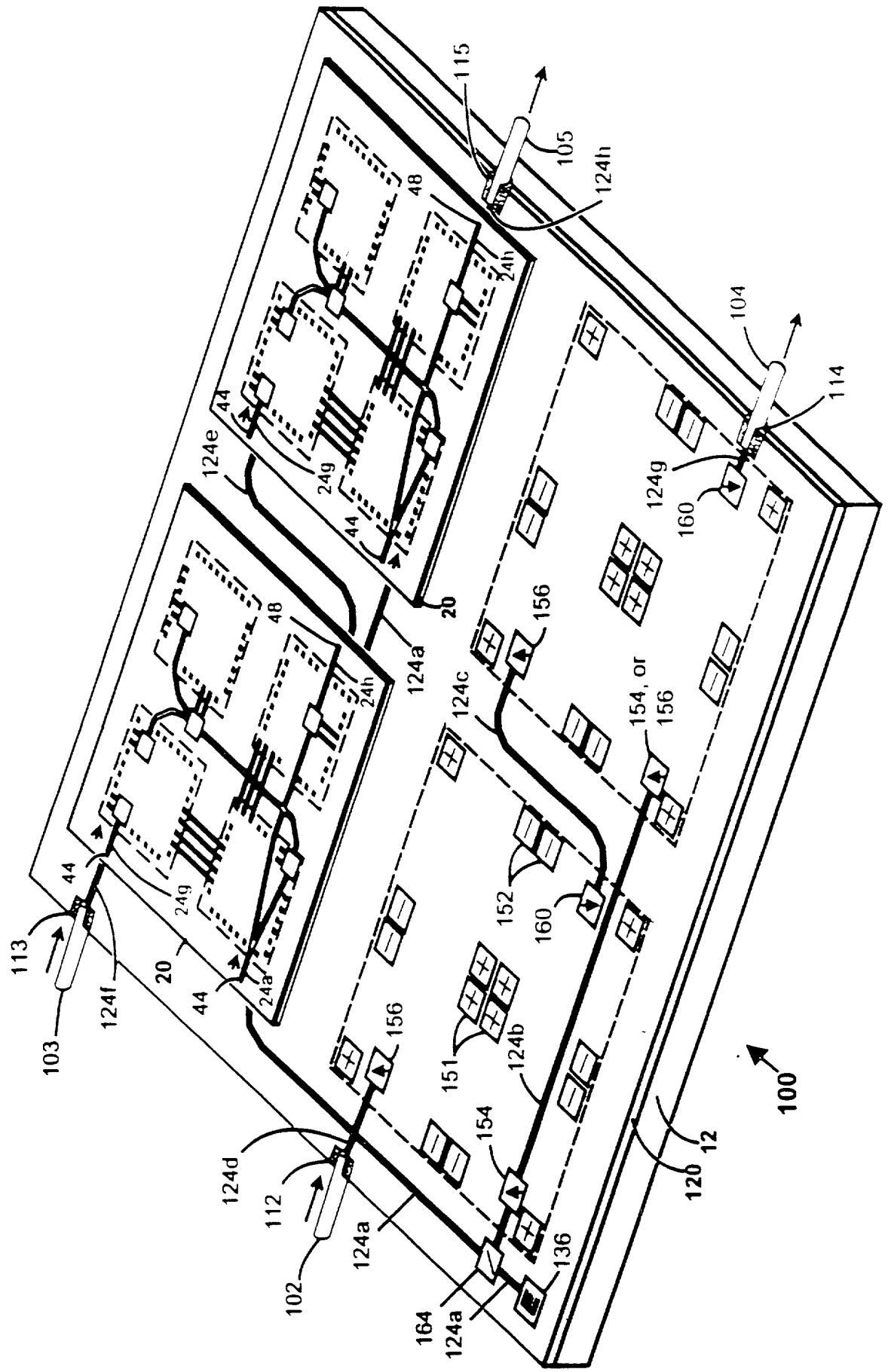


FIG. 21

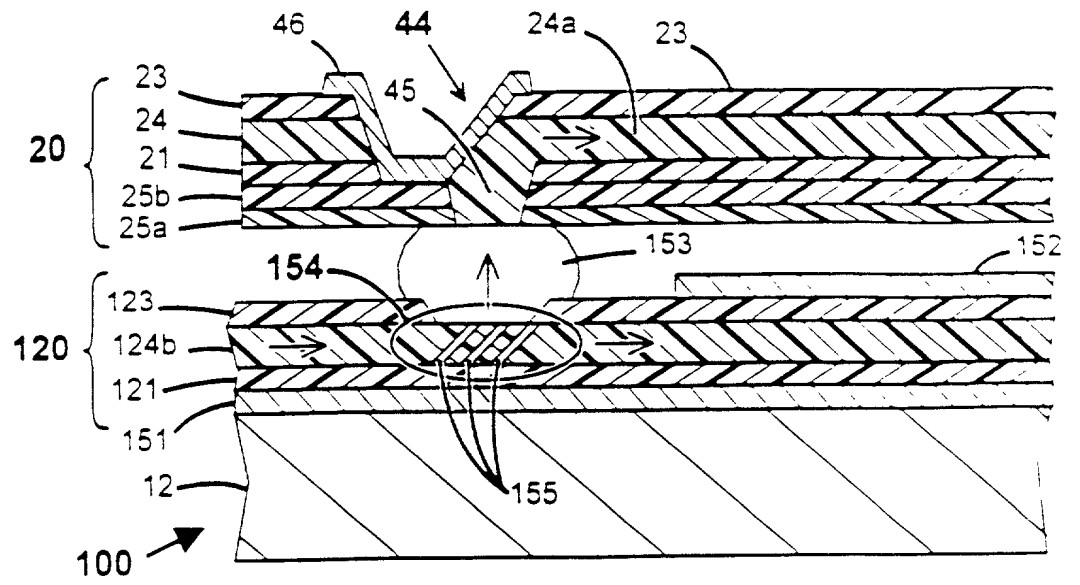


FIG. 22

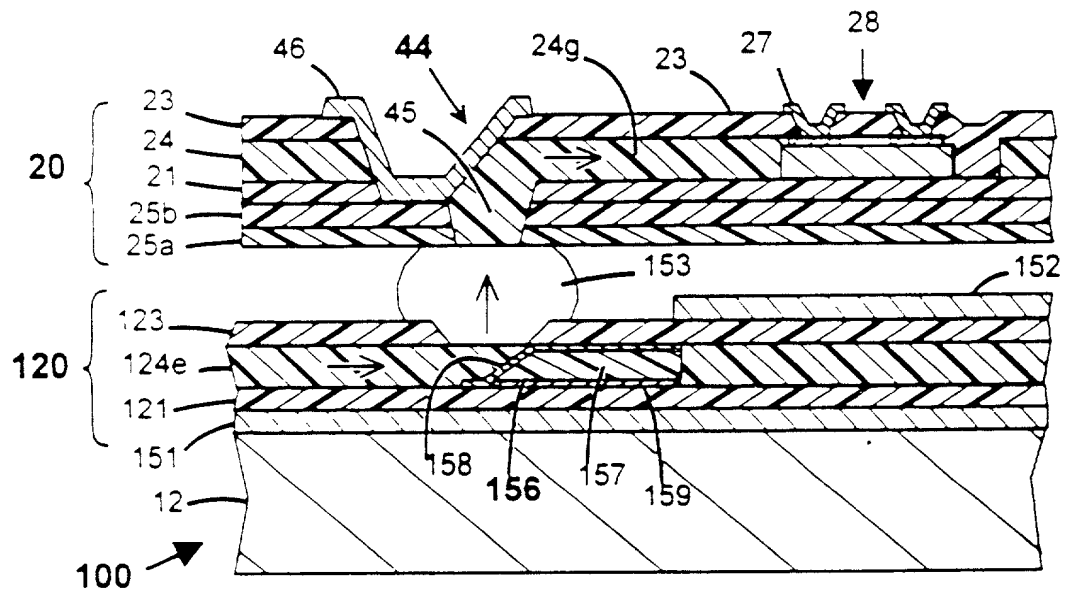


FIG. 23

FIG._27

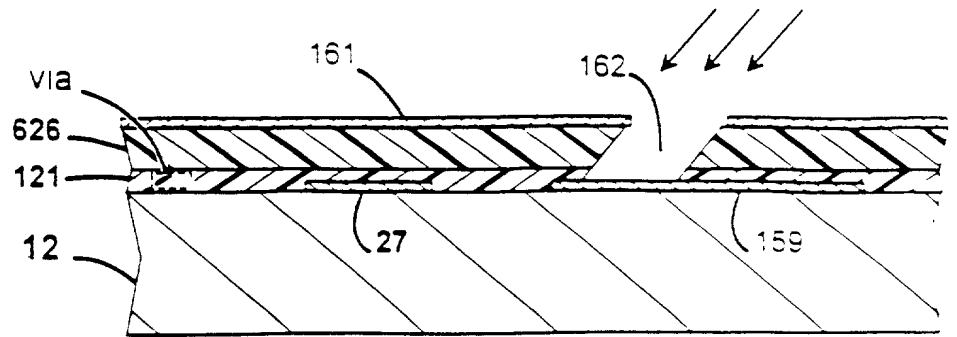


FIG._28

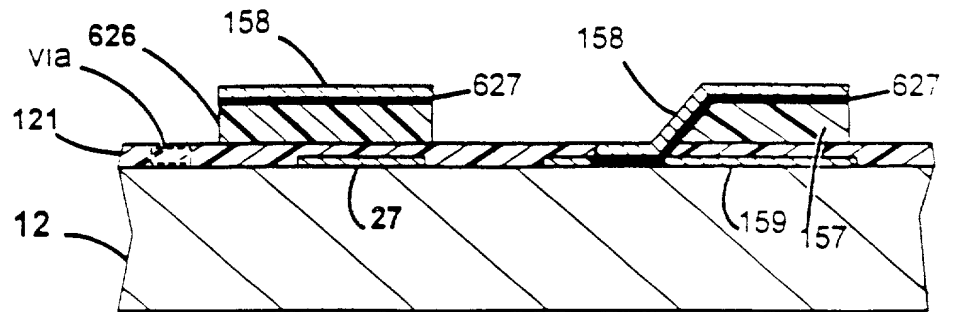


FIG._29

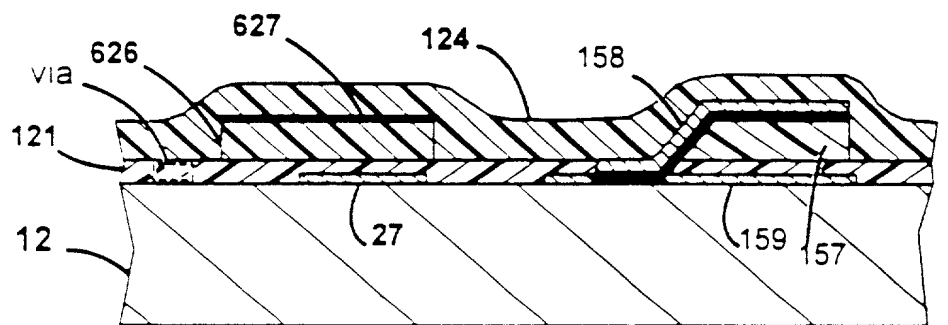
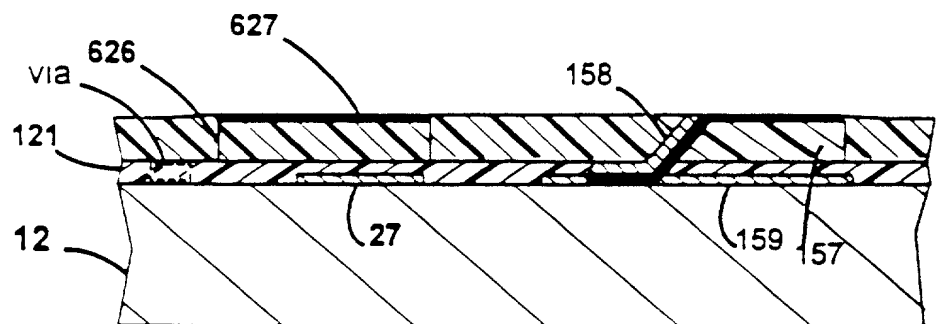
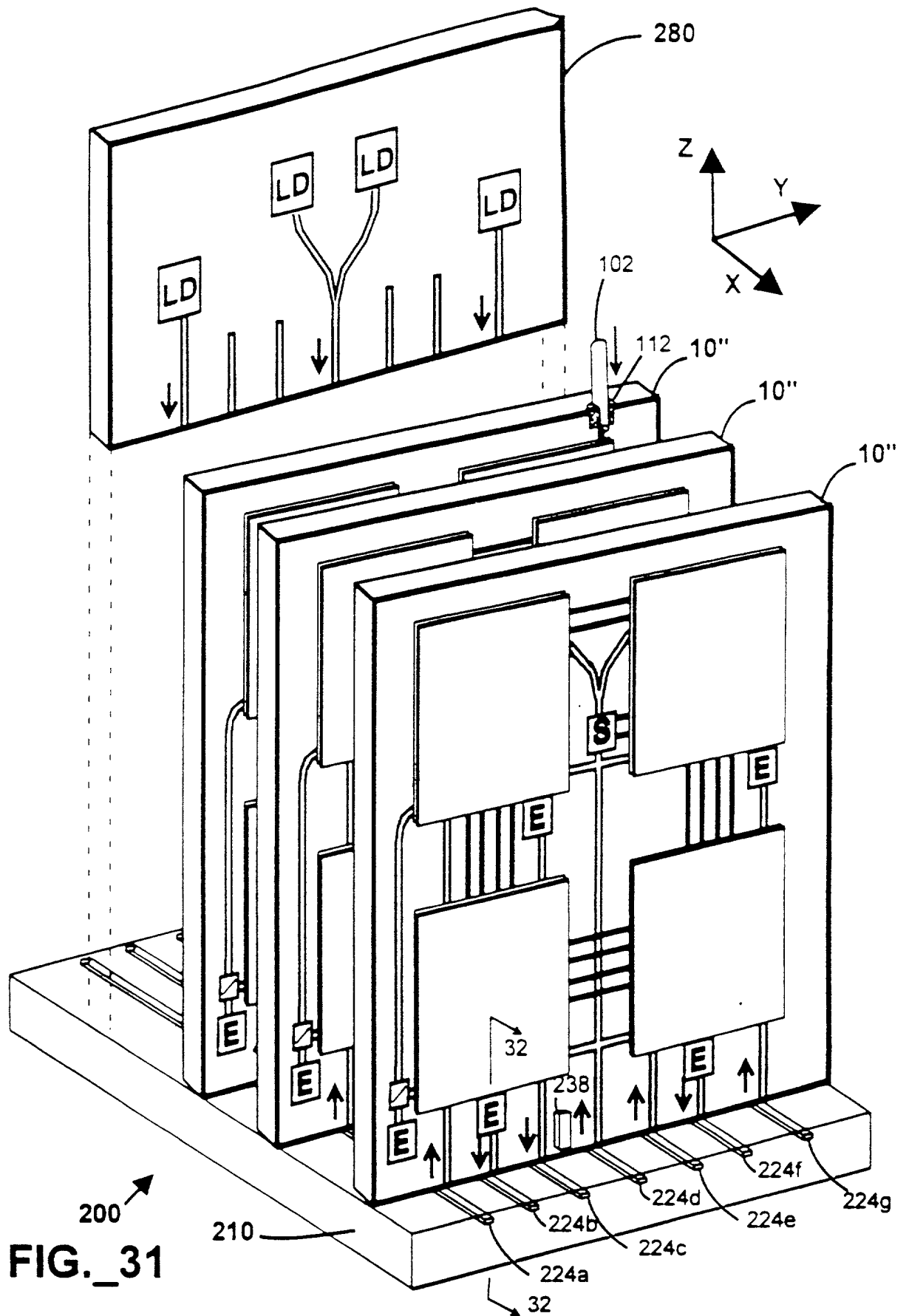
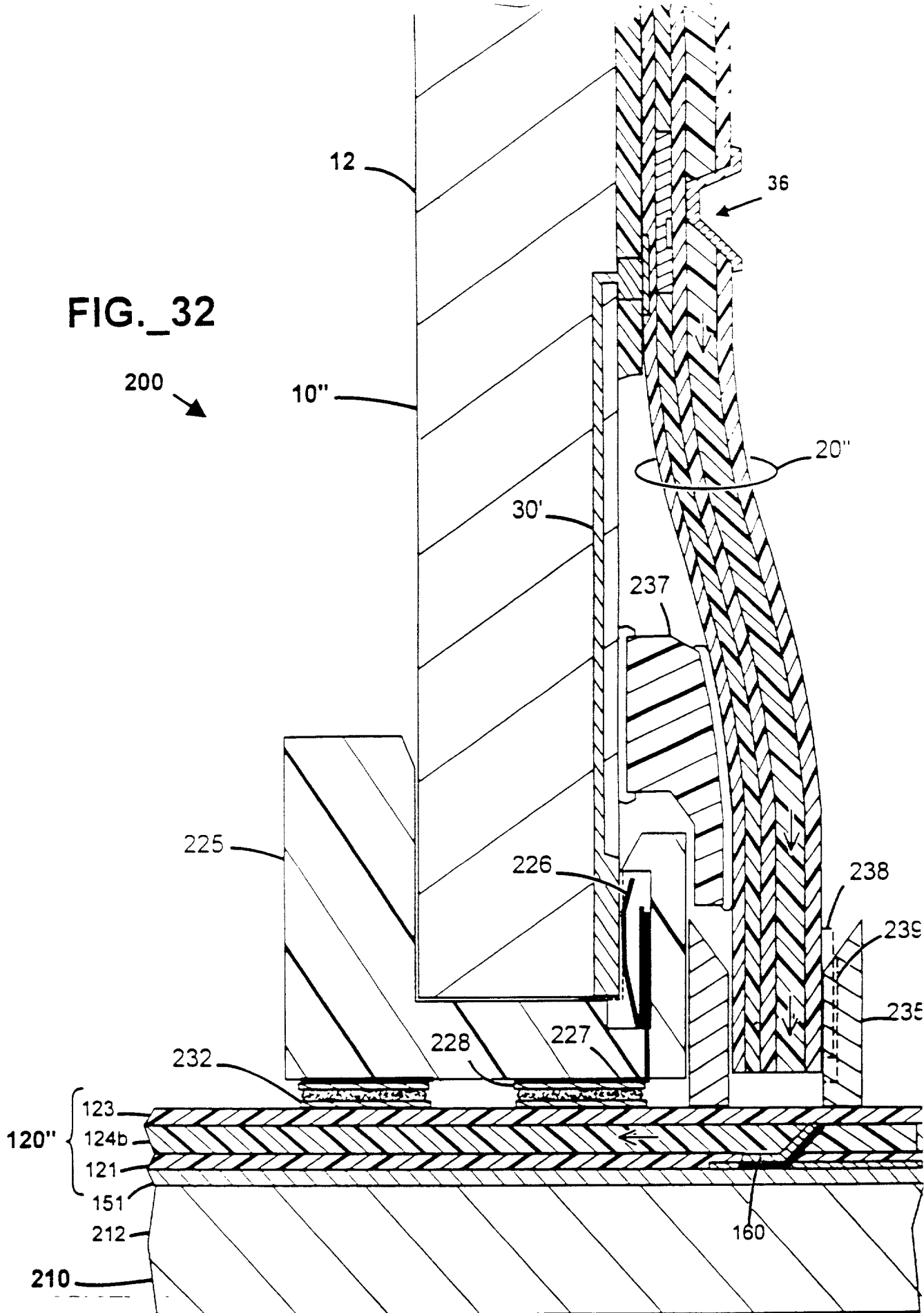
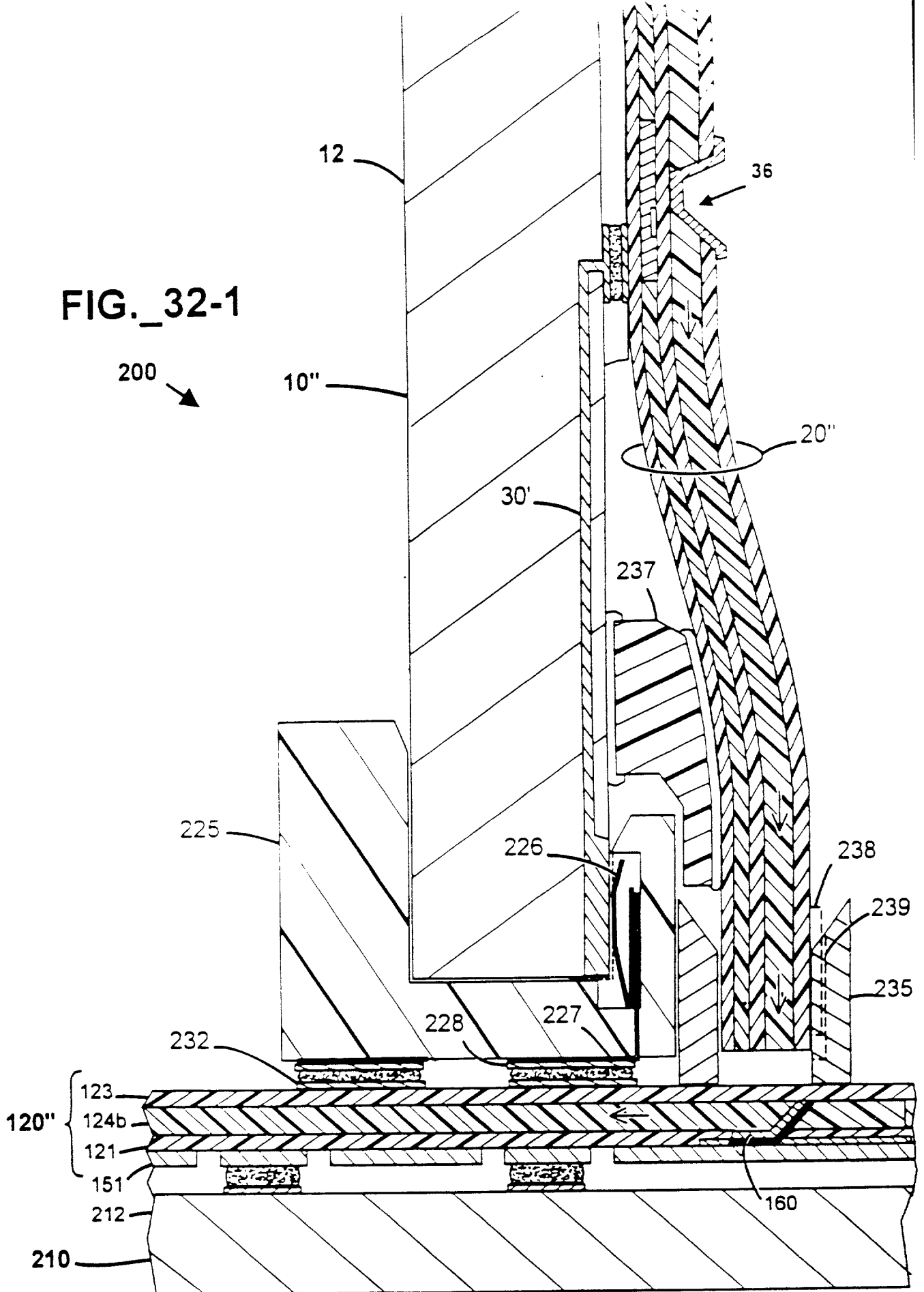


FIG._30









[illegible]

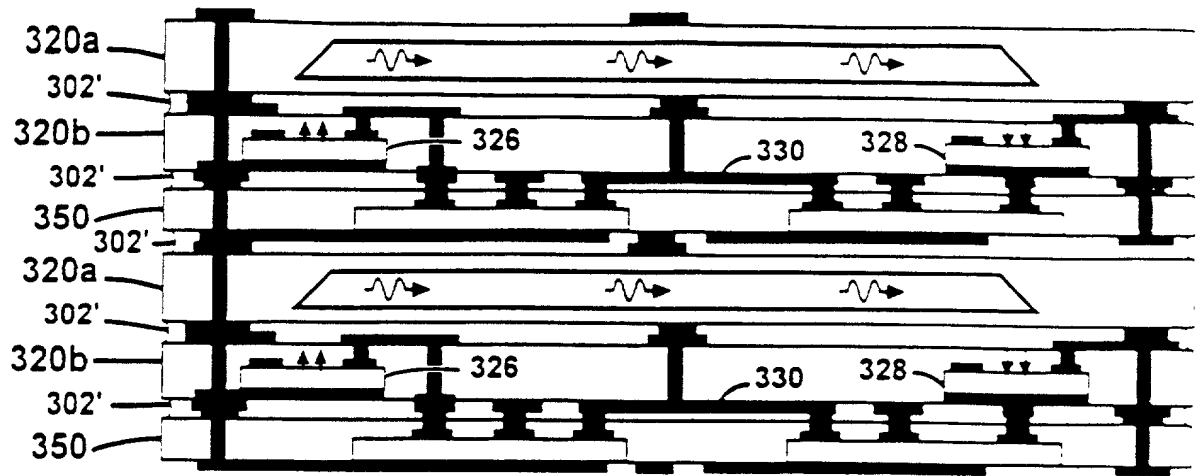


FIG. 36

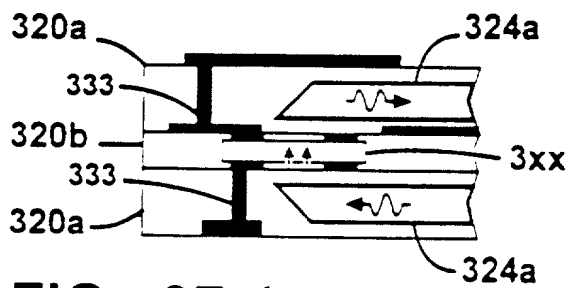


FIG. 37-1

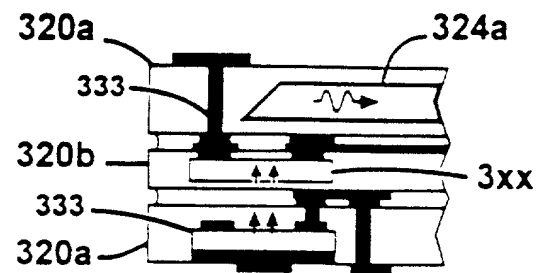


FIG. 37-2

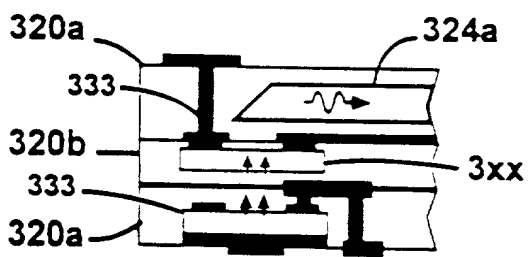


FIG. 37-3

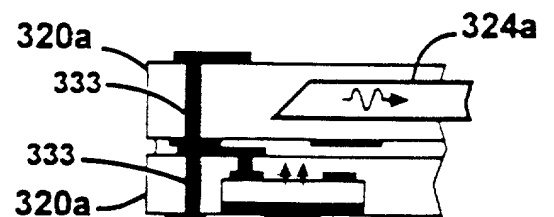


FIG. 37-4

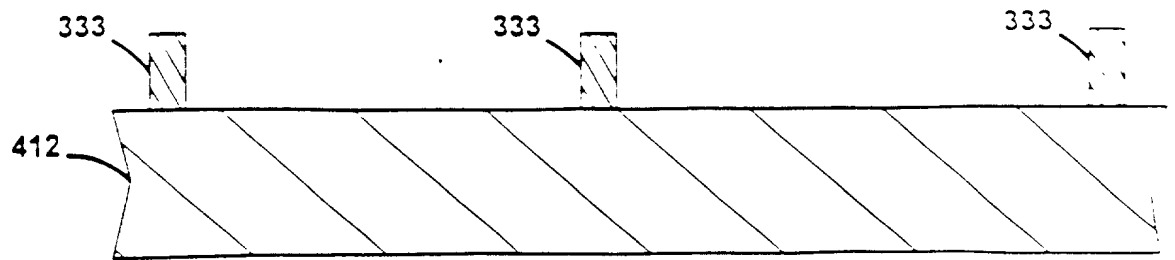


FIG. 38

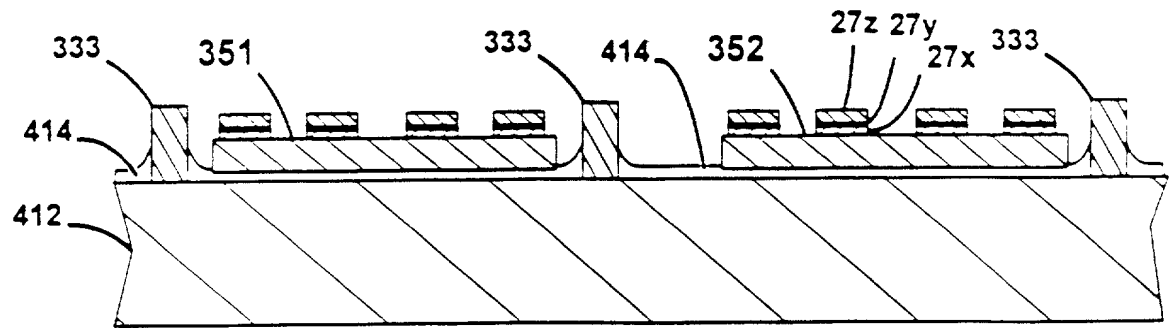


FIG. 39

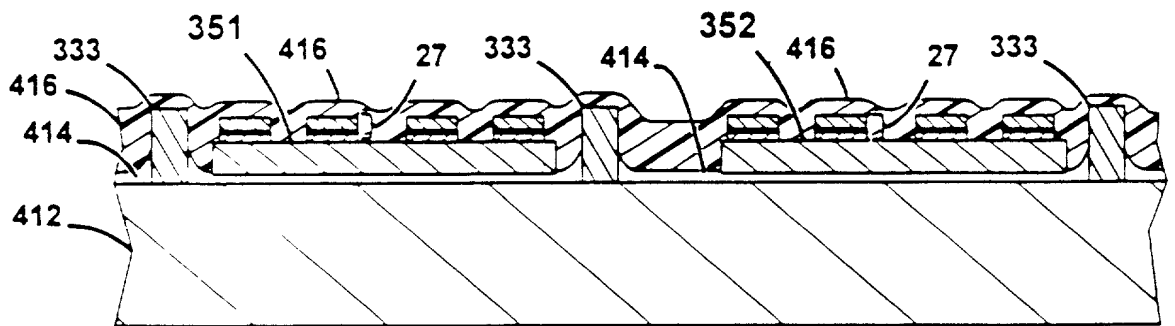


FIG. 40

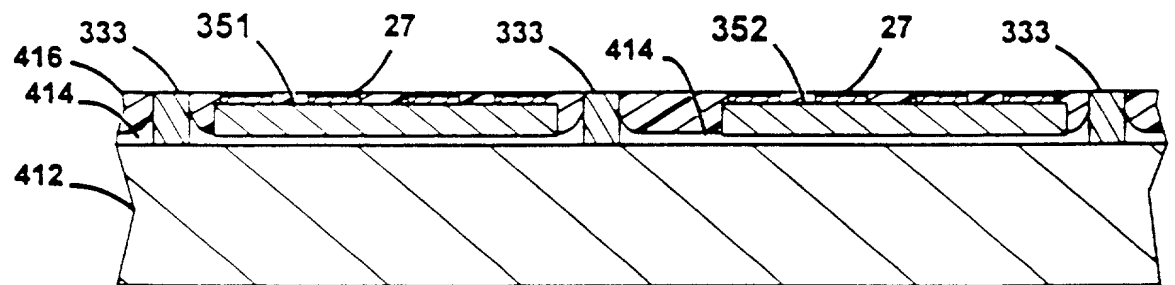


FIG. 41

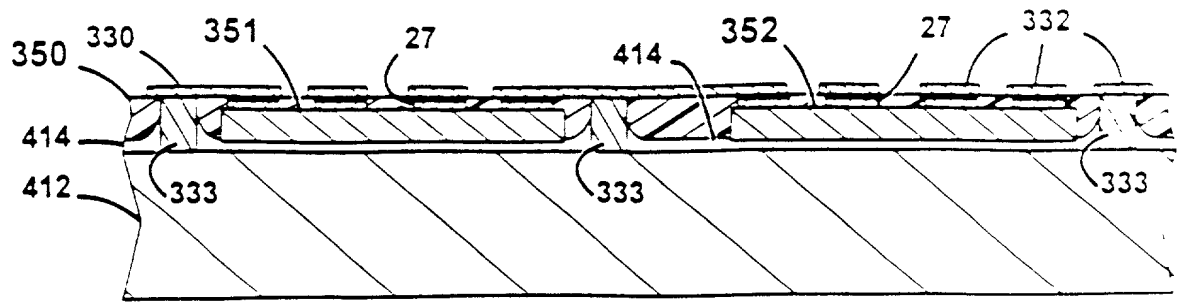


FIG. 42

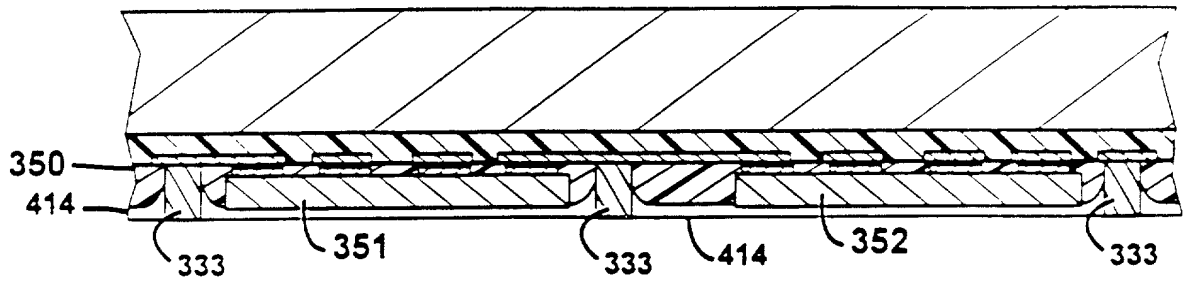


FIG. 43

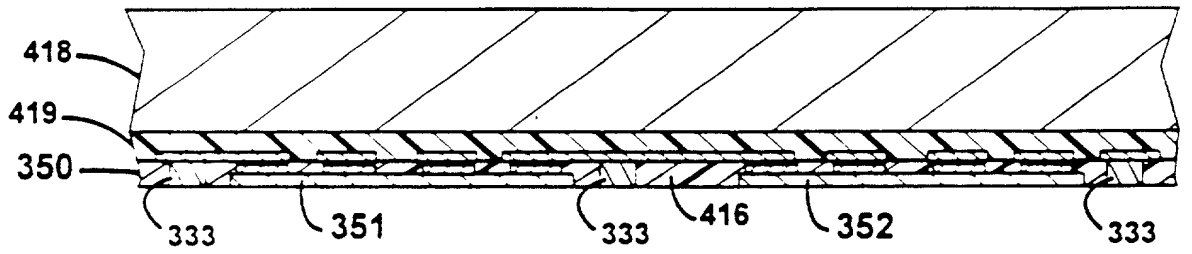


FIG. 44

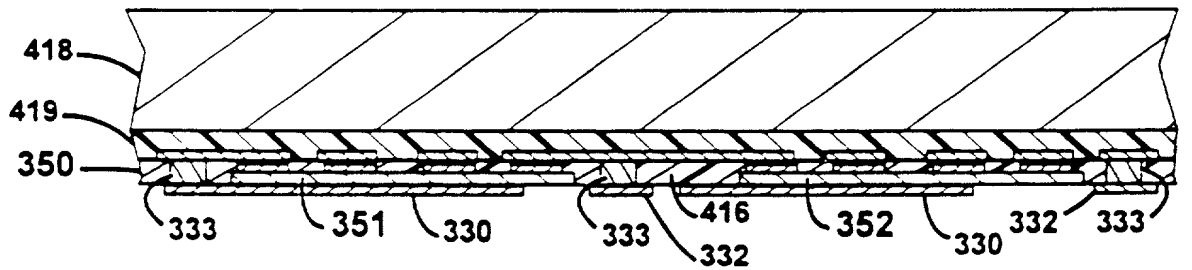
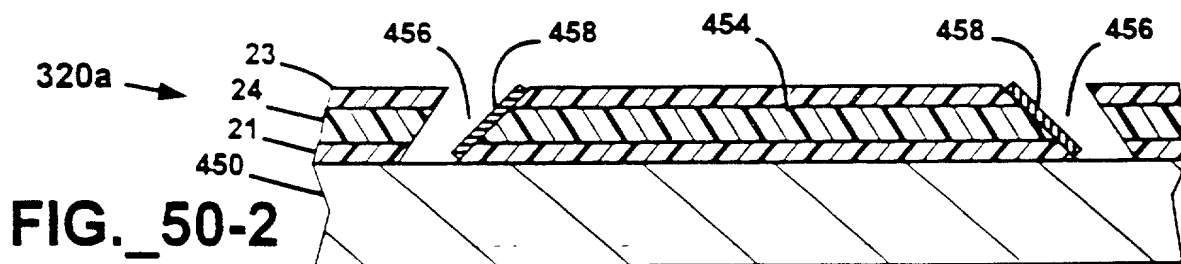
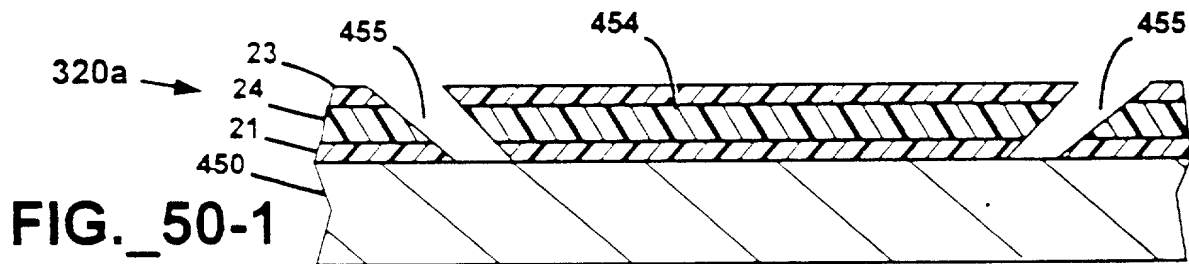
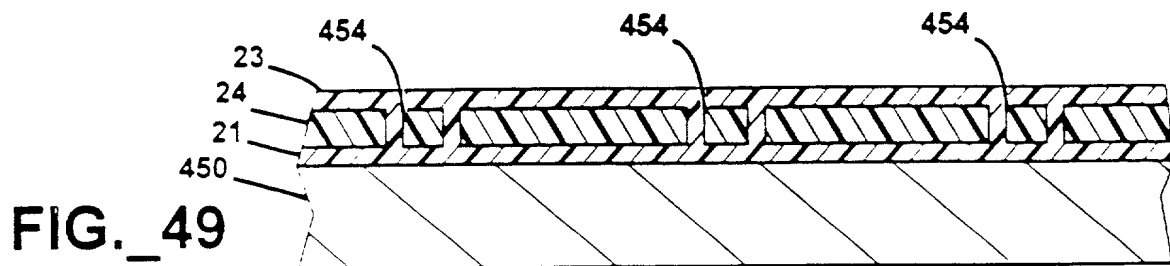
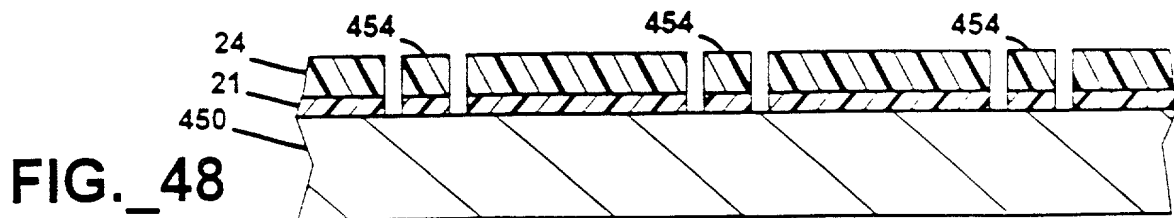
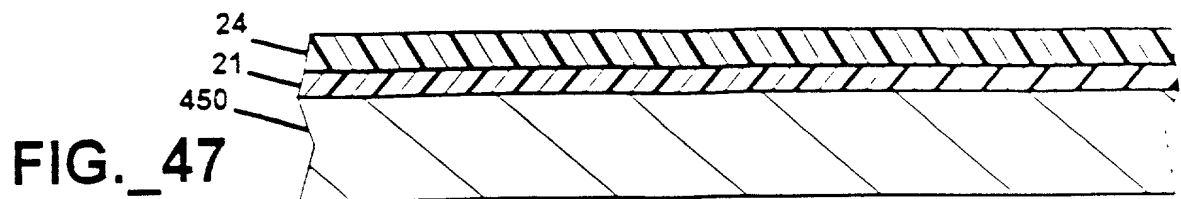
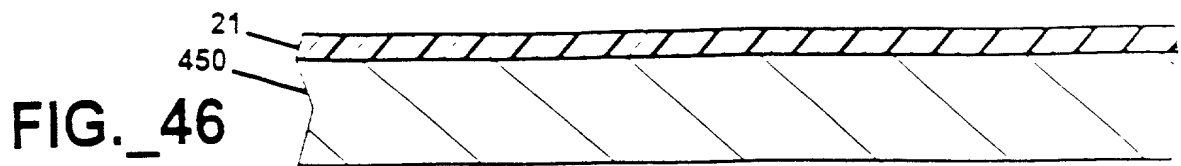
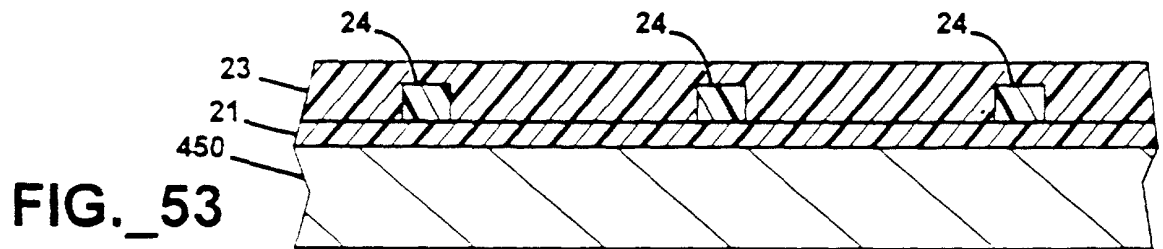
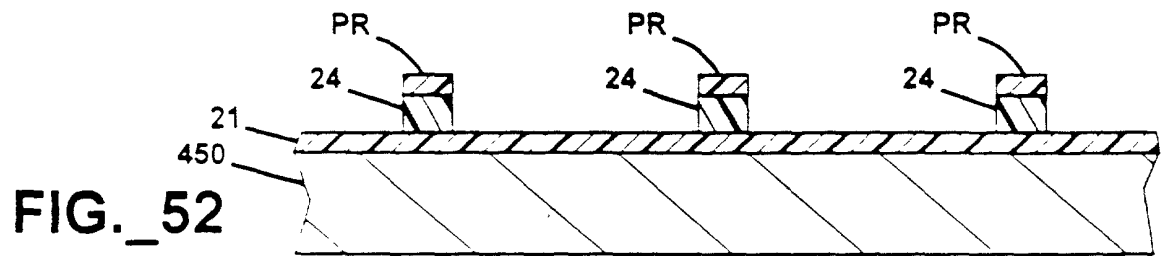
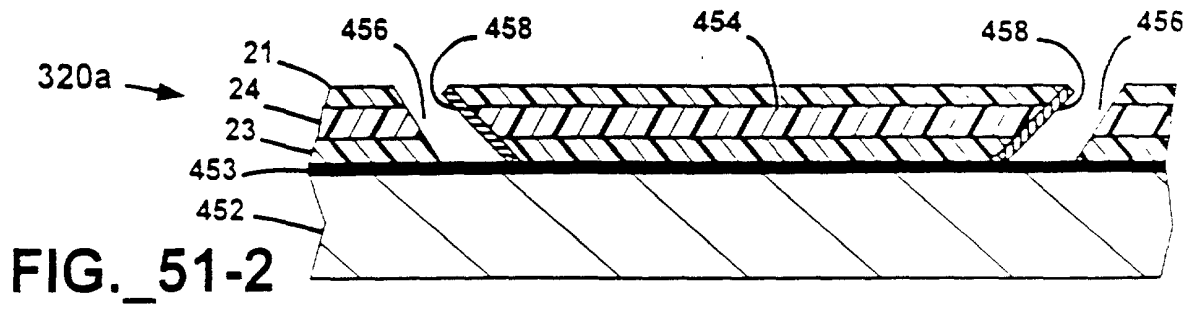
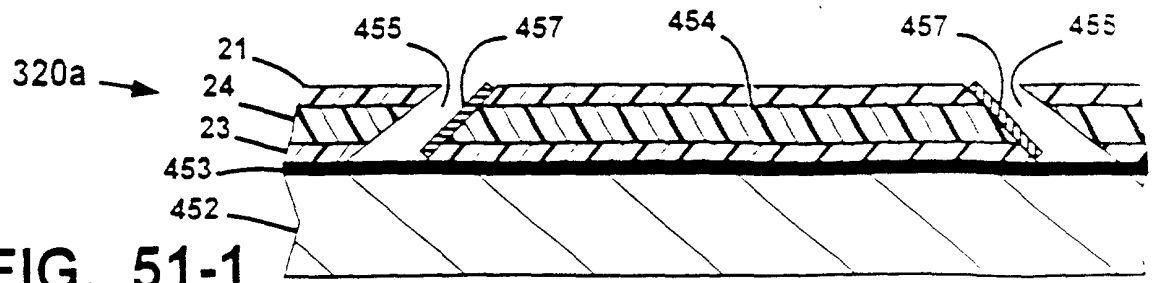
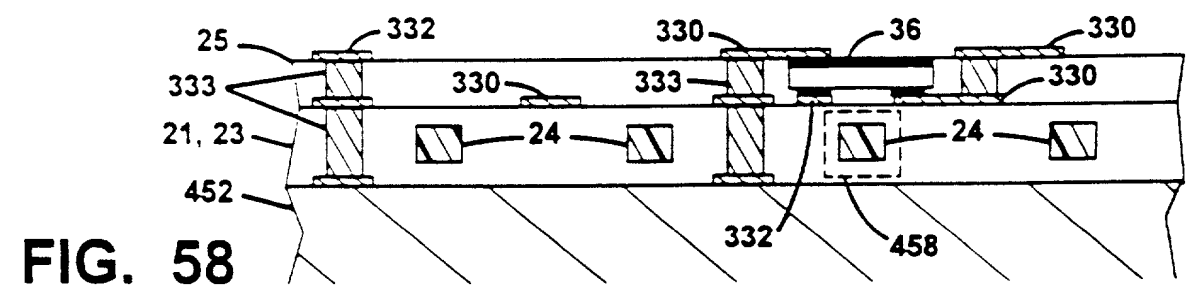
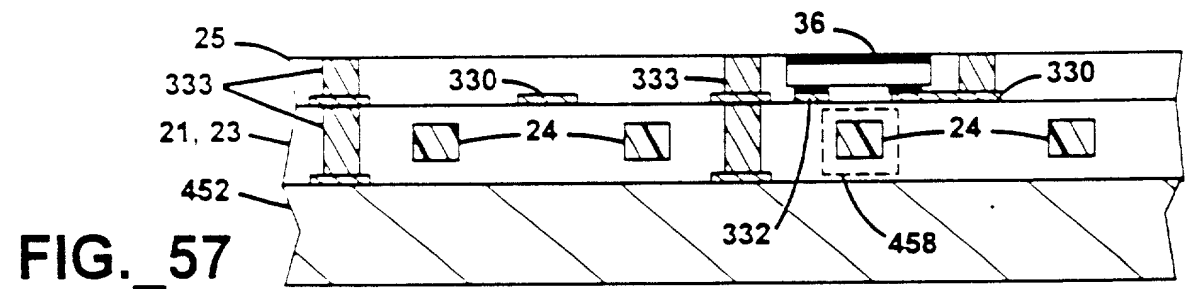
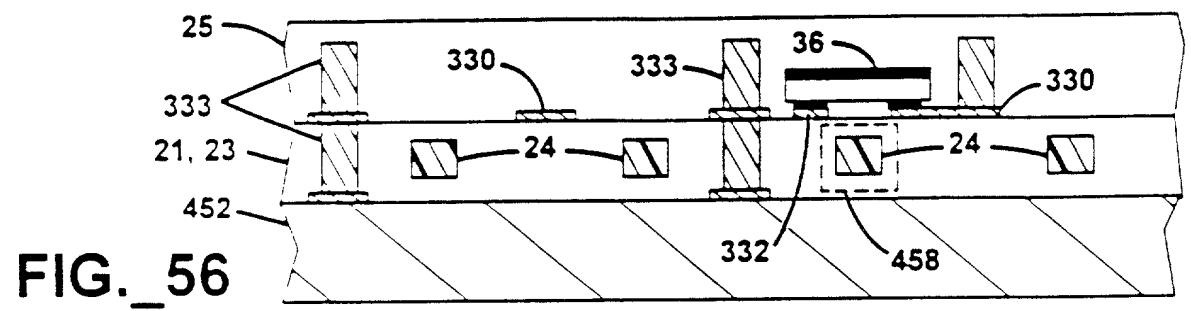
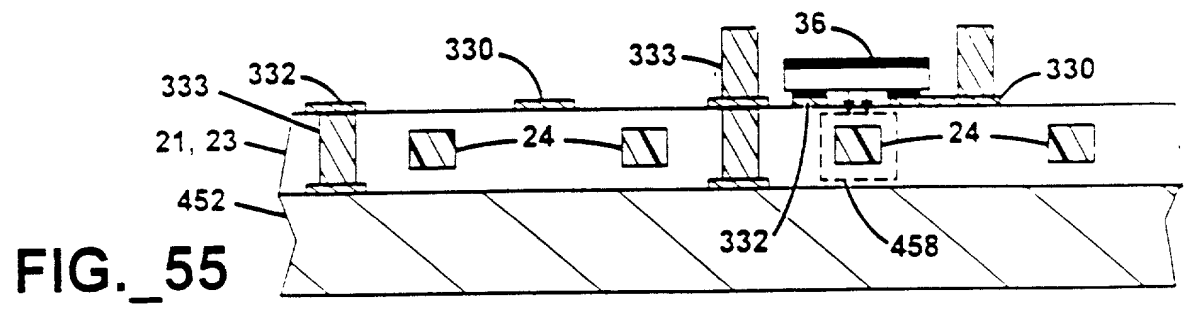
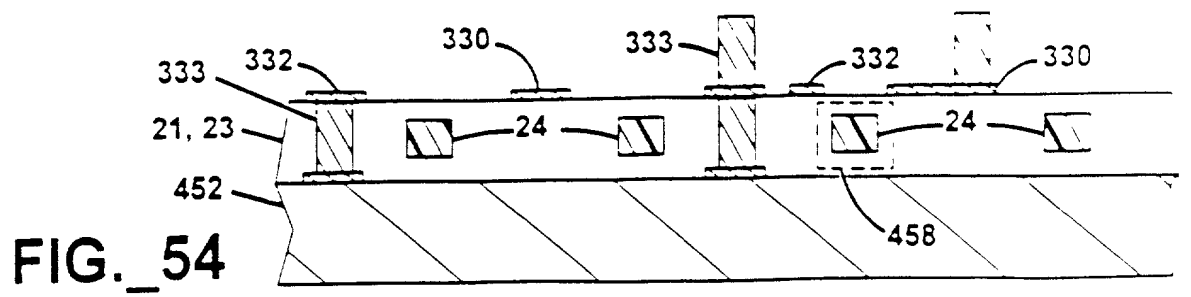


FIG. 45







21b
21a
12
26

This diagram shows a cross-sectional view of a second embodiment of the device. It features a substrate 12 with a top surface 21a and a bottom surface 21b. A layer 26b is disposed on the top surface 21a. A layer 26a is disposed on the bottom surface 21b. The layer 26a has a hatched pattern, and the layer 26b has a cross-hatched pattern.

Diagram illustrating a sheet 21b with four horizontal slots 26a, 26b, 26c, and 26d. Arrows labeled 62 point to the left and right edges of the sheet.

A cross-sectional view of a semiconductor device. A substrate 12 is shown at the bottom. A first conductive layer 21a is formed on the substrate. A second conductive layer 21b is formed on top of the first conductive layer 21a. A third conductive layer 26b is formed on top of the second conductive layer 21b.

A cross-sectional view of a semiconductor device. It shows a substrate 12 with a thin layer 21a on its top surface. Above layer 21a is a layer 24. A structure 26b is formed on layer 24, consisting of a central rectangular block with a cross-hatched pattern, flanked by two regions with diagonal hatching. The entire structure is covered by a top layer with diagonal hatching.

FIG. 65

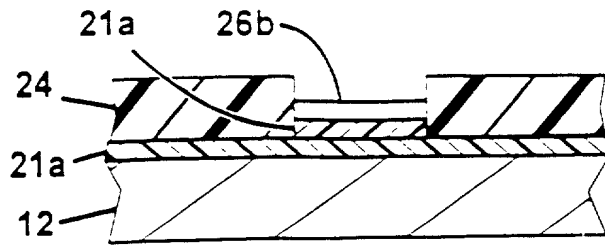


FIG. 66

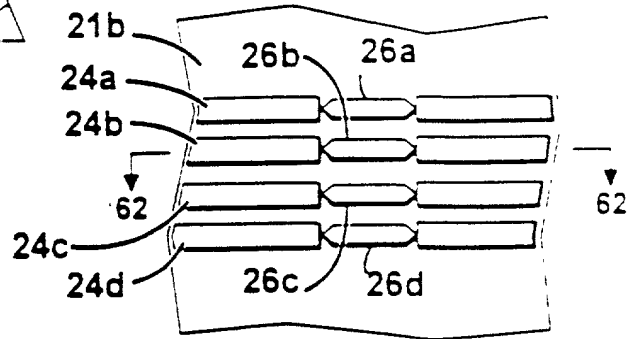


FIG. 67

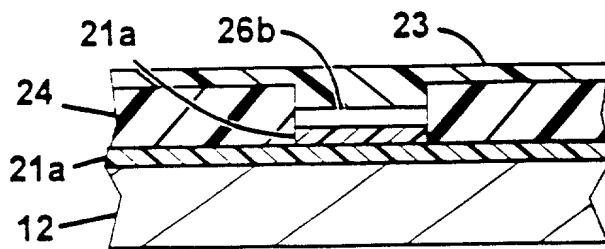


FIG. 68

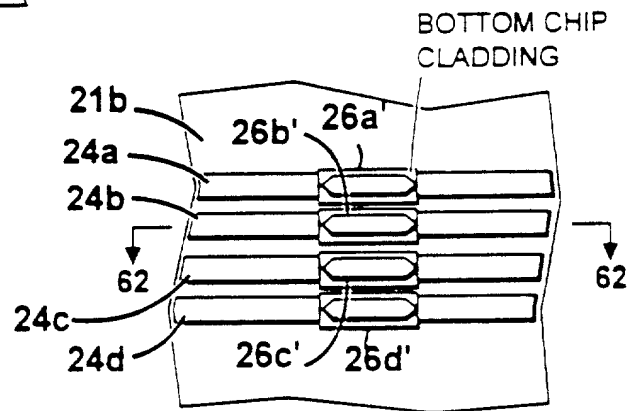


FIG. 67-2

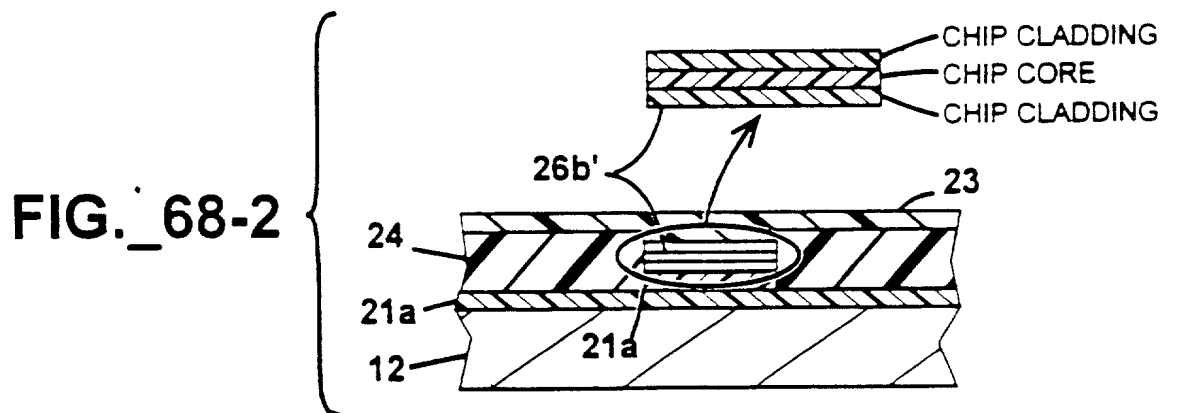


FIG. 68-2

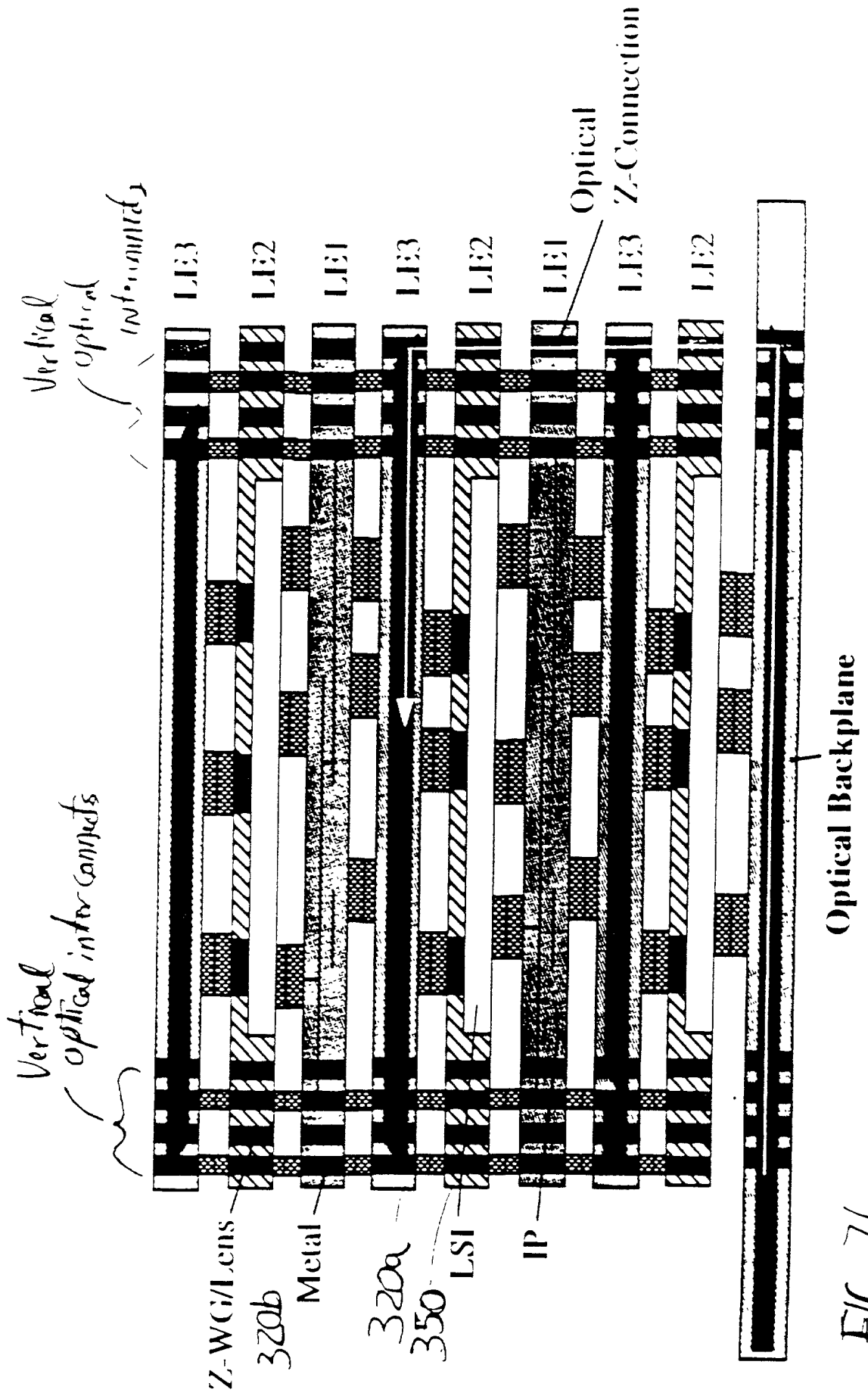
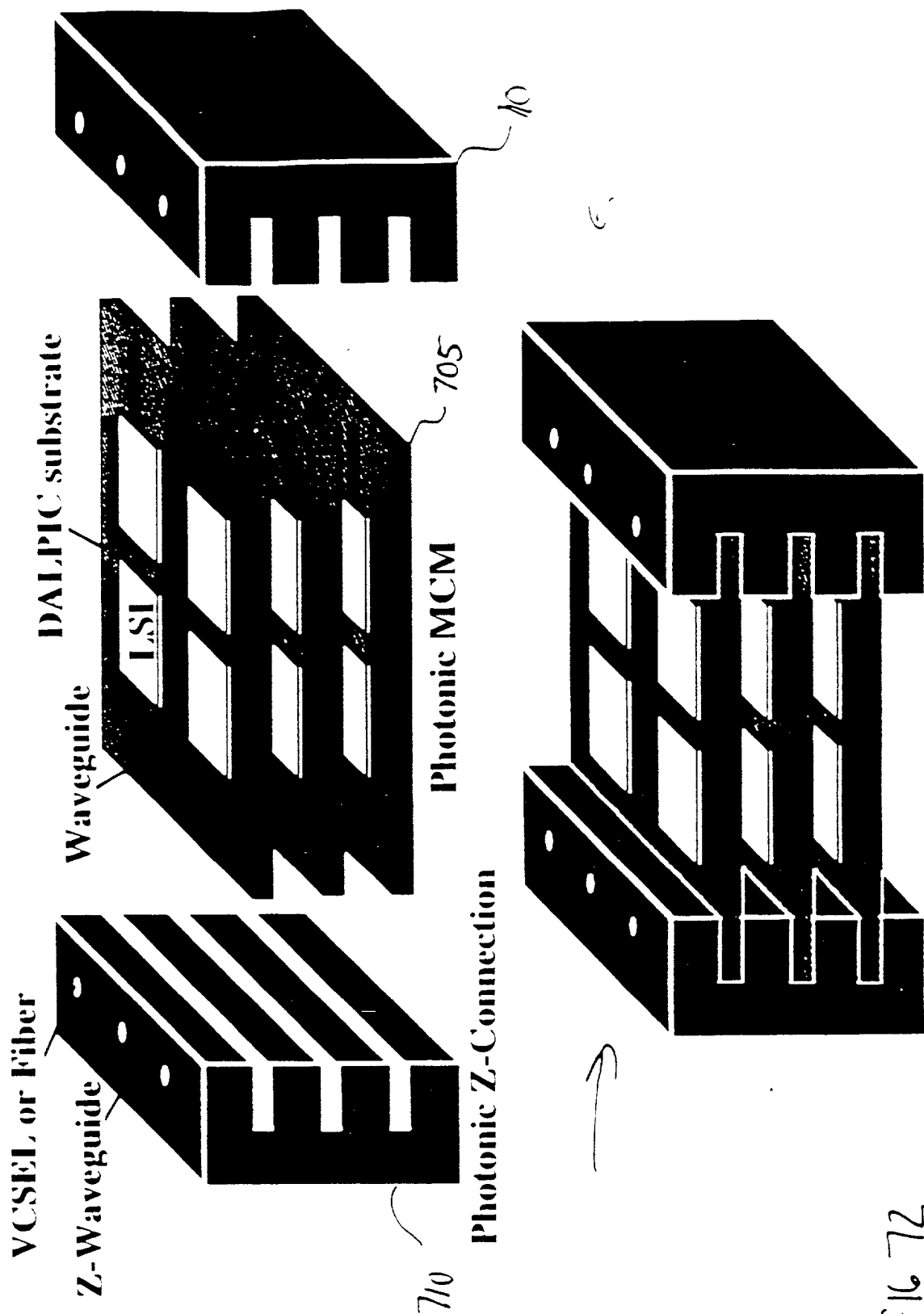
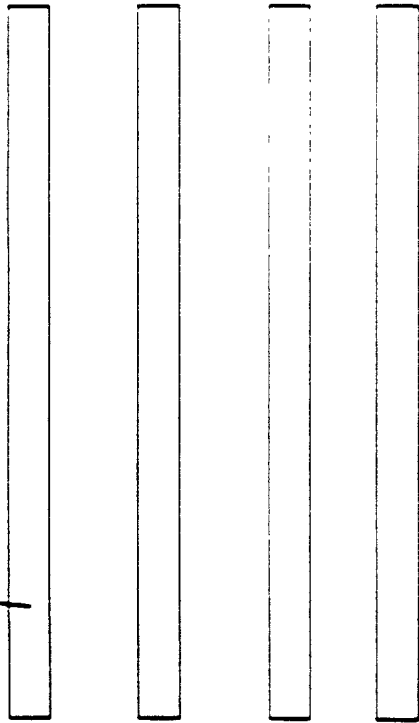


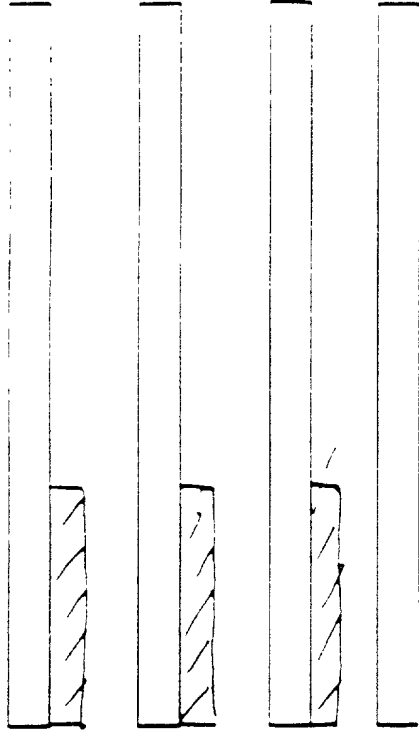
FIG. 71



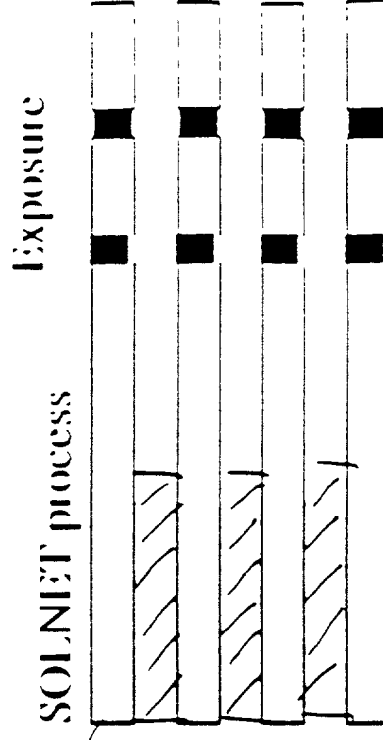
Flexible Photo-imagable sheet (Polyguide)



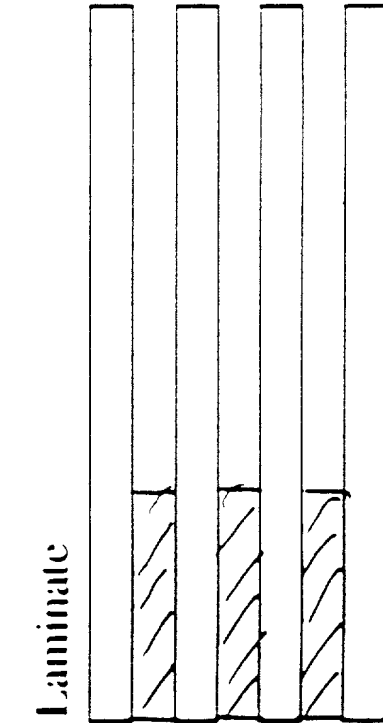
Bonding sheet attach



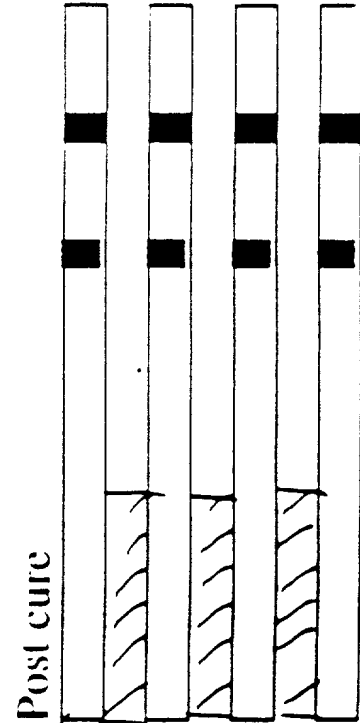
SOLNET process



Laminate



Post cure



Assemble

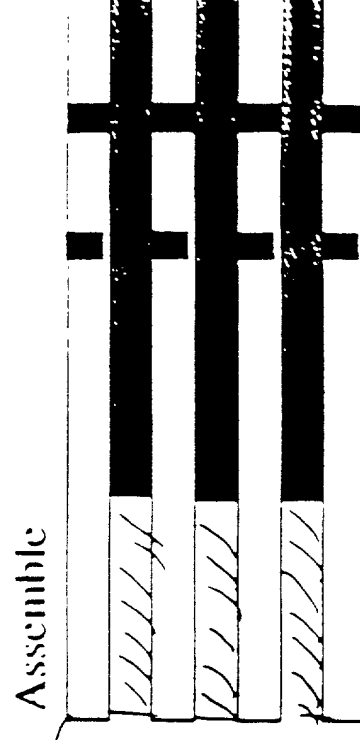


FIG. 10

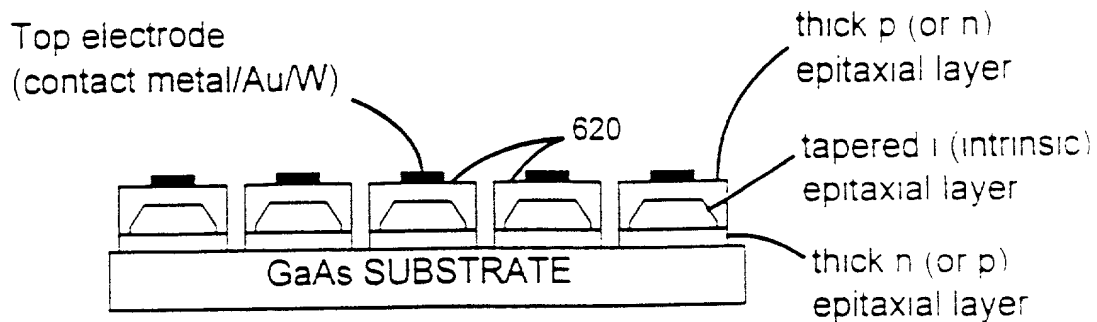


FIG._74 (Epitaxial growth and patterning)

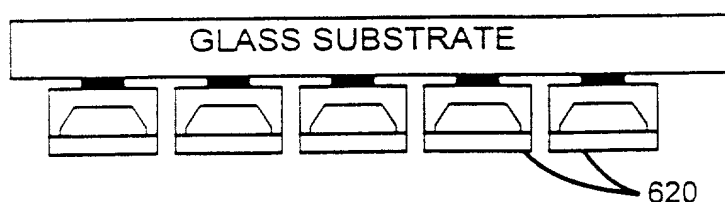


FIG._75 (Epitaxial liftoff)

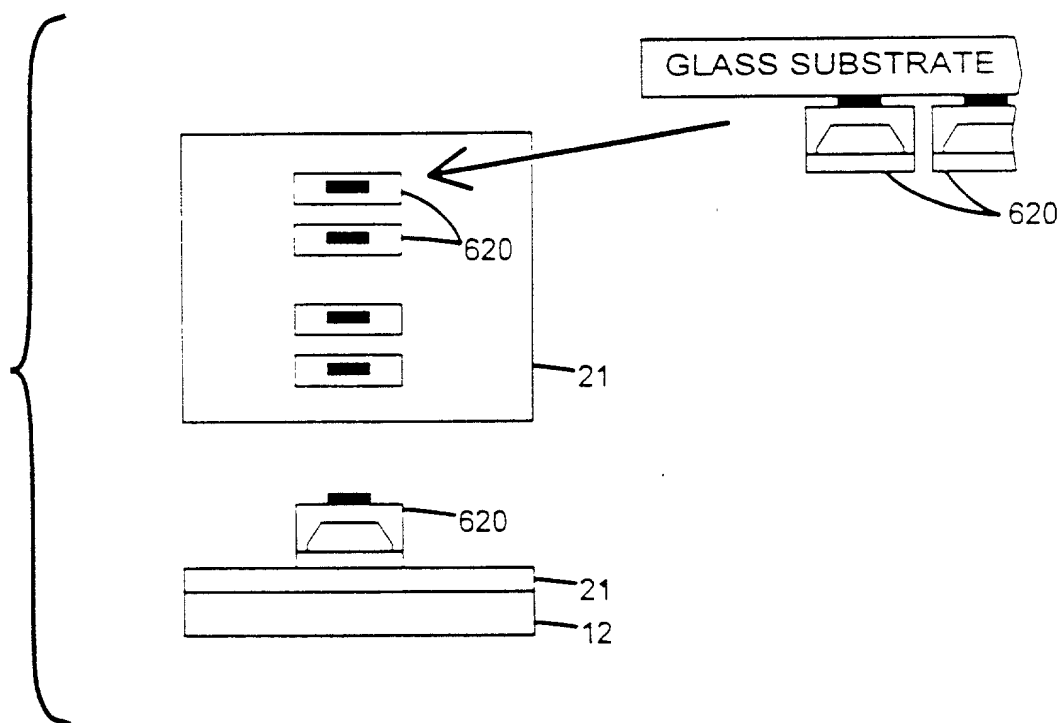
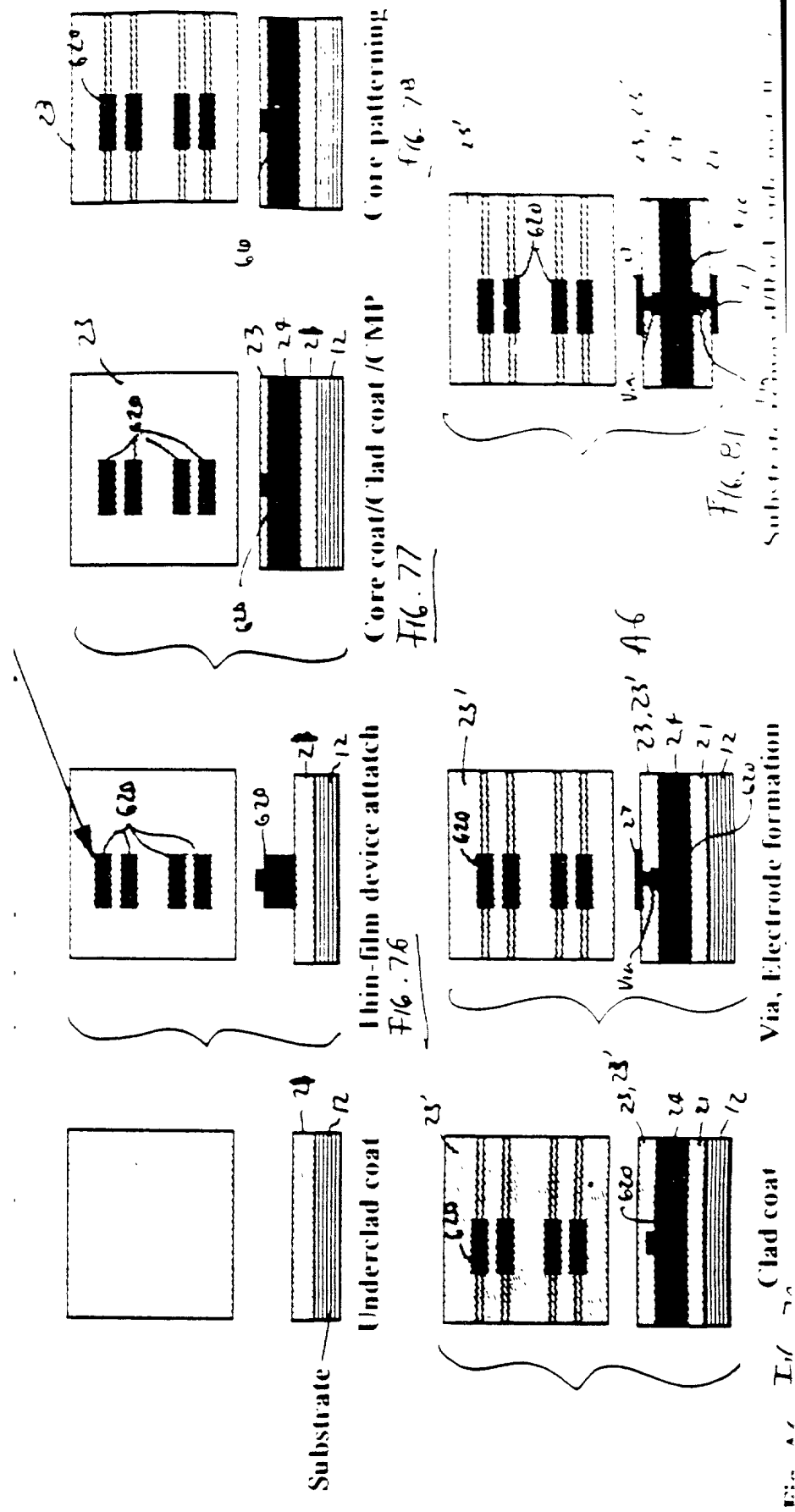
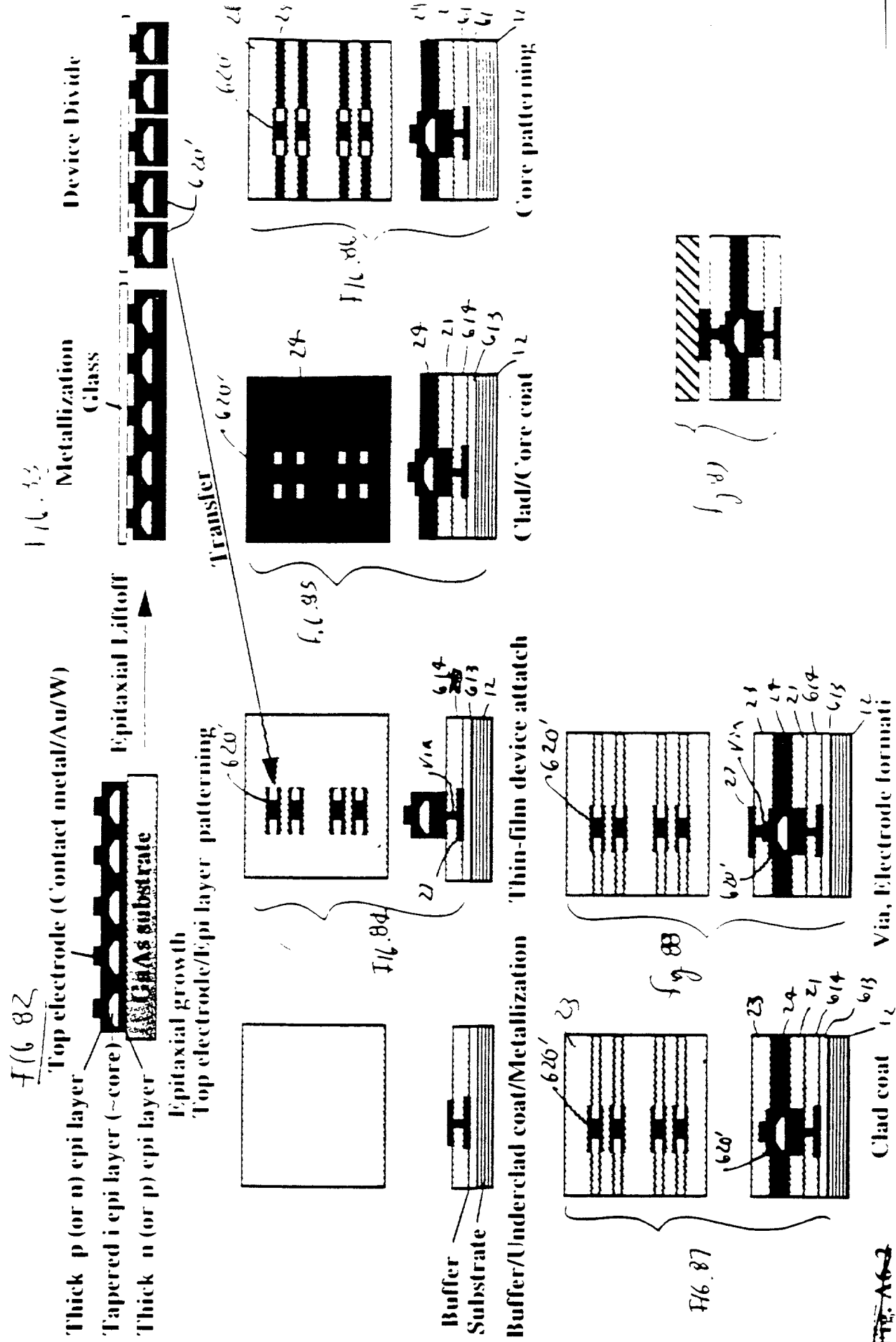
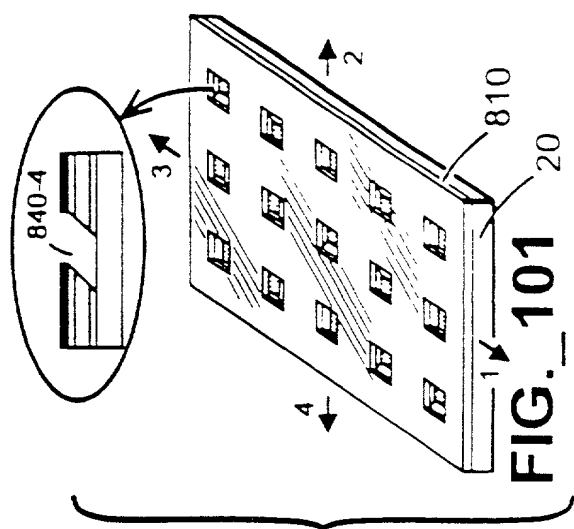
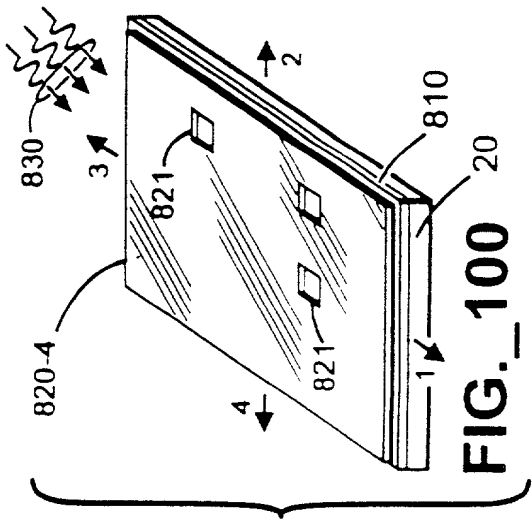
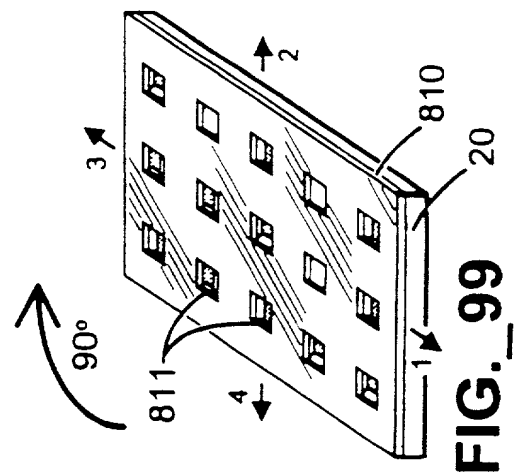
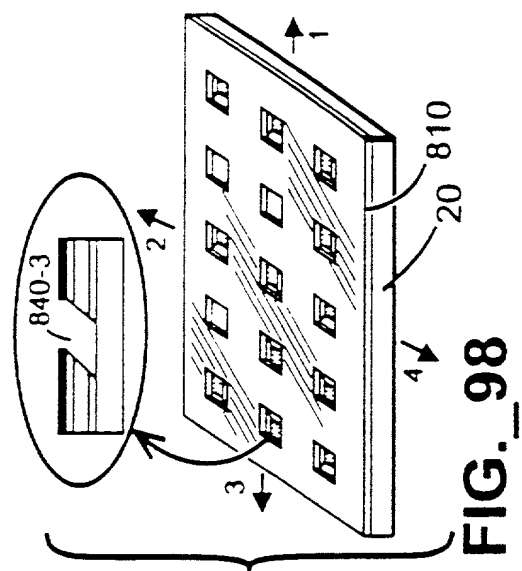
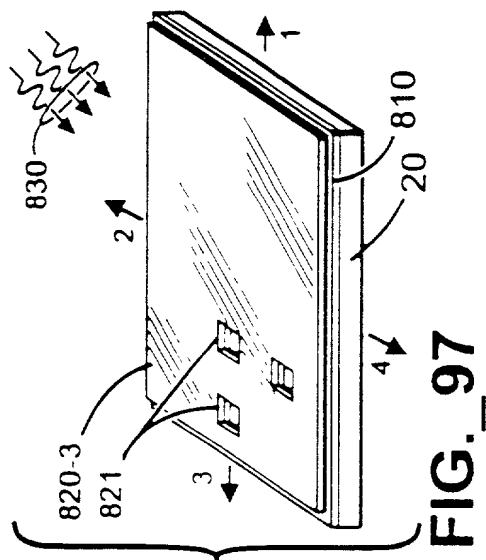
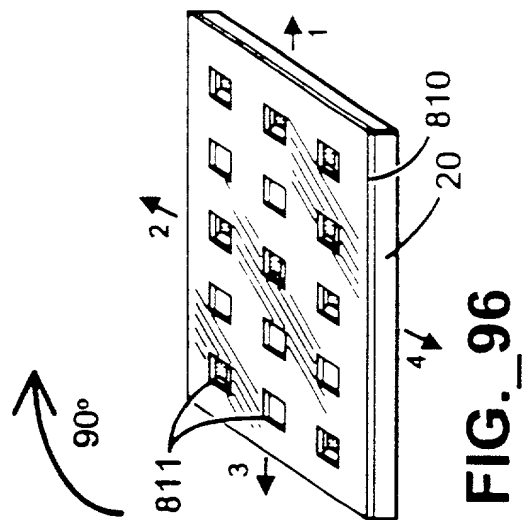
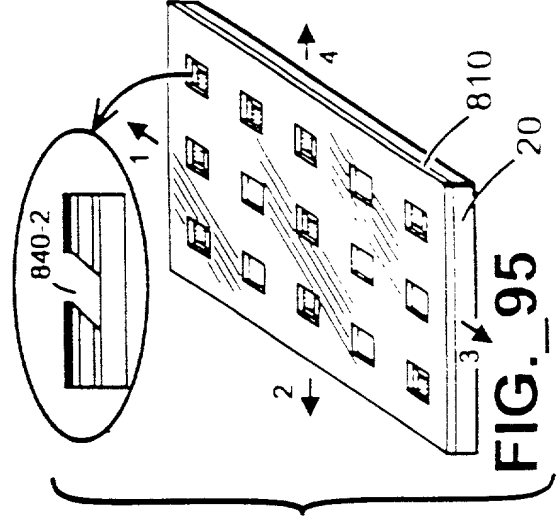
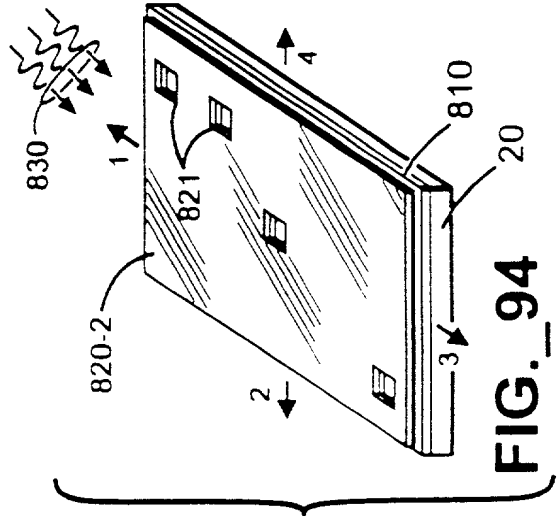
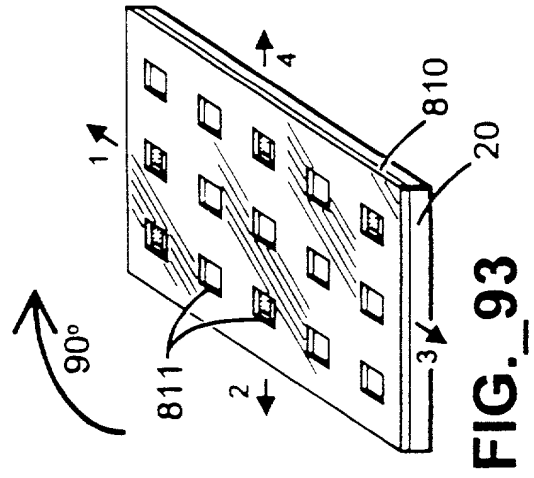
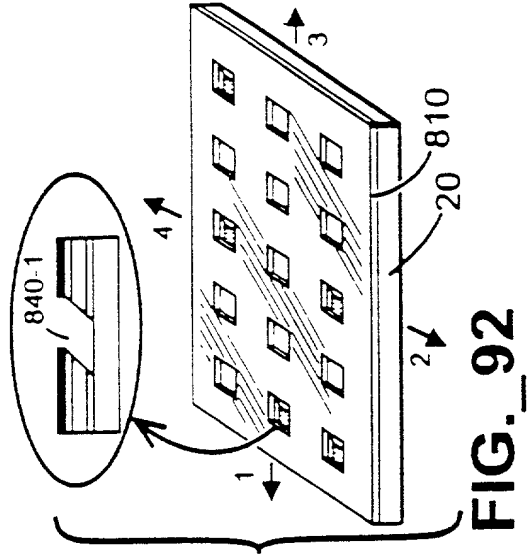
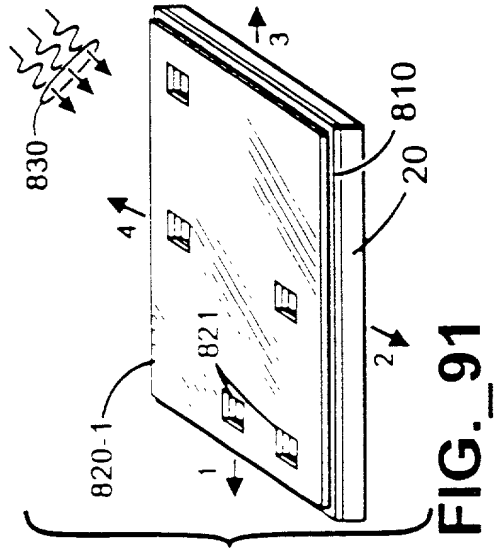
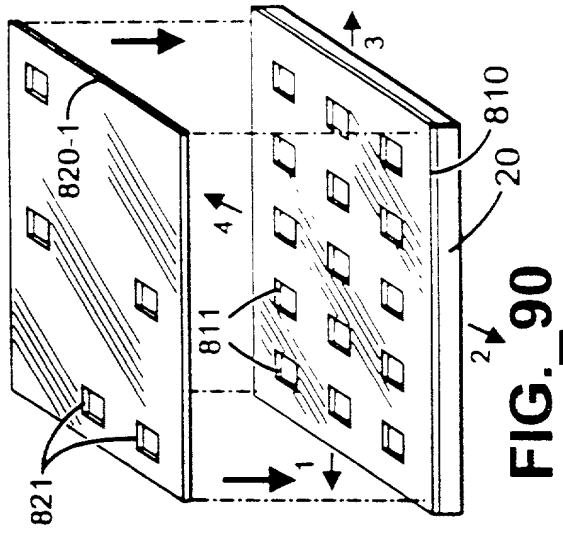


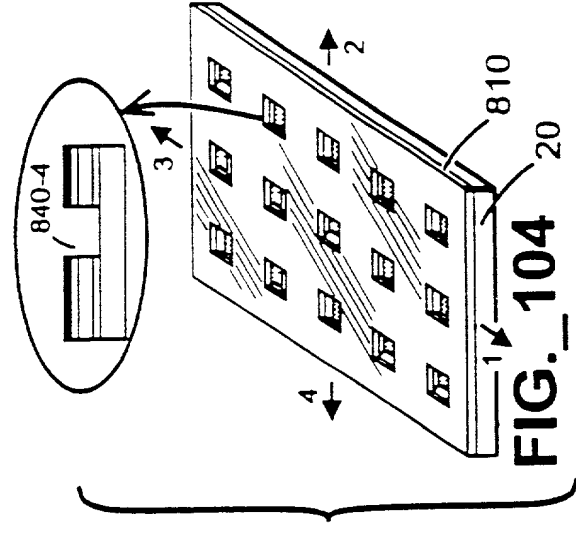
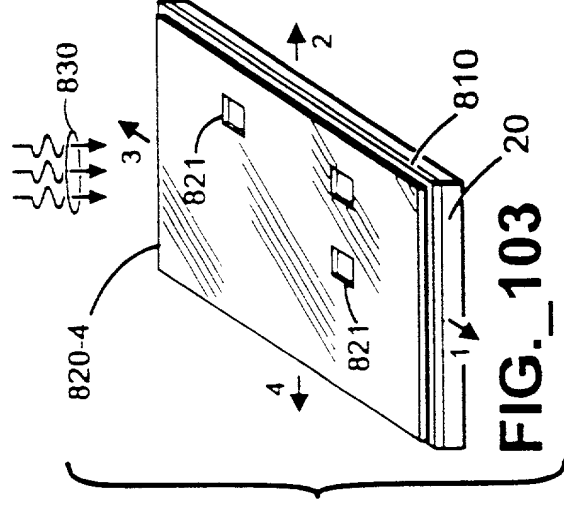
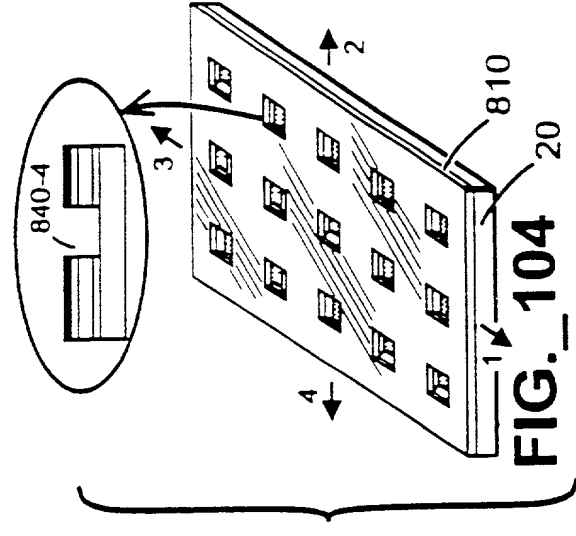
FIG._76 (Transfer)











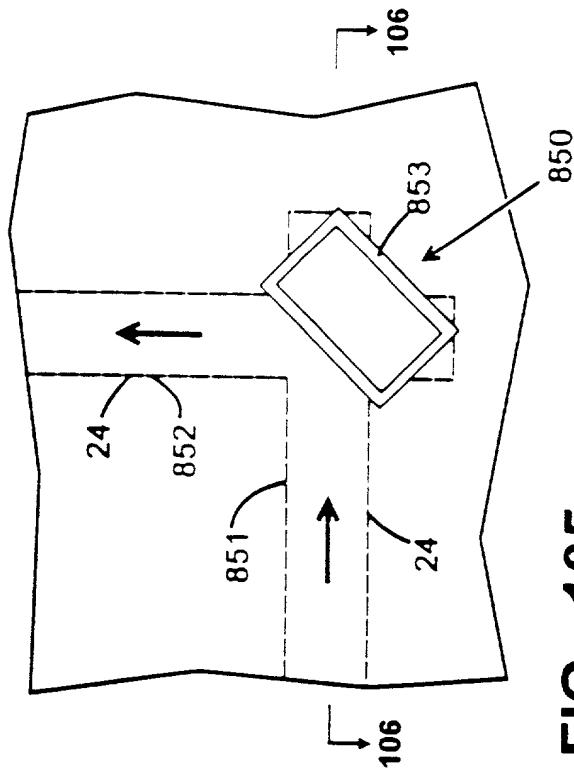


FIG. 105

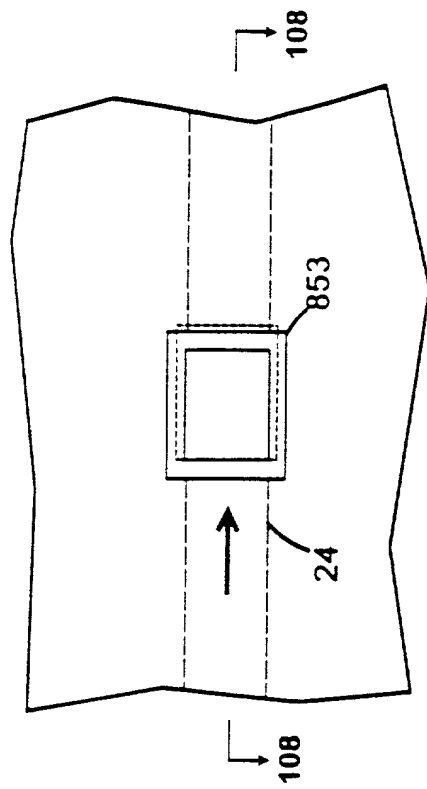


FIG. 107

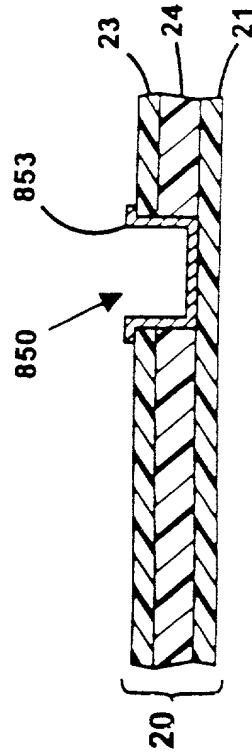


FIG. 106

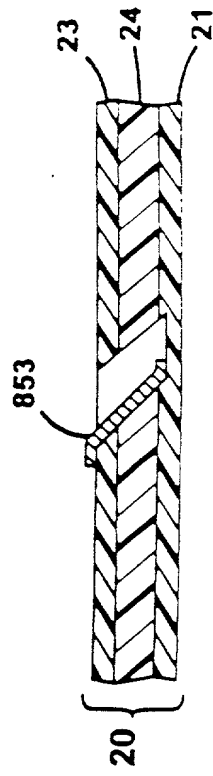
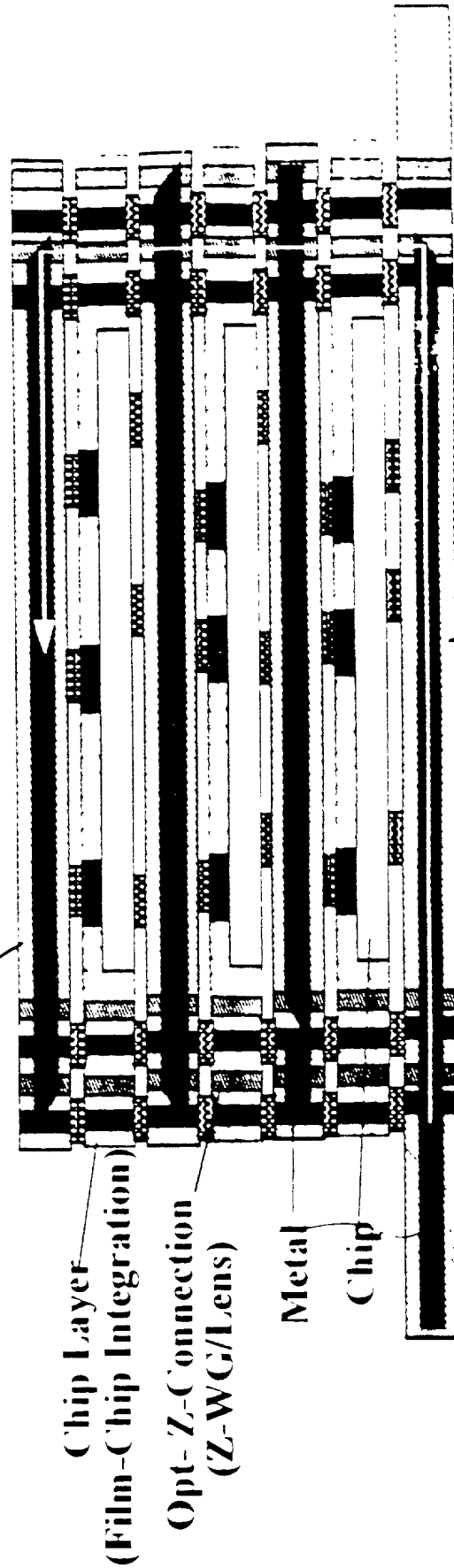


FIG. 108

FUJITSU Computer Packaging Technologies, Inc. **FCPT**
GS CX/CXX OE Solution --- OE-3D-Stack

OE-film-DW (I) or (M)



OE-film-DW

A 22

FIG. 109

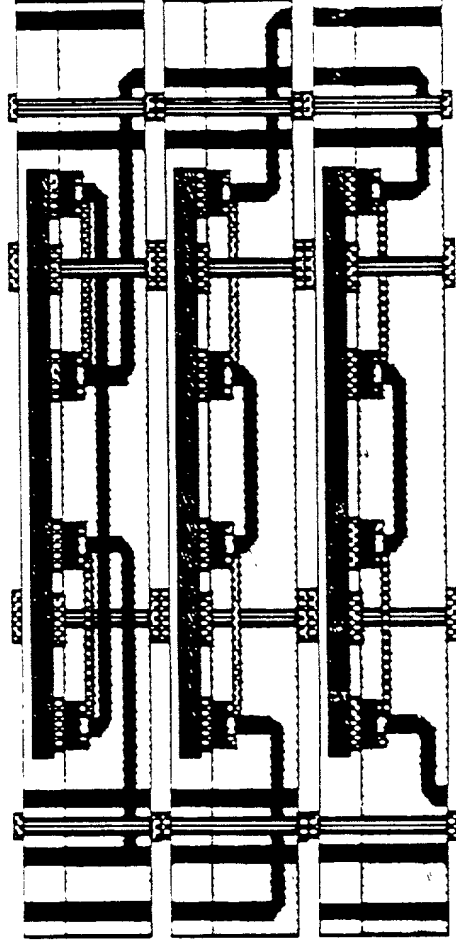
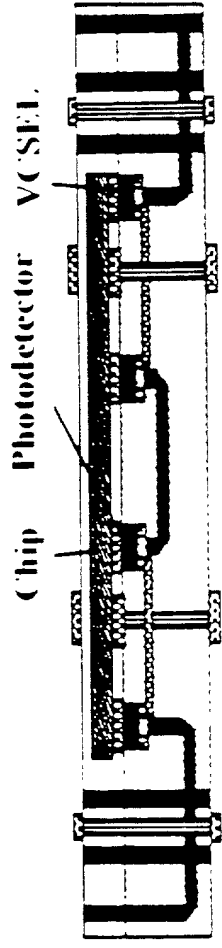


Fig. 110

A23

(2/23/99) AA1 Detail picture Example for 3D-stack'

(New version of the AA1 of 2/5/99)

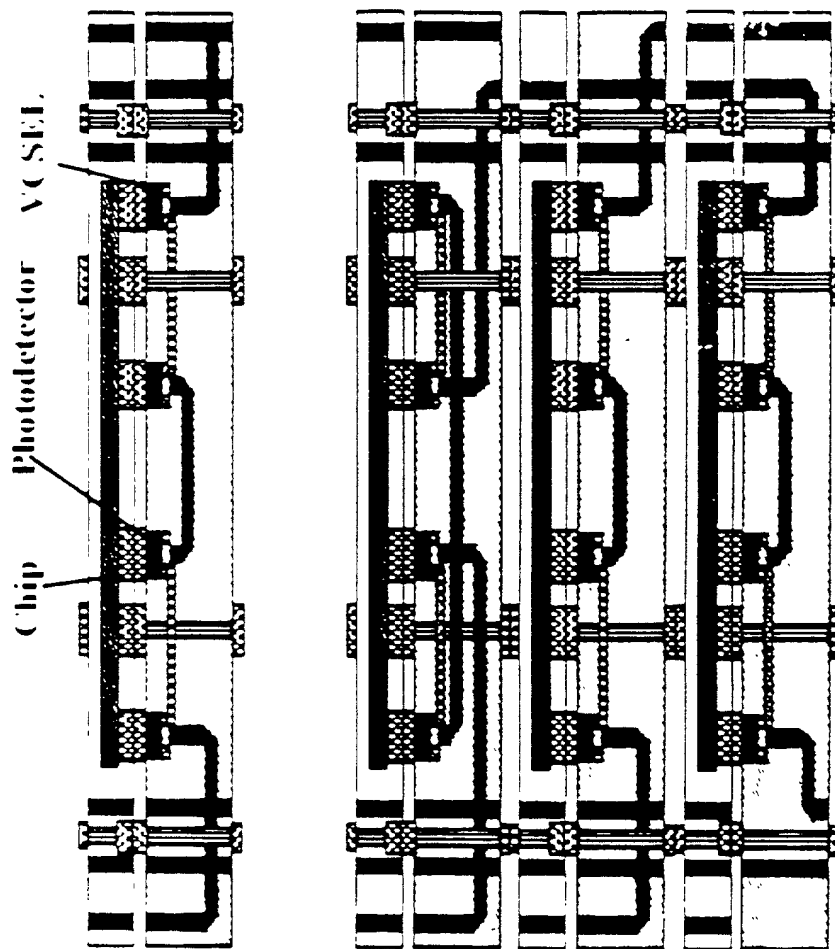


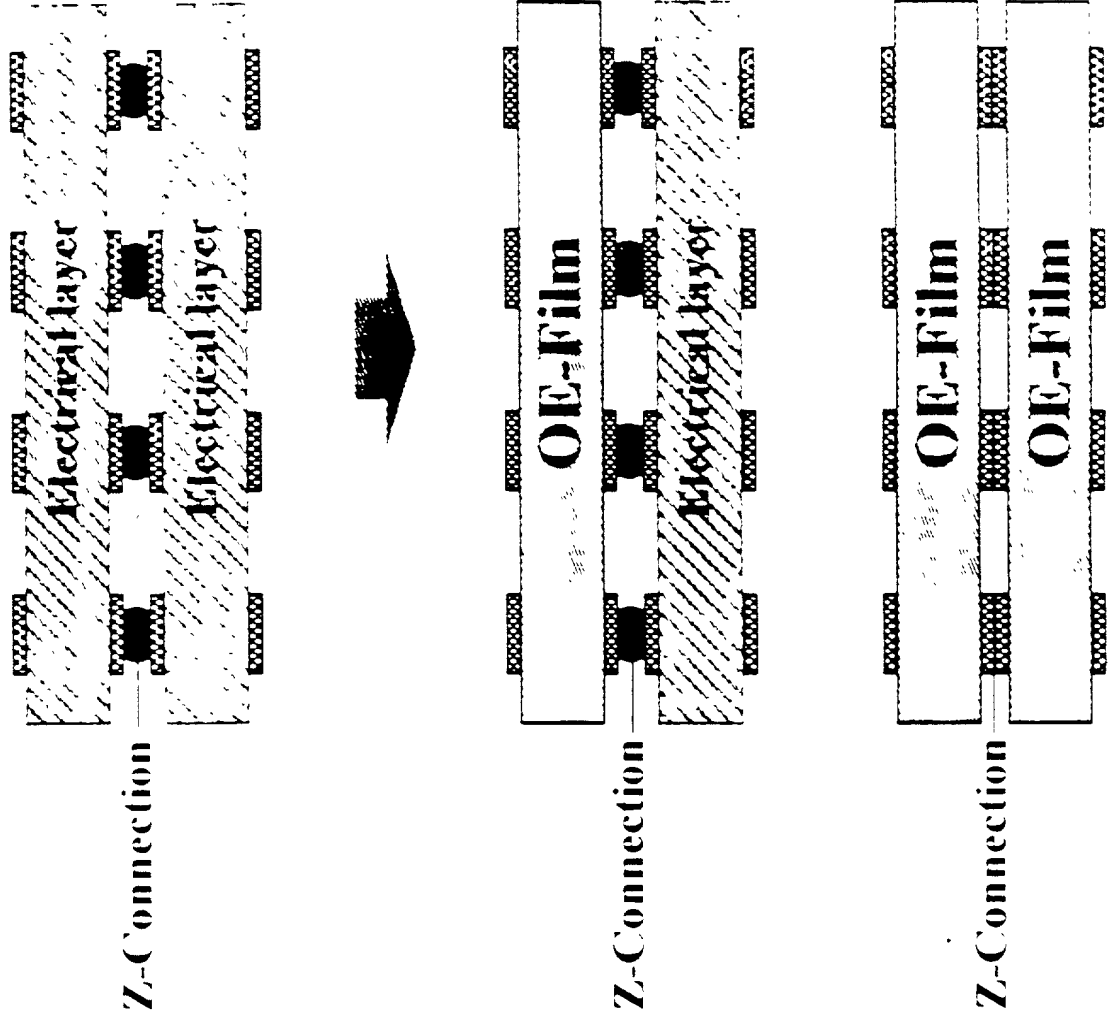
Fig. 110

A24

(2/23/99) AA2 Detail picture Example for 3D-stack'

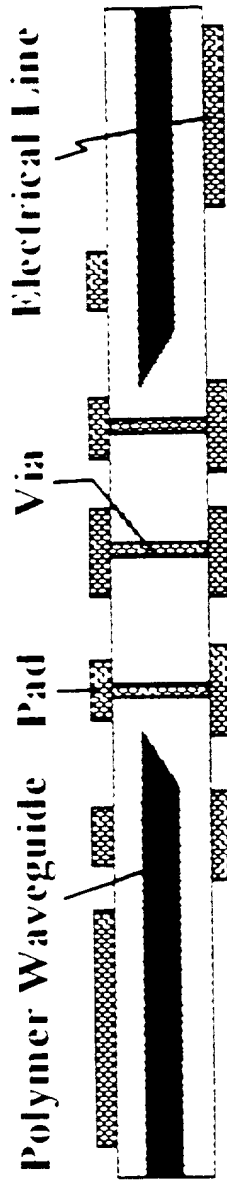
(New version of the AA2 of 2/5/99)

Film/Z-Connection Application to OE-Substrate



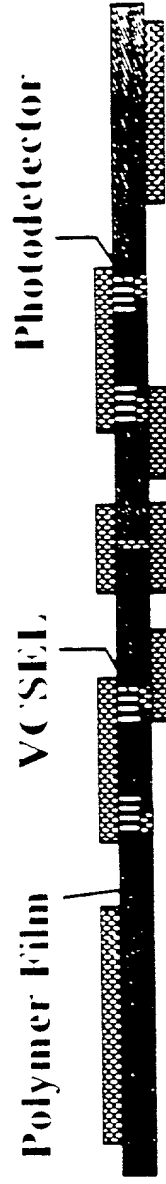
47

OE-Films



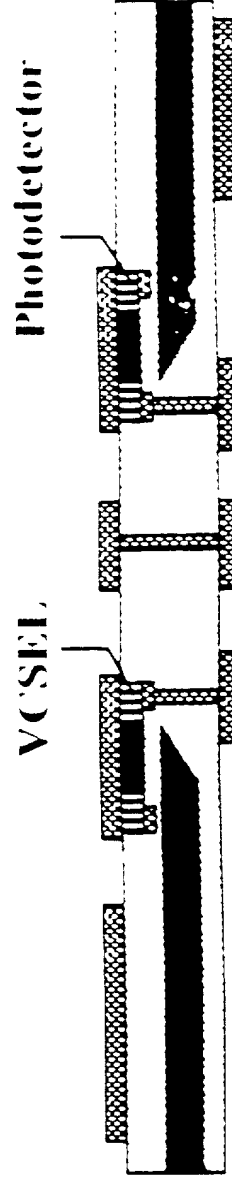
OE-film-W

FIG. 113



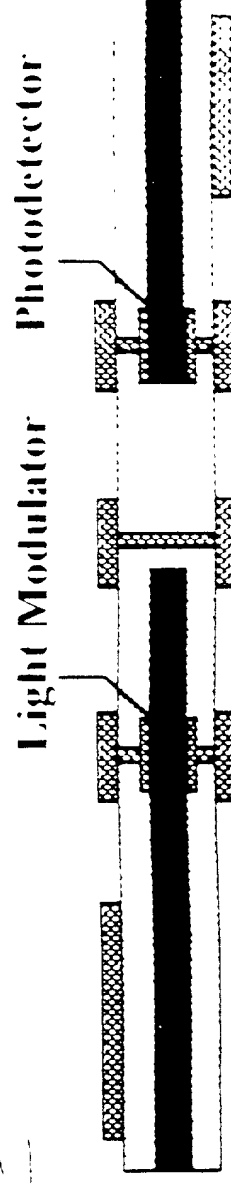
OE-film-D

FIG. 114
A8



OE-film-DW(V)

FIG. 115



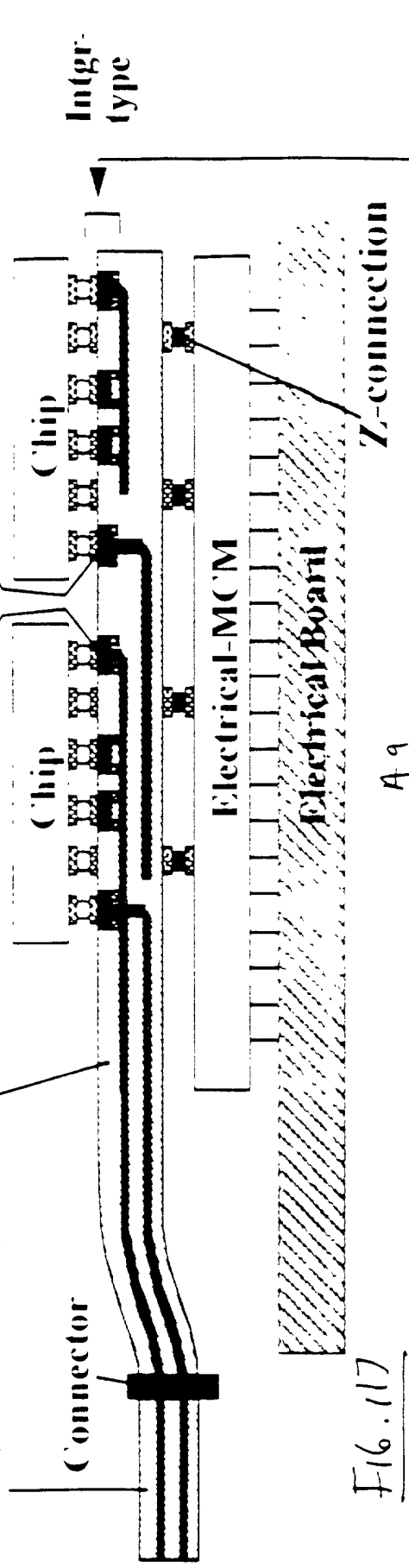
OE-film-DW(M)

2/17/99-added 2

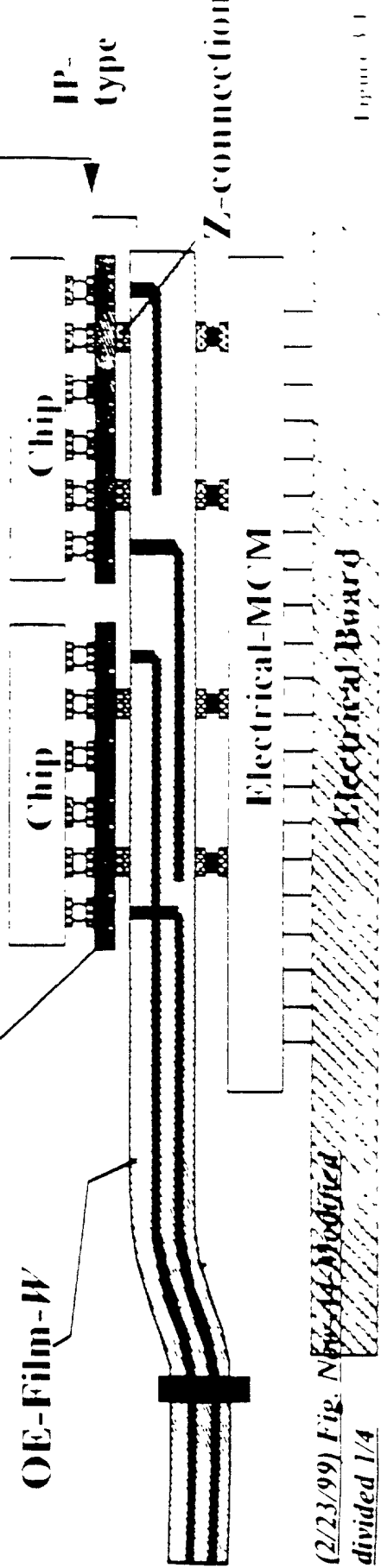
FIG. 116
117

FOLM

**Fiber Array OE-Film-DW (1)
Image Guide Waveguide Array**



OE-Film-D



(2/23/99) Fig. New-14 Modified
divided 1/4

Fig. 118
10 2/23/99

FOLM

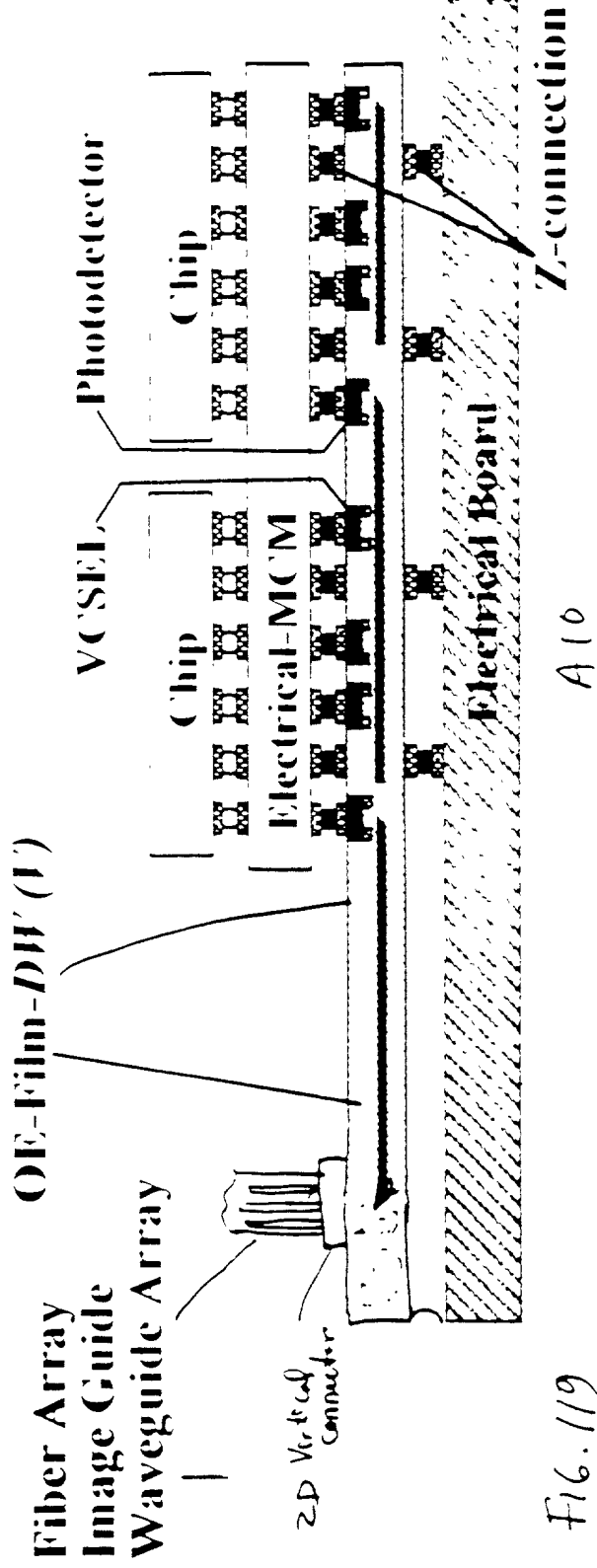
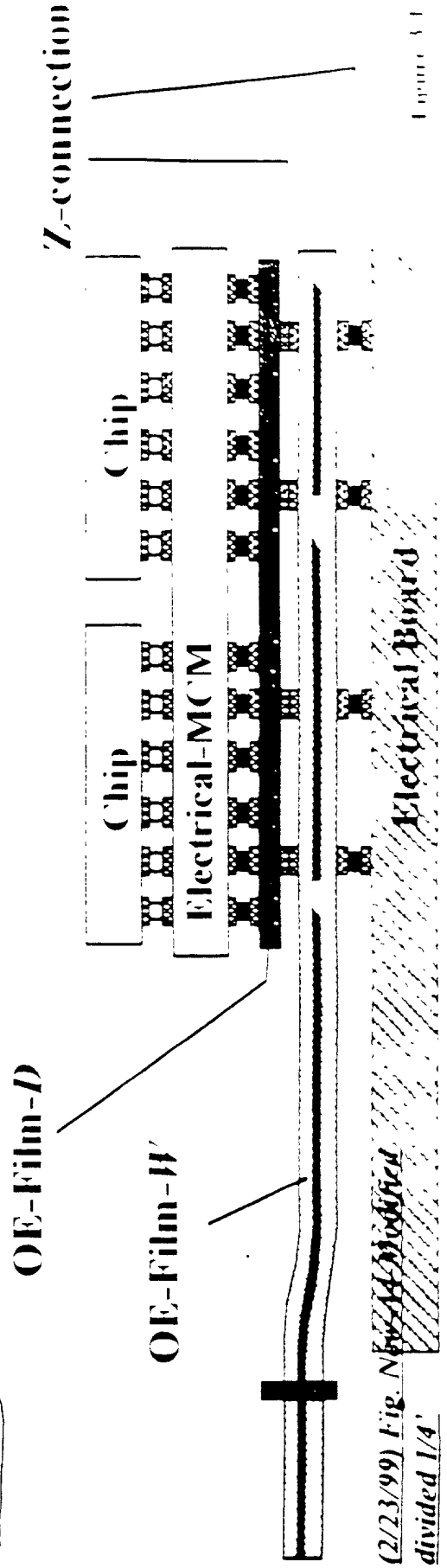


Fig. 119



(2/23/99) Fig. New-A4 Modified divided 1/4'

Fig. 120

FUJITSU Computer Packaging Technologies, Inc. **FCPT**
FOLM with Optical Path Length Controller, Connector Buffer

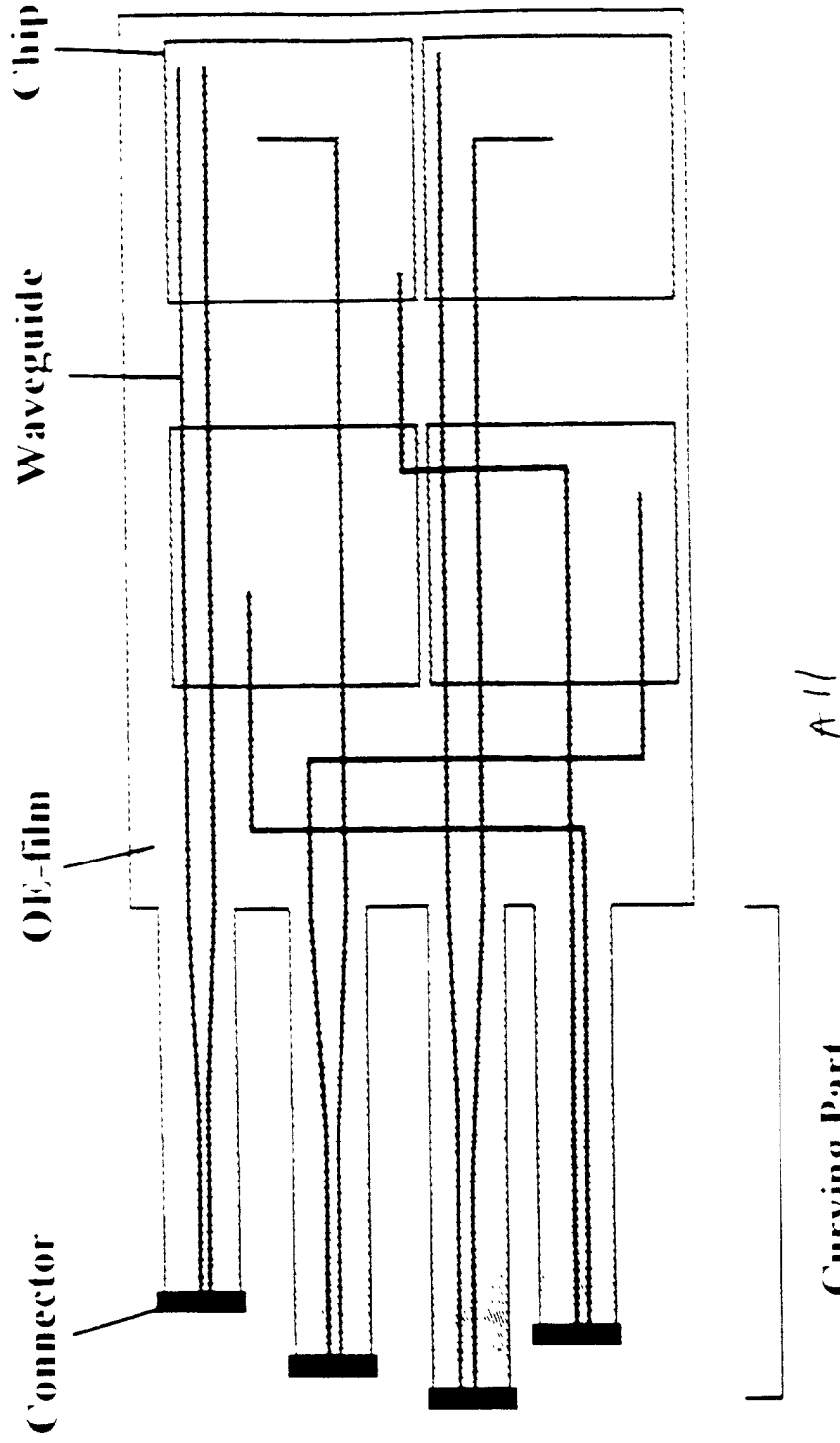


FIG. 121

(2/17/99) Fig. New-A4-Modified
divided 2/4

FUJITSU Computer Packaging Technologies, Inc. **FCPT**
FOLM with Optical Path Length Controller, Connector Buffer

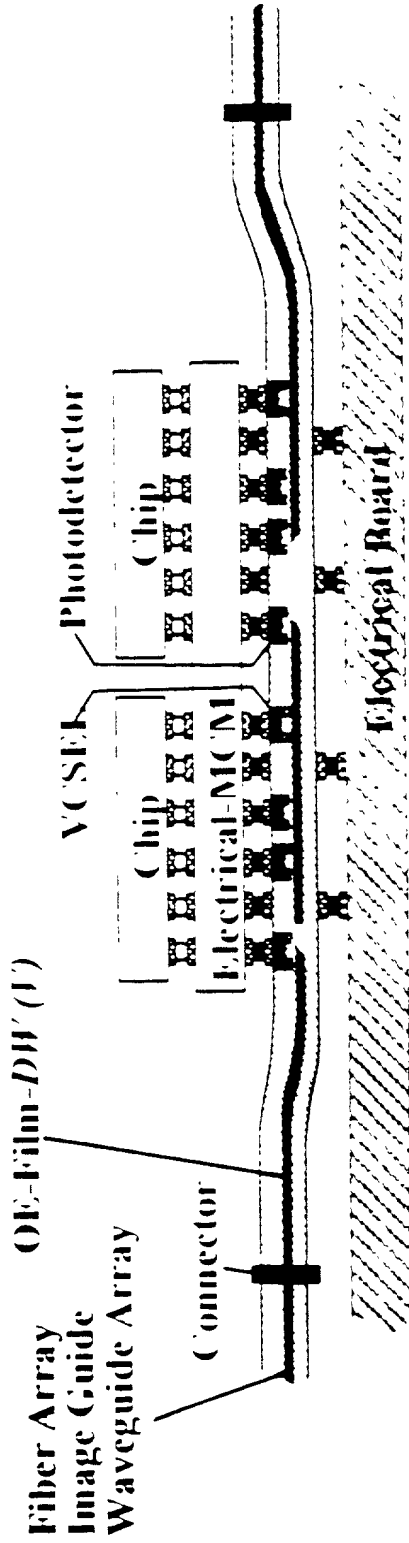


FIG. 123

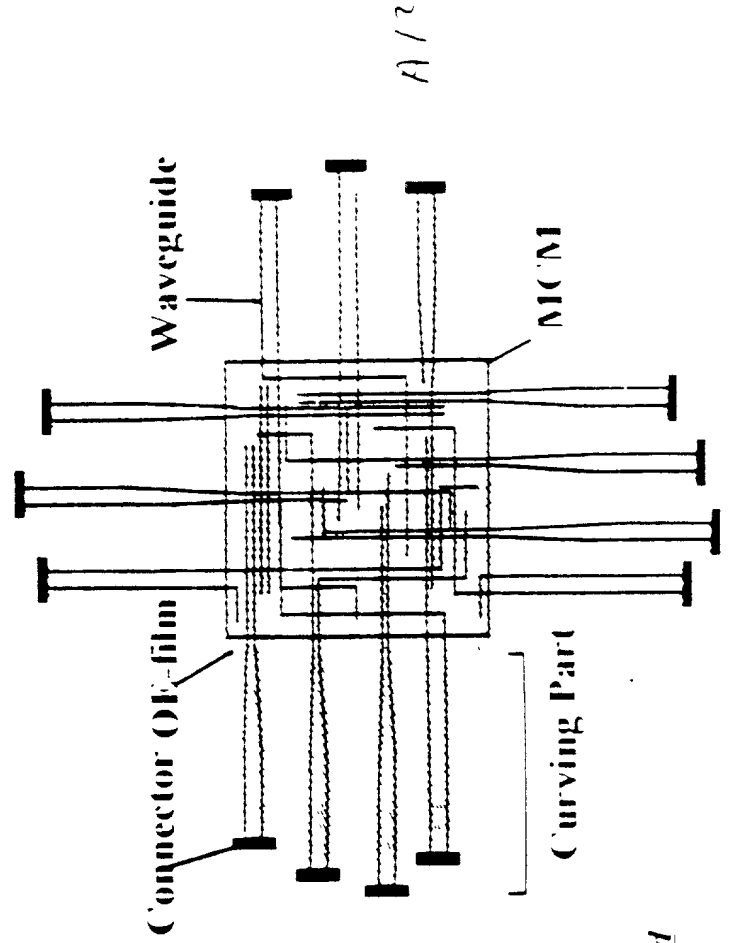
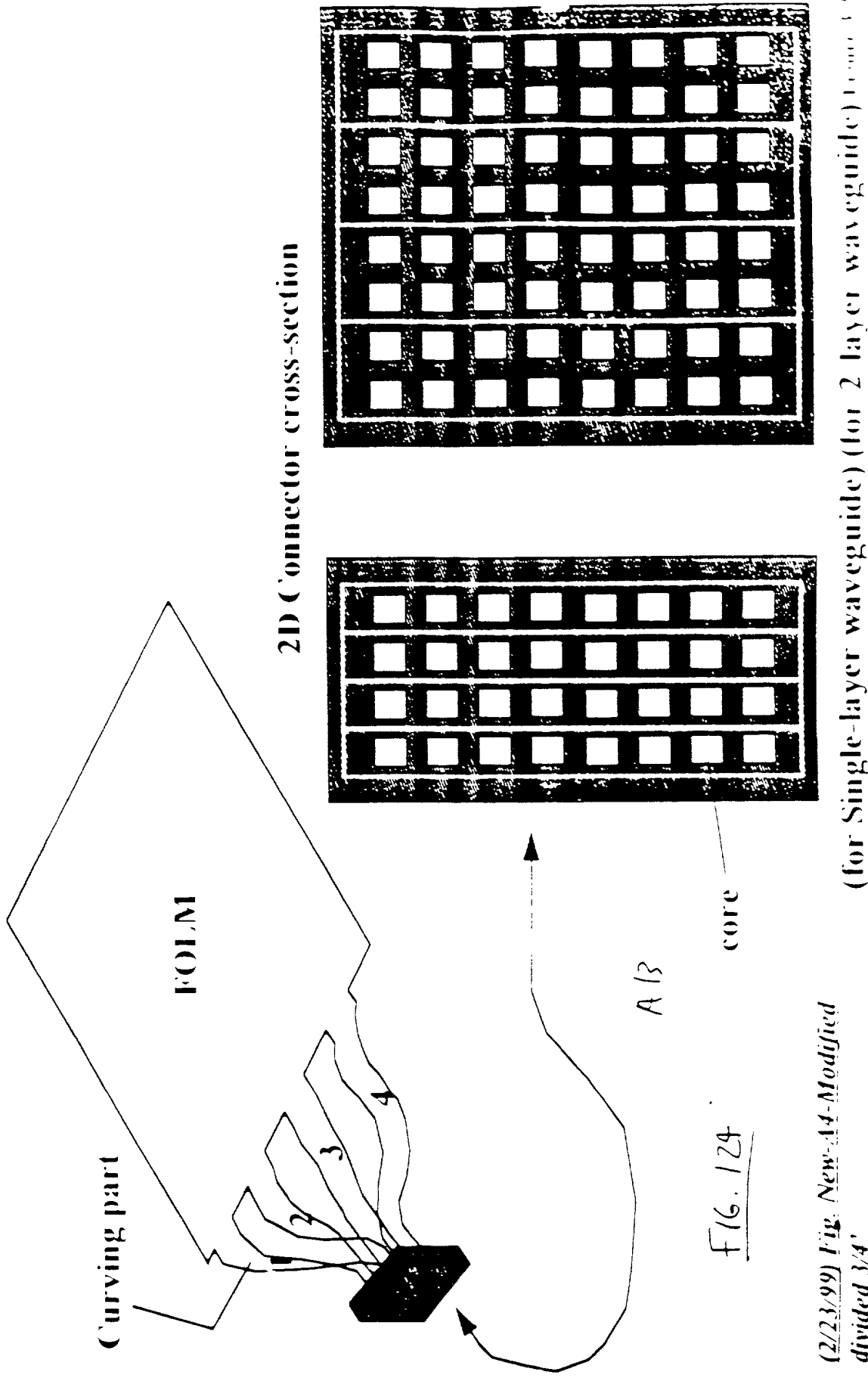


FIG. 122

(2/23/99) Fig. New-A4-Modified
 divided 2/4'

FOLM with 2D Waveguide Connector



(2/23/99) Fig. New-A4-Modified
divided 3/4

FOLM: High-Speed Option

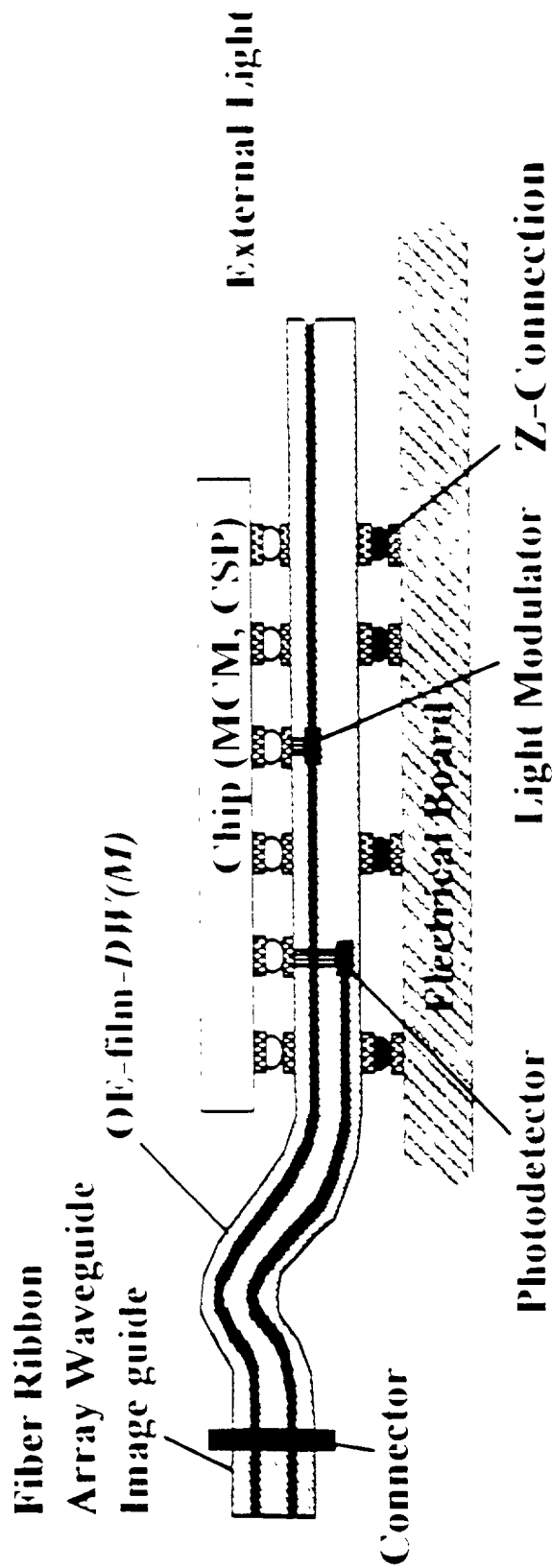


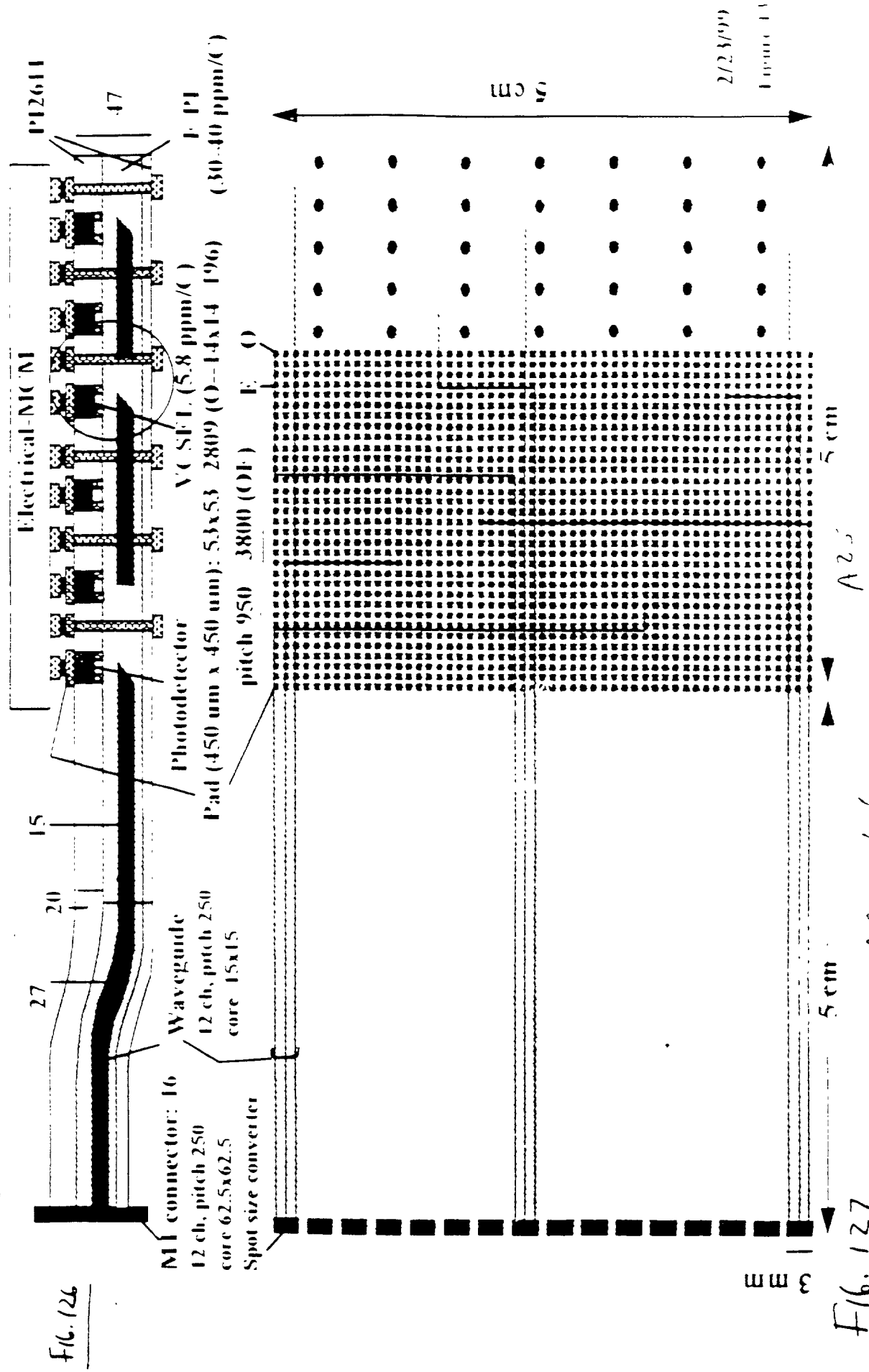
Fig. 125

A 14

FOLM Structure Example (Overall)

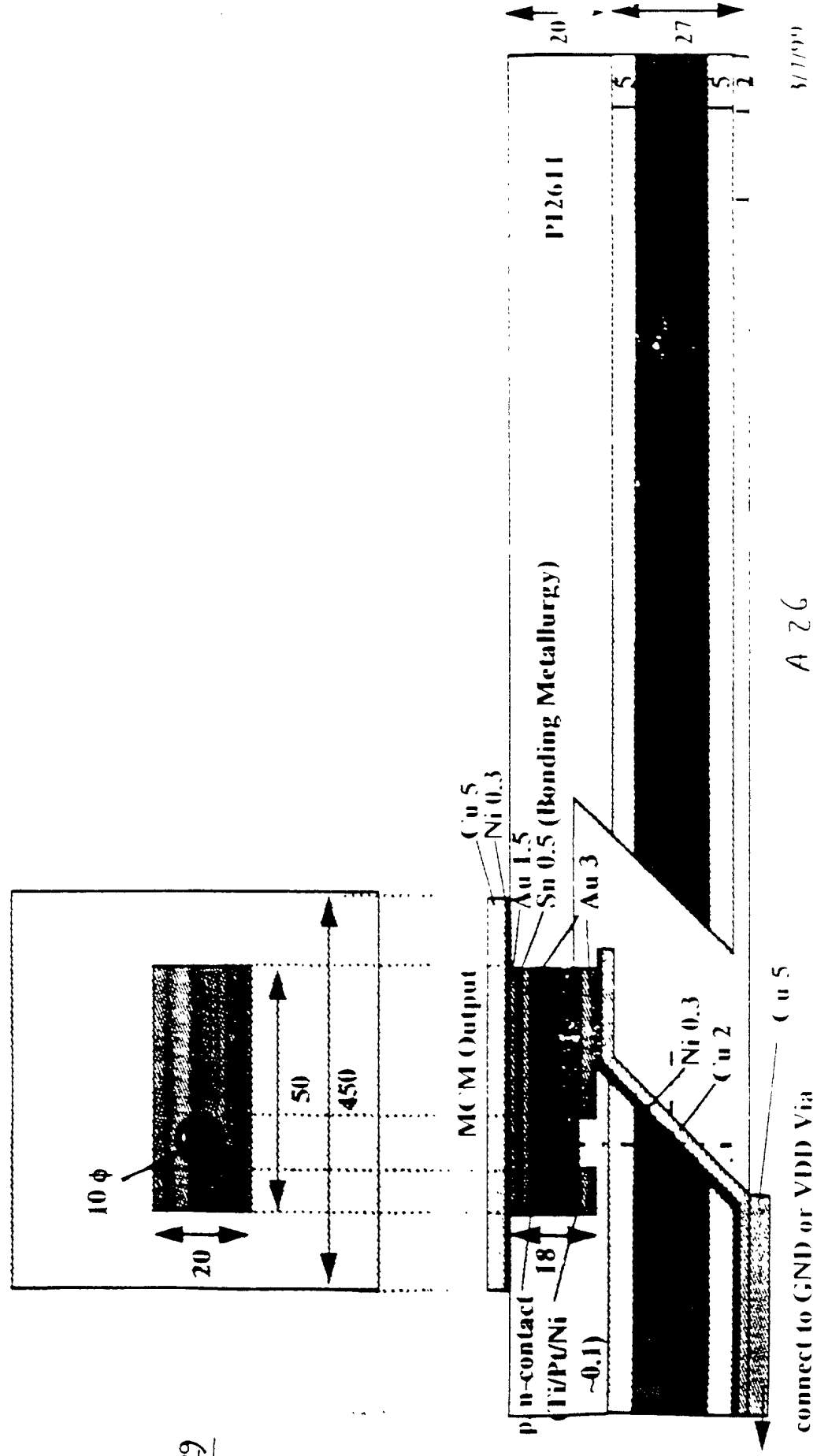
Through put: 1.5 pbs x 196 ch Assume SSA MCM Size is .5 cm x 5 cm

Unit: 100



F16.127

FUJITSU Computer Packaging Technologies, Inc. FCPT
FCOLM Structure Example (VCSEL part)



A 26

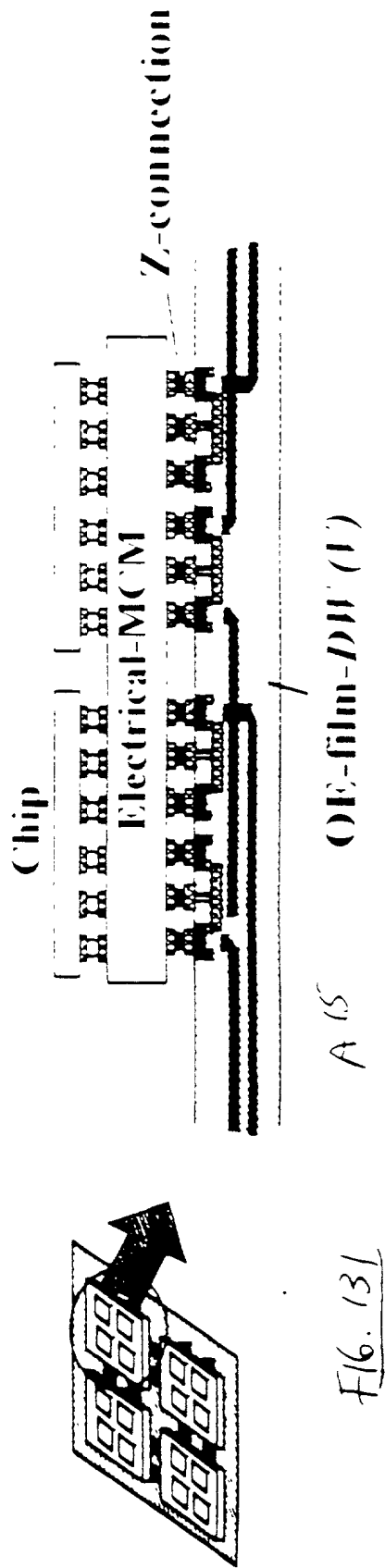
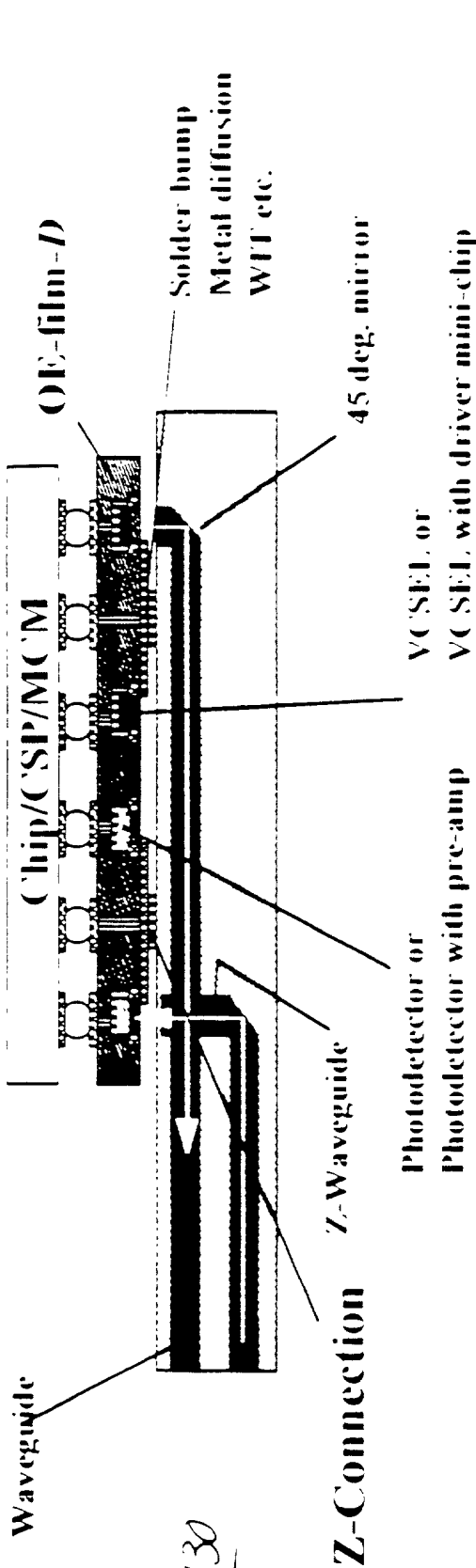
3/1/99

Unit : mm

Fig. 128

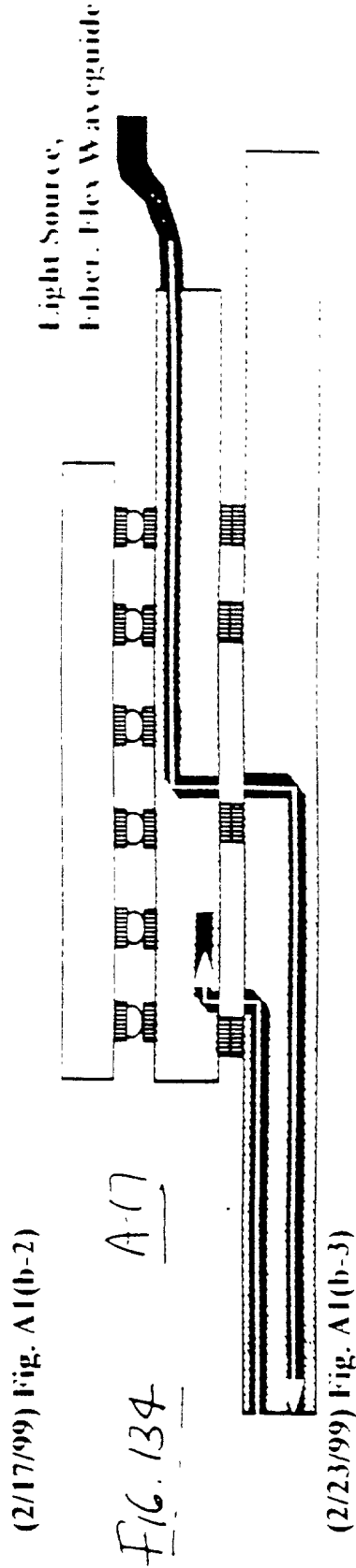
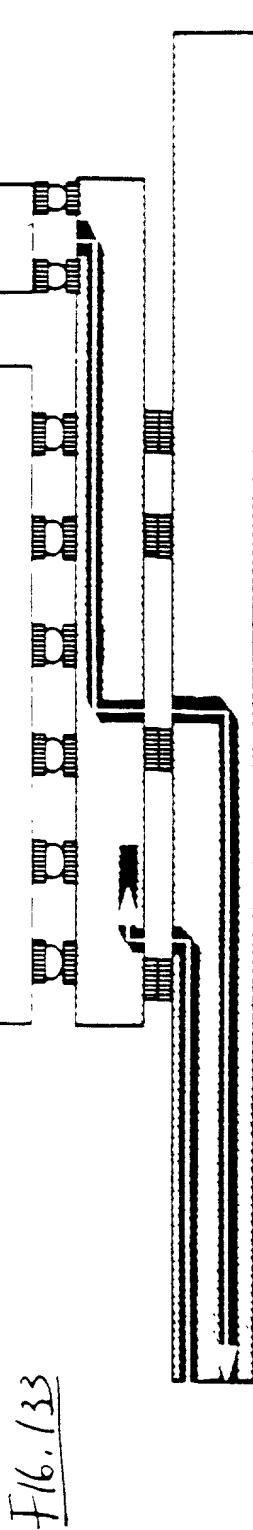
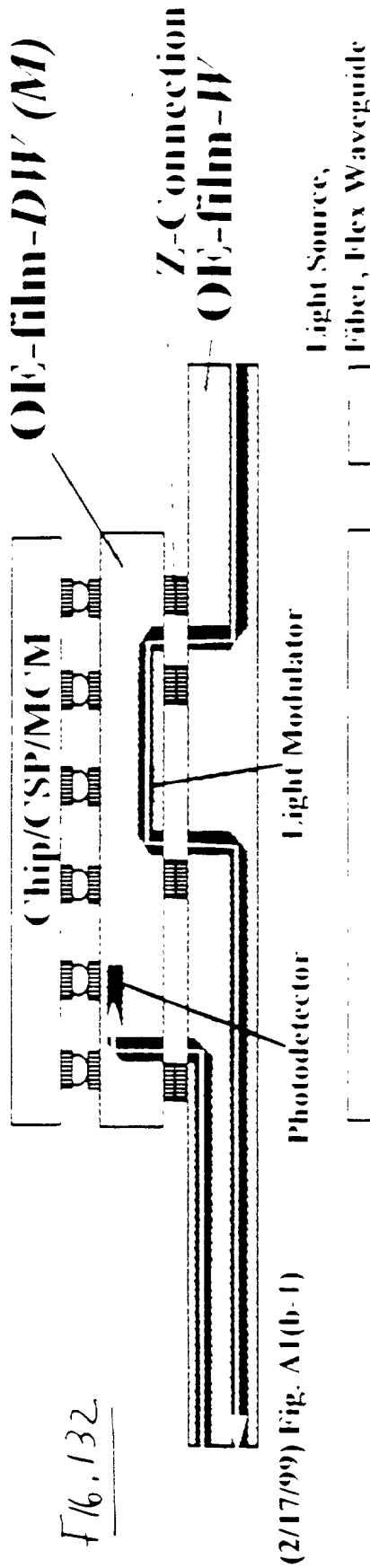
Fig. 129

OE-film: OE-IP, OE-Film-MCM



(2/23/99) Fig. New-A1-Modified

OE-film: Light Modulator Transmitters



OE-film: Both-Side Packaging

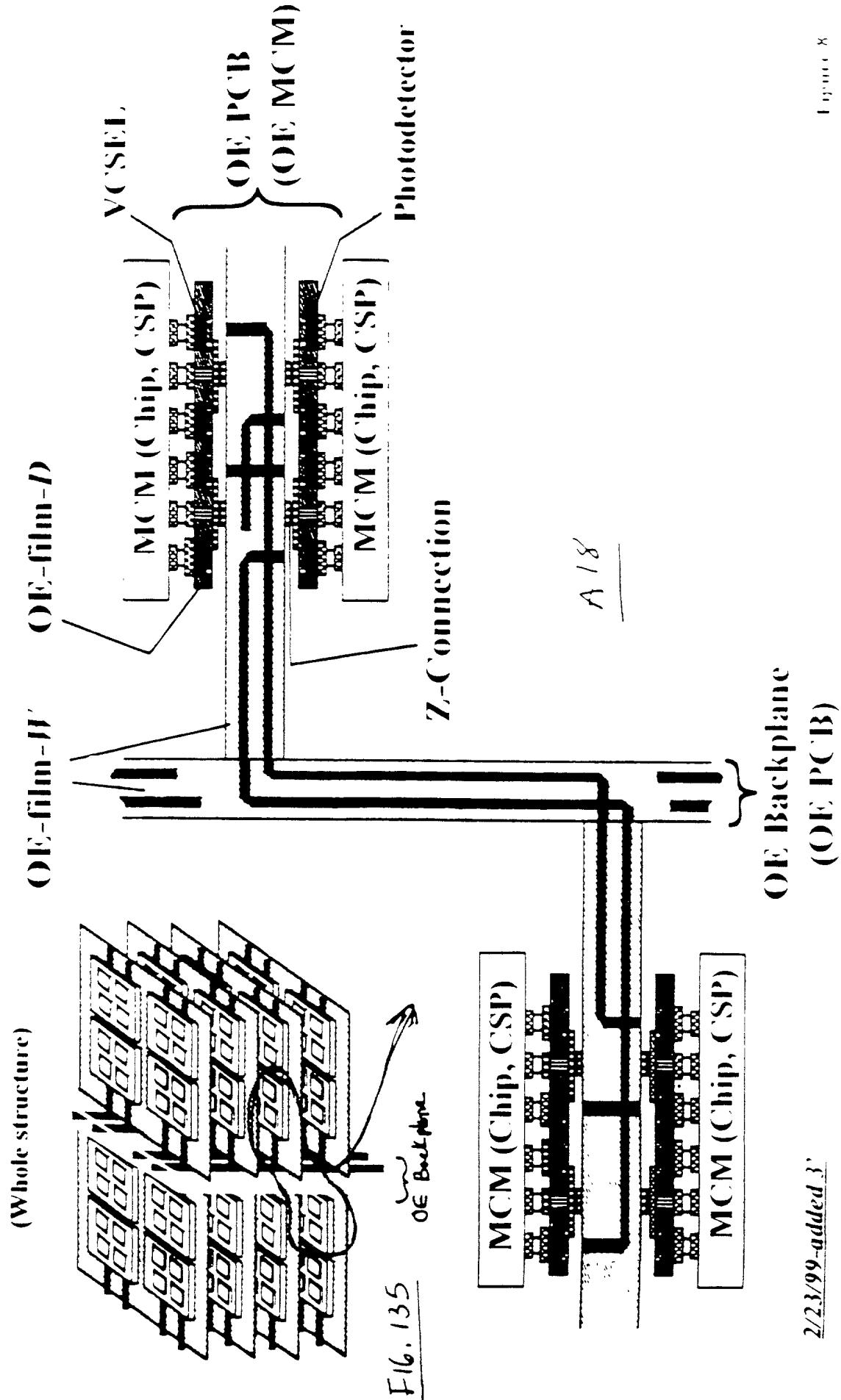
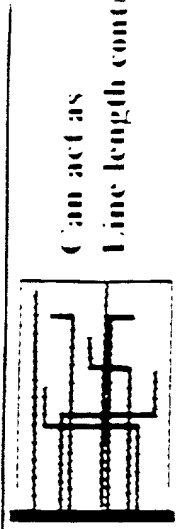


Fig. 135

Direct Jump from LSI



Fiber Ribbon Film Waveguide with Device Integration

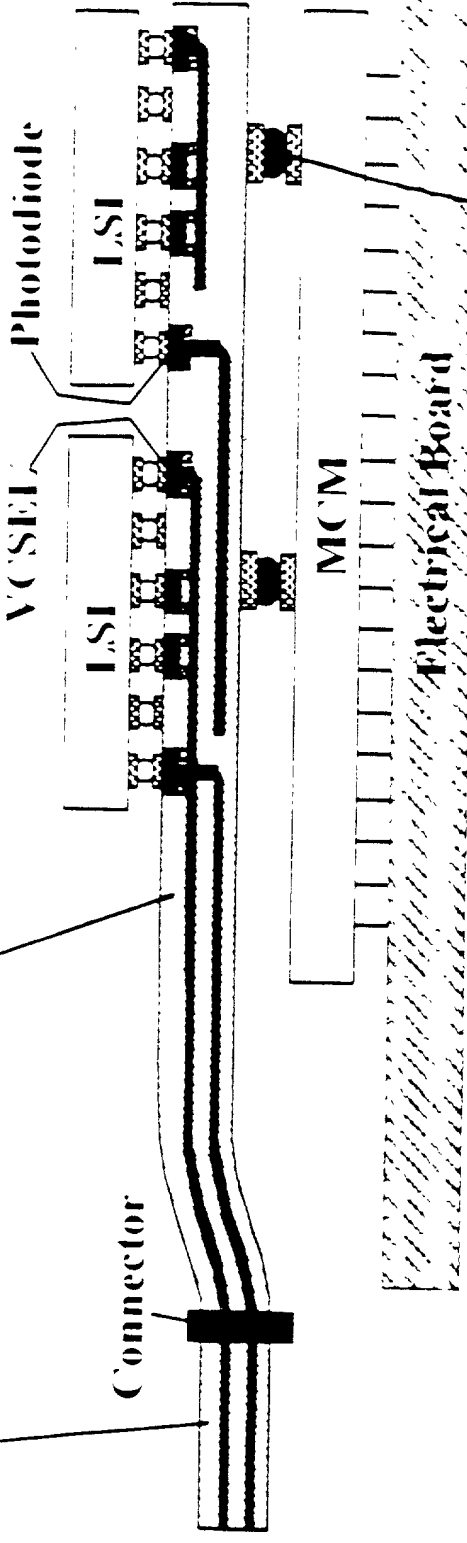


Fig. 136

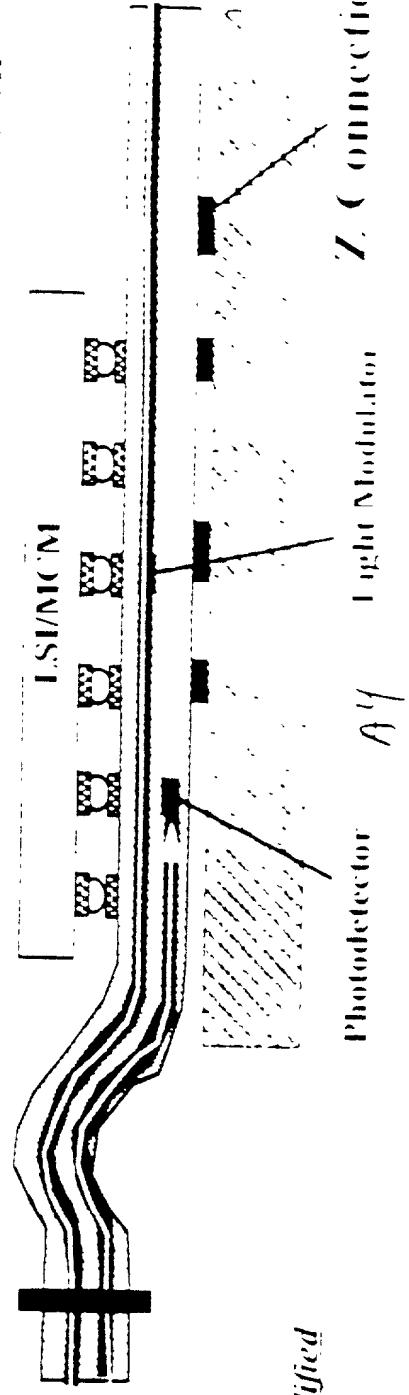
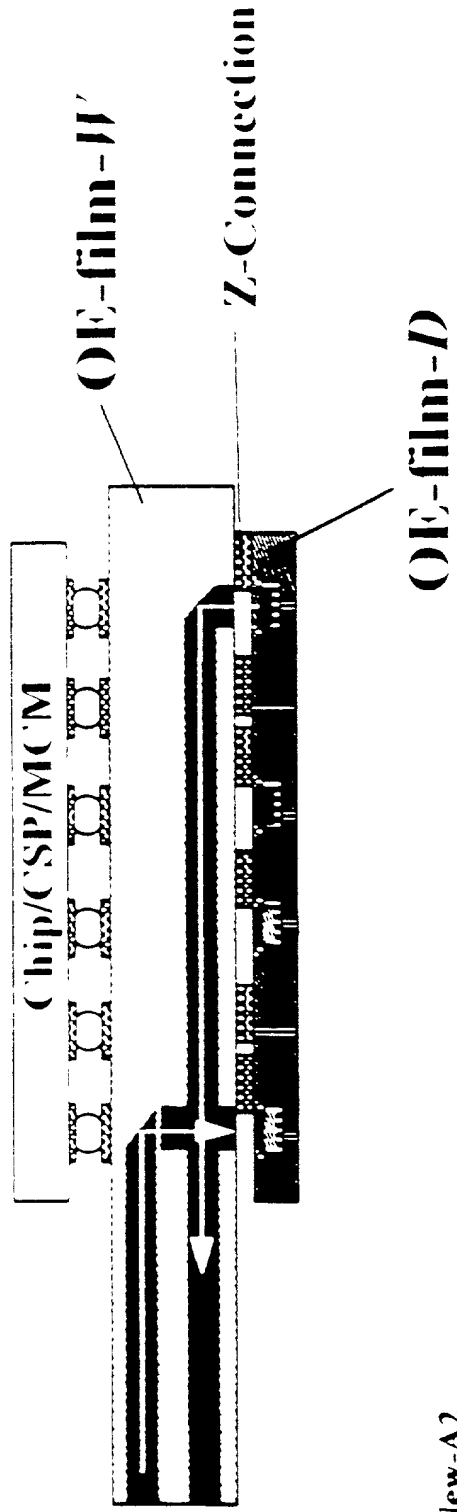


Fig. 137

Fig. New-44-Modified

OE IP is Placed on the Oposit Side



(2/23/99) Fig. New-A2

FL6.138

A20

OF MCM

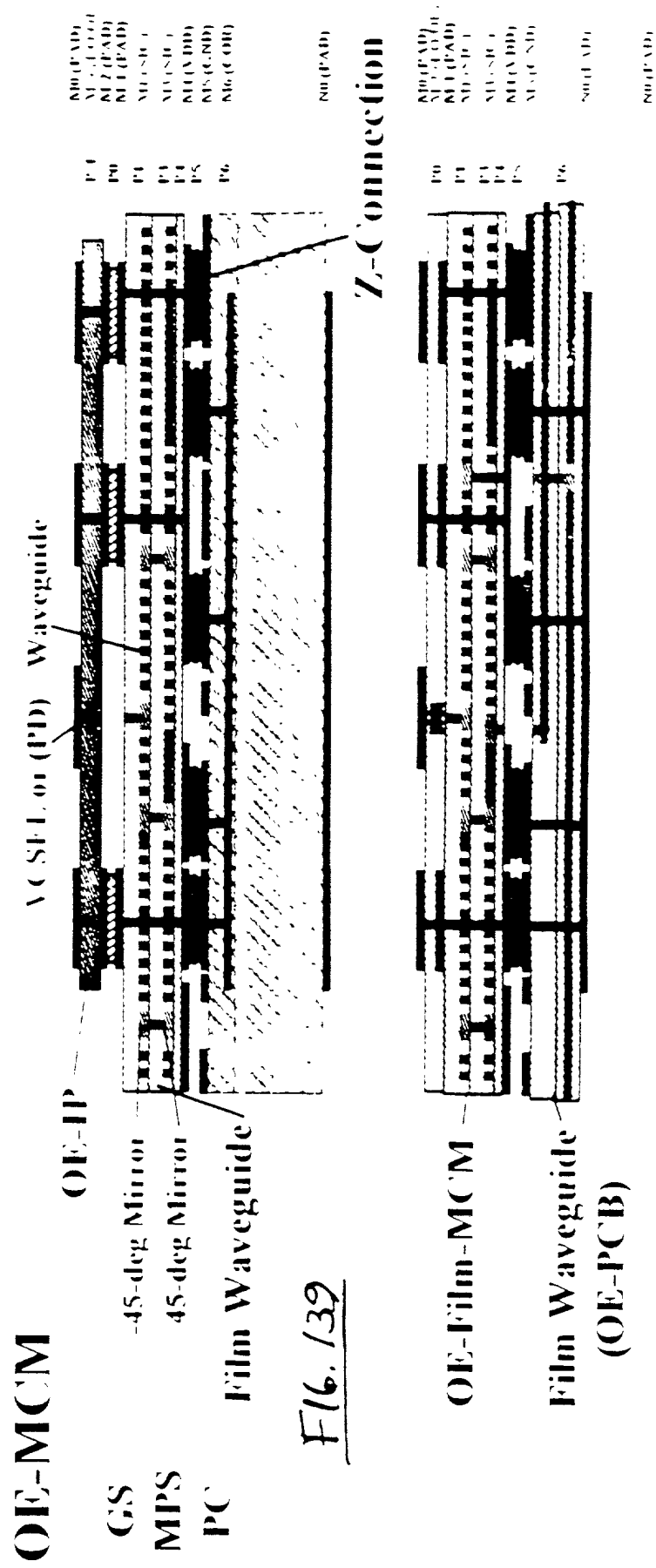


Fig. A5-Modific

F/6.140

A5 1/18/99

OE-film: Smart Pixel



Fig 141

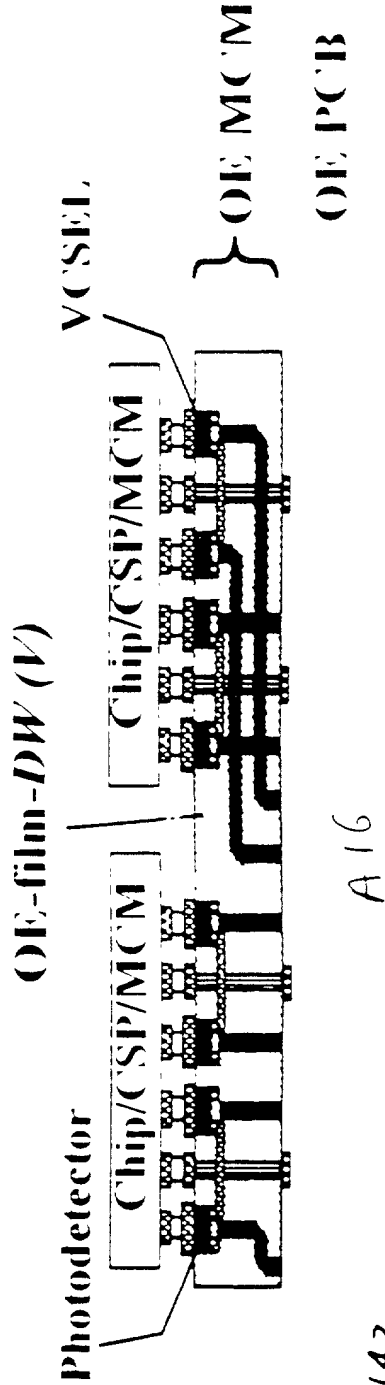


Fig. 142

OE-Film/OE-Film Stack --- Back-Side Connection

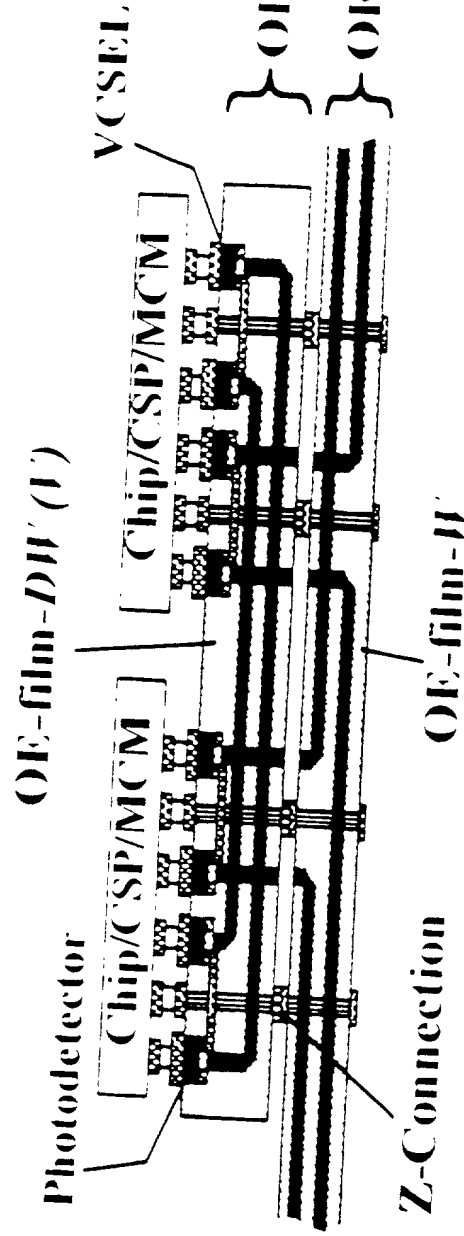
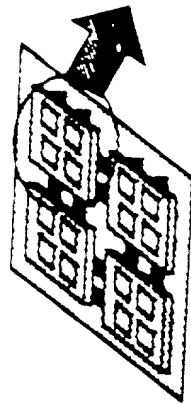


FIG. 14B

A19

2/23/99-added 4'

Figure 9

OE-MCM/OE-Bord Stack

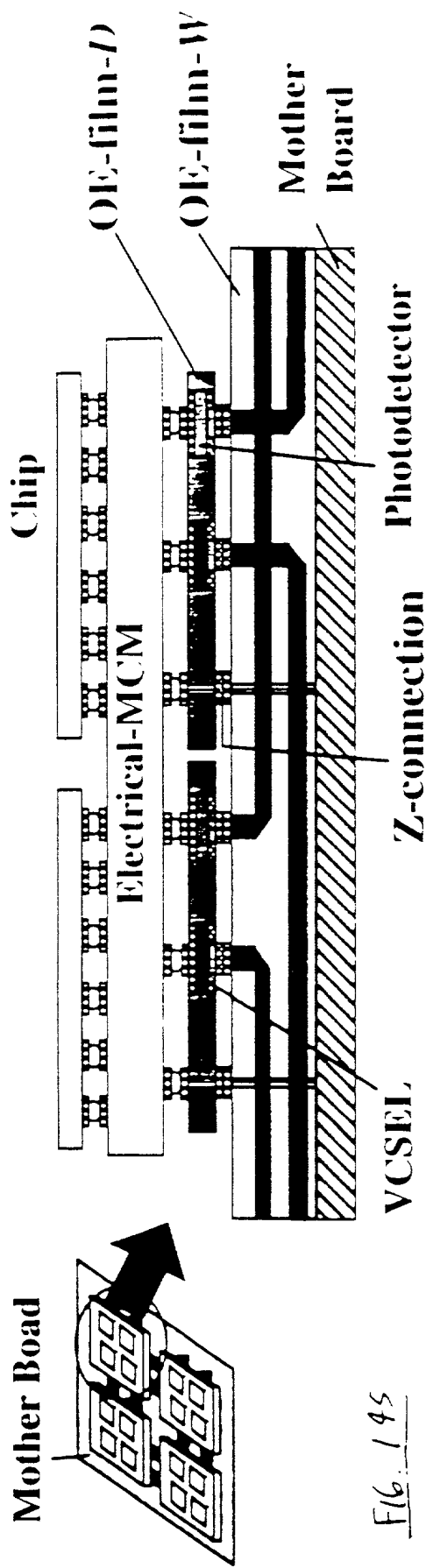


Fig. 145

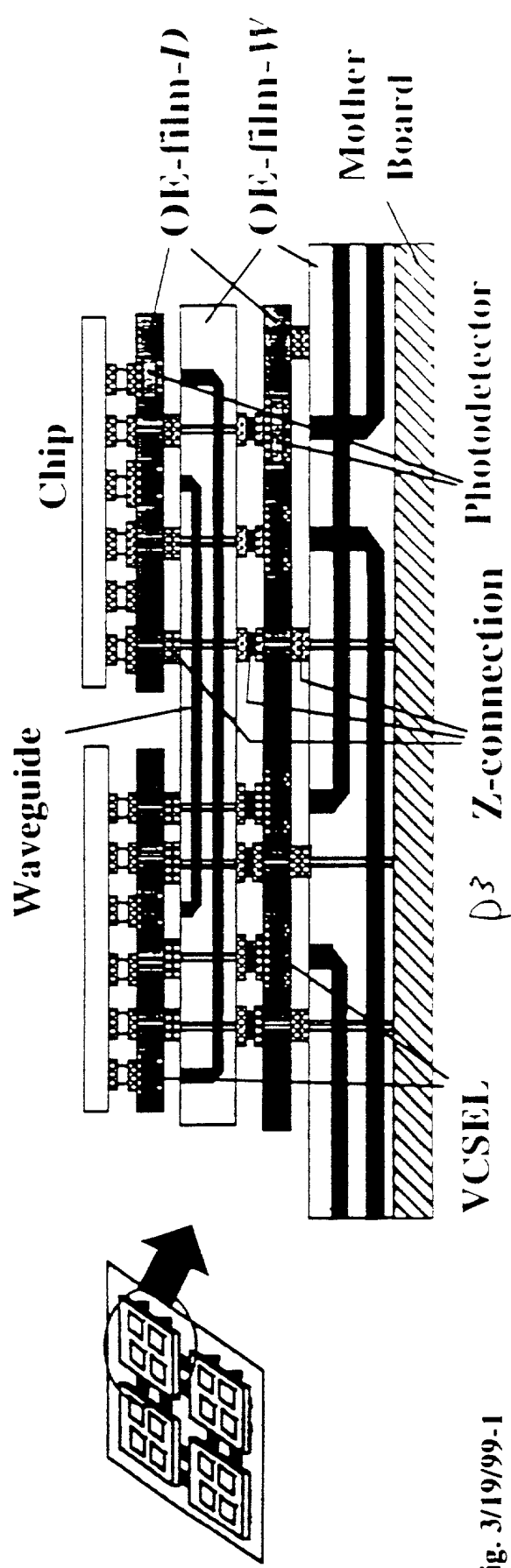
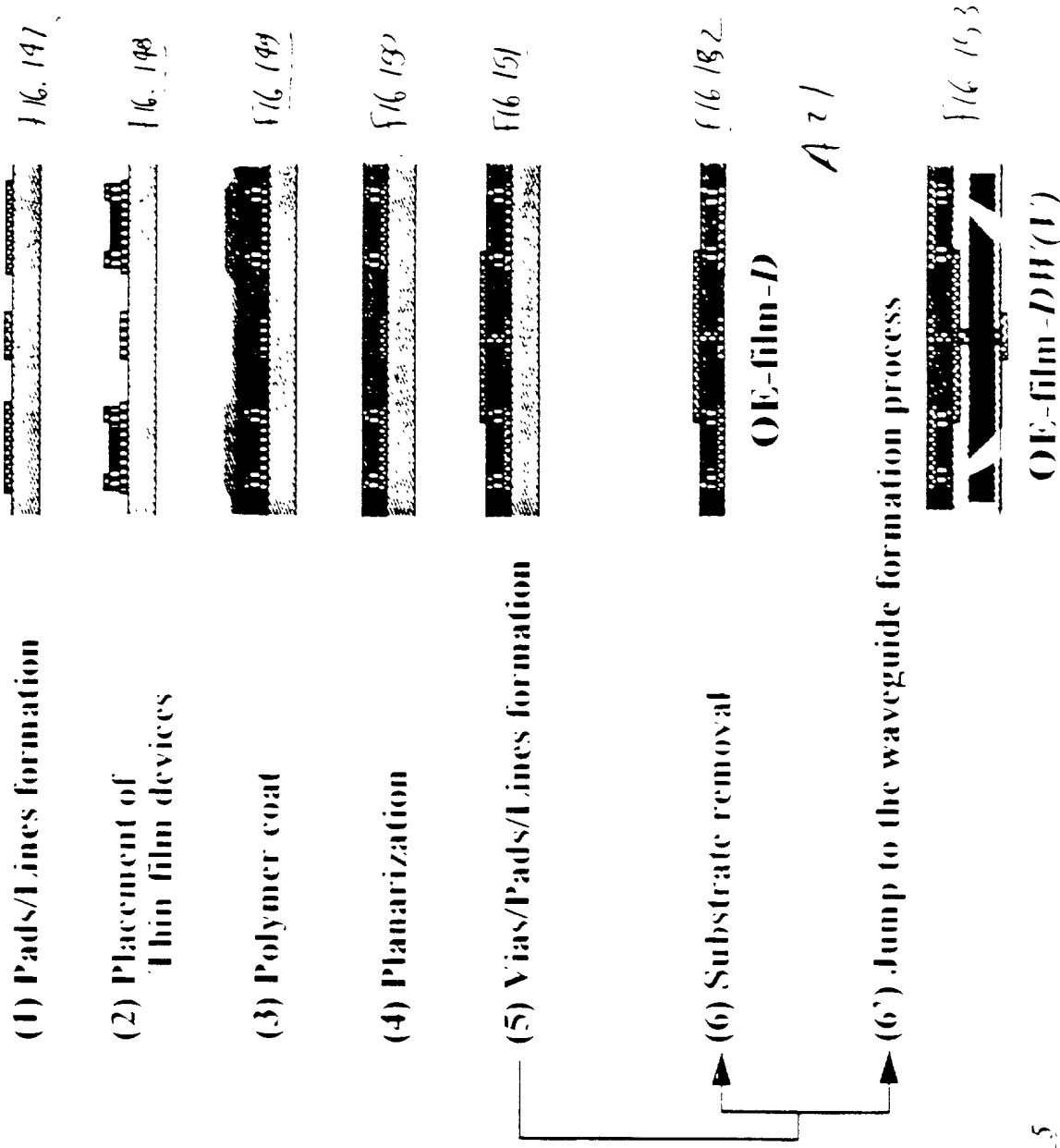


Fig. 3/19/99-1

Fig. 146

Device Integration Process



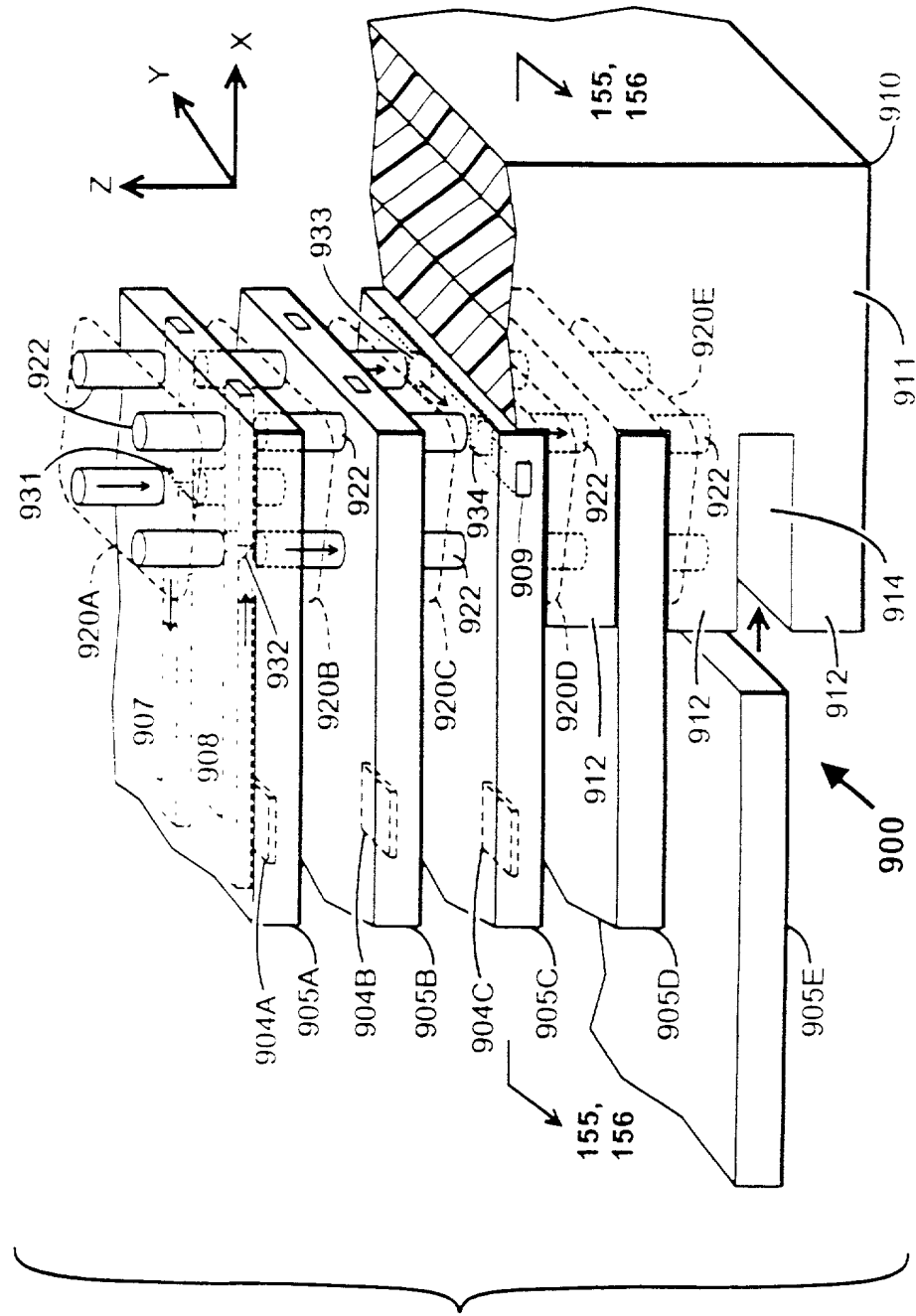


FIG. 154

1/XX

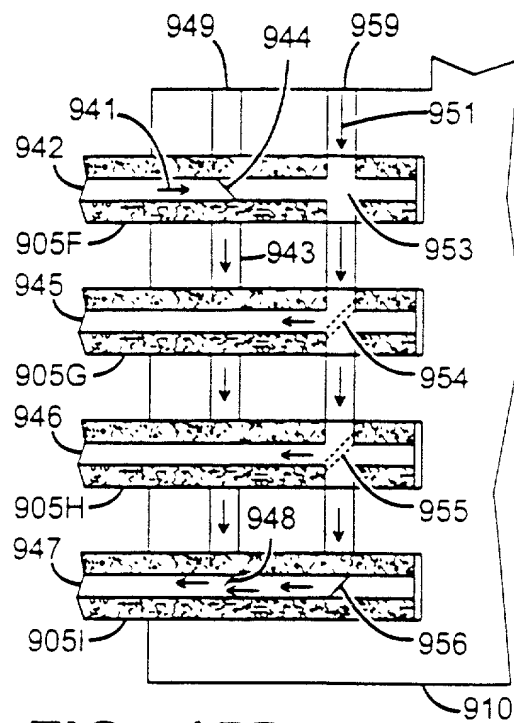


FIG. 155

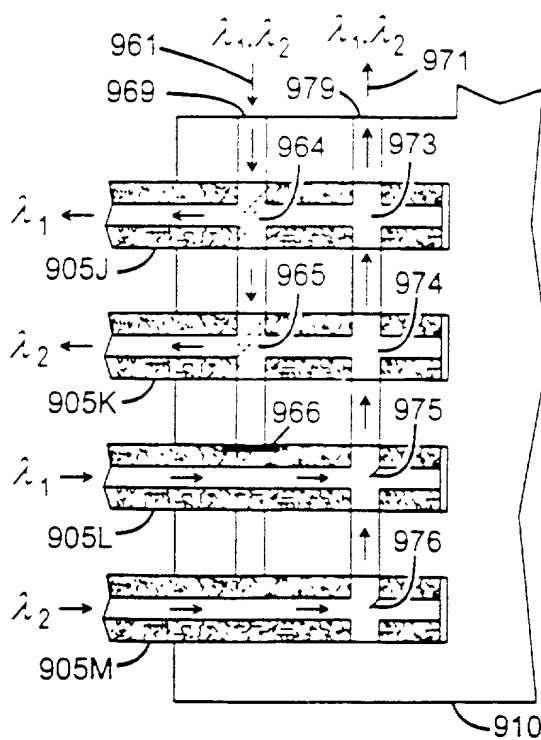


FIG. 156-1

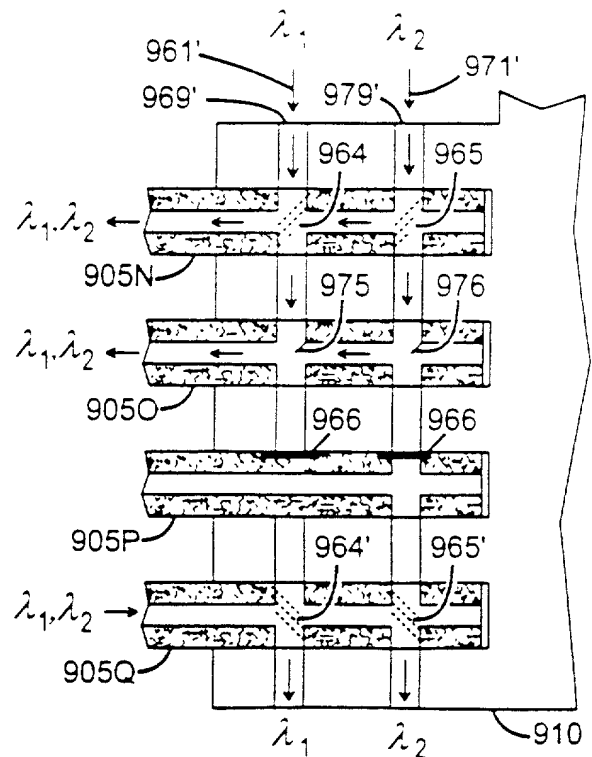


FIG. 156-2

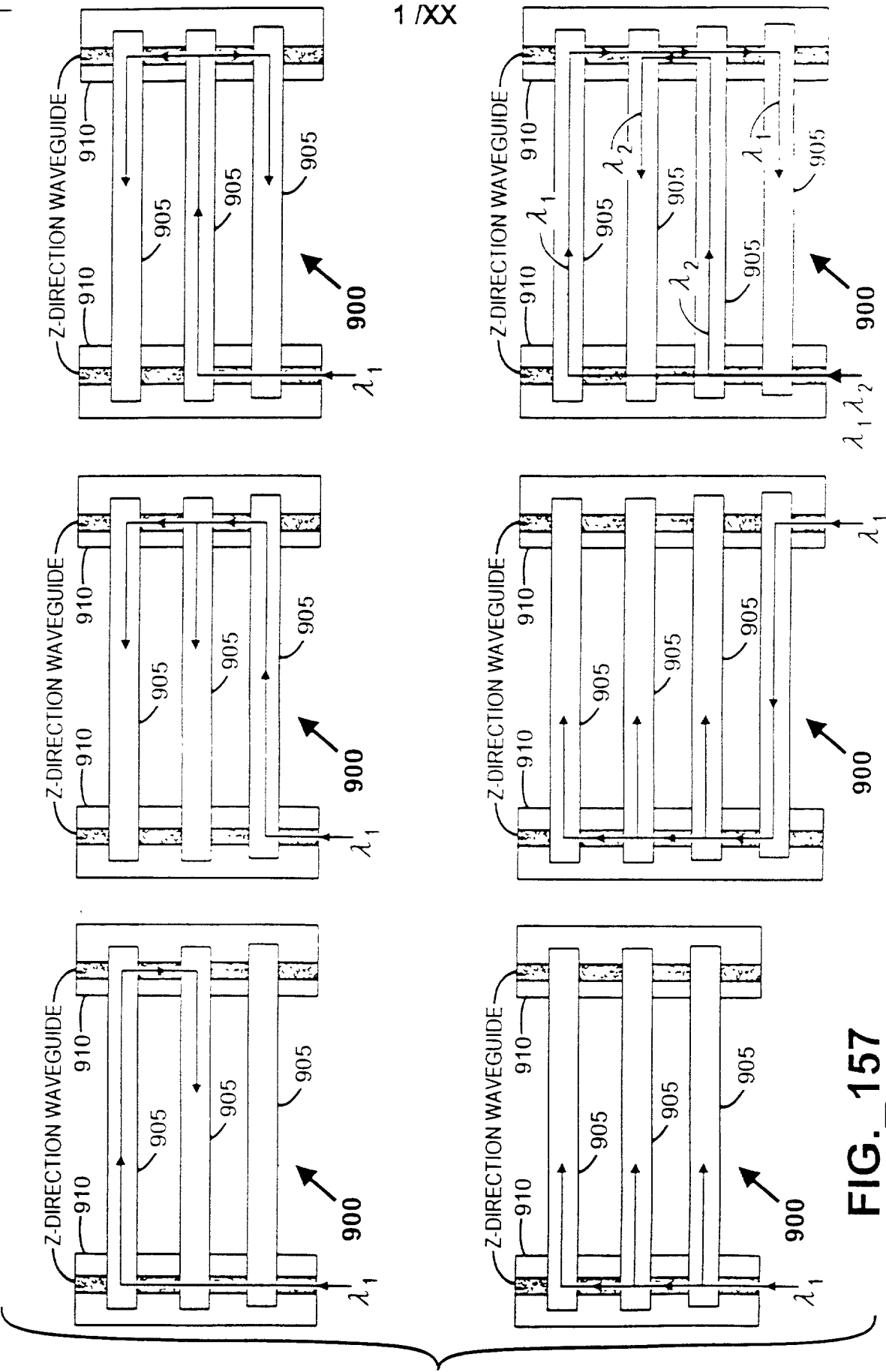


FIG. 157

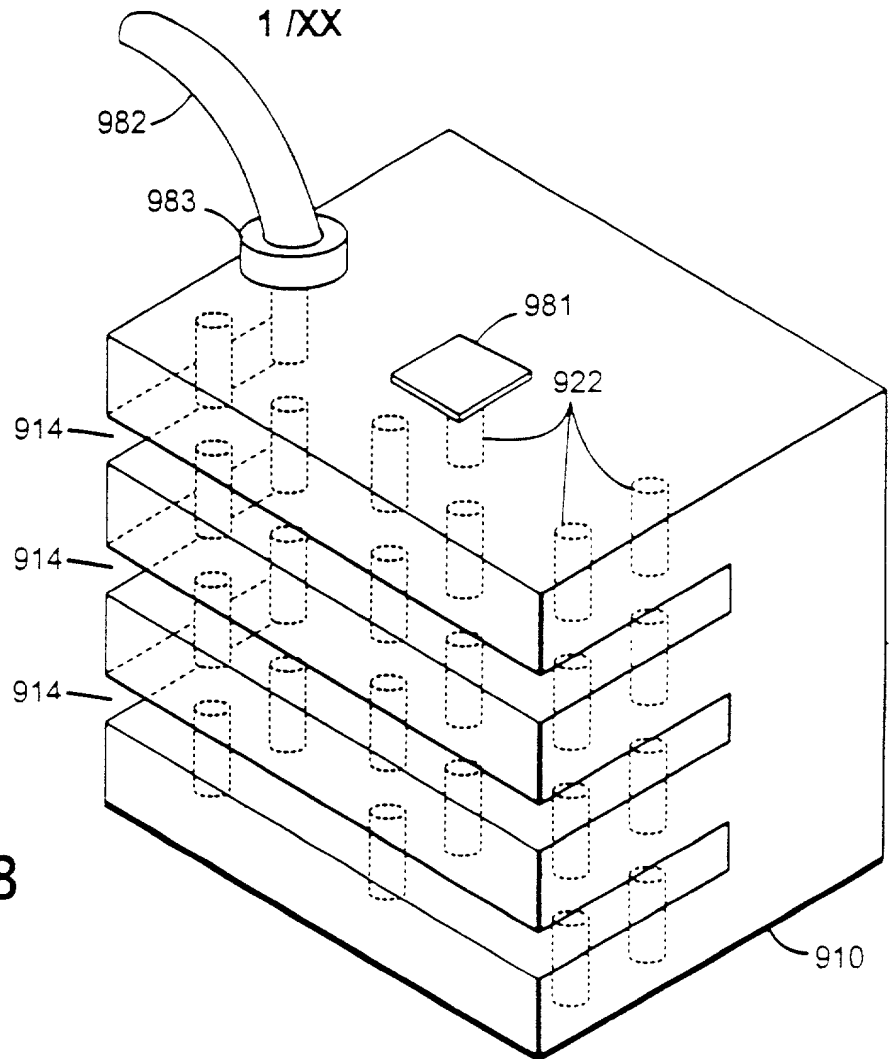


FIG._158

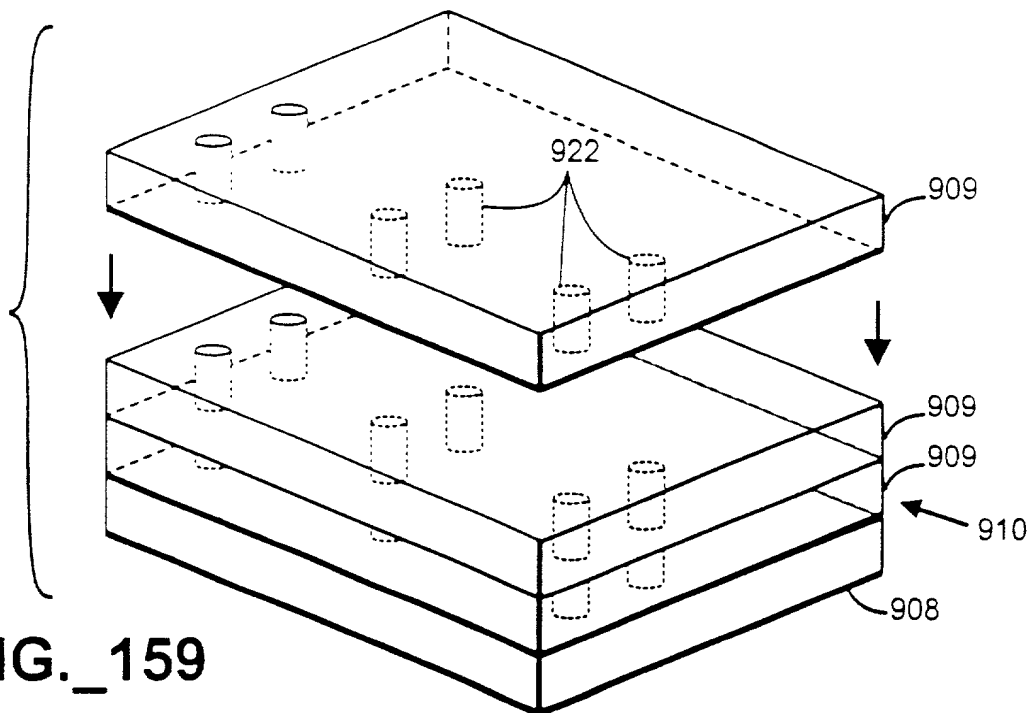


FIG._159

FIG._160

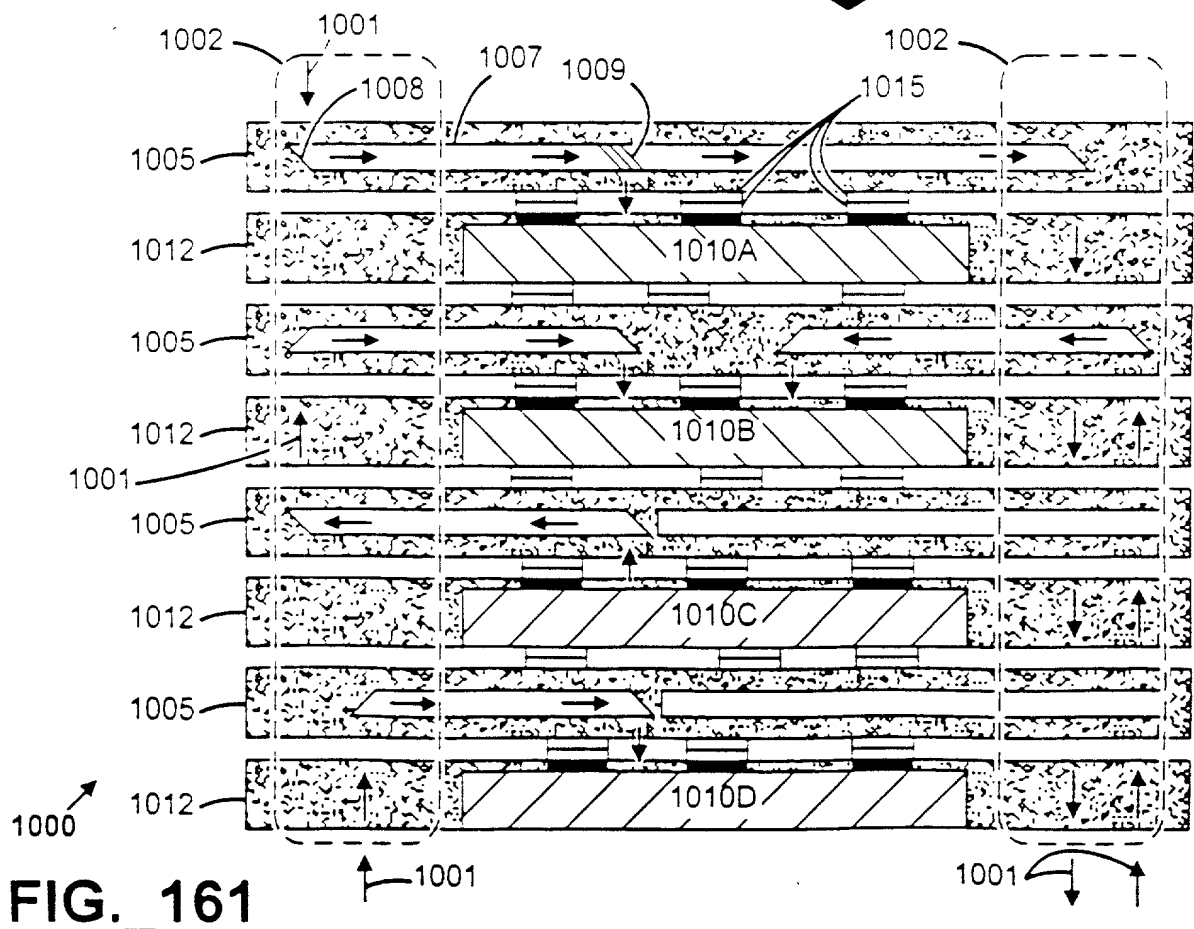
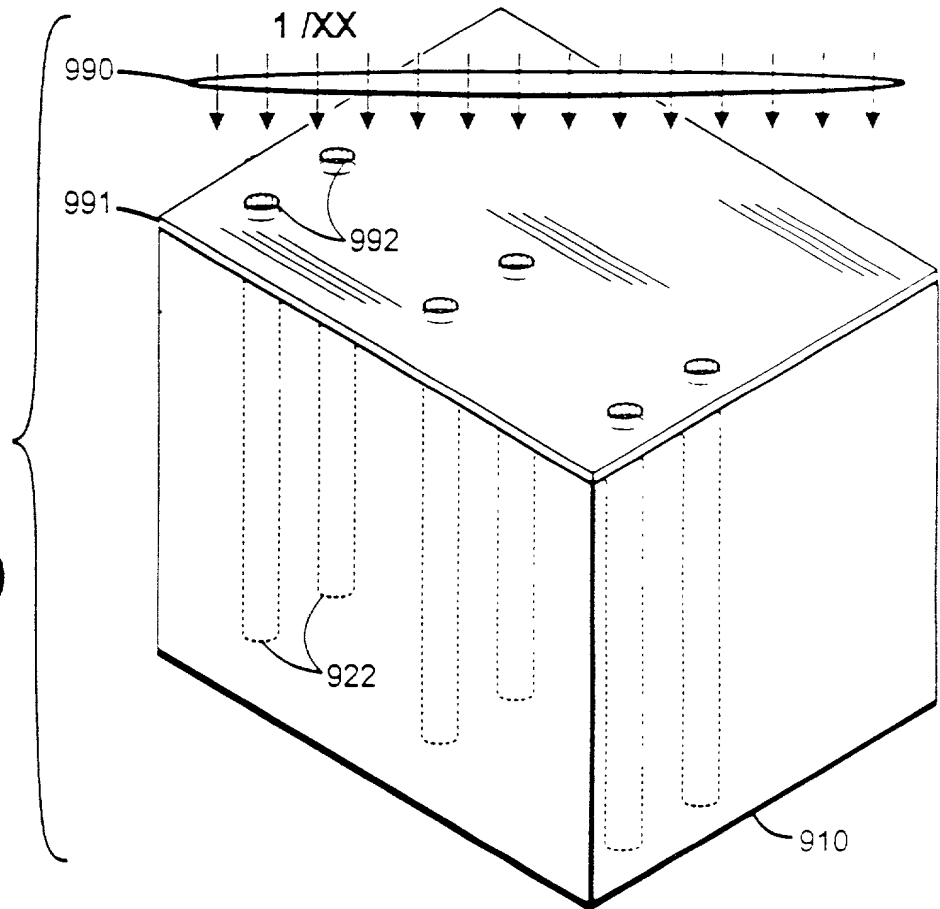
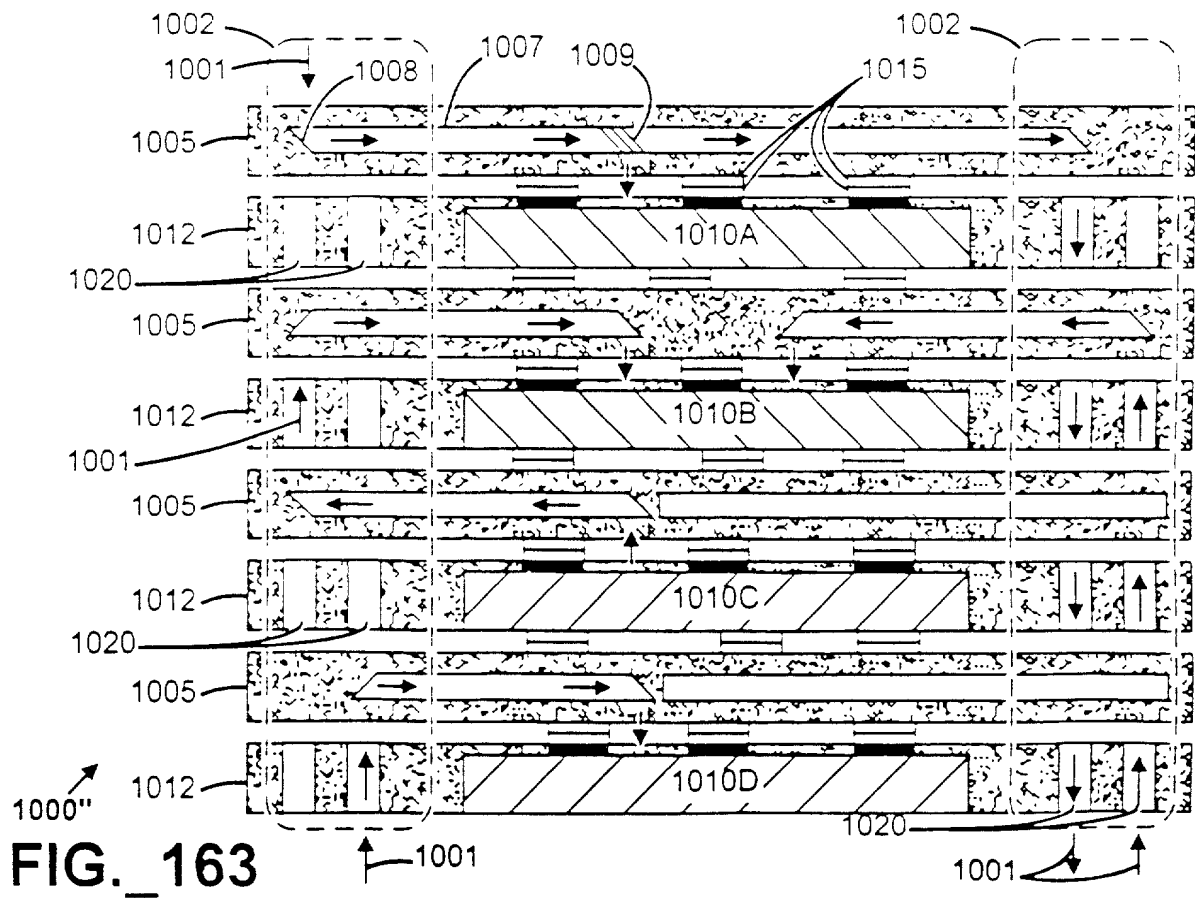
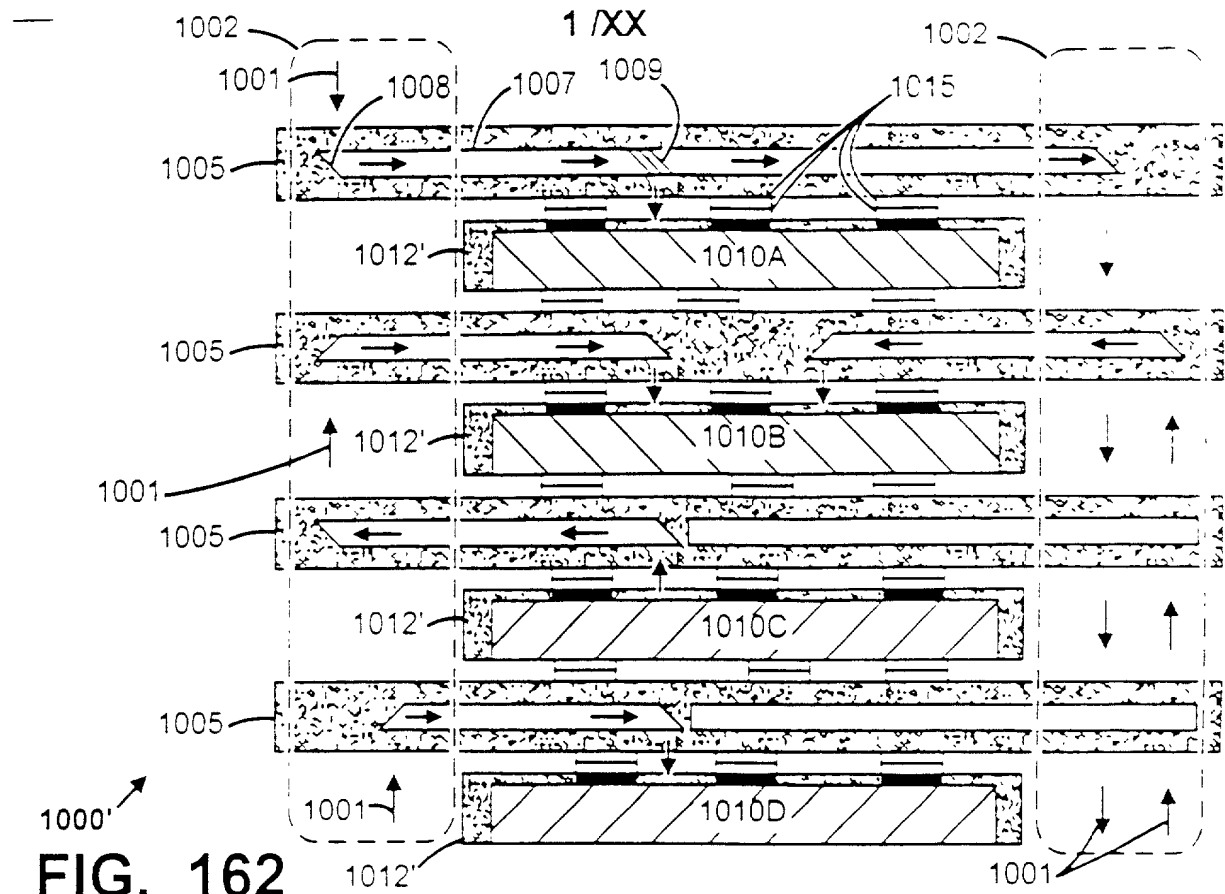
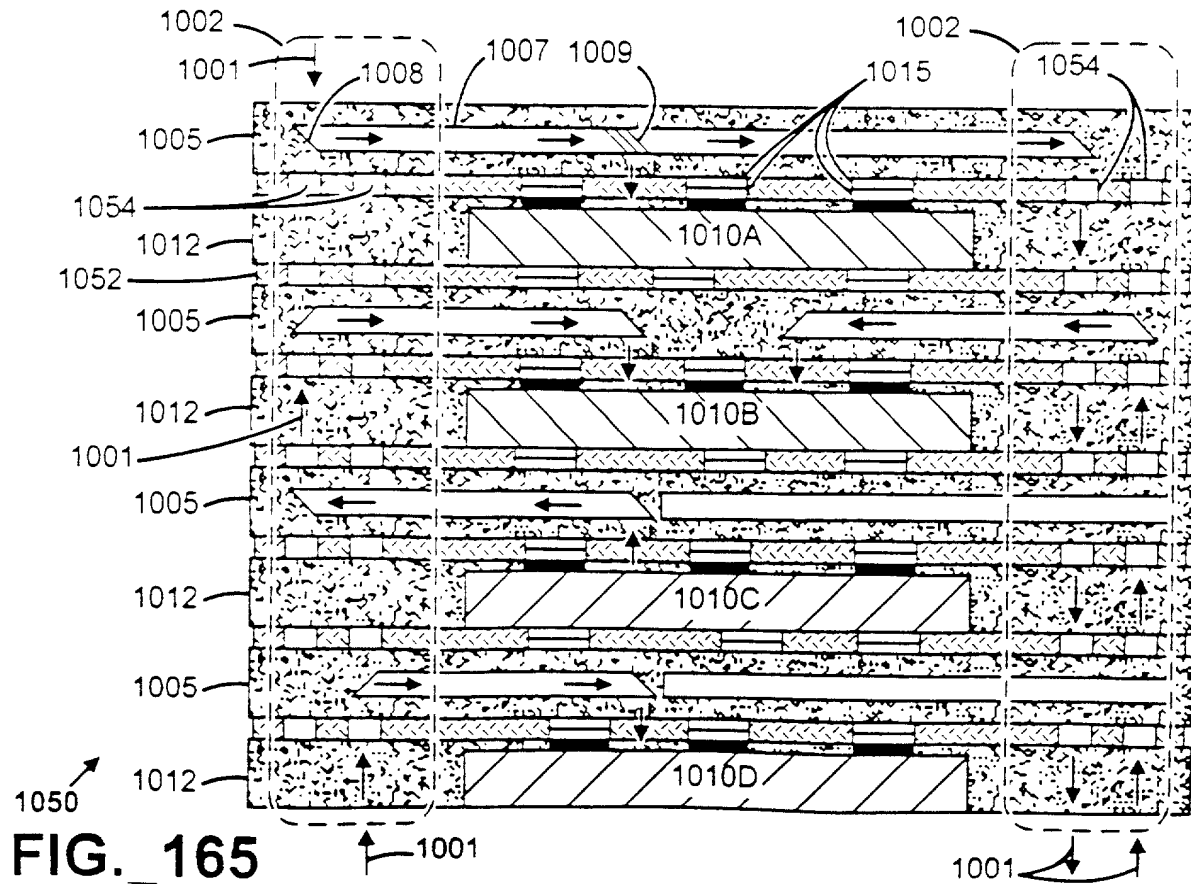
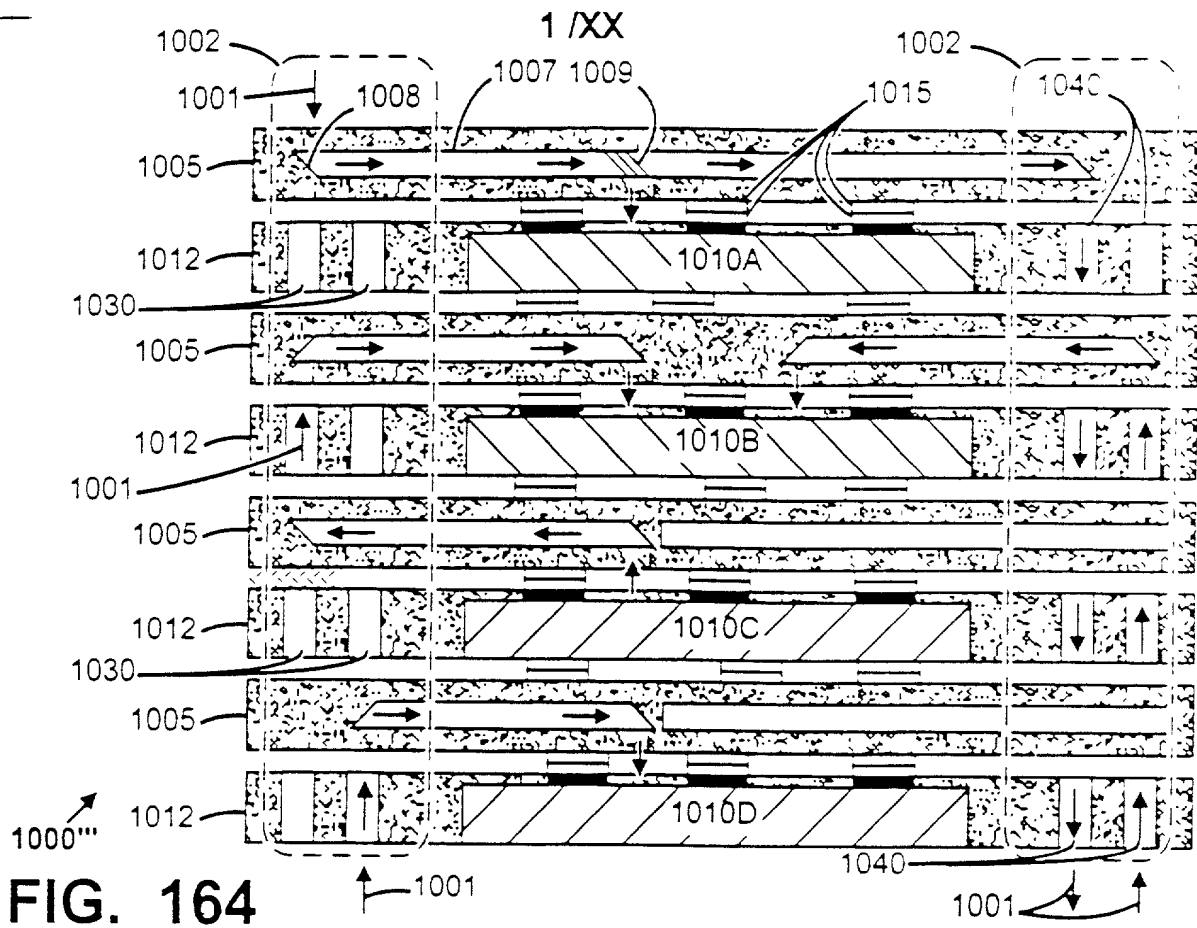
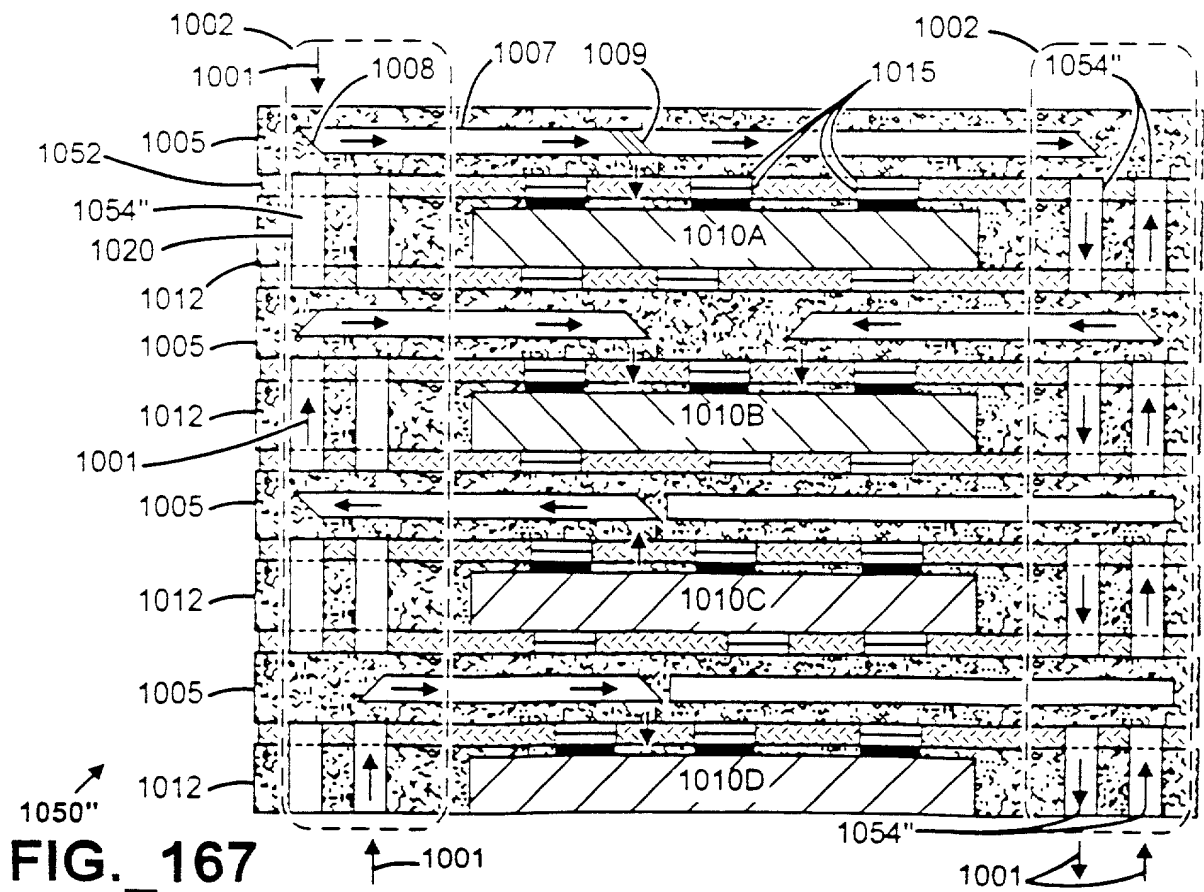
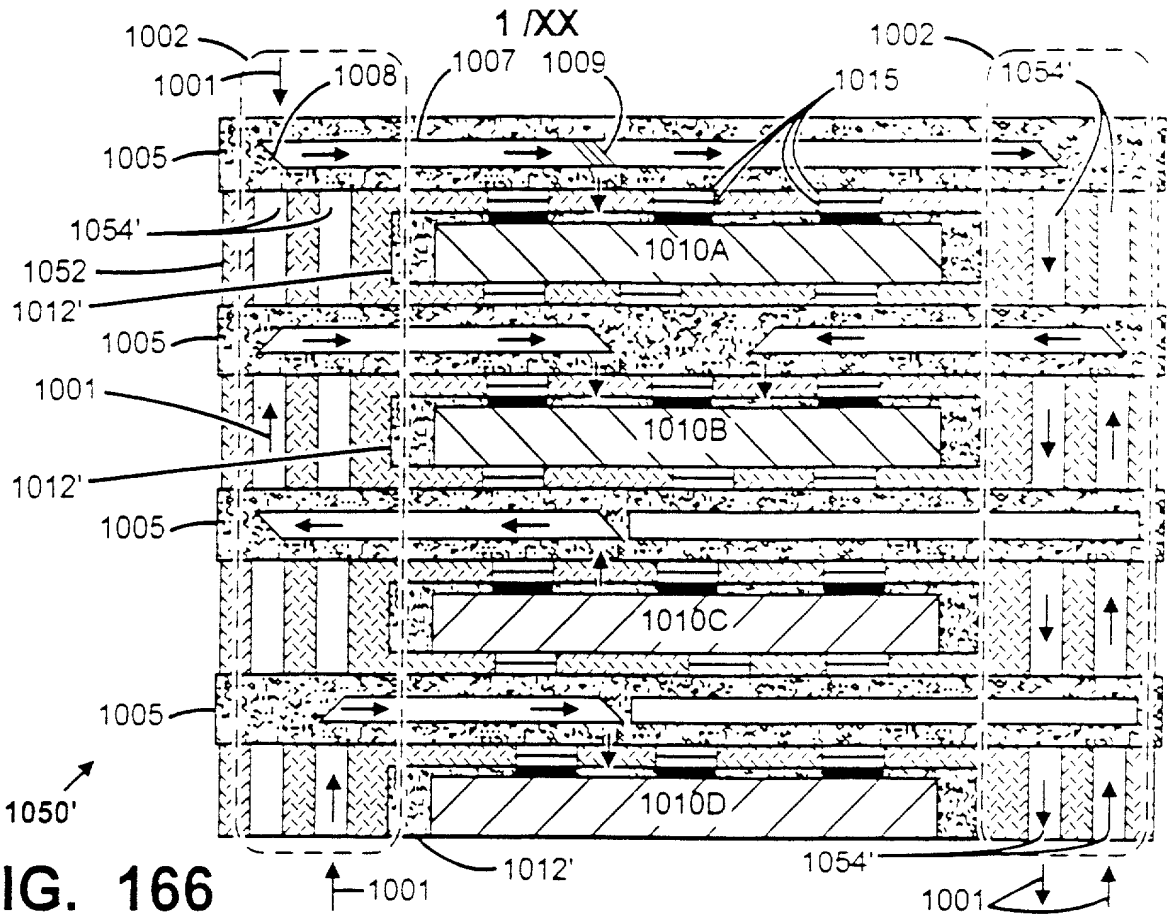
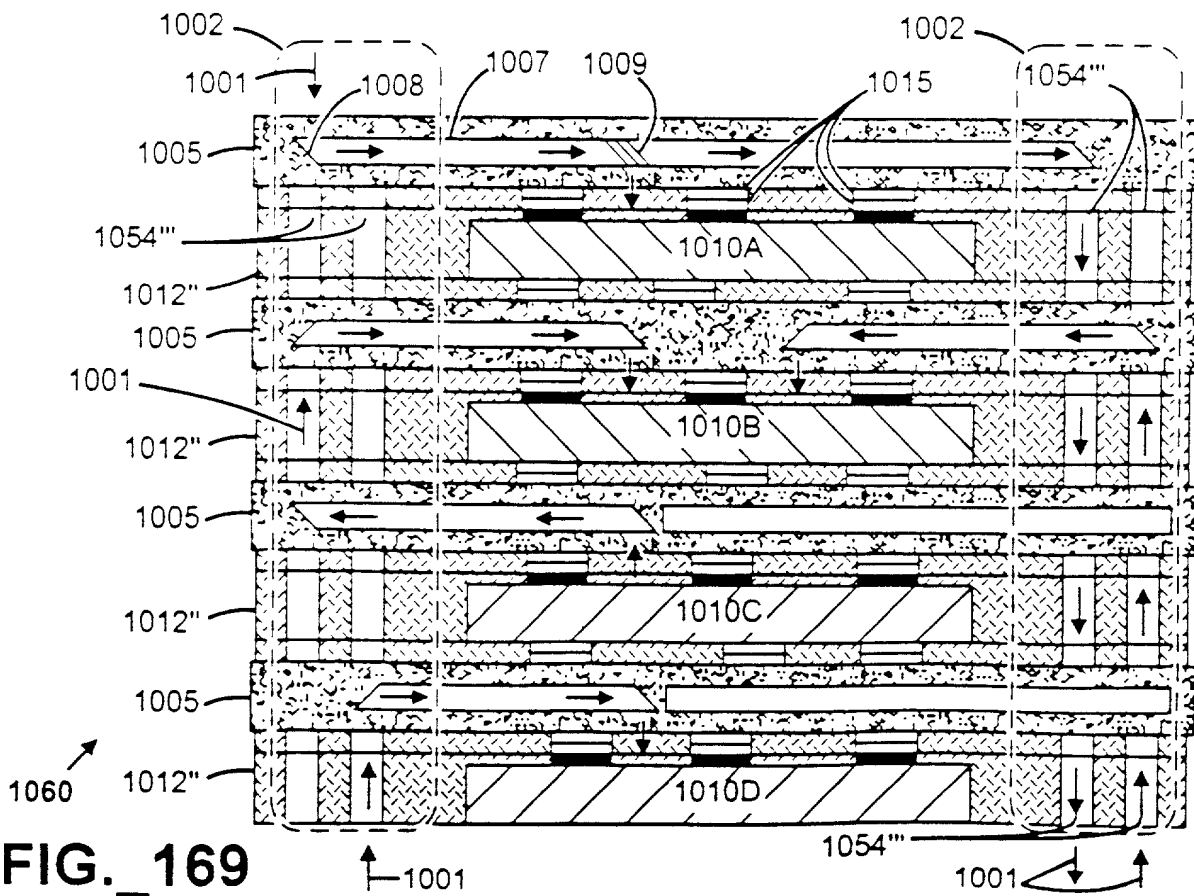
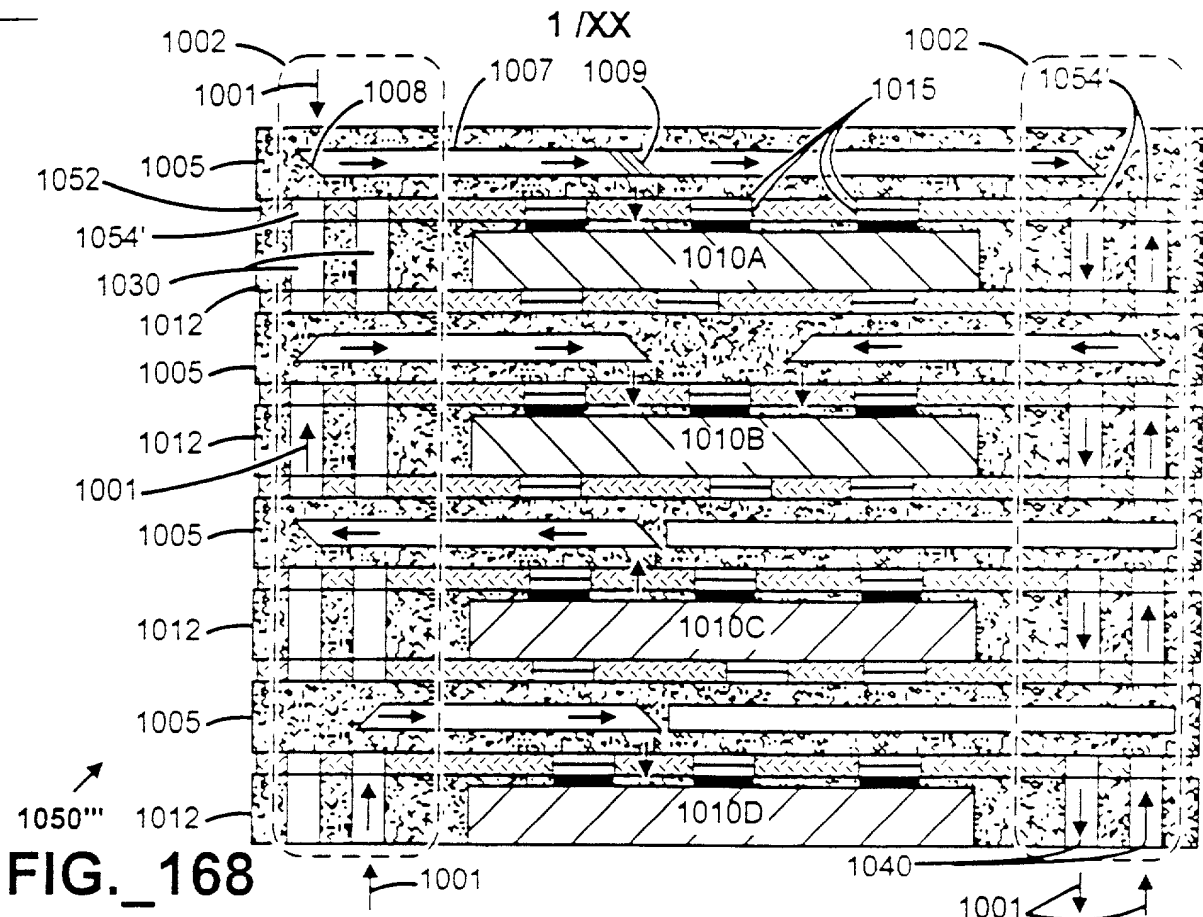


FIG._161









1/XX

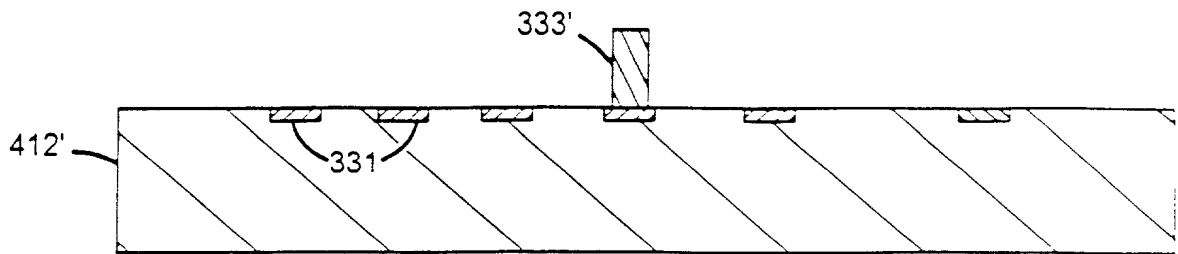


FIG._170

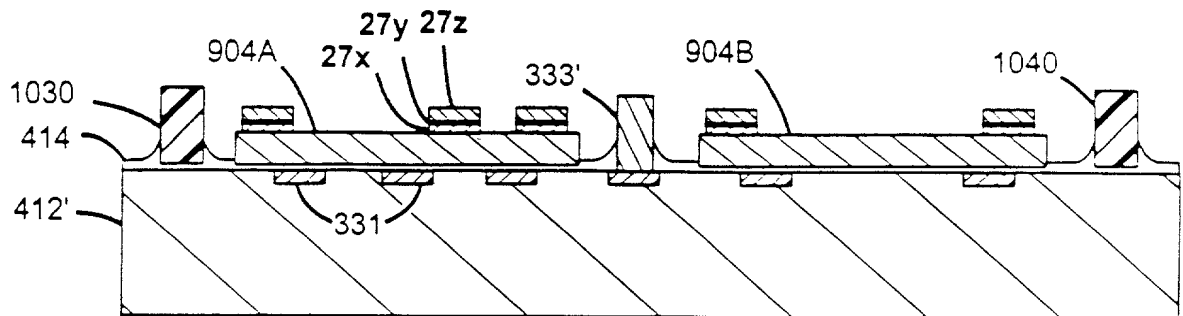


FIG._171

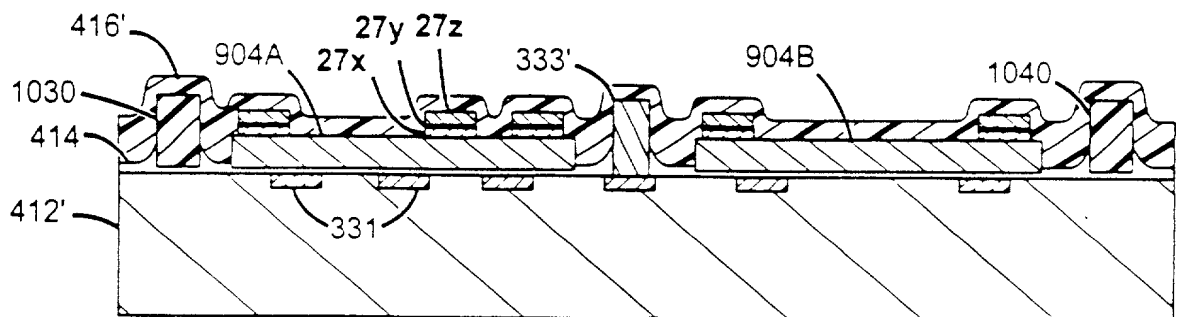


FIG._172

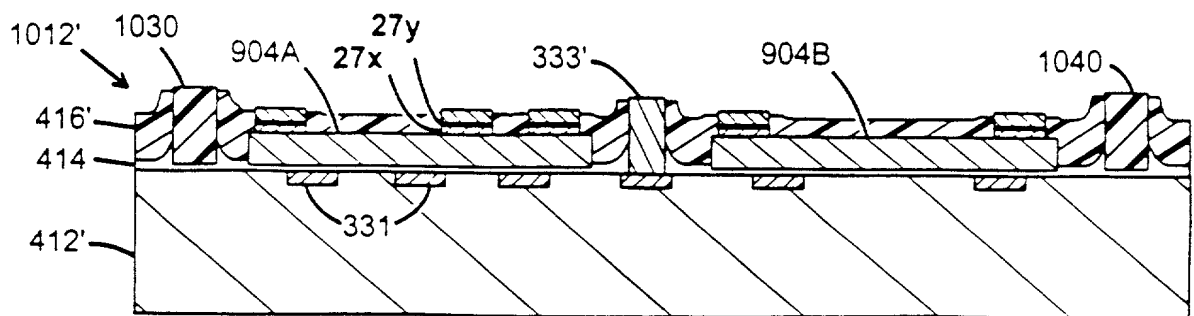


FIG._173

1/XX

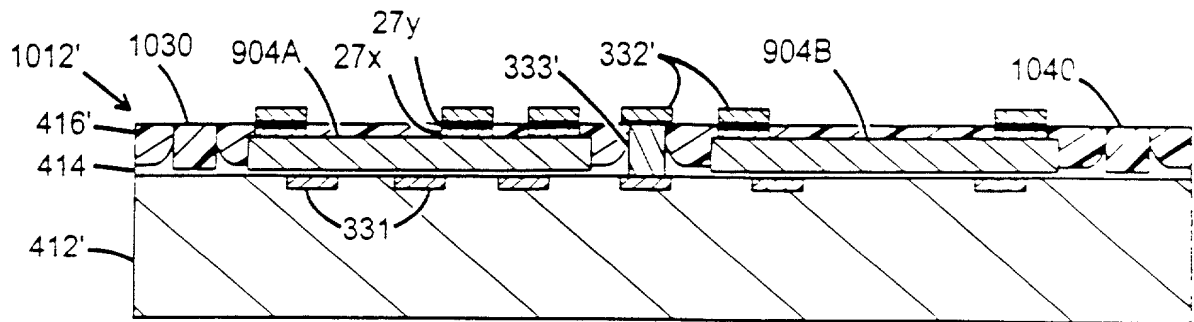


FIG._174

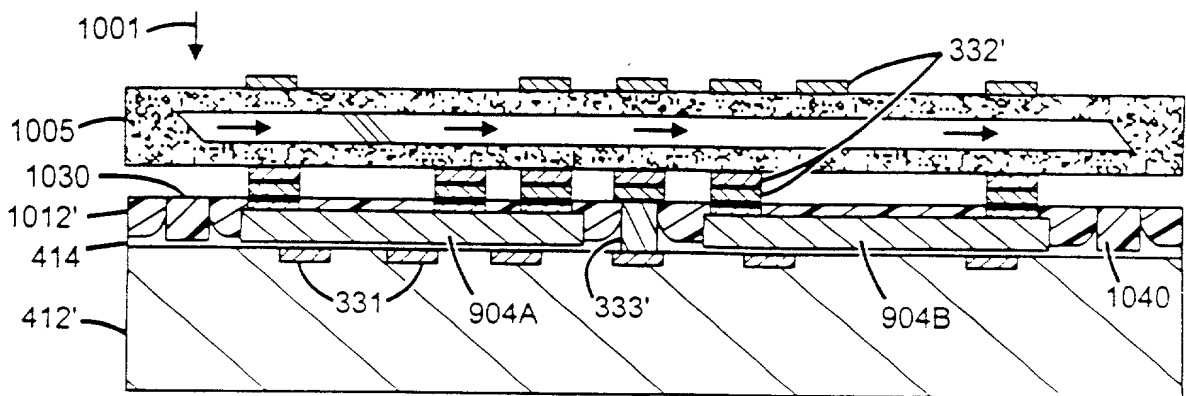


FIG._175

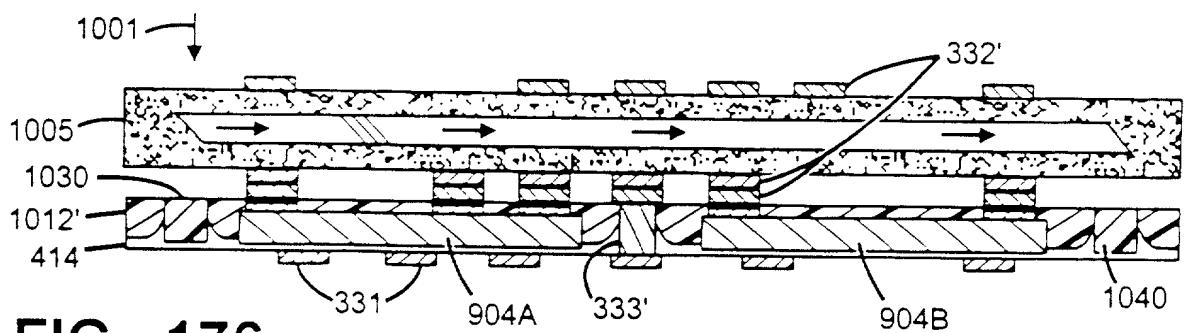


FIG._176

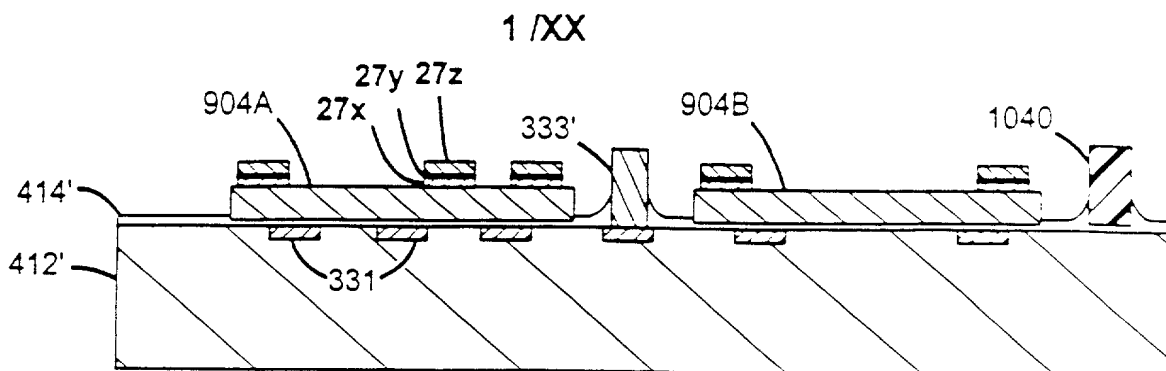


FIG._177

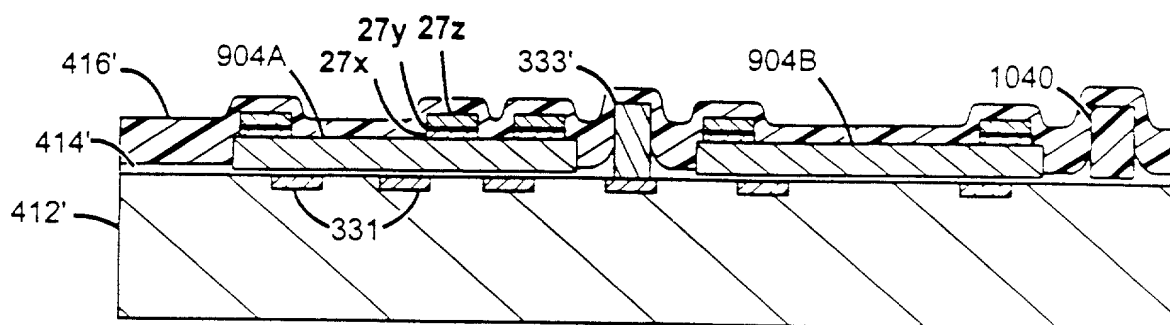


FIG._178

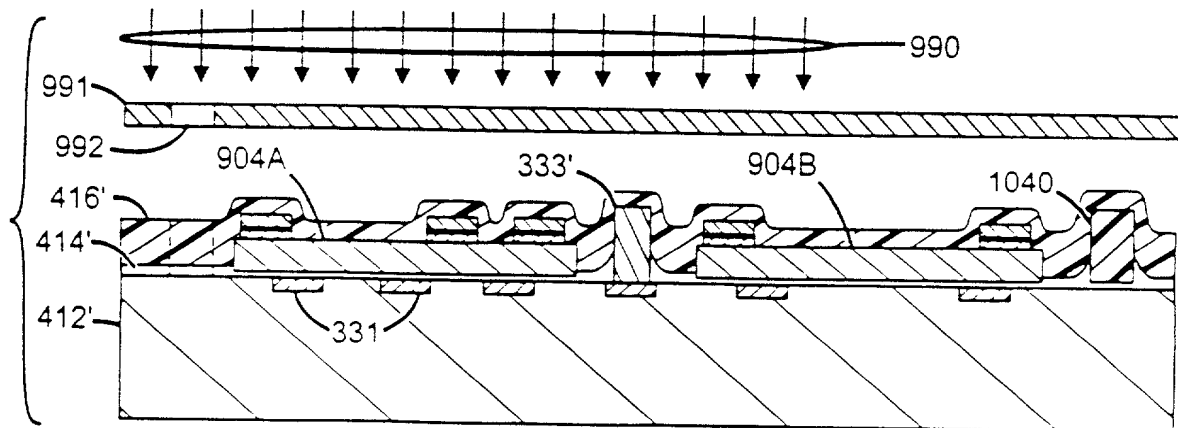


FIG._179

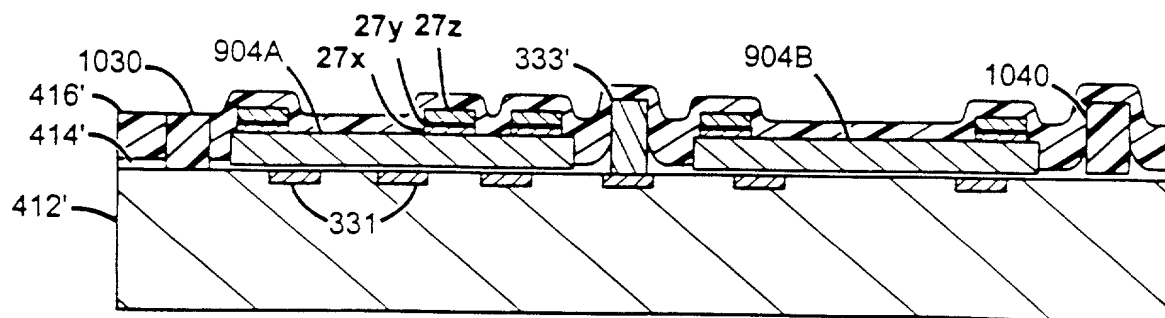
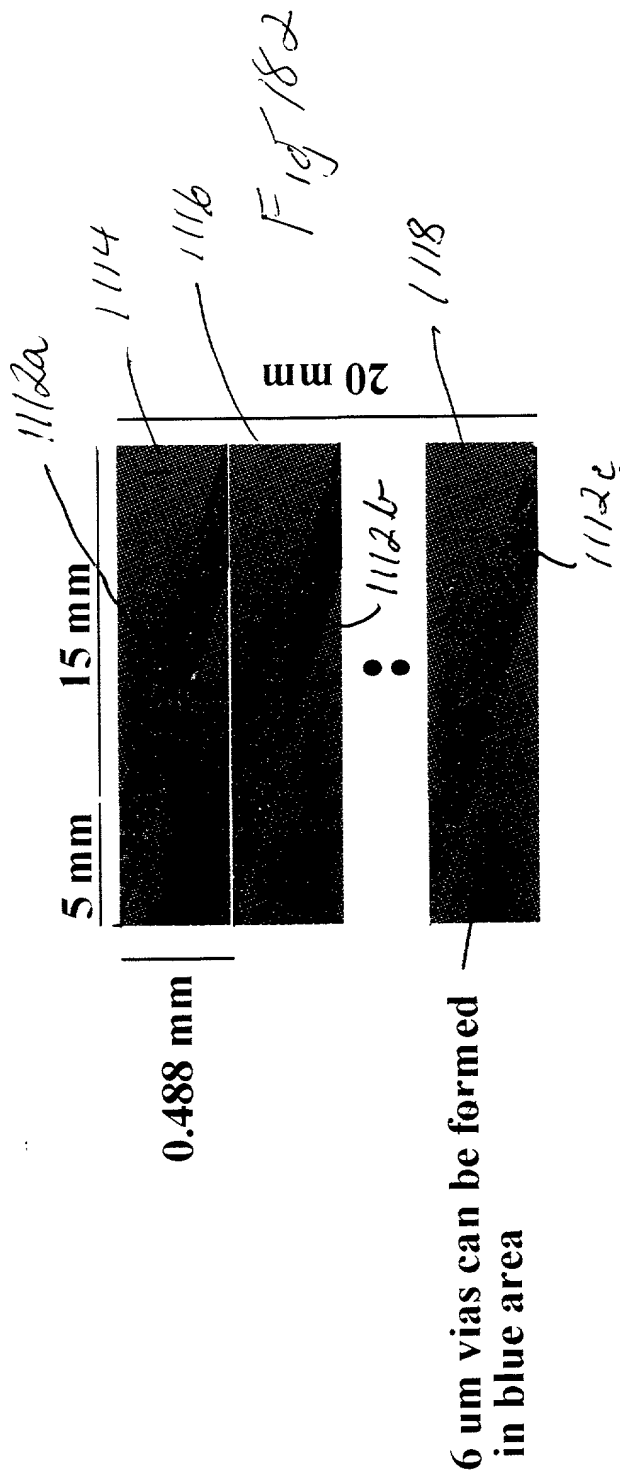
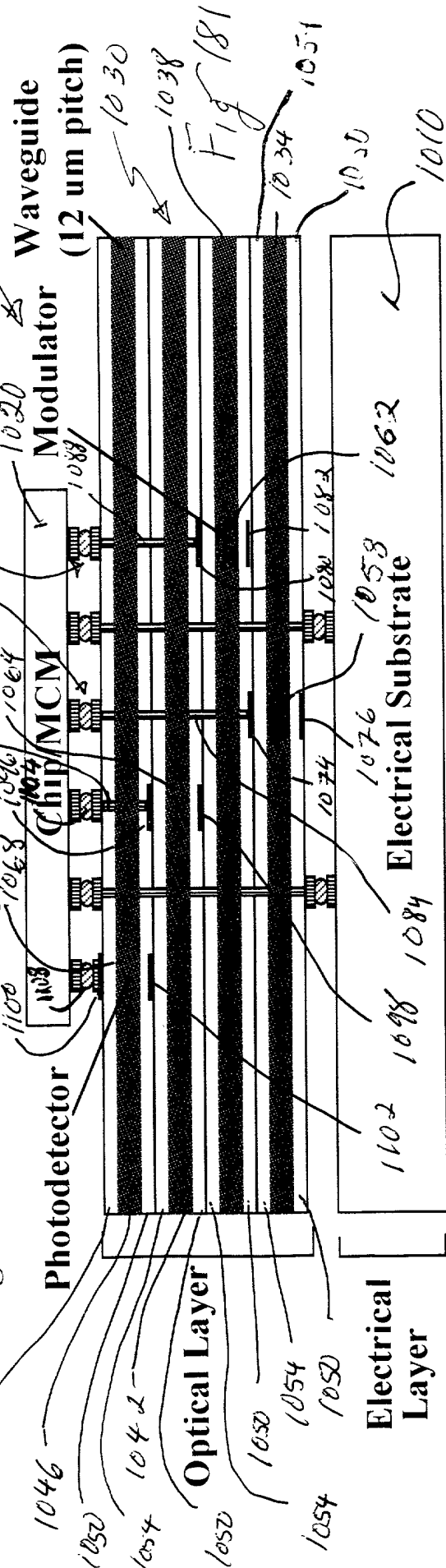


FIG._180

I/O Connection in OE Substrate (Planar Modulator)

Signal I/O count: 6000 = $\lceil 1500 \text{ I/O per Layer} \rceil \times \lceil 4\text{-Layer} \rceil$



I/O Connection in OE Substrate (OE-VLSI)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

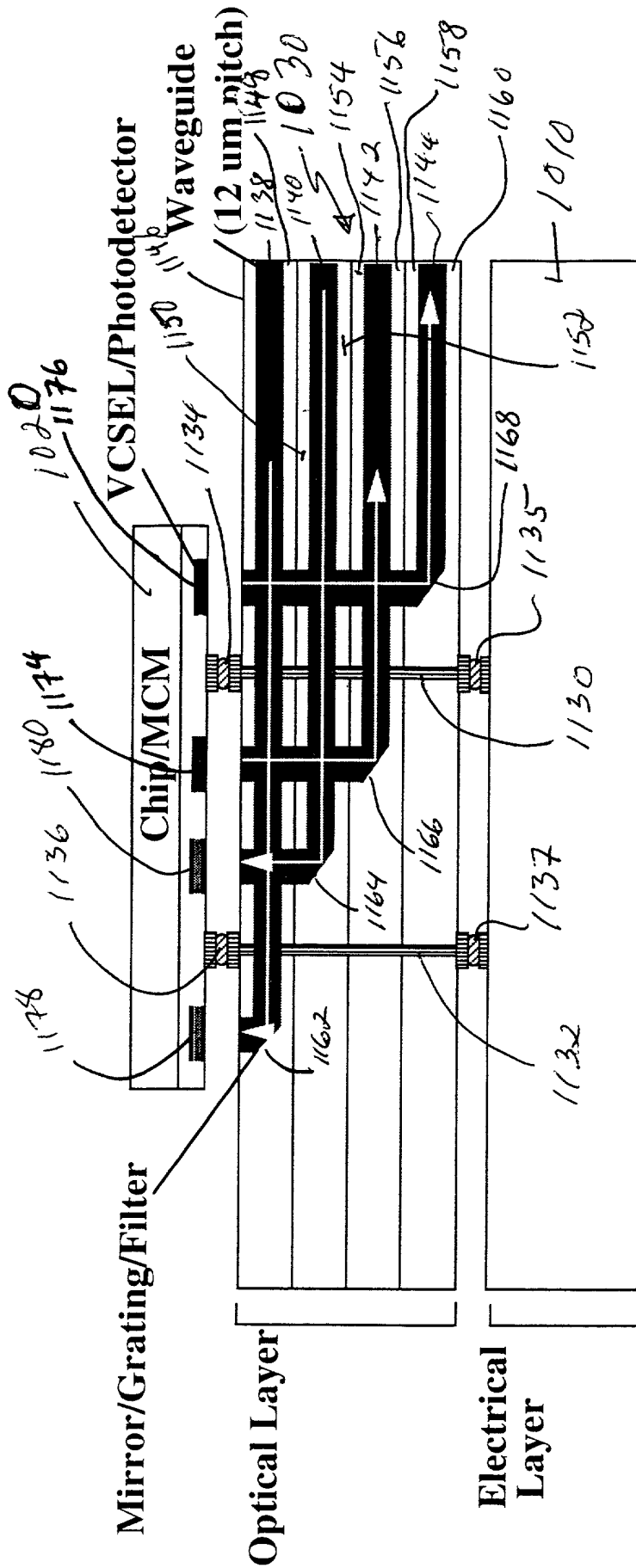


Fig 185

I/O Connection in OE Substrate (OE-VLSI)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

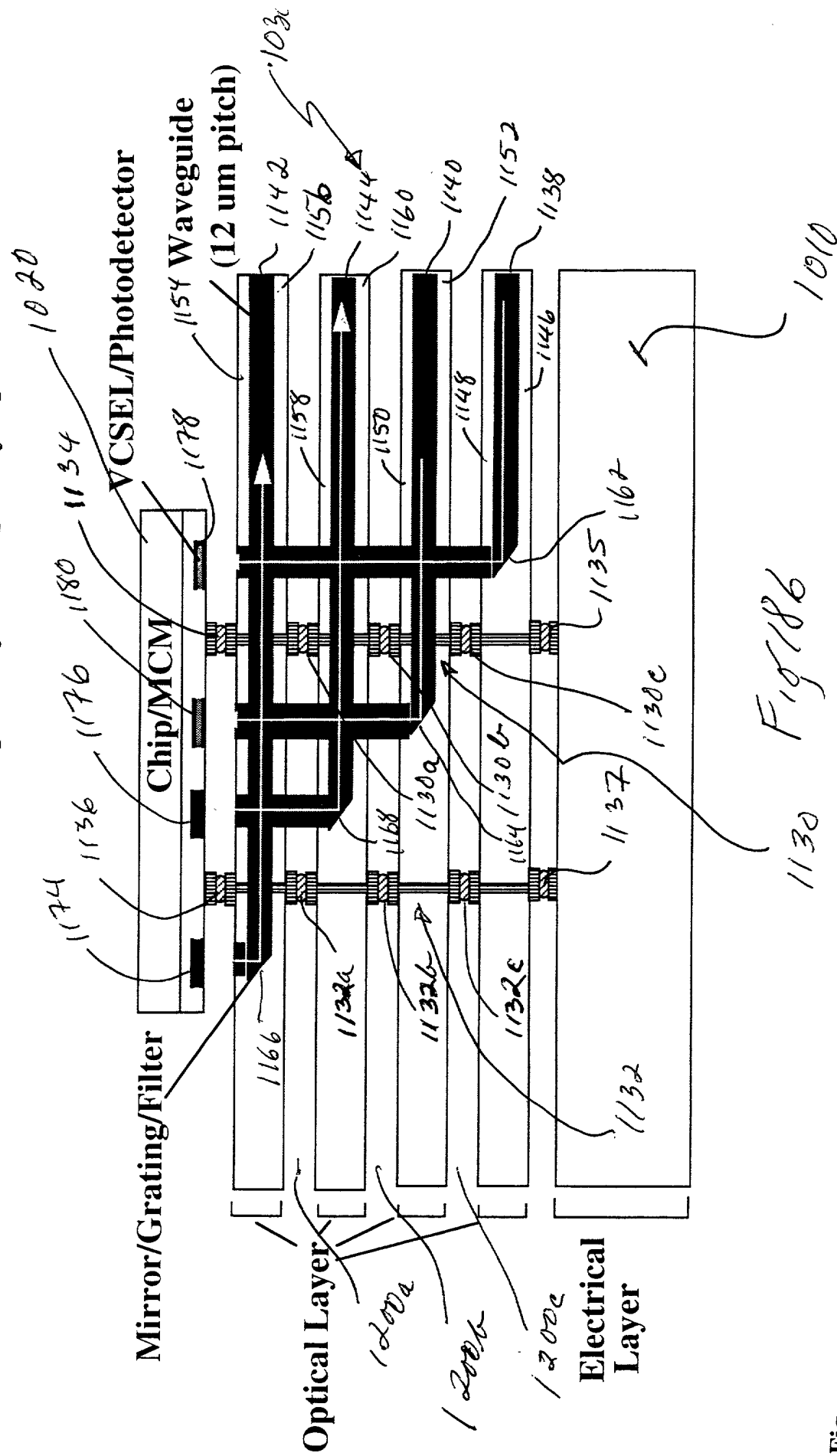


Fig.

I/O Connection in OE Substrate (OE-VLSI, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

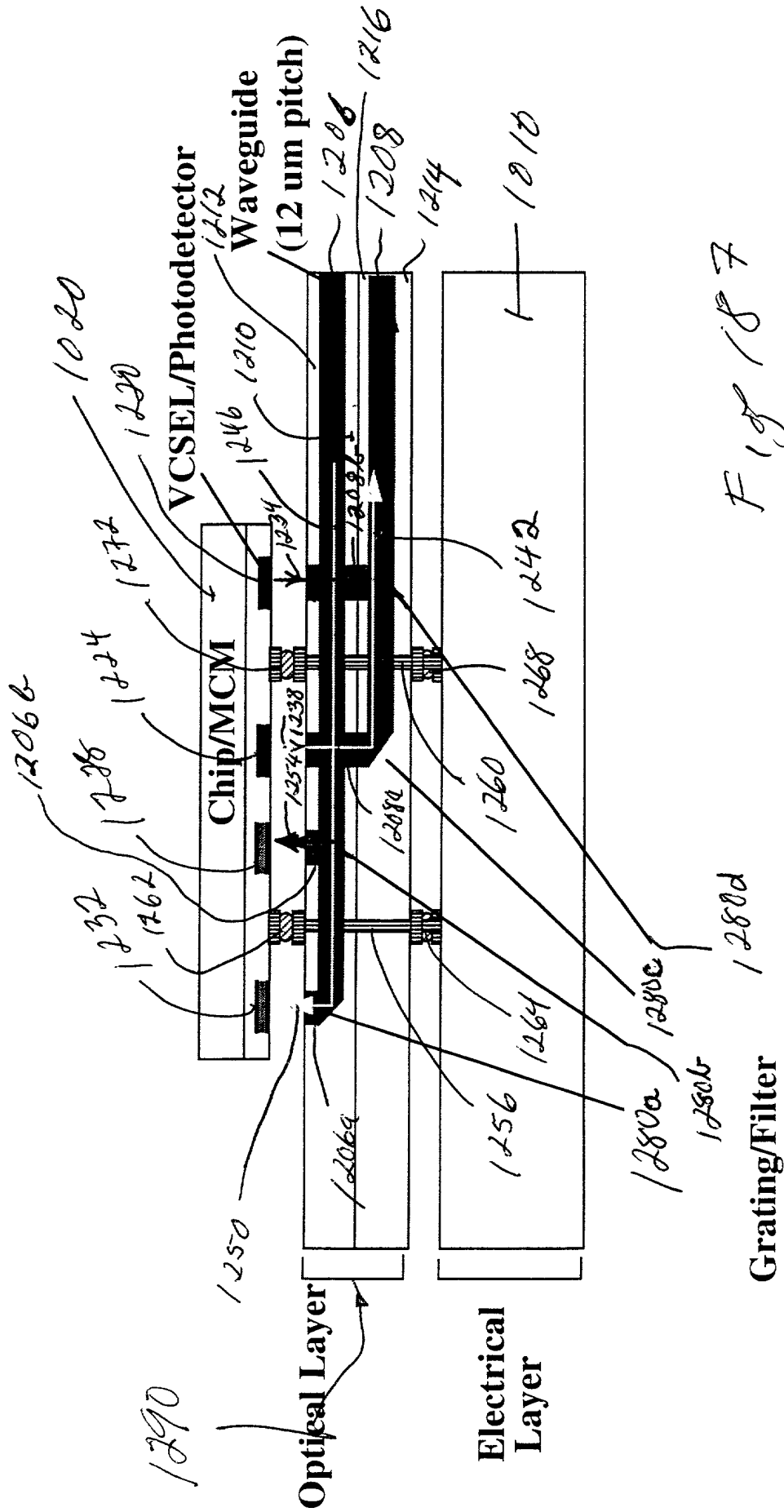


Fig 187

I/O Connection in OE Substrate (OE-VLSI, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

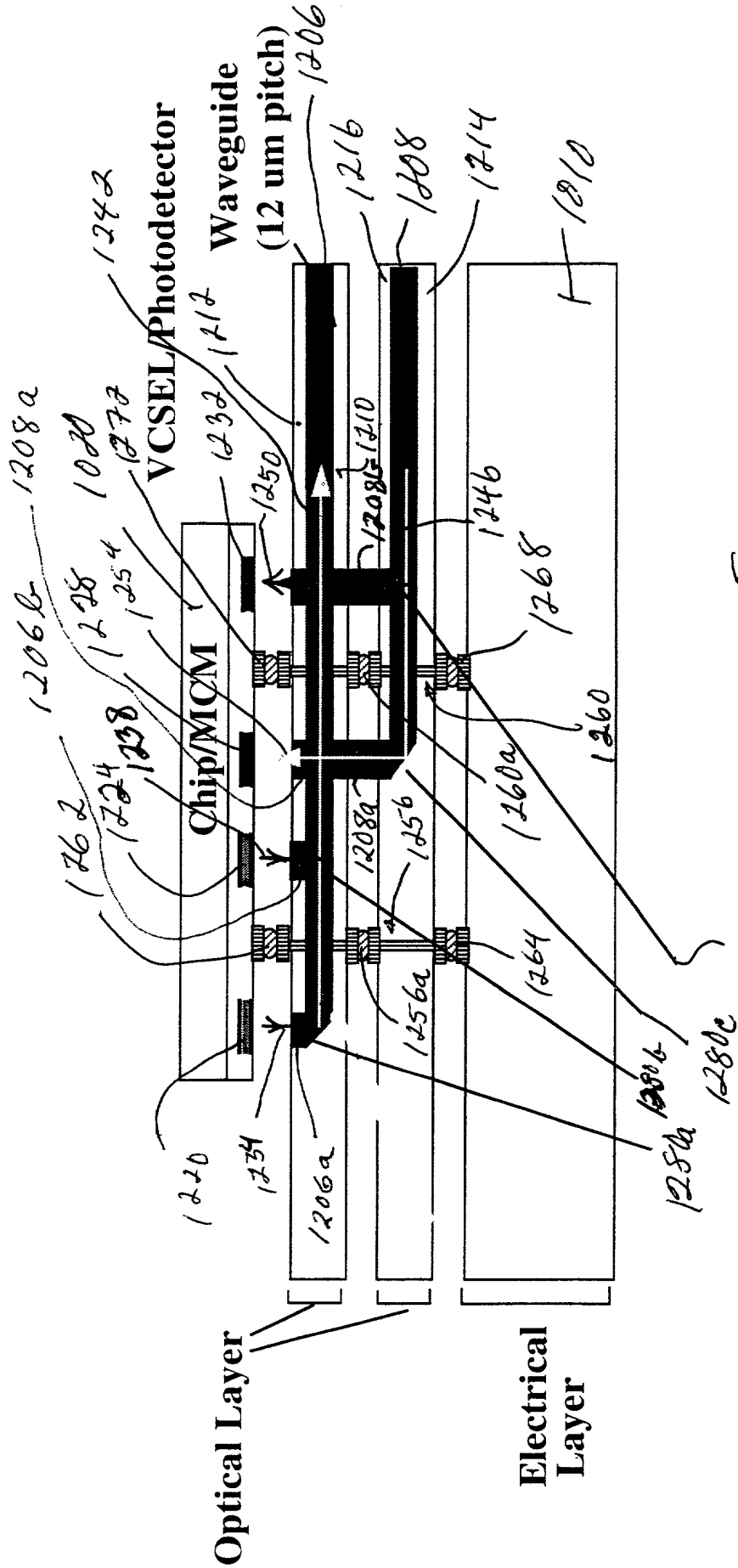


Fig 188

I/O Connection in OE Substrate (Active OE Layer)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

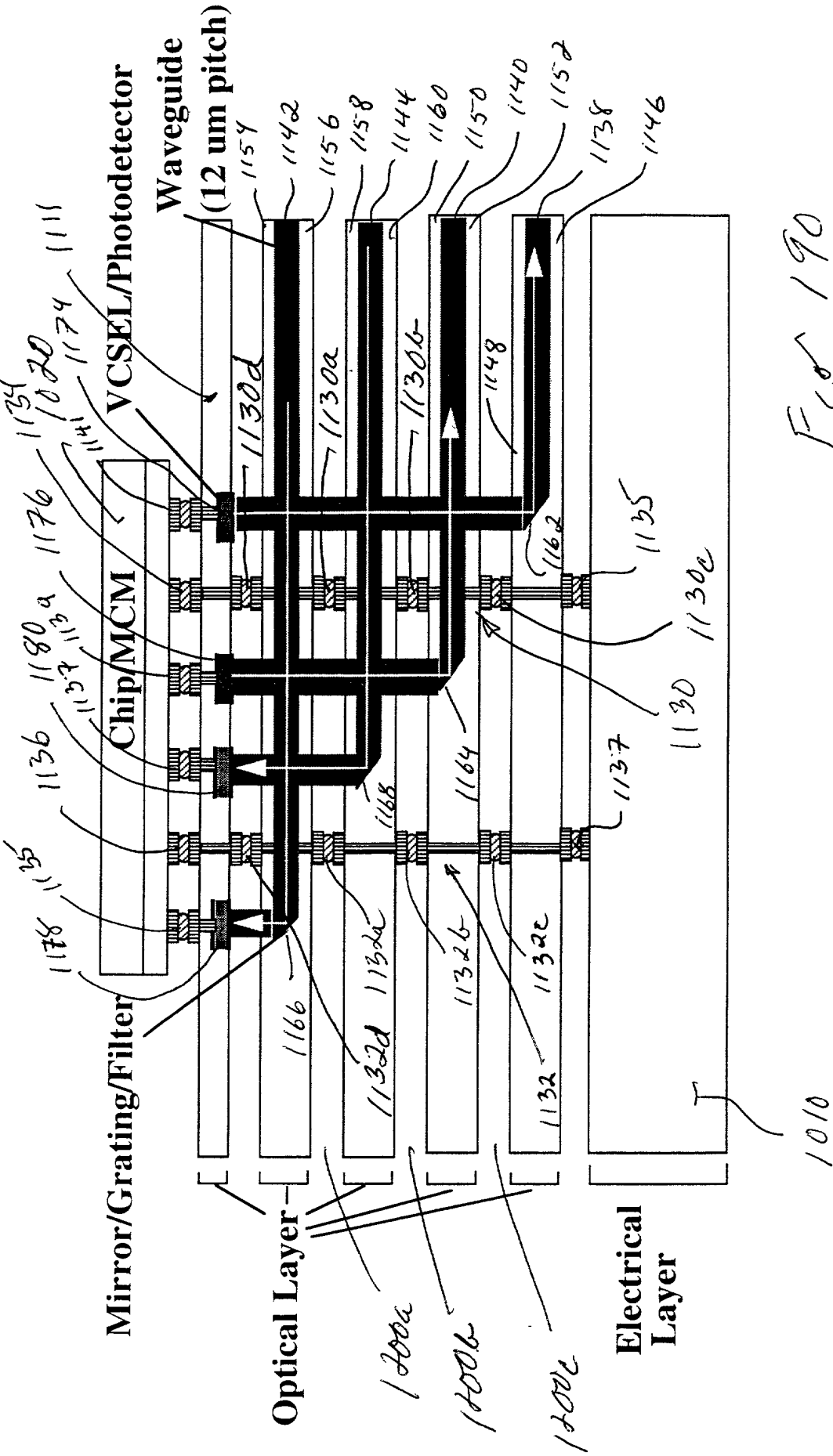


Fig. 9

I/O Connection in OE Substrate (Active OE Layer, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

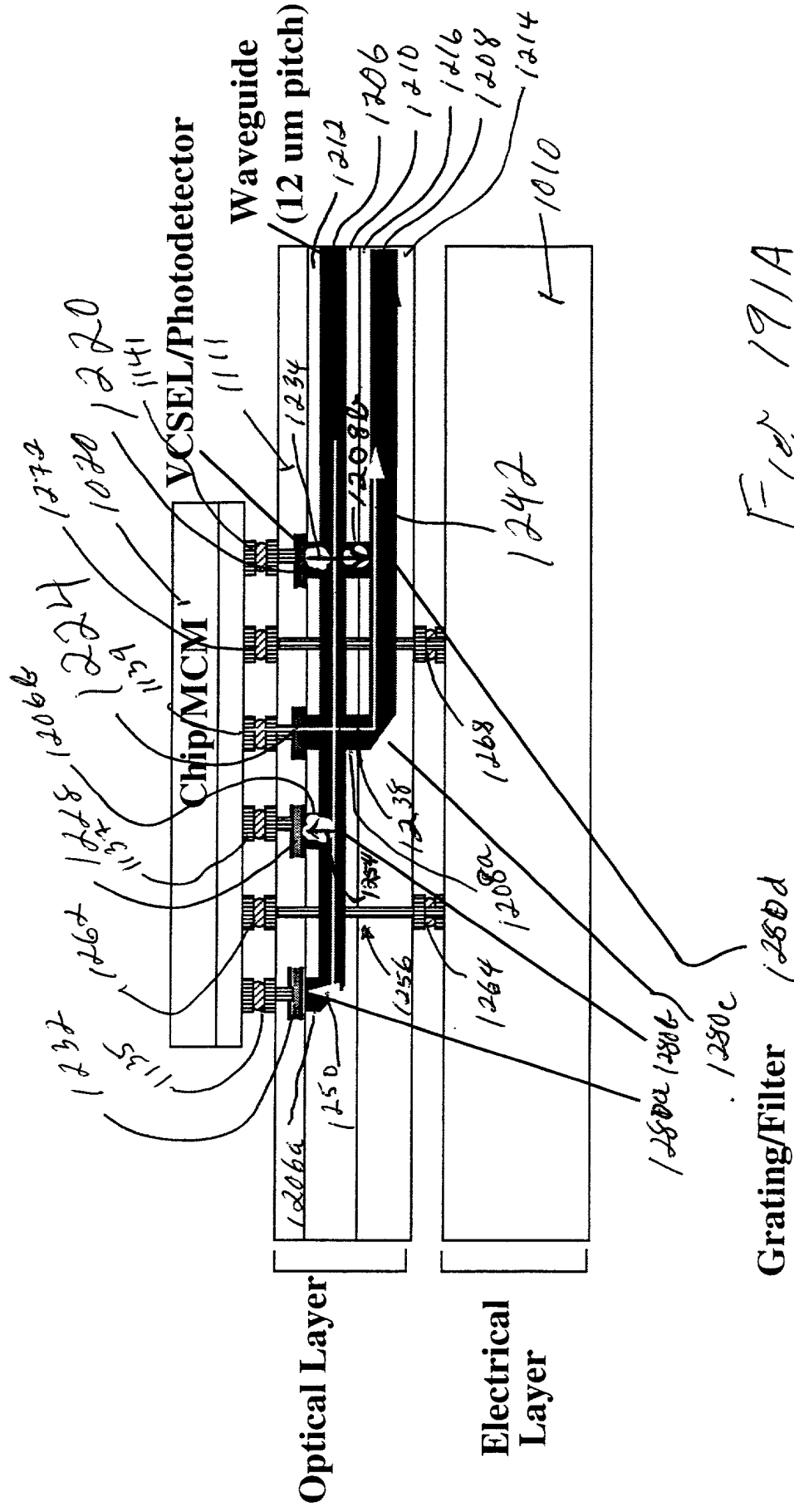


Fig. 10

I/O Connection in OE Substrate (Active OE Layer, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

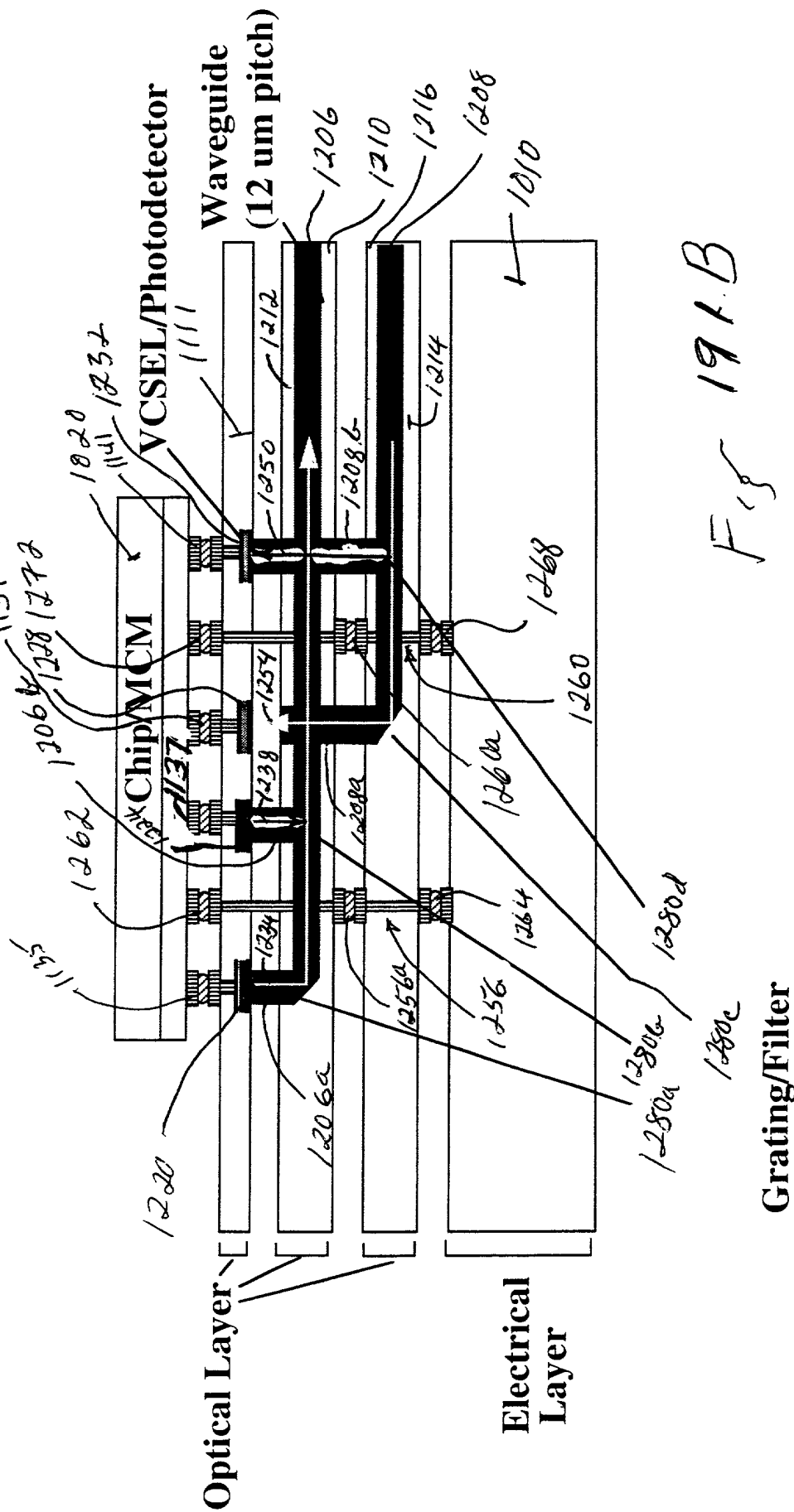
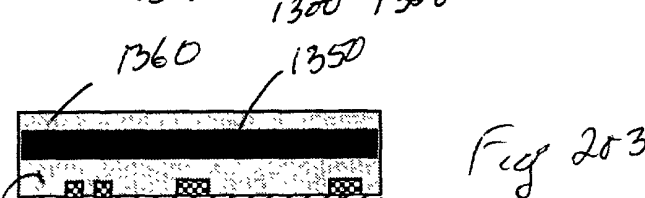
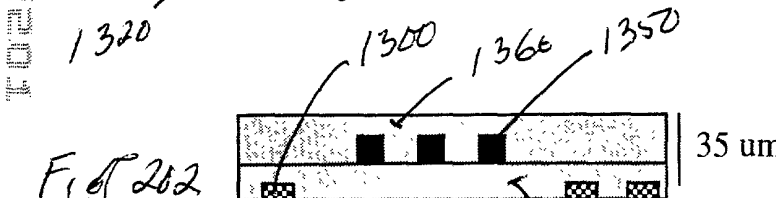
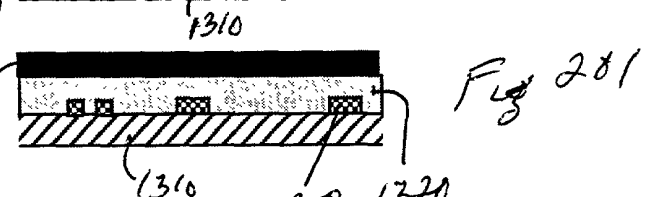
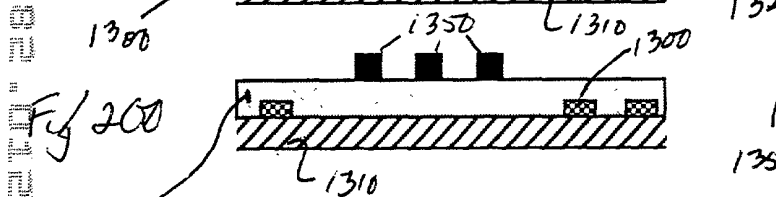
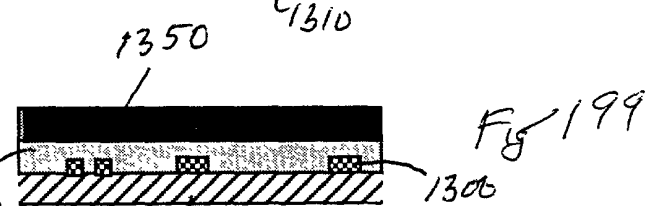
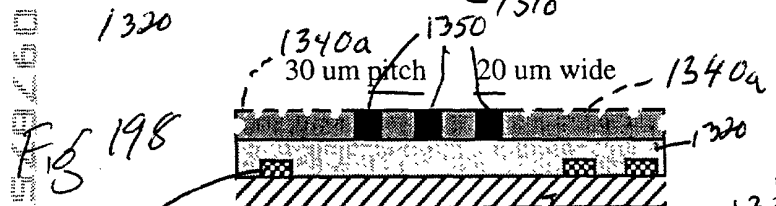
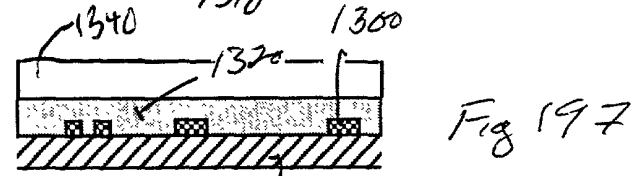
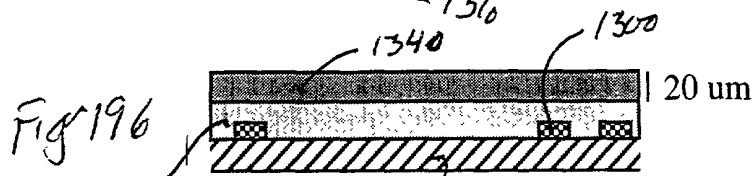
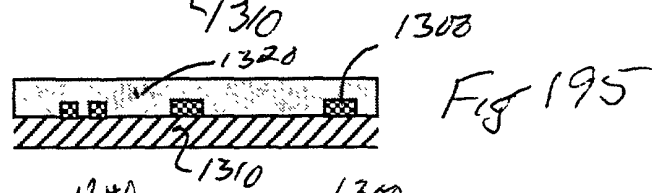
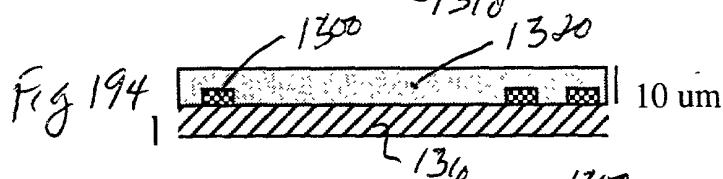
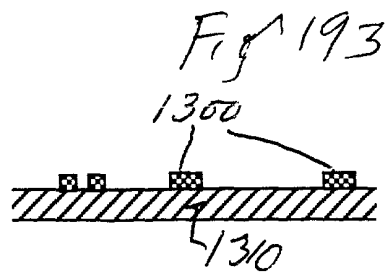
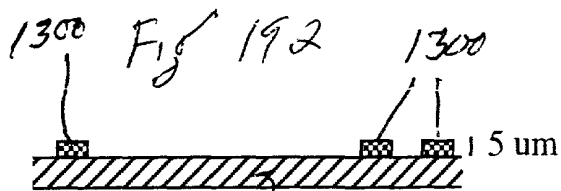


Fig. 11



2022-01-20 10:22:27

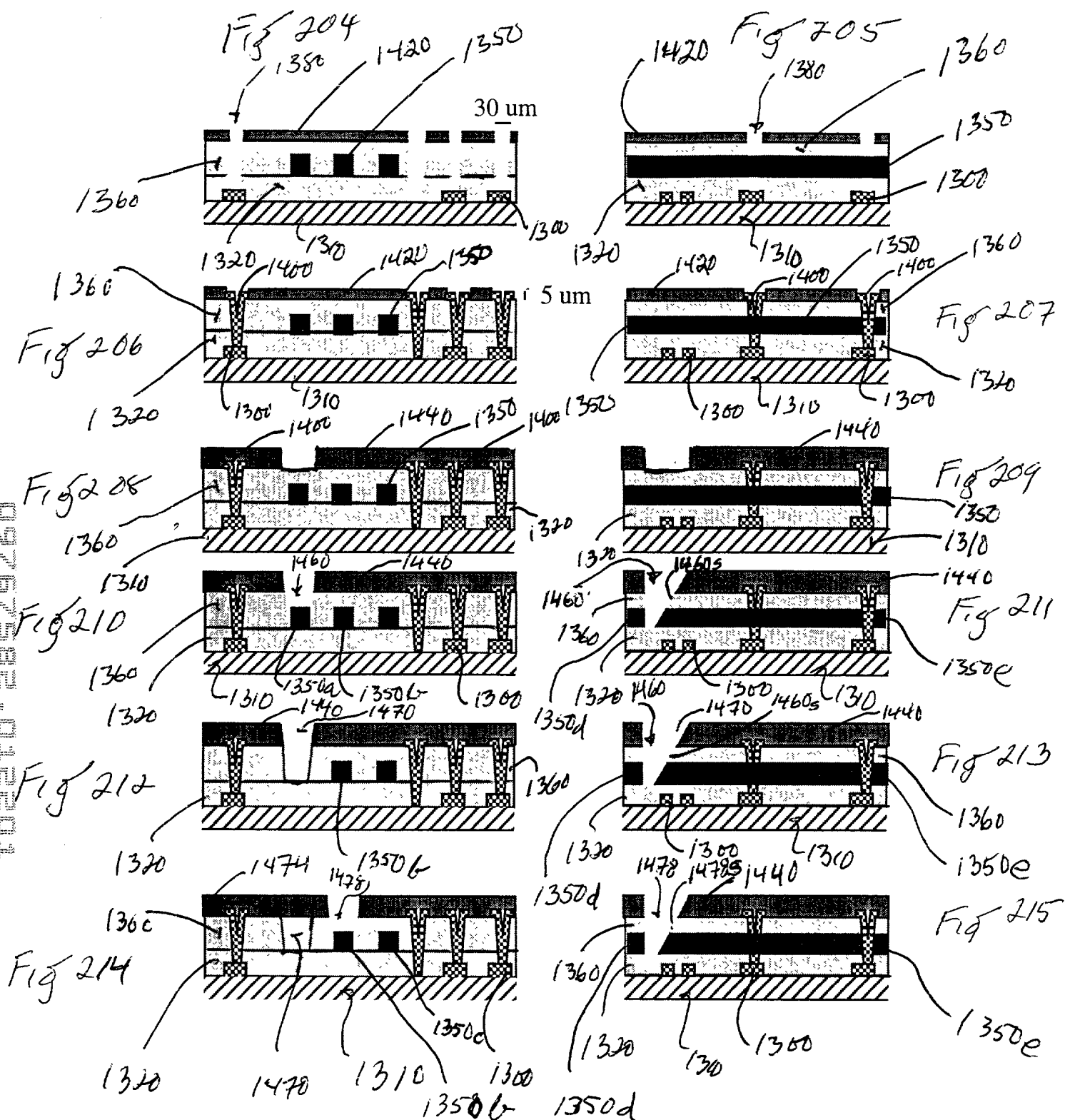


Fig 216

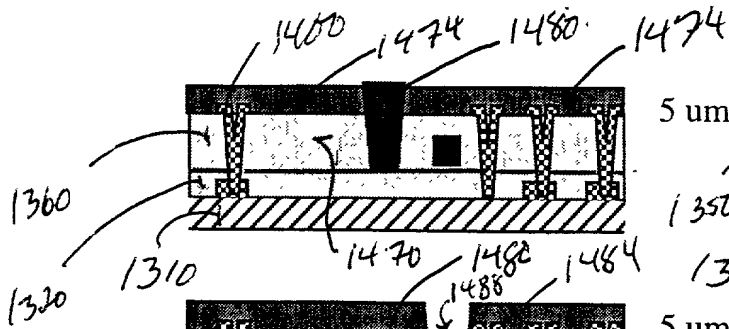


Fig 218

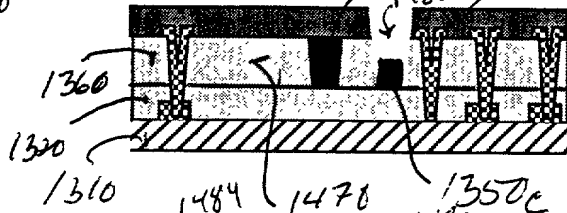


Fig 220

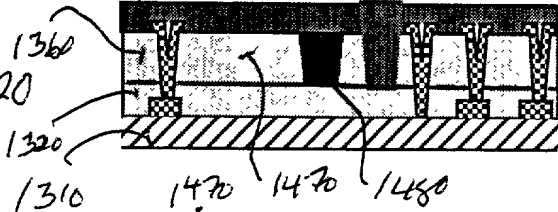


Fig 222

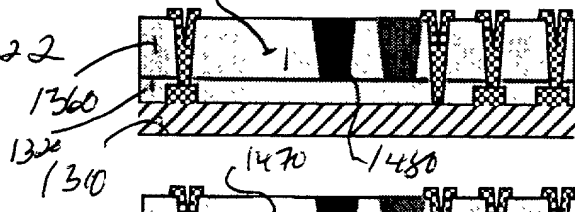


Fig 224

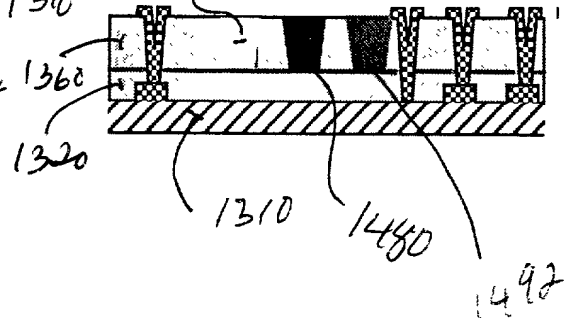
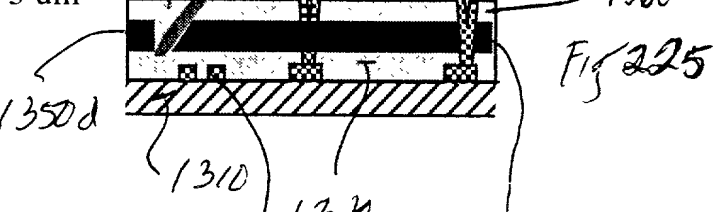
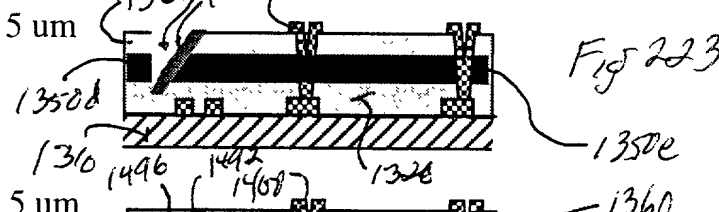
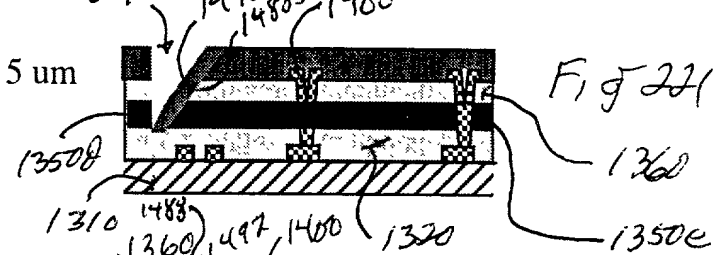
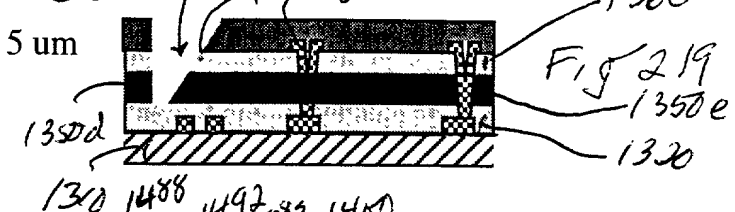
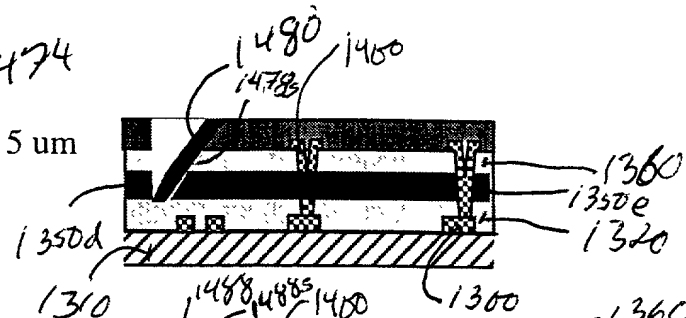


Fig 217



1300

1350e

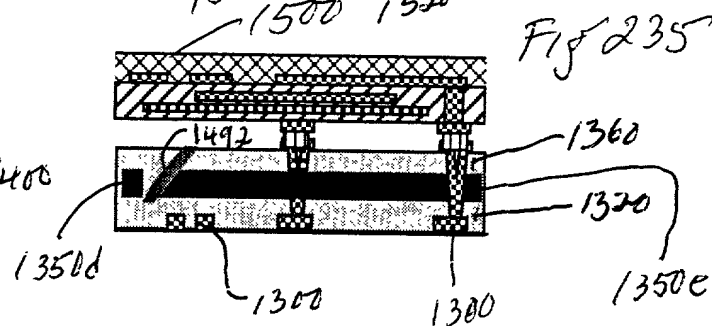
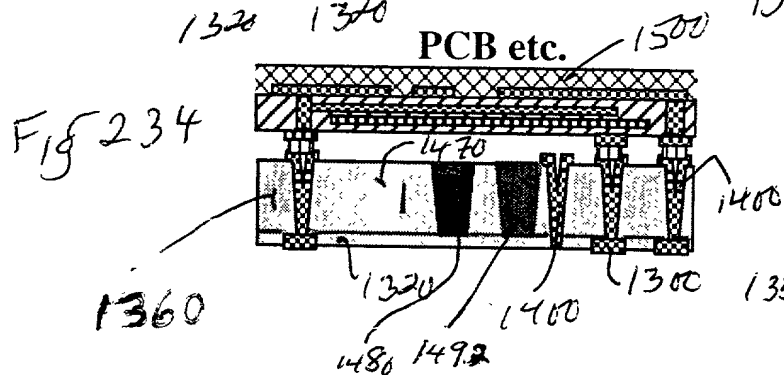
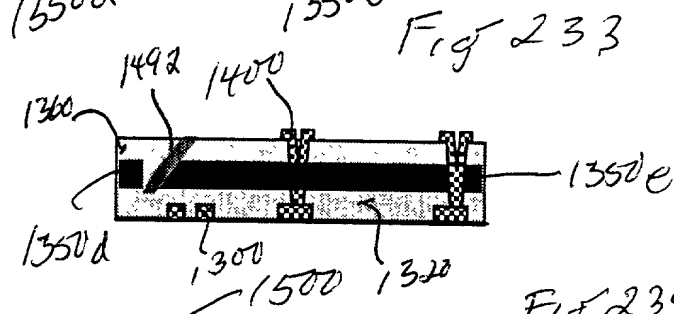
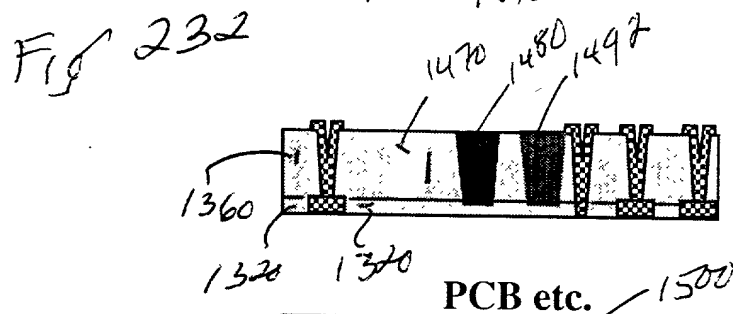
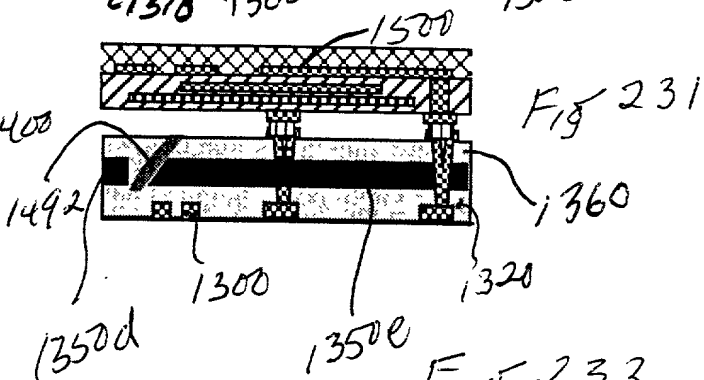
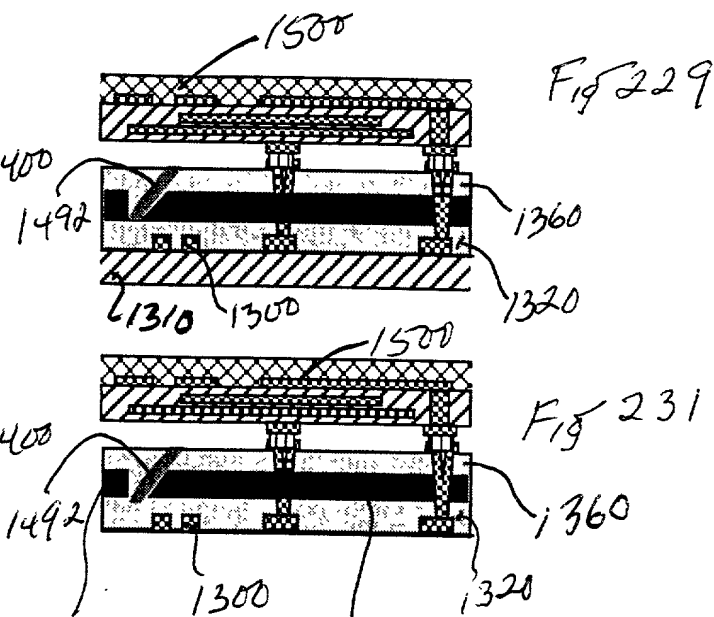
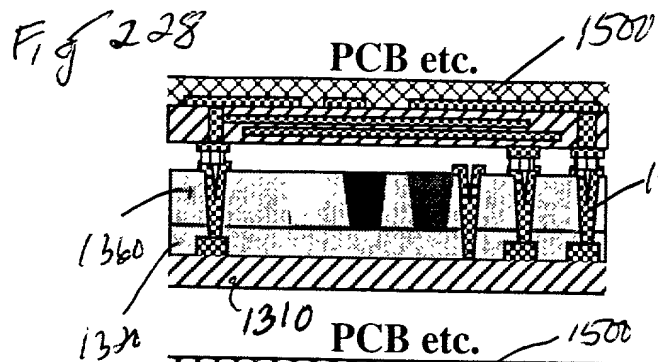
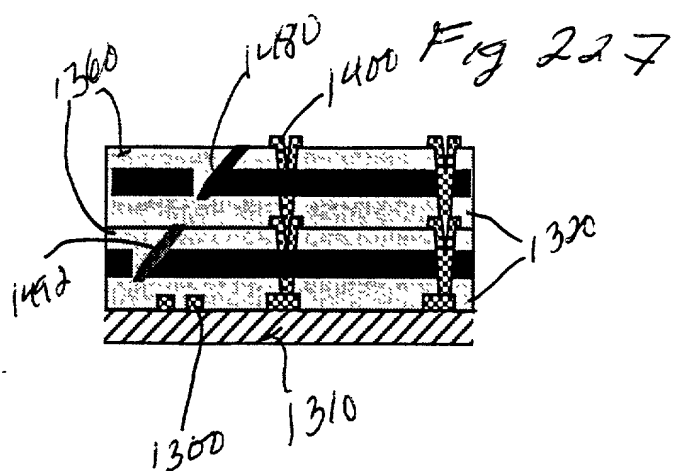
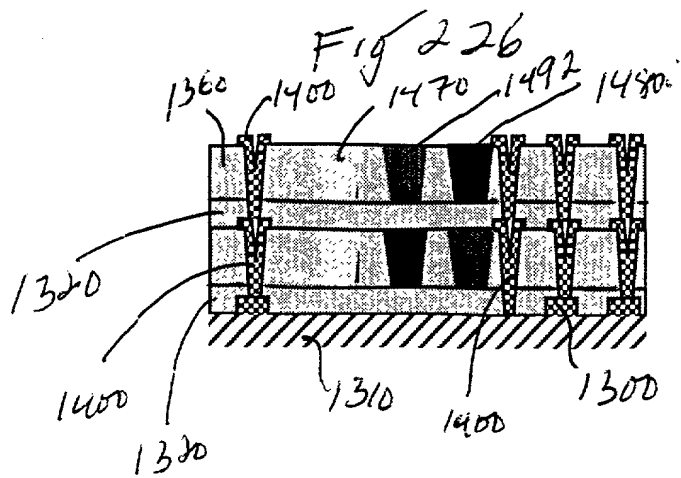


Fig 236

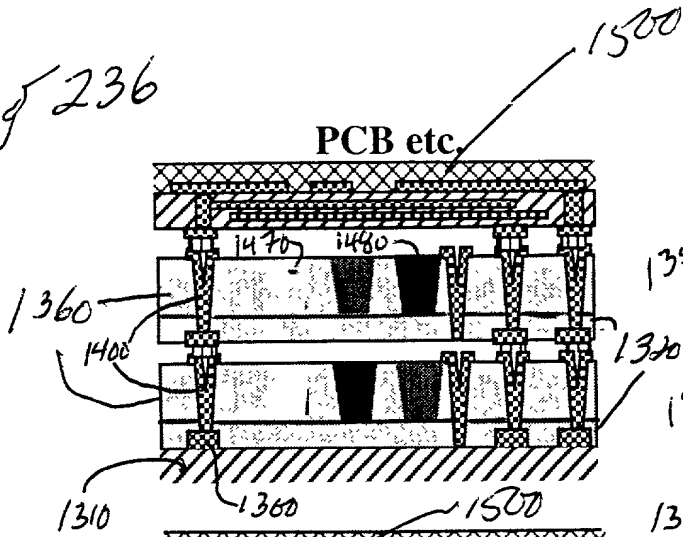


Fig 237

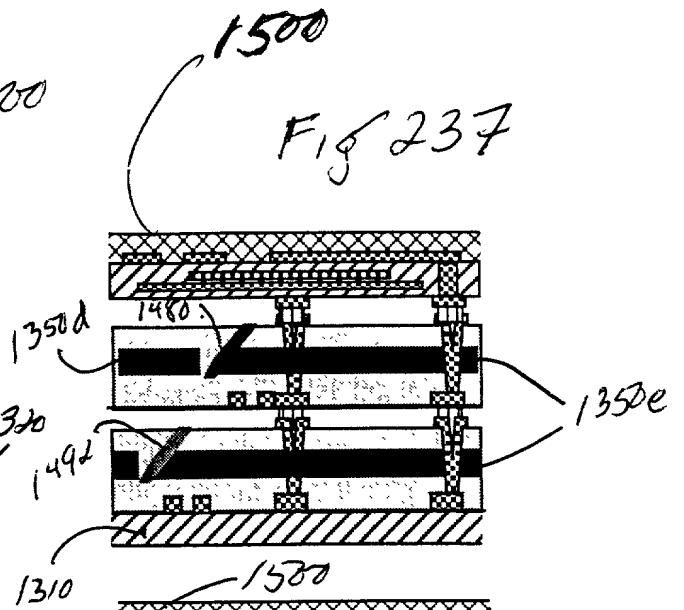


Fig 238

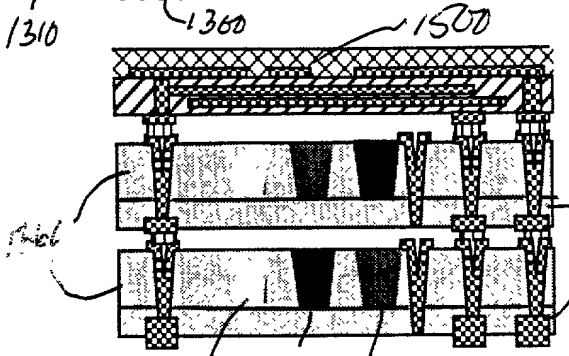


Fig 239

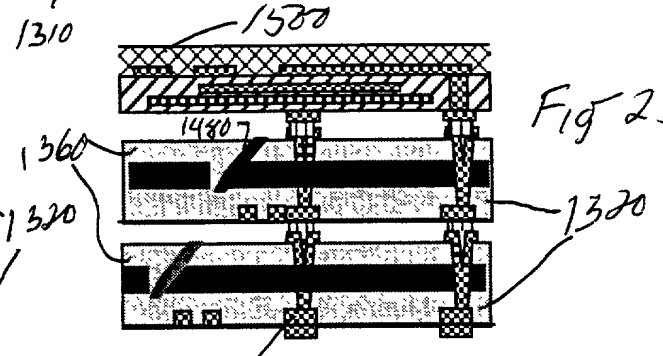


Fig 240

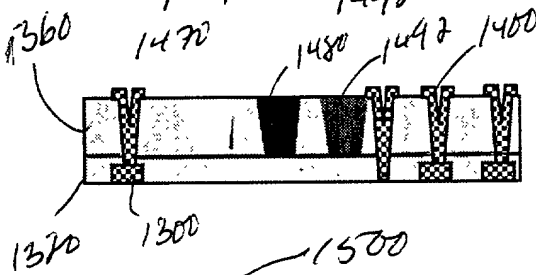


Fig 241

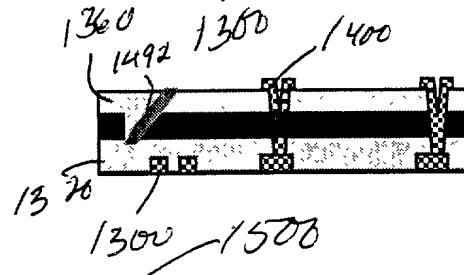


Fig 242

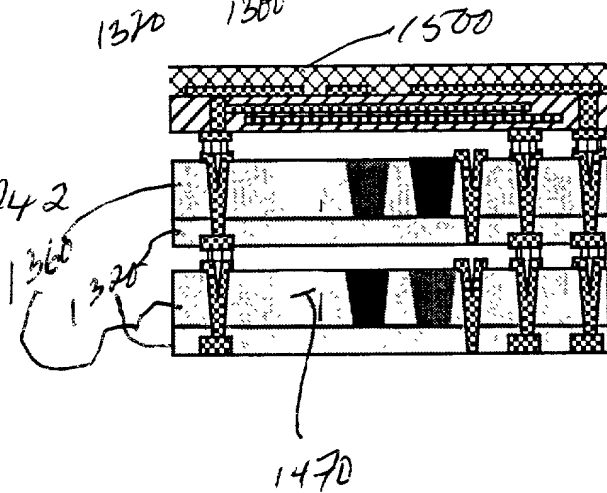


Fig 243

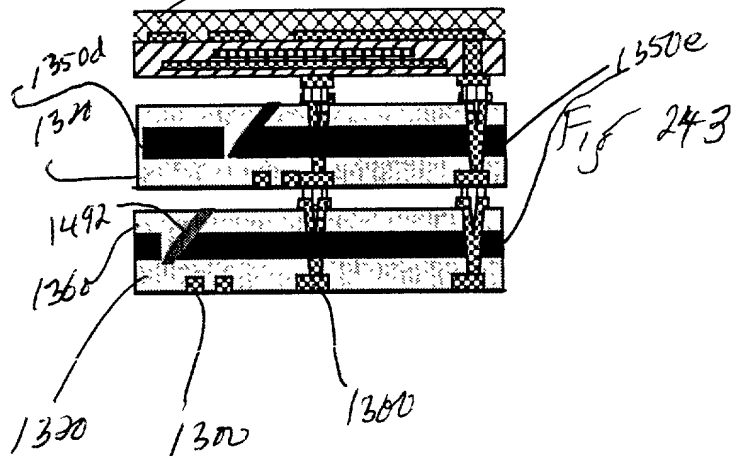


Fig 244



Fig 246

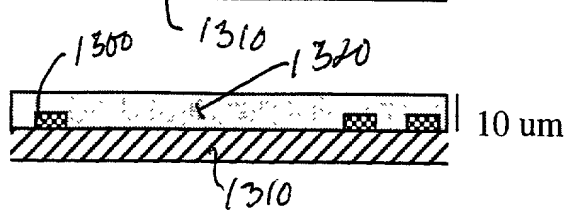


Fig 248

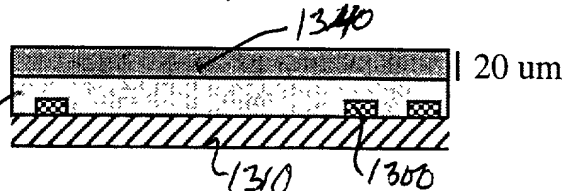


Fig 250

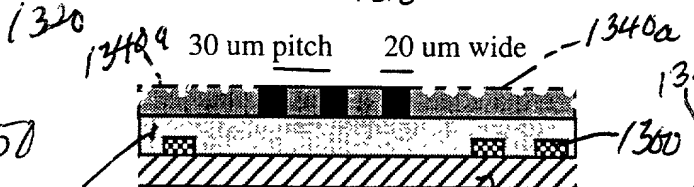


Fig 252

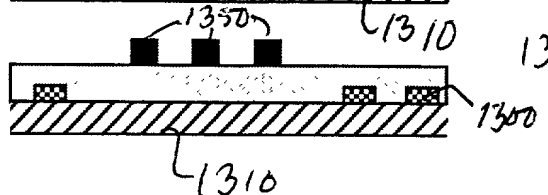


Fig 254

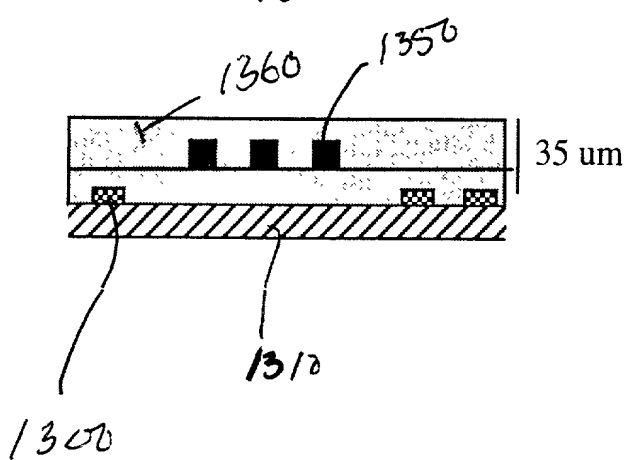


Fig 245

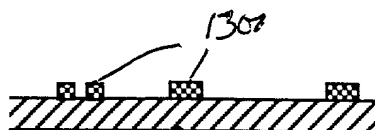


Fig 247

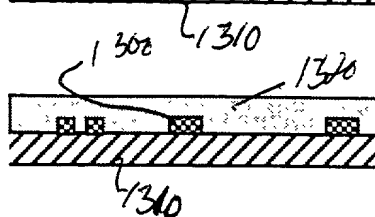


Fig 249

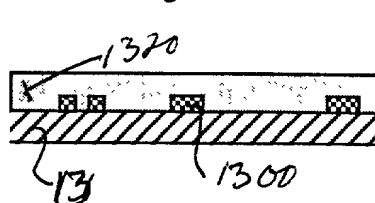


Fig 251

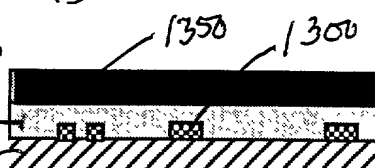


Fig 253

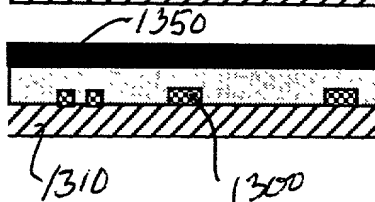
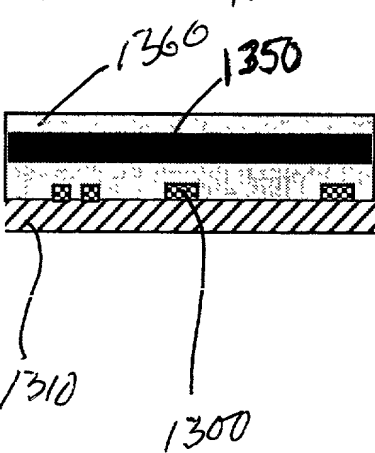
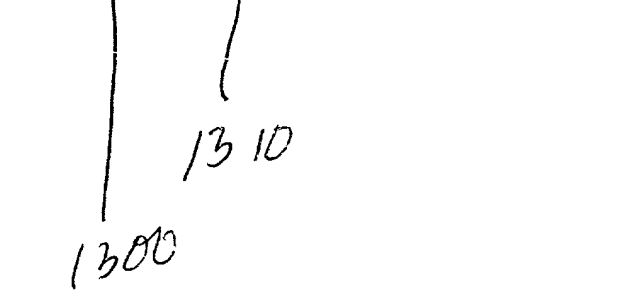
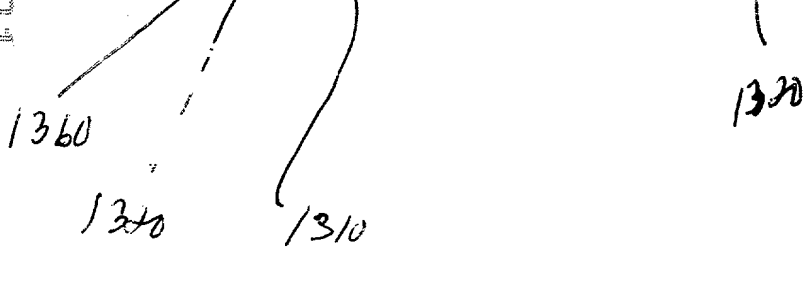
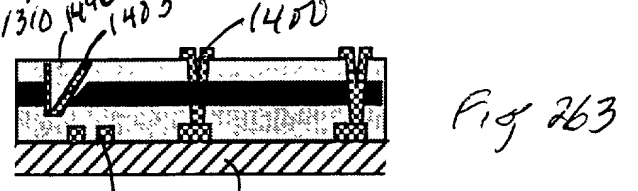
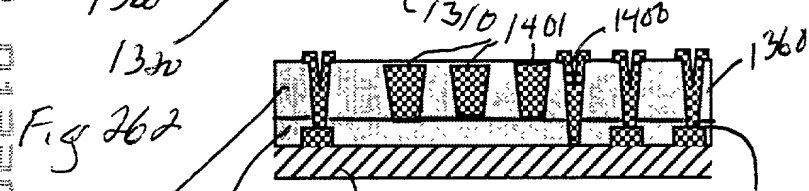
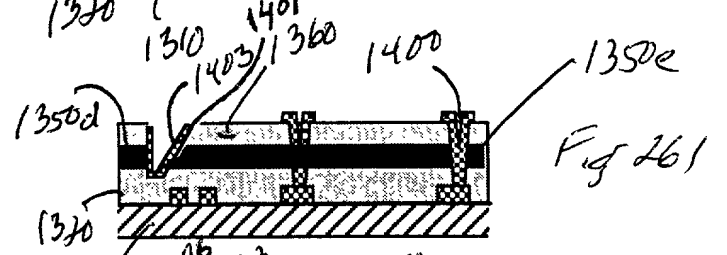
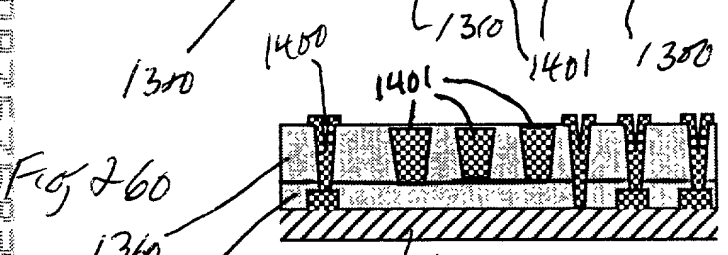
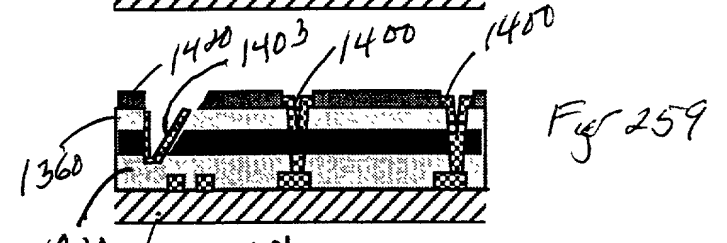
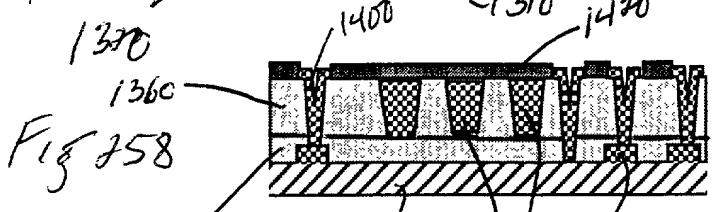
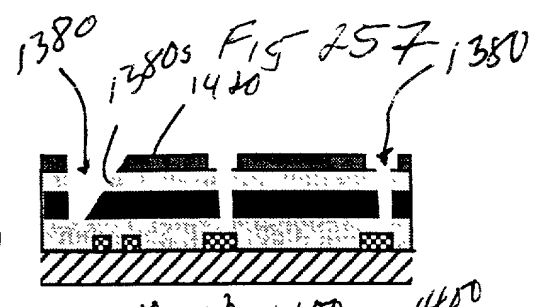
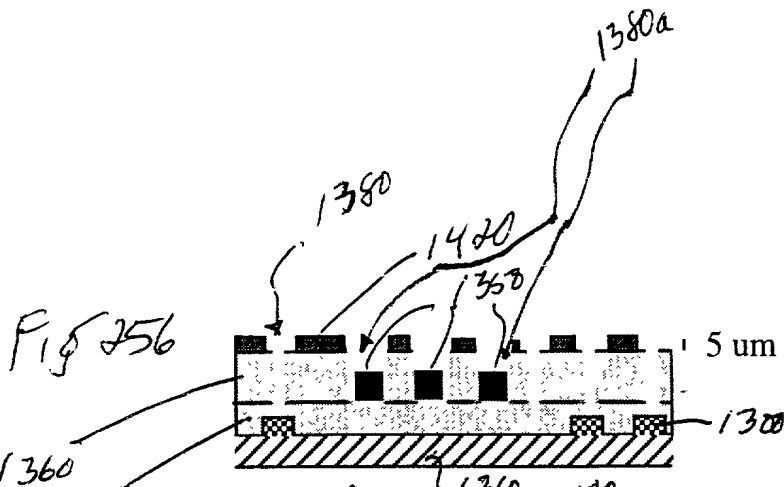
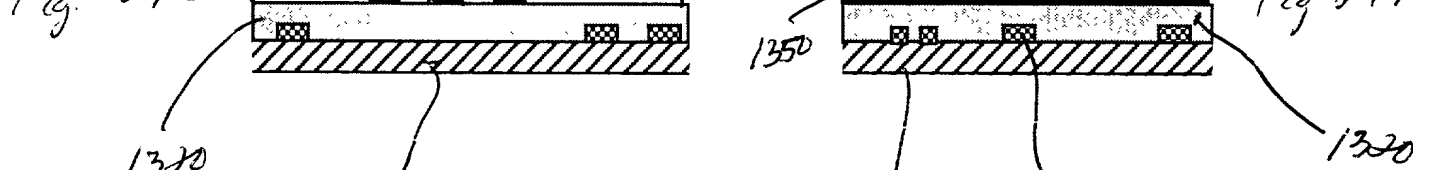
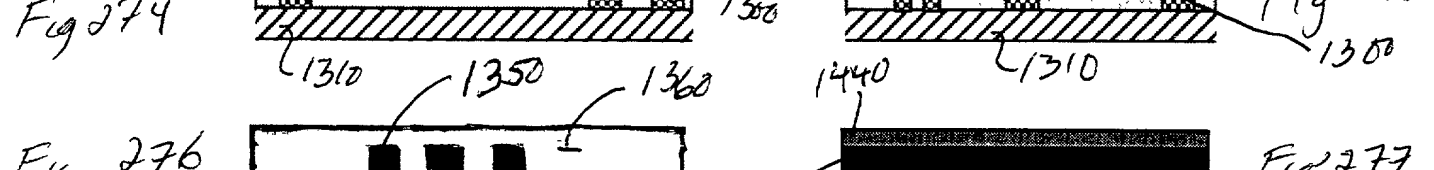
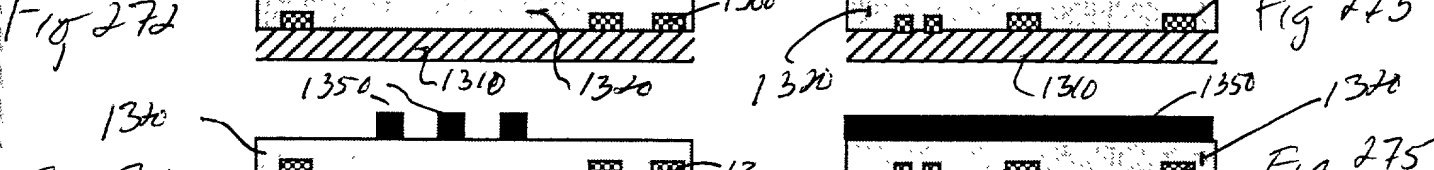
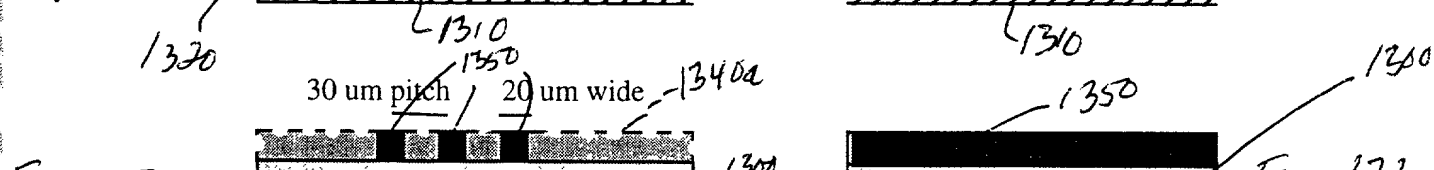
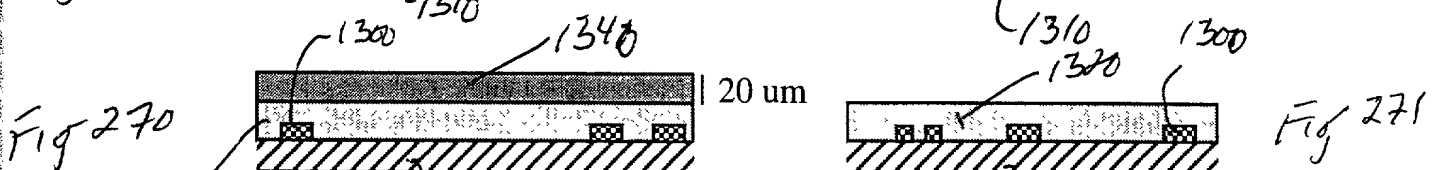
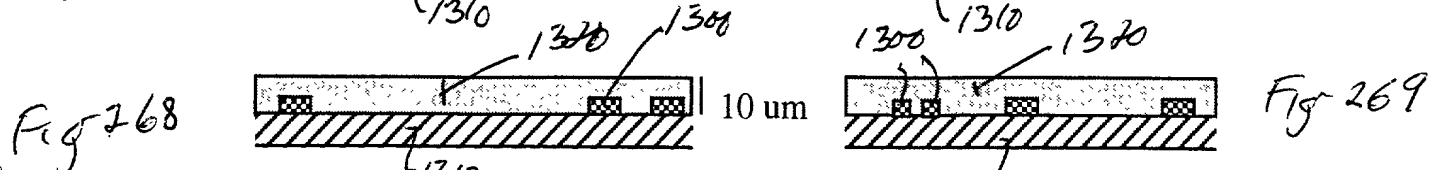
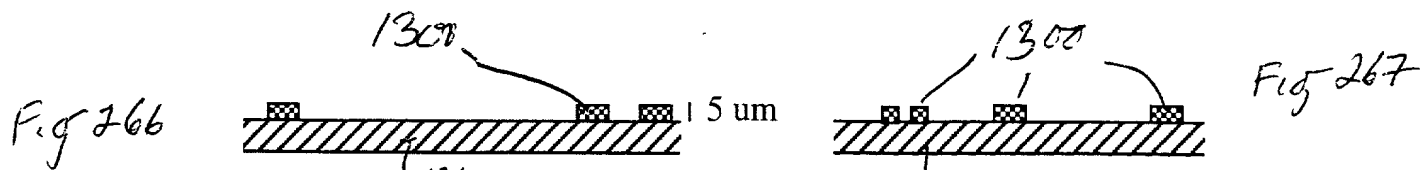
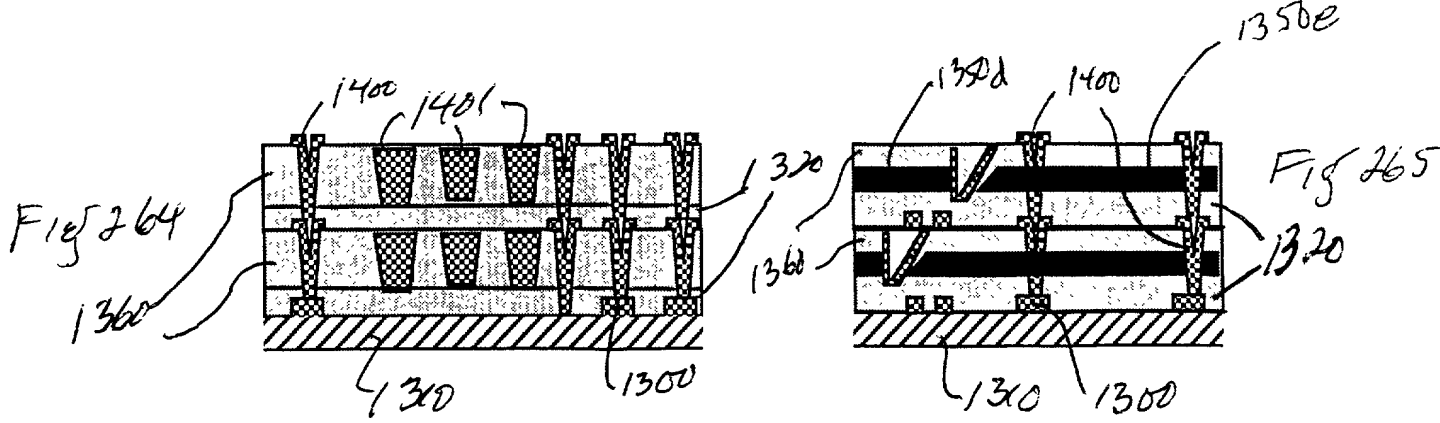


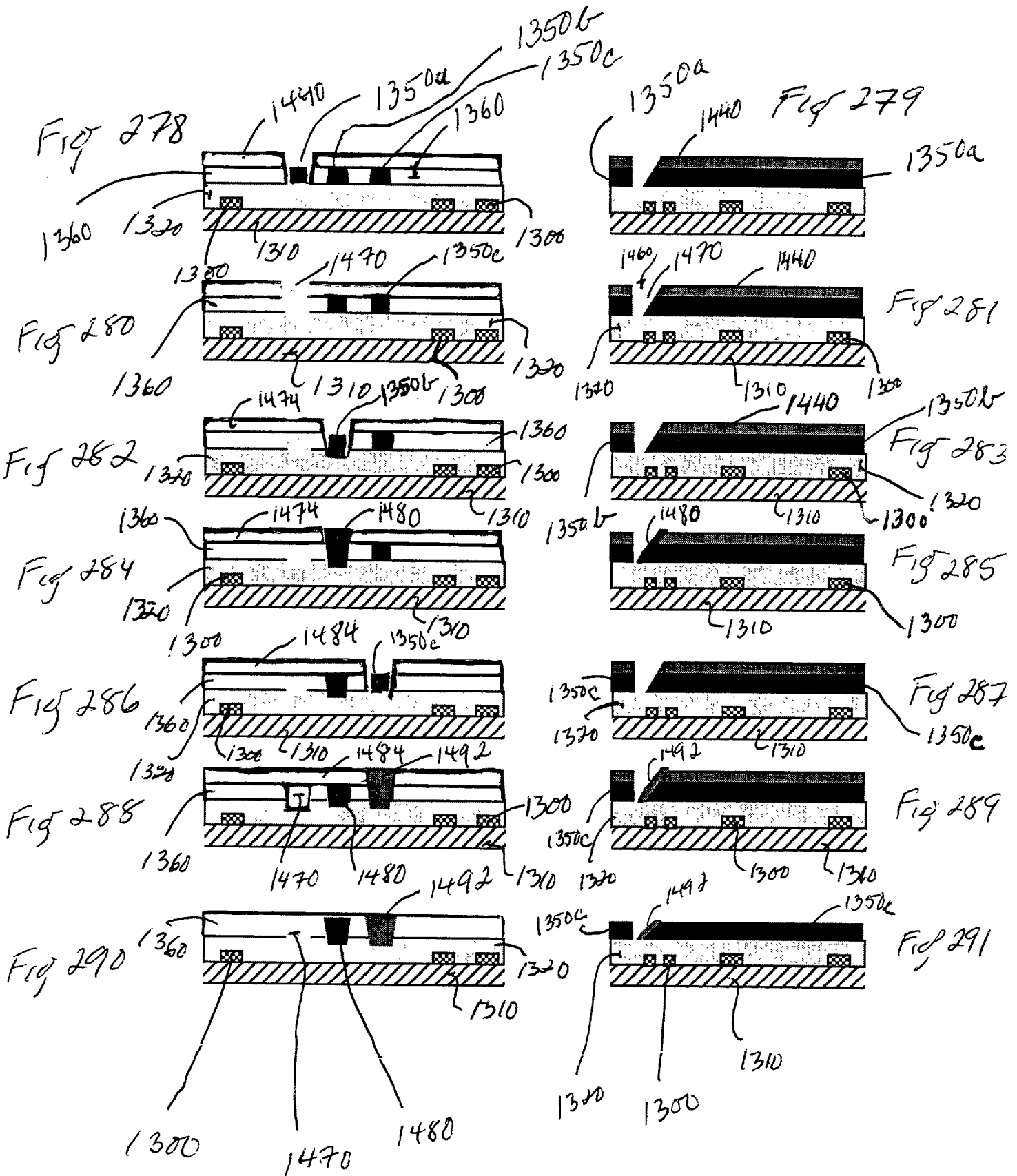
Fig 255

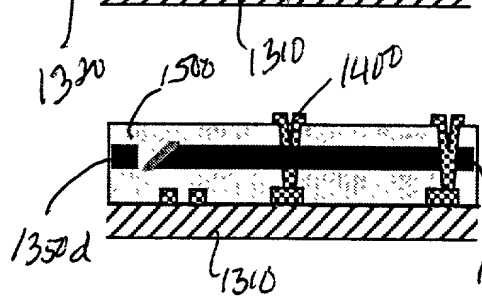
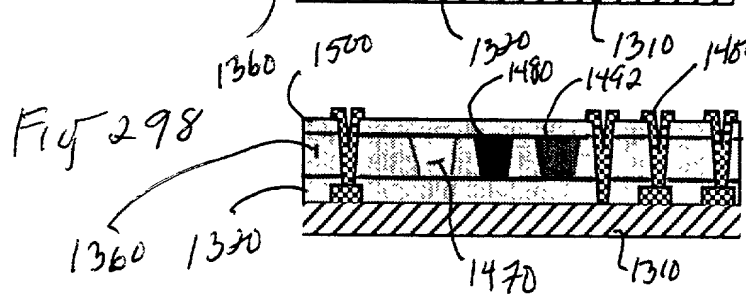
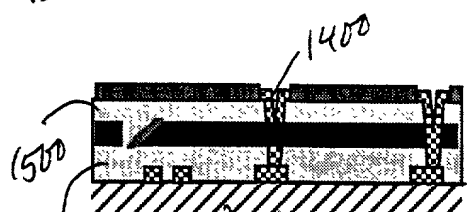
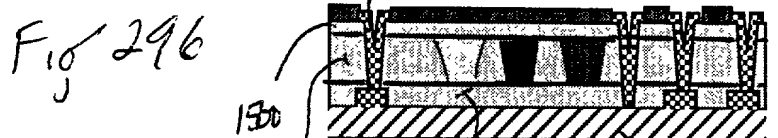
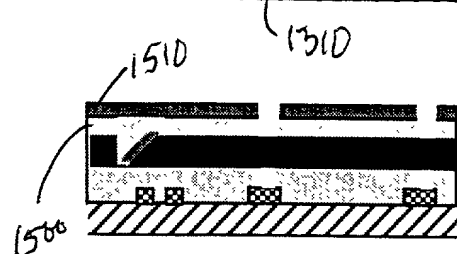
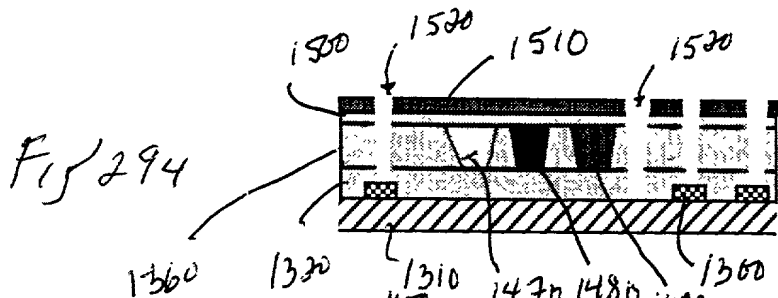
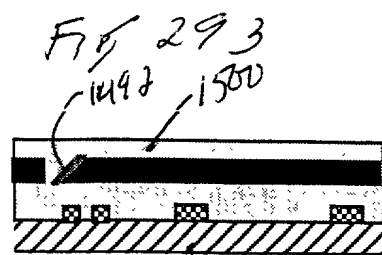
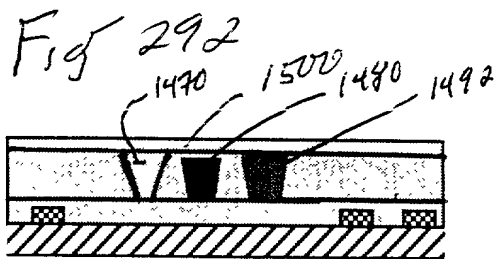






09767582.01201





1350e

In the case of multi layer (a1-a16) process is repeated on the (a16).

-it is also possible to repeat (a3-a16) or (a1, a3-a16)

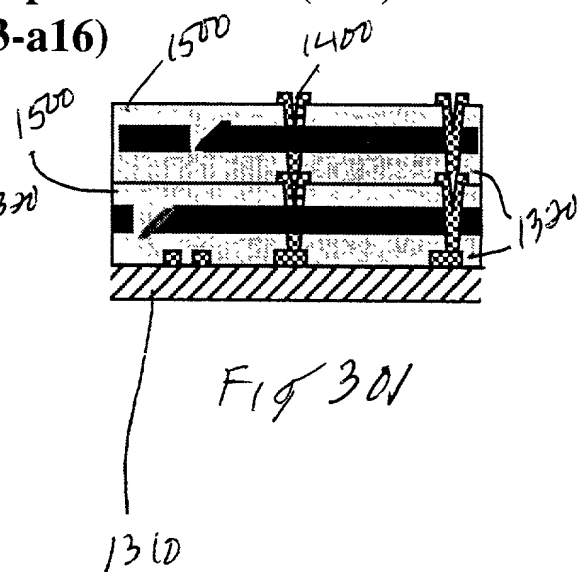
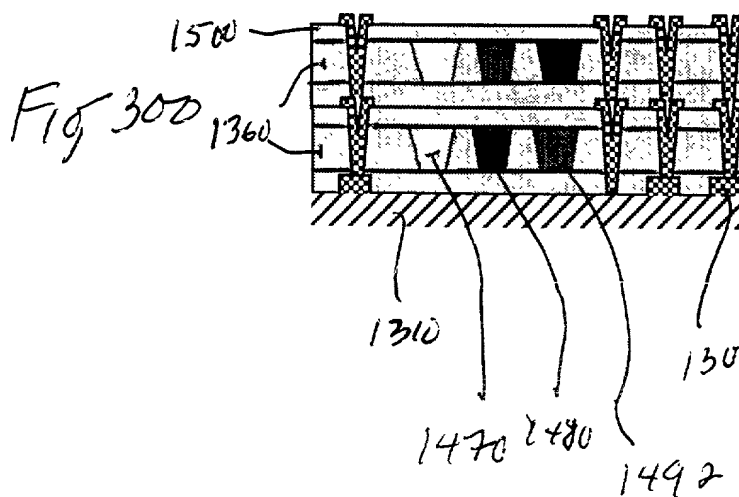


Fig 302

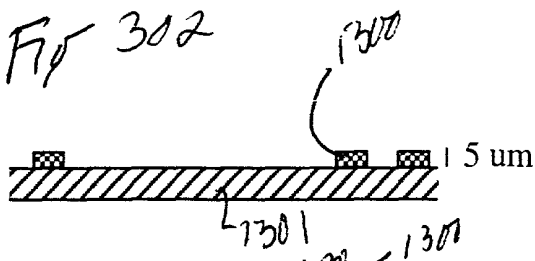


Fig 303

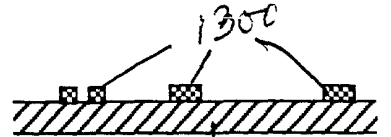


Fig 304

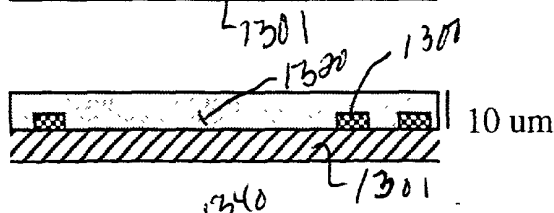


Fig 305

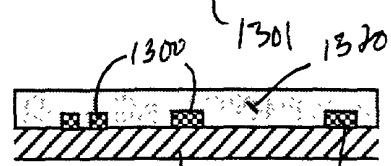


Fig 306

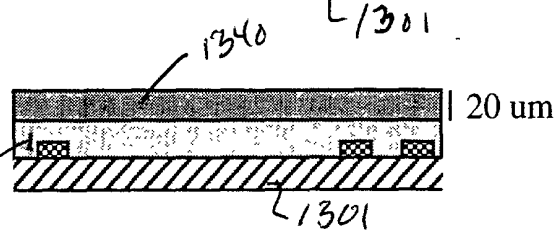


Fig 307

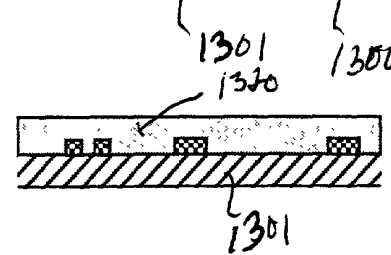


Fig 308

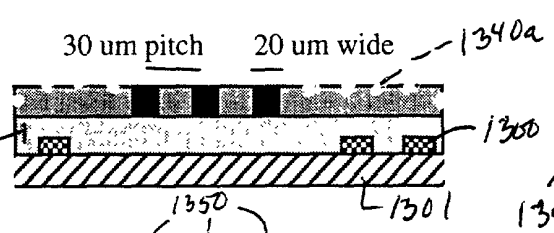


Fig 309

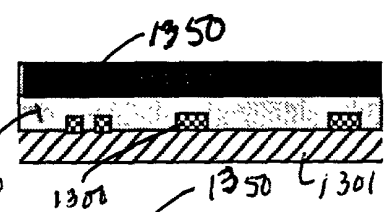


Fig 310

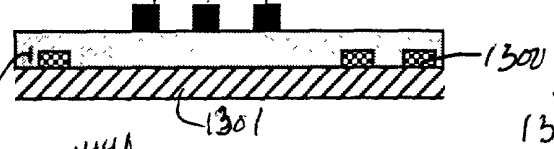


Fig 311

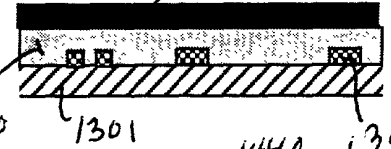
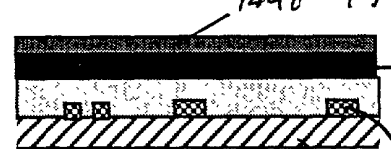


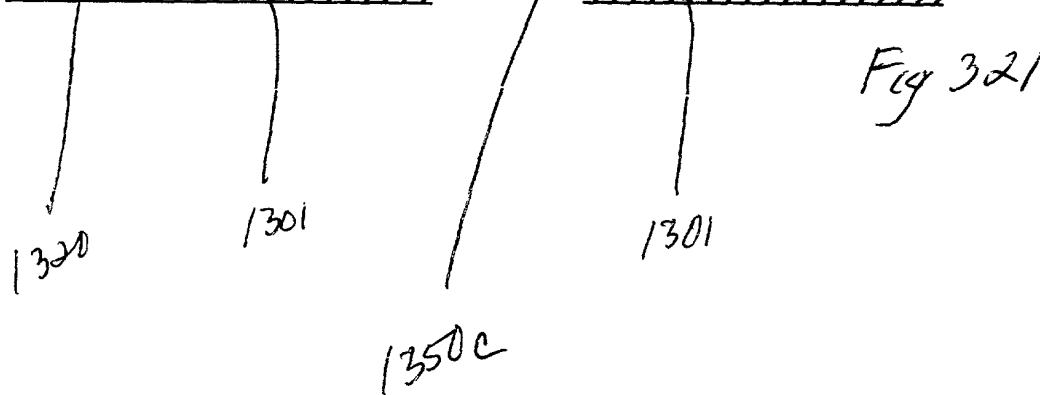
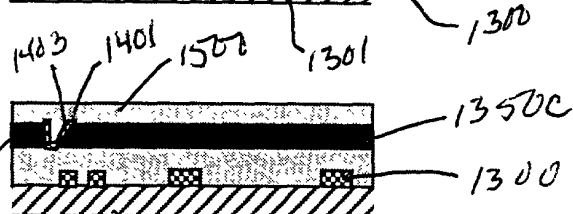
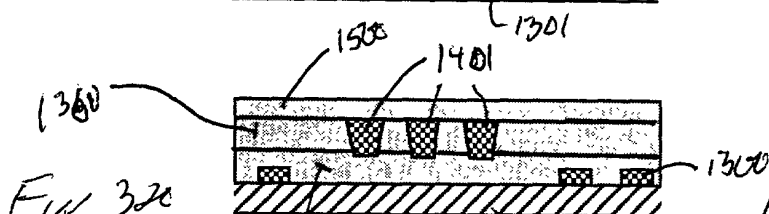
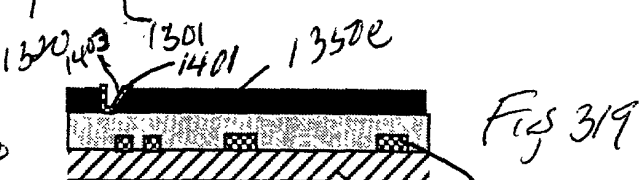
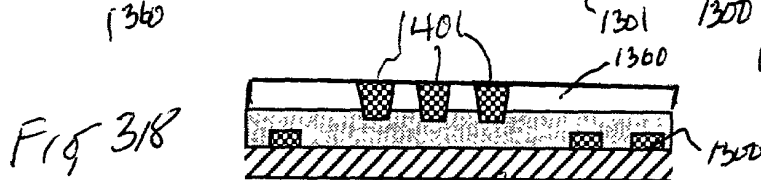
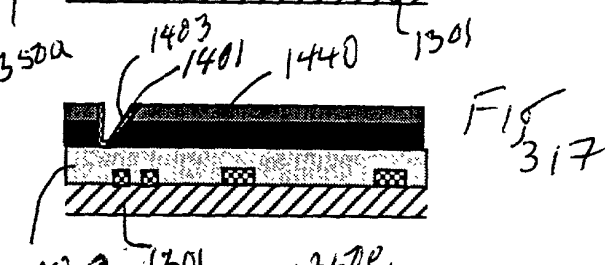
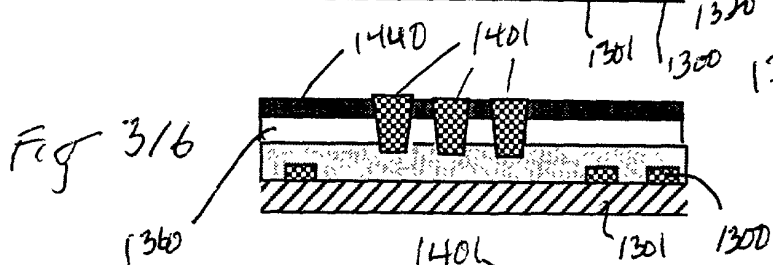
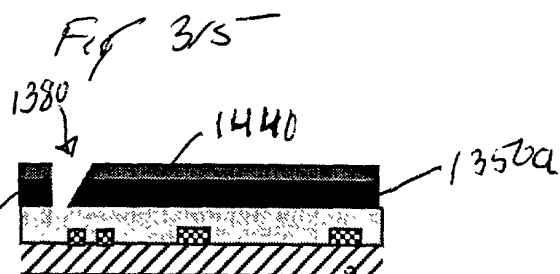
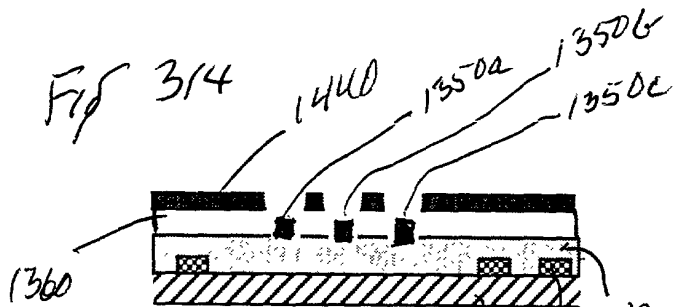
Fig 312



Fig 313



09767533.012001



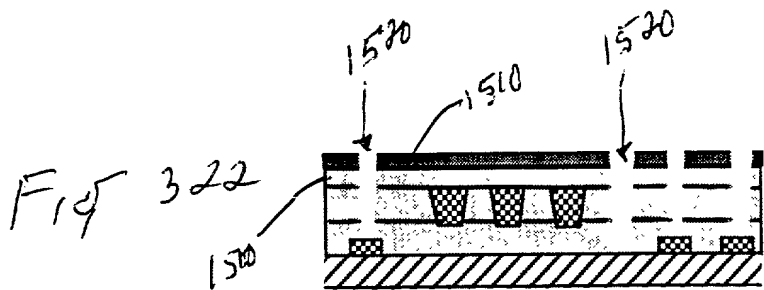


Fig 323

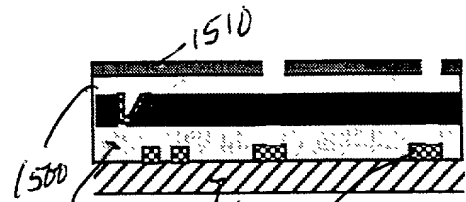


Fig 324

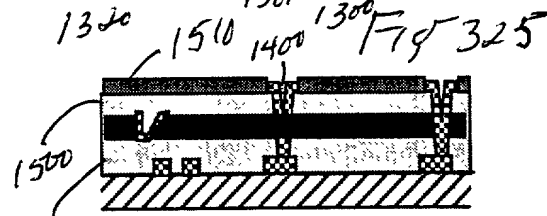
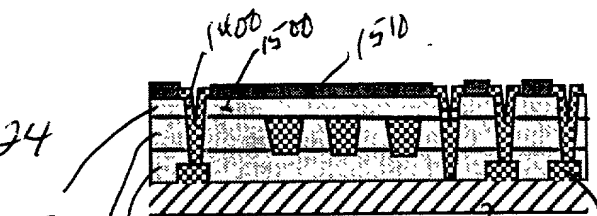
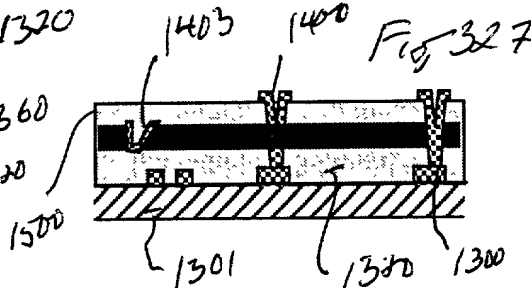
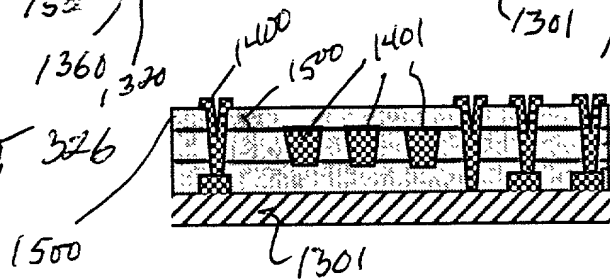


Fig 326



In the case of multi layer (a1-a12) process is repeated on the (a12).
-it is also possible to repeat (a3-a12) or (a1, a3-a12)

Fig 328

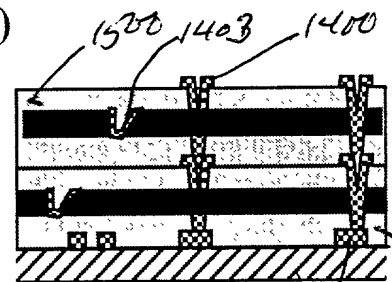
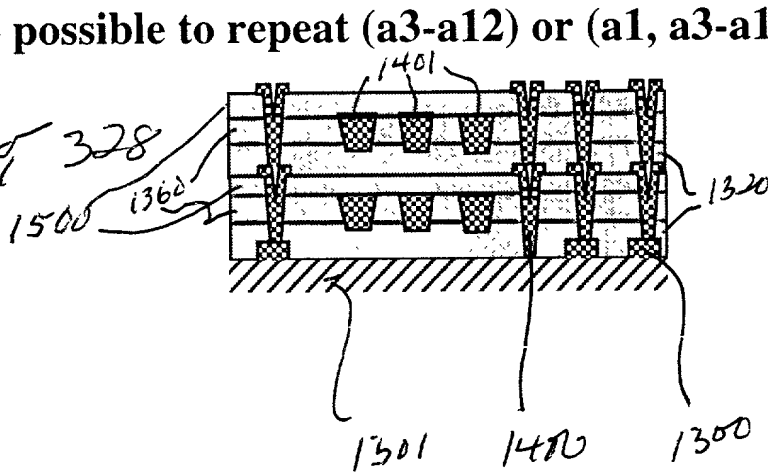
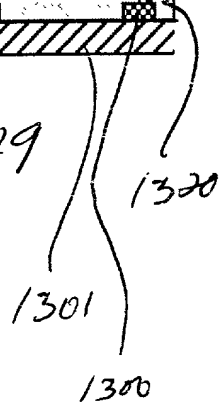


Fig 329



Invented Corner Turning Structure (A)

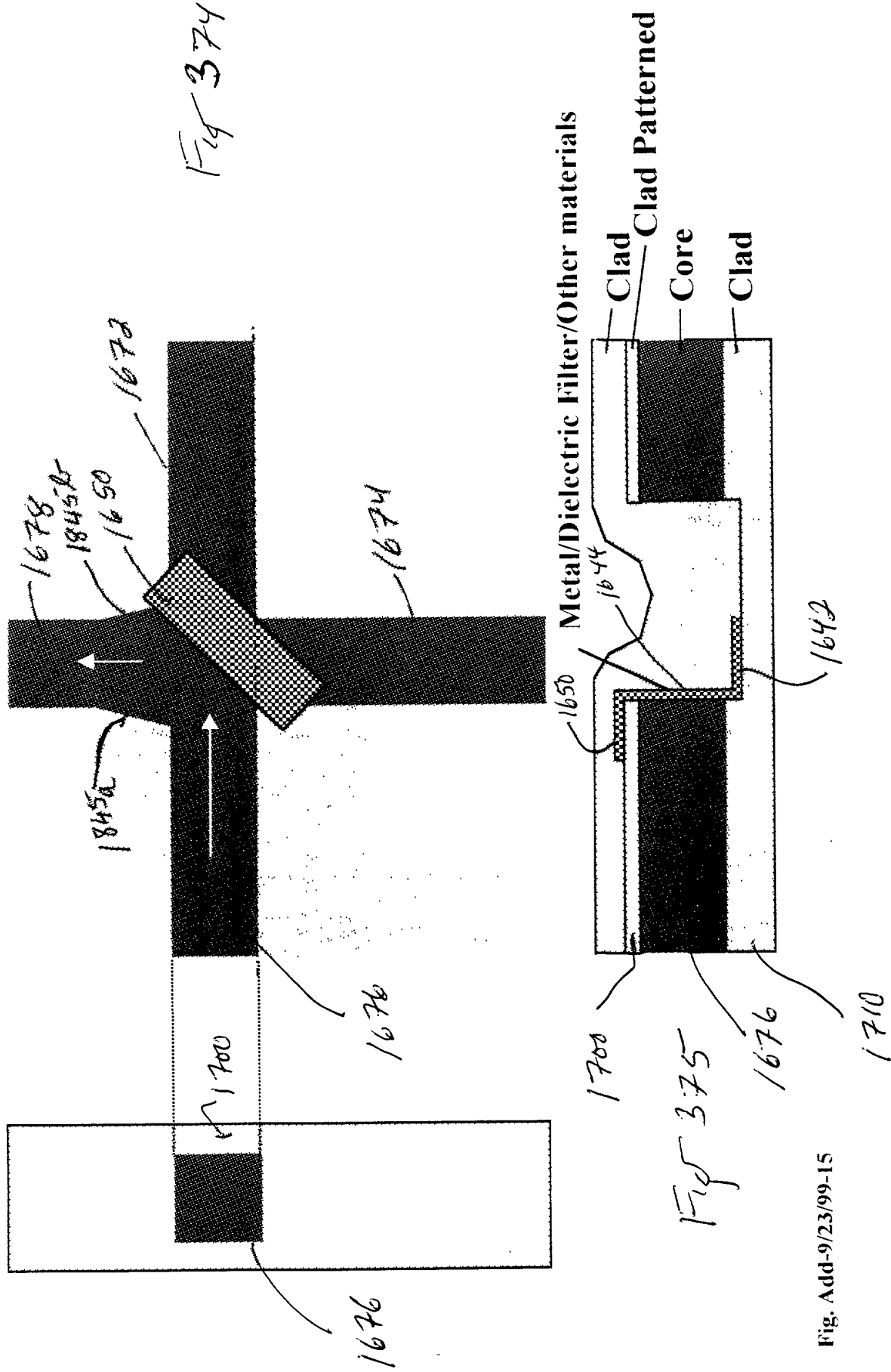
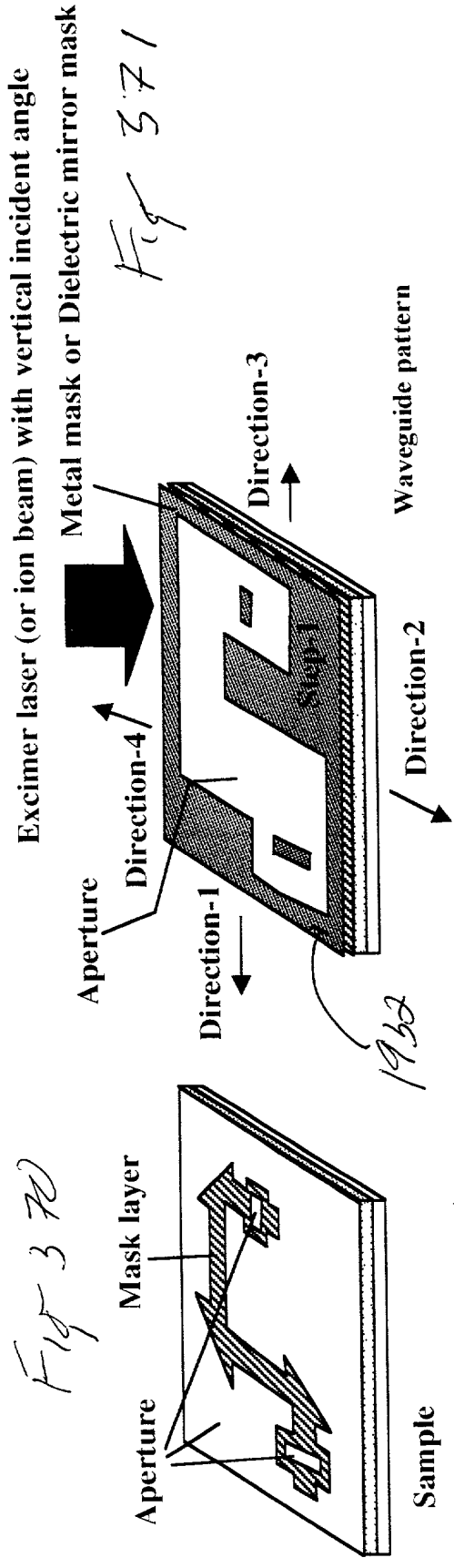


Fig. Add-9/23/99-15

MNA, MNE Example for Add2 example



Excimer laser (or ion beam) with tilted incident angle

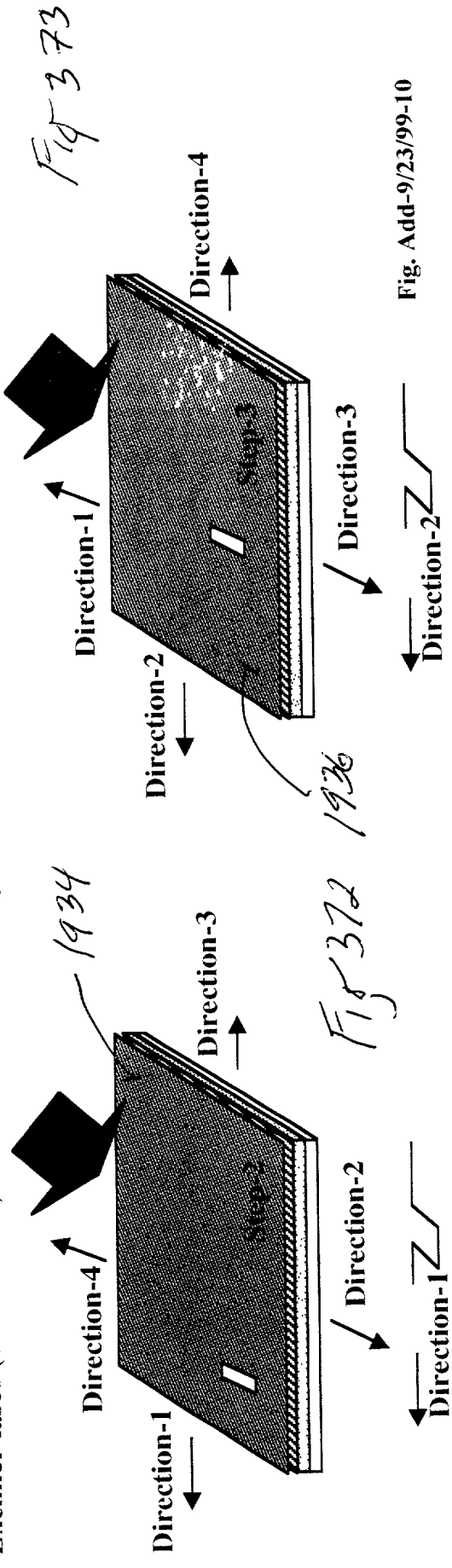


Fig. Add-9/23/99-10

Another Process Flow for Structure (II)

Fig 350

Buffer/Clad/Core/Clad Waveguide Formation

Mask formation For Waveguide/Coupler

MNA or MNE Aperture

Fig 350

Fig 351

Fig 352

Fig 353

Fig 354

Fig 355

Fig 356

Fig 357

Fig 358

Fig 359

Fig 360

Fig 361

Fig 362

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation I

MNA or MNE

Aperture

Fig 357

Fig 358

Fig 359

Fig 360

Fig 361

Fig 362

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation II

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation I

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation II

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation I

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation II

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation I

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation II

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation I

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation II

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Fig 377

Fig 378

Fig 379

Fig 380

Fig 381

Fig 382

Fig 383

Fig 384

Fig 385

Coupler Formation I

MNA or MNE

Aperture

Fig 363

Fig 364

Fig 365

Fig 366

Fig 367

Fig 368

Fig 369

Fig 370

Fig 371

Fig 372

Fig 373

Fig 374

Fig 375

Fig 376

Excimer Laser Ablation Example for Beveled Cut (2)

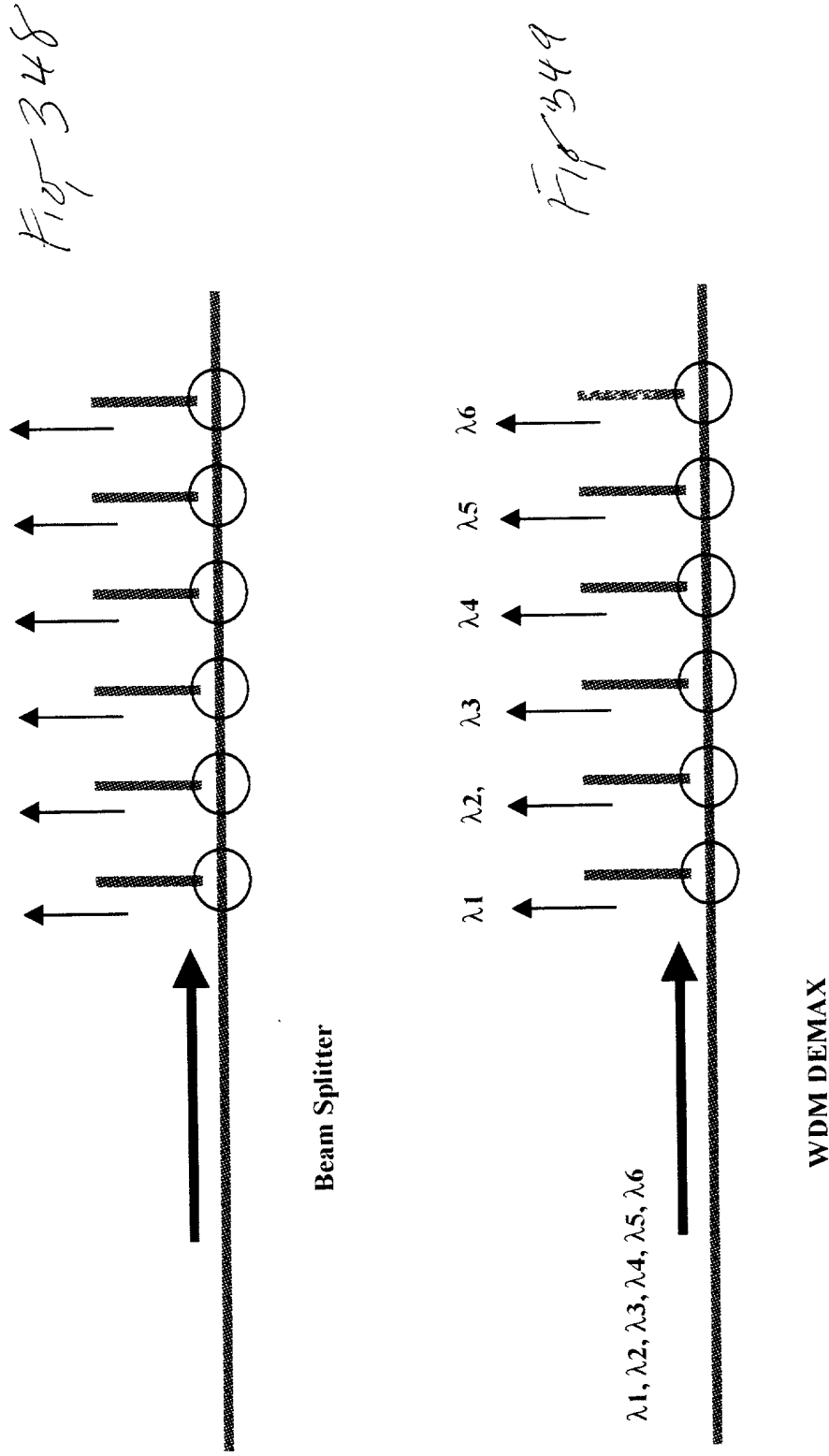


Fig. Add-9/23/99-8

Invented Coupler Structure (II)

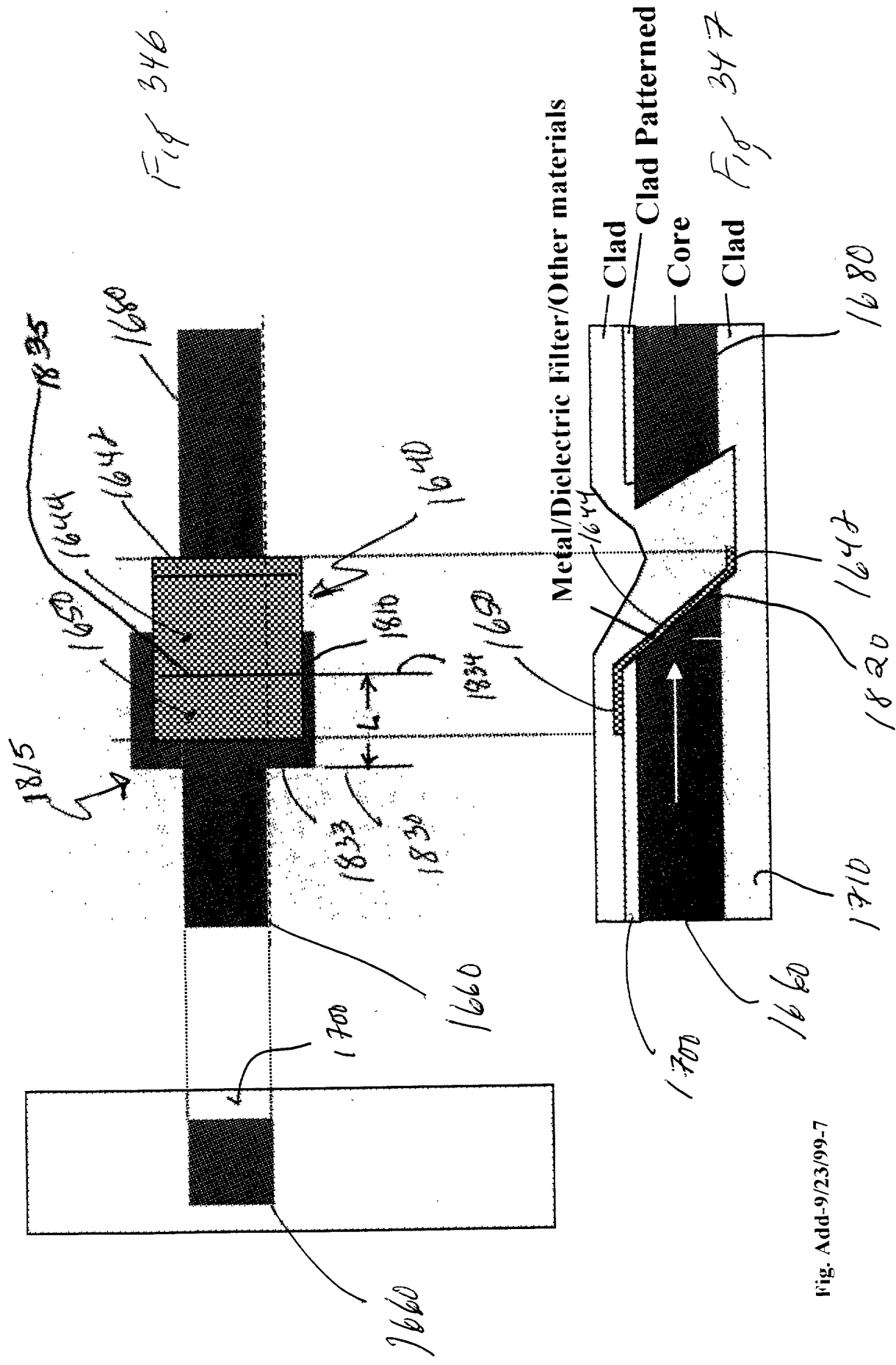


Fig. Add-9/23/99-7

Invented Coupler Structure (I)

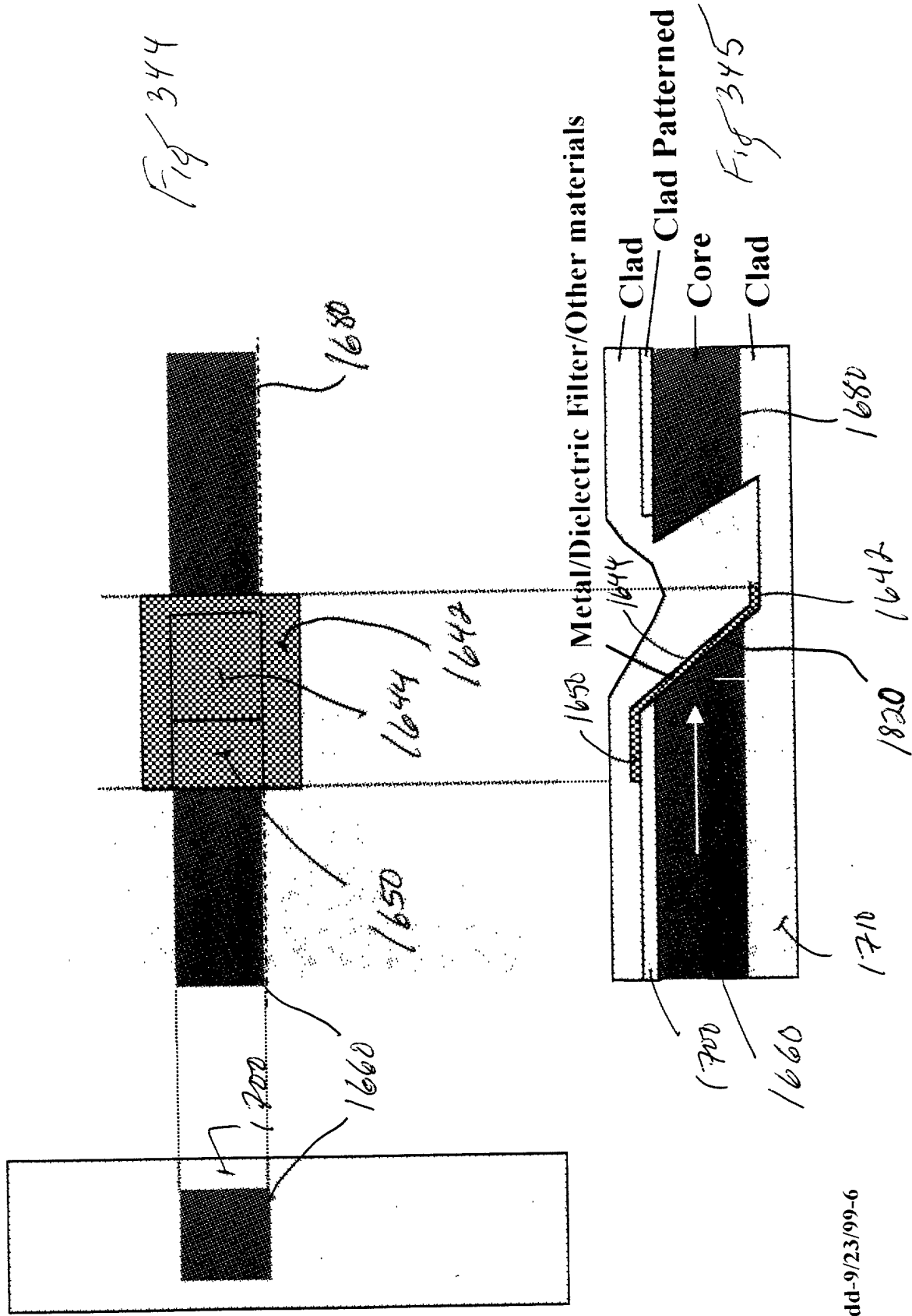


Fig. Add-9/23/99-6

Conventional Coupler Structure (I)

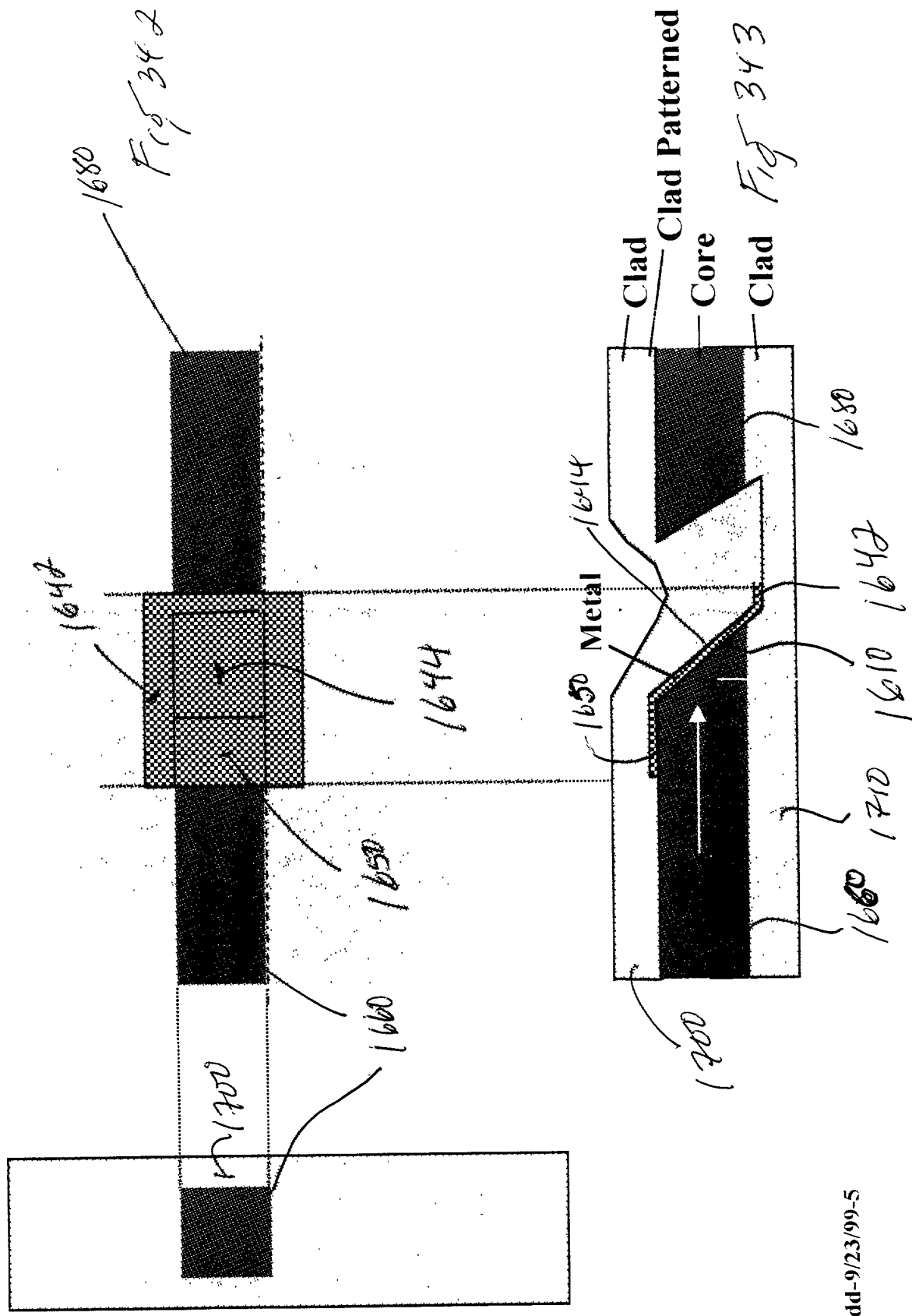


Fig. Add-9/23/99-5

Invented Corner Turning Structure (II)

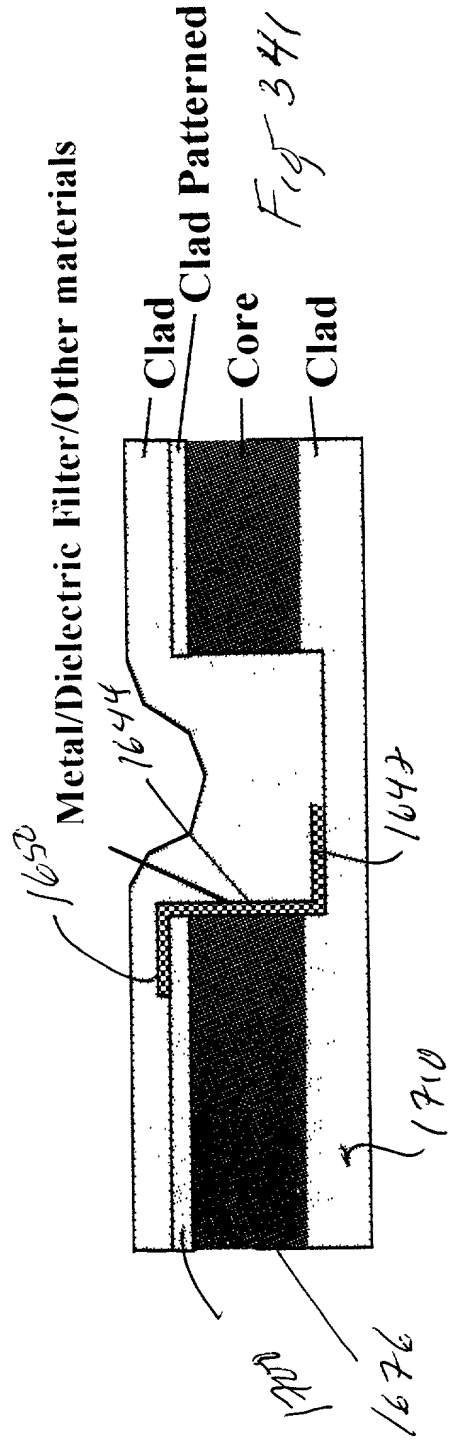
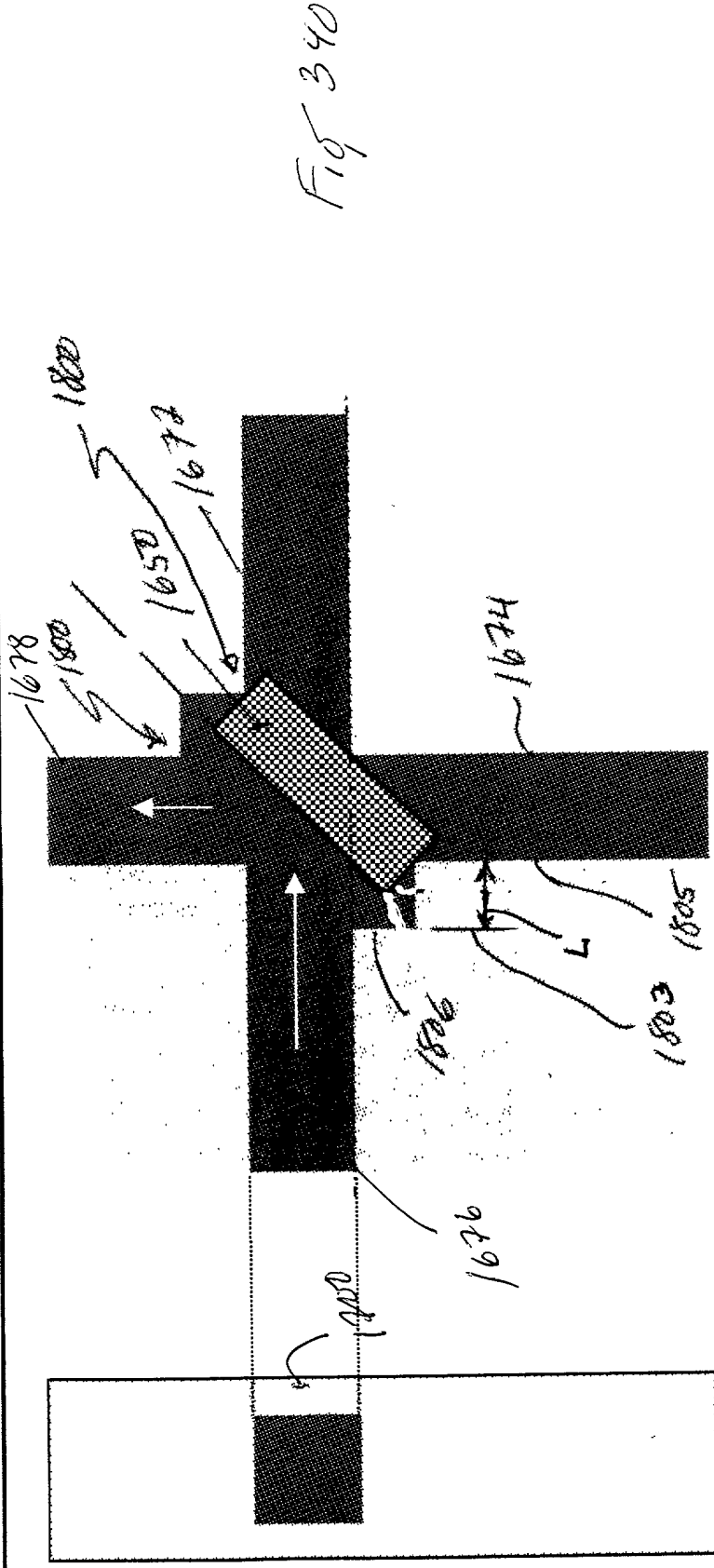


Fig. Add-9/23/99-4

Invented Corner Turning Structure (I)

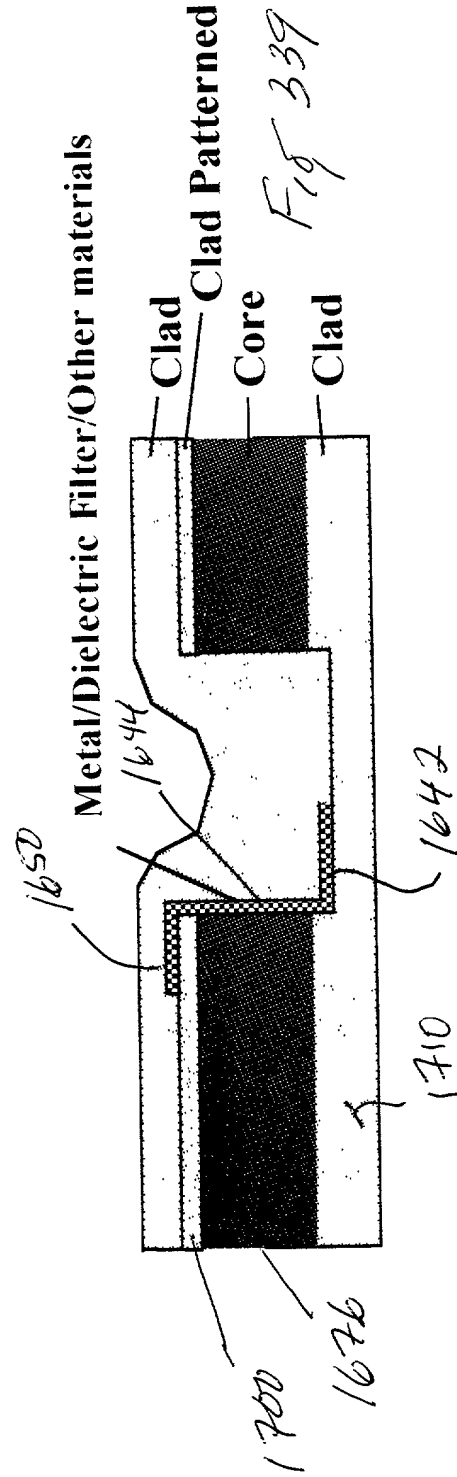
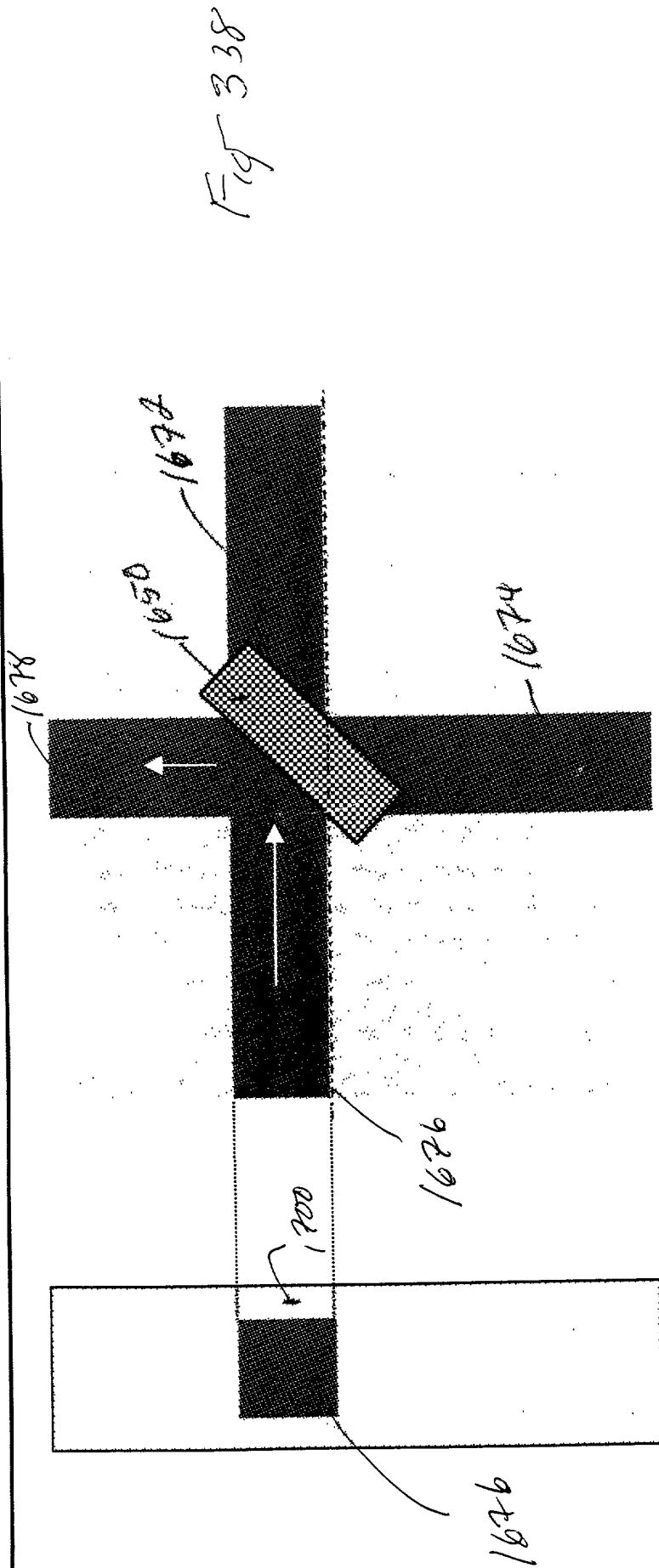


Fig. Add-9/23/99-3

Conventional Corner Turning Structure

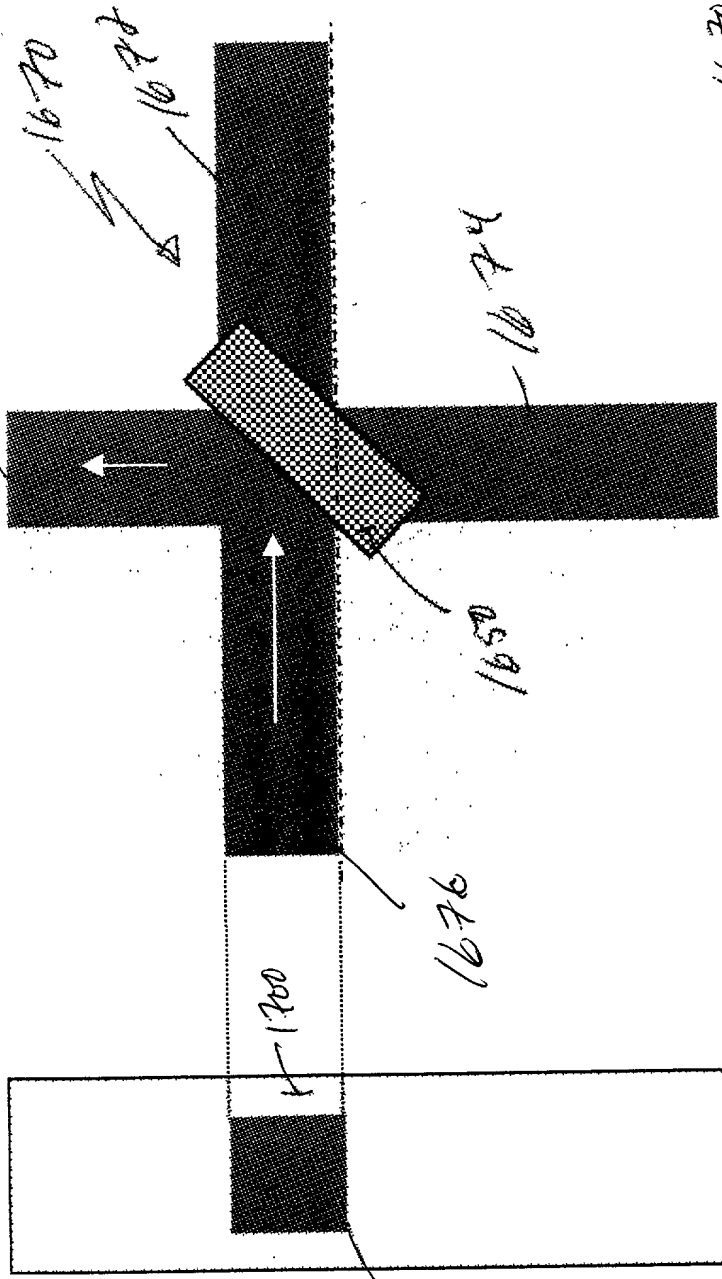


Fig 336
1676

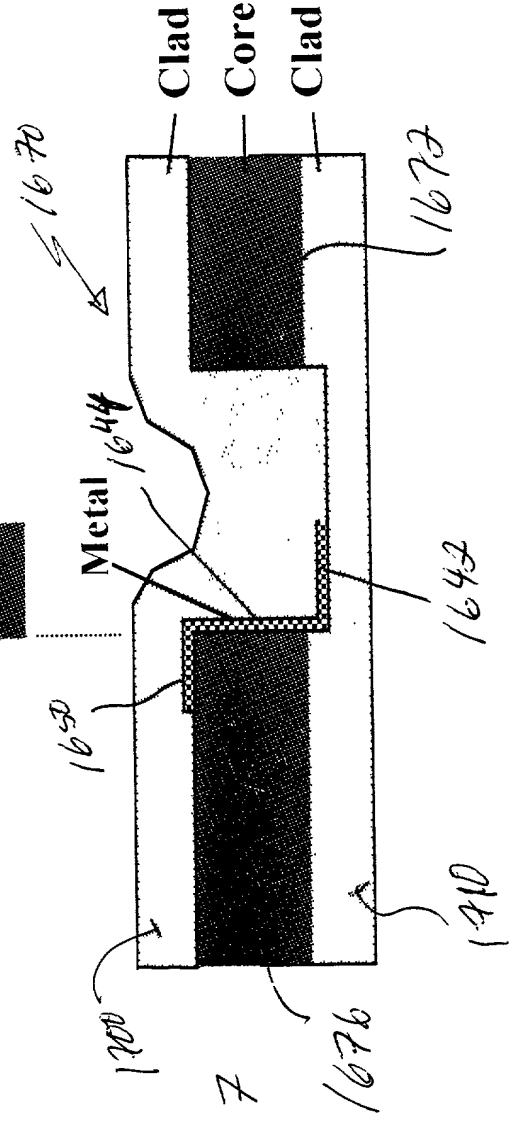
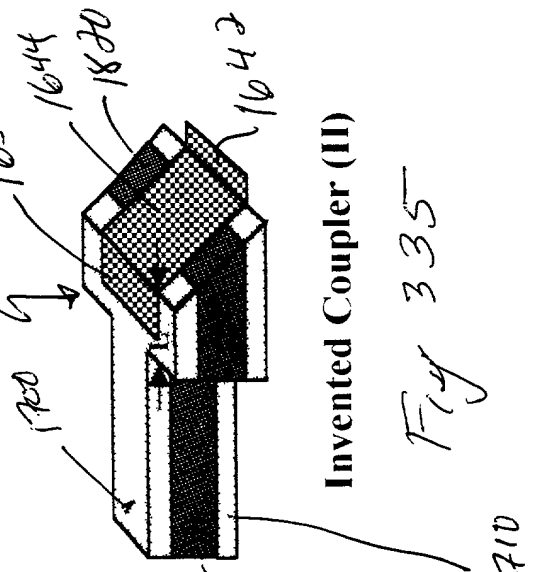
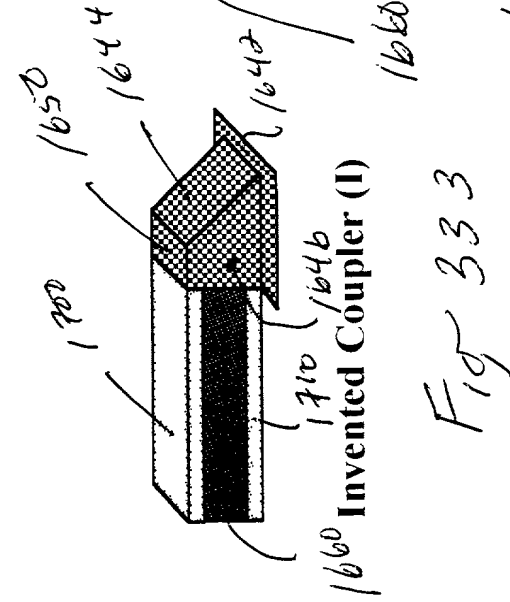
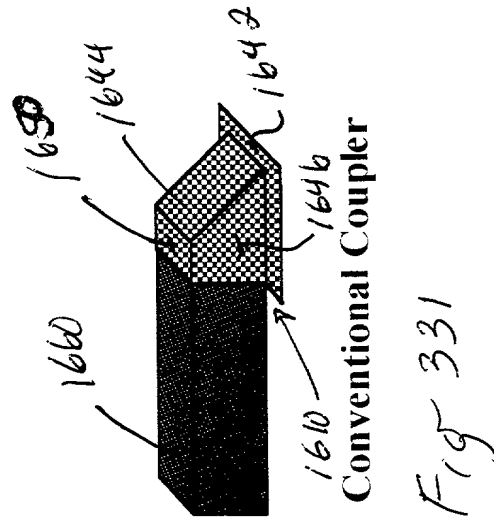
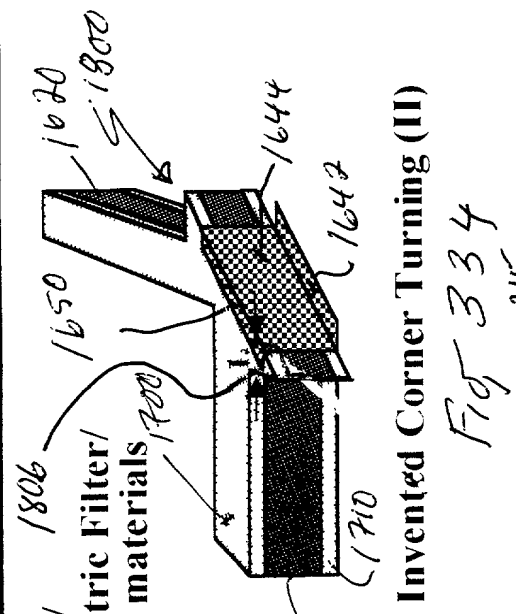
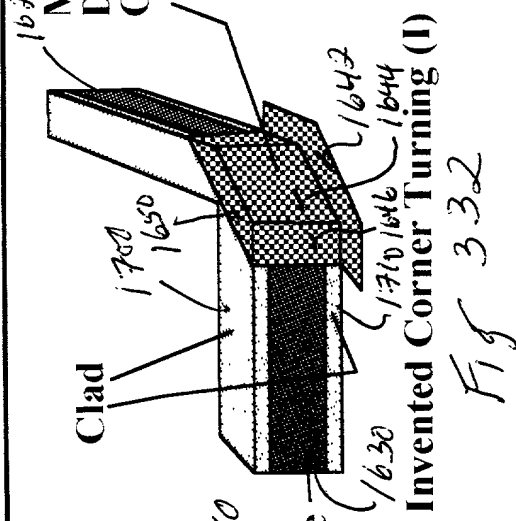
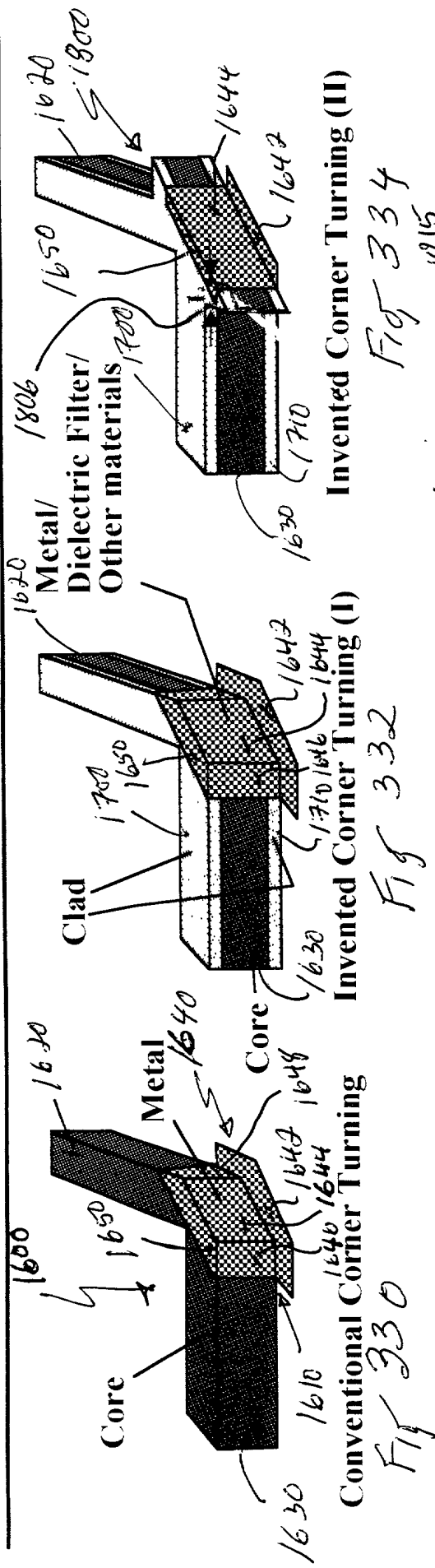


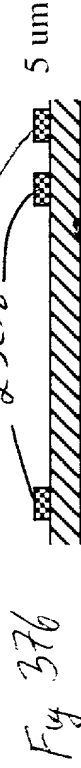
Fig 337

Conventional and Invented Waveguide Structure Examples



Example 3: Z waveguide Fab. Process 1

(a1) Metal pattern formation

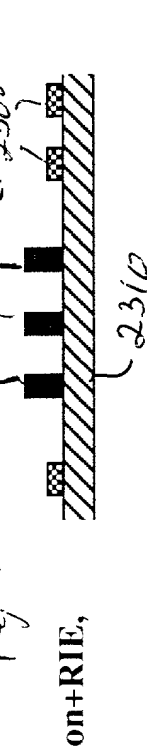


(a2) Core coat9



[DuPont, AlliedSig, ORMOCERS or F-PI]

(a3) Z-WG core patterning



[UV-Exposure, mask-formation+RIE,

Laser, or Dupont process]

Development

(for AlliedSig, ORMOCERS)

(a4) Clad coat



(for planarization viscosity adjust

if necessary CMP)

(a5) Core coat



[DuPont, AlliedSig, ORMOCERS or F-PI]

(a6) WG core patterning



[UV-Exposure, mask-formation+RIE,

Laser, or Dupont process]

Development

(for AlliedSig, ORMOCERS)

Example 3: Z waveguide Fab. Process 1

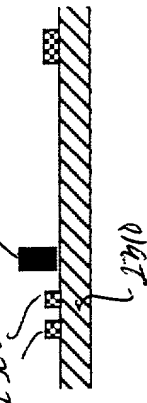


Fig. 16-1

2330a

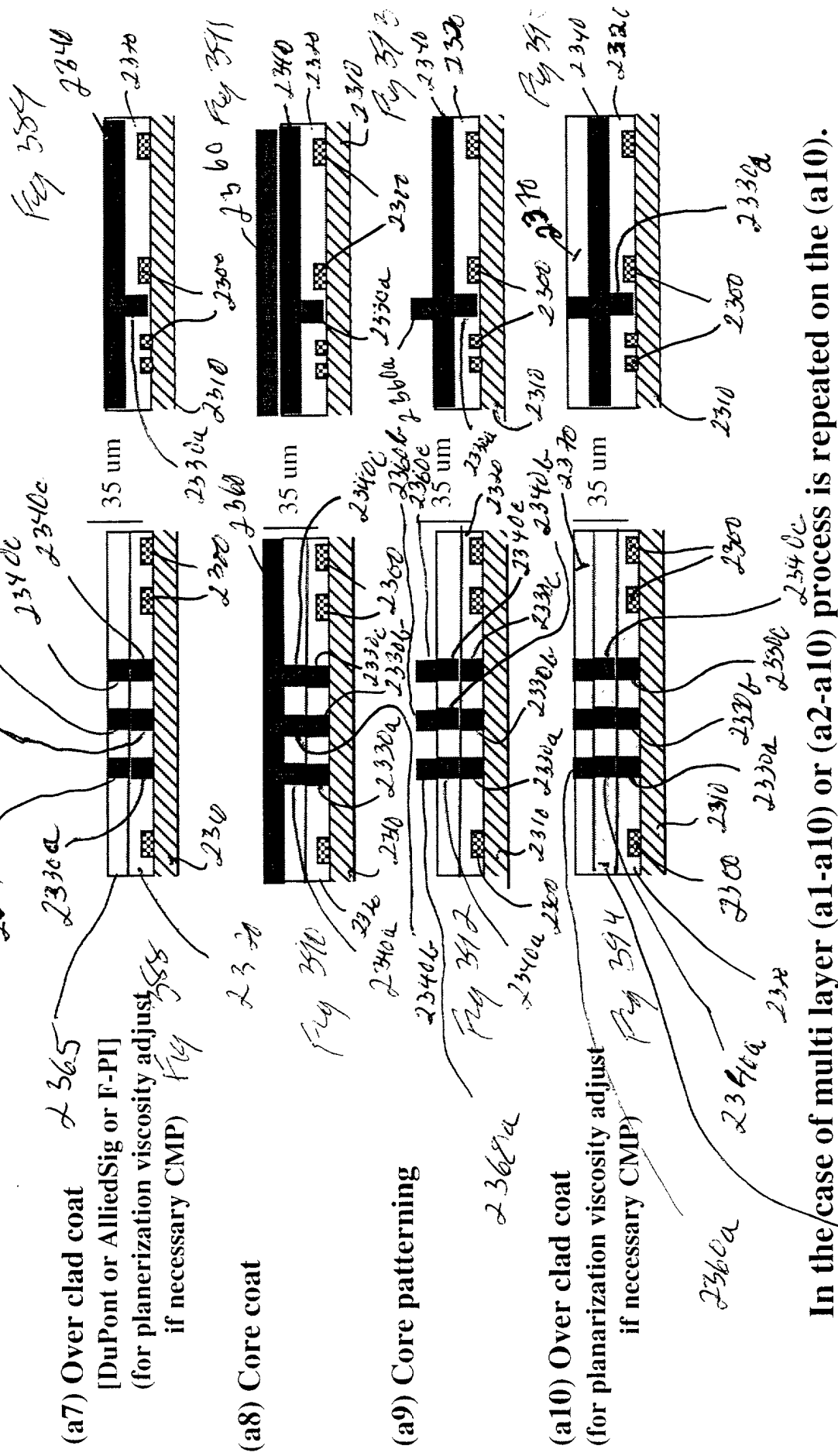


Fig. 16-2

Example 4: Z waveguide Fab. Process 2

- (a1) Metal pattern formation
[DuPont, AlliedSig, ORMOCERs or F-PI]
Laser or Dupont process]
- (a2) Clad coat
[UV-Exposure, mask-formation+RIE, Development
(for AlliedSig, ORMOCERs)]
- (a3) Clad patterning
[UV-Exposure, mask-formation+RIE, Laser or Dupont process]
- (a4) Core coat
[UV-Exposure, mask-formation+RIE, Laser or Dupont process]
- (a5) WG core patterning
[UV-Exposure, mask-formation+RIE, Laser or Dupont process]
- (a6) Over clad coat
[DuPont or AlliedSig or F-PI]
(for planarization viscosity adjust
if necessary CMP)

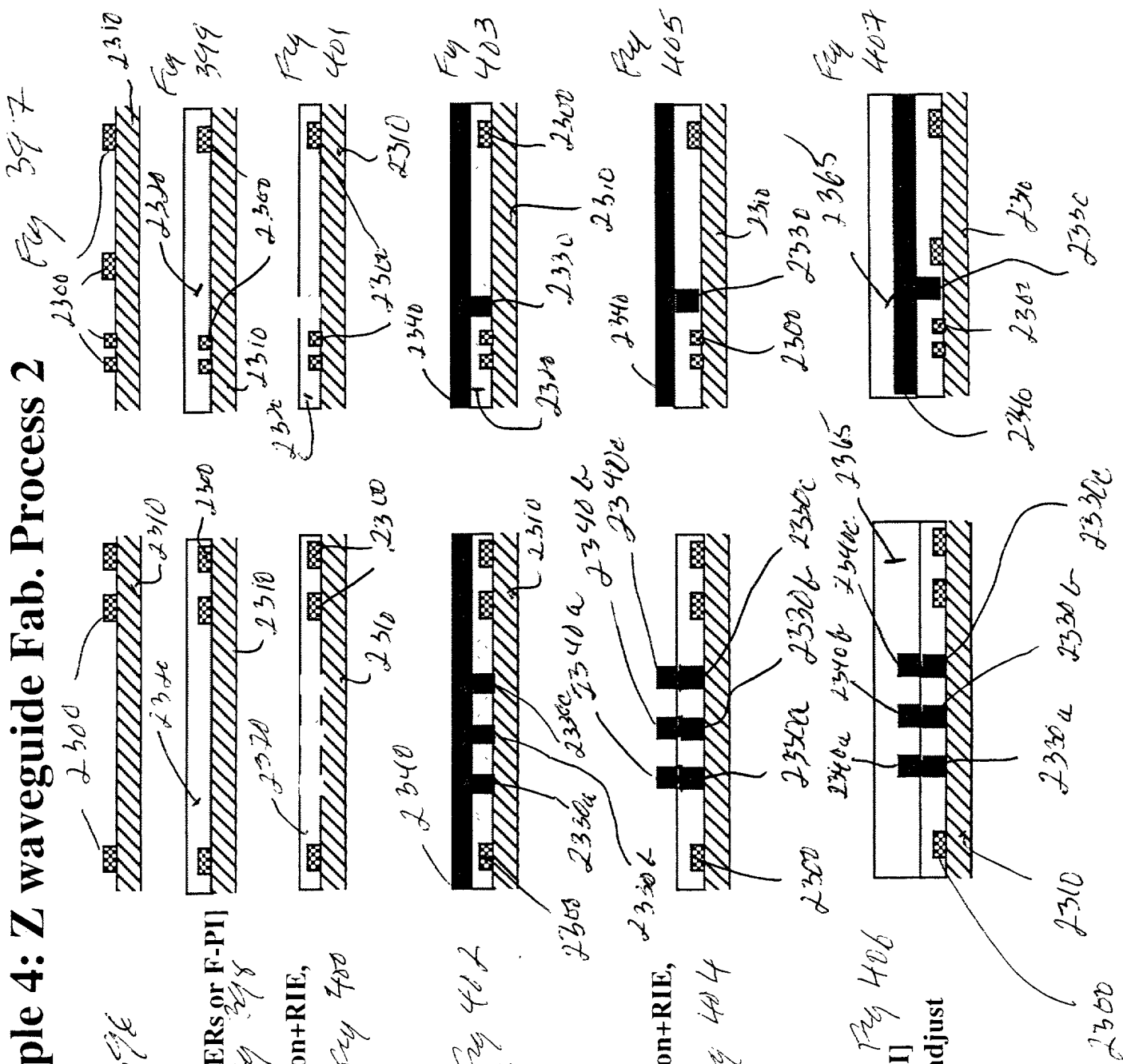
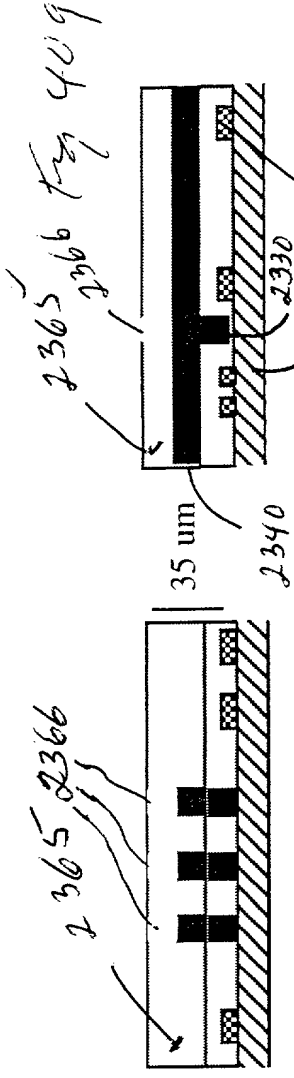


Fig. 17-1

(a7) Clad patterning

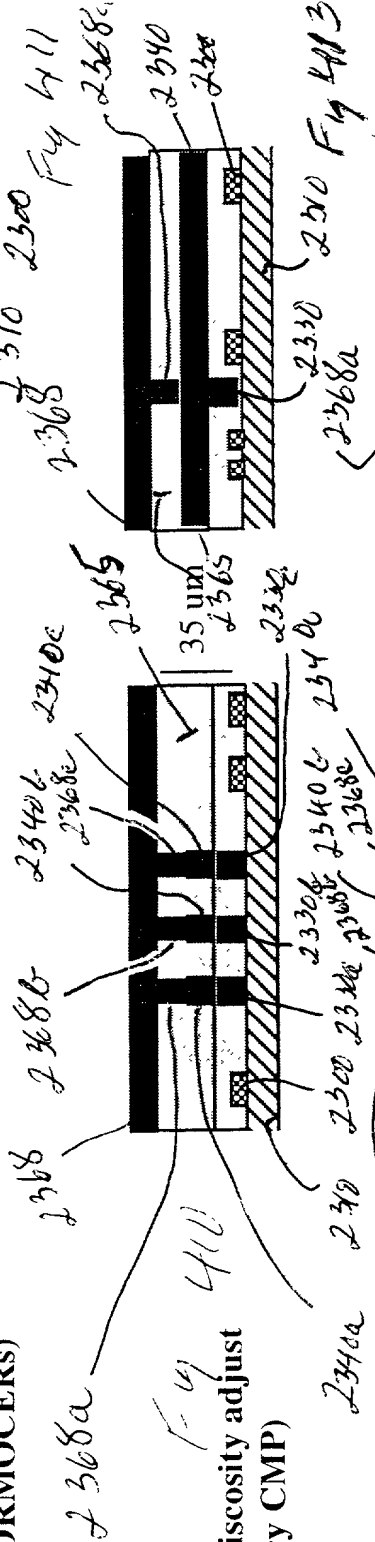
[UV-Exposure, mask-formation+RIE,
Laser or Dupont process] Fig 408
Development

(for AlliedSig, ORMOCERS)



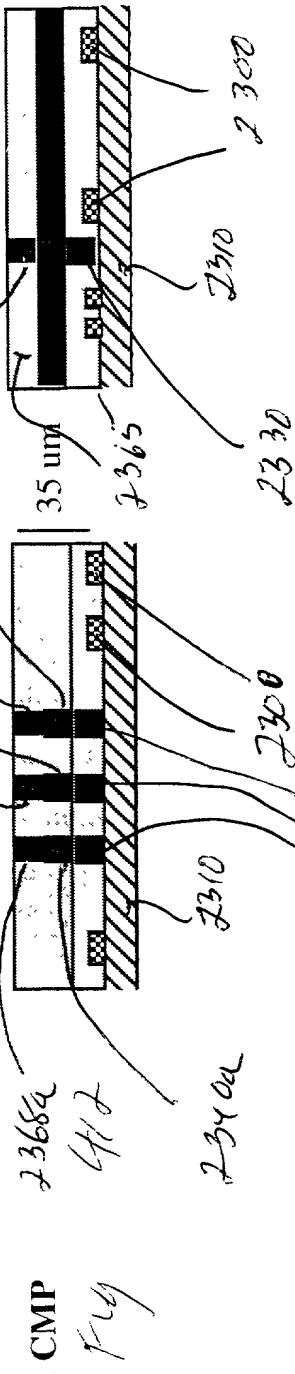
(a8) Core coat

(for planarization viscosity adjust
if necessary CMP)



or

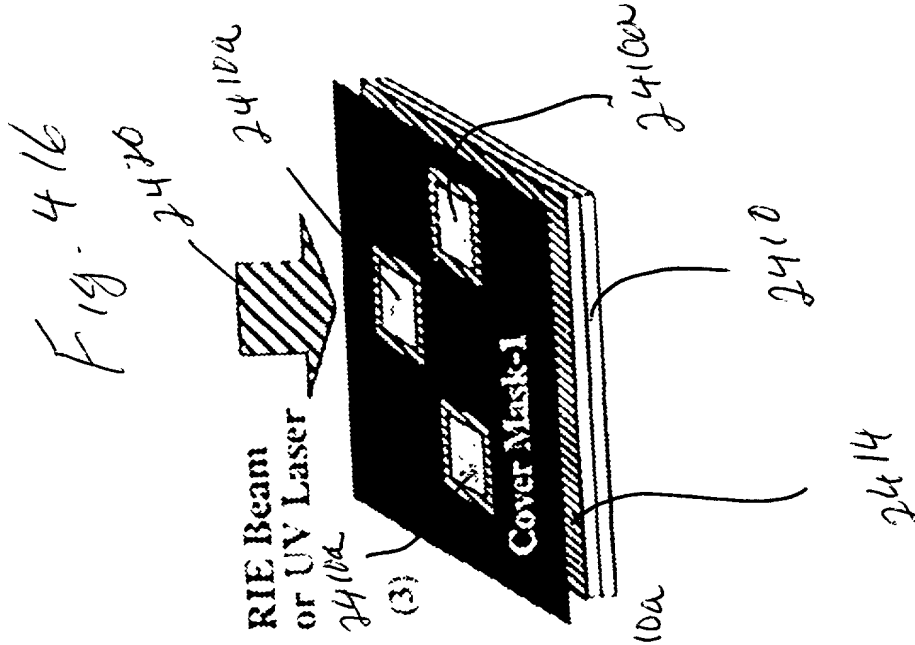
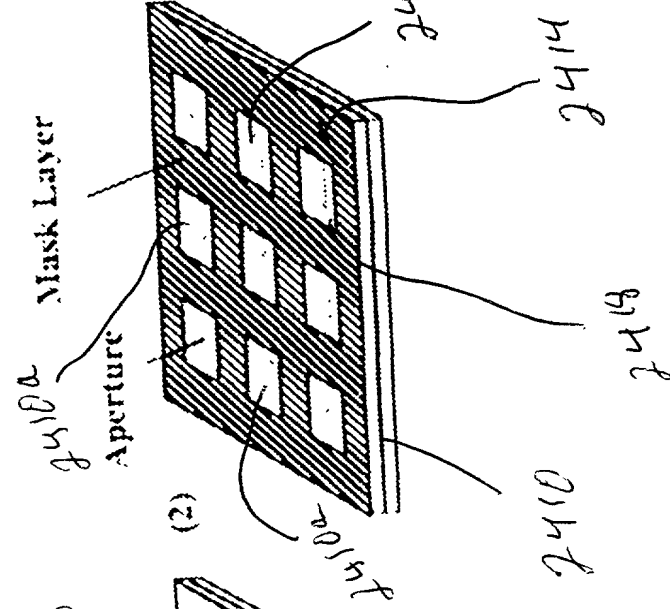
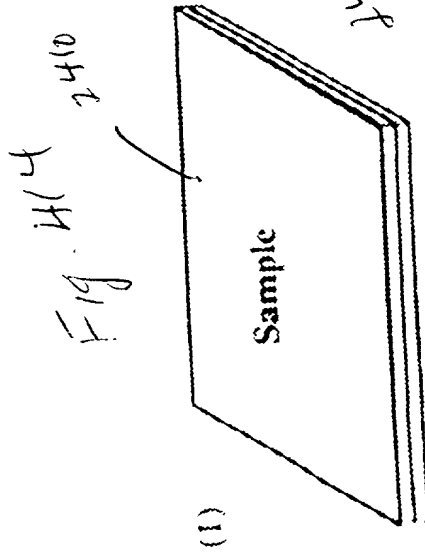
(a8) Core coat and CMP

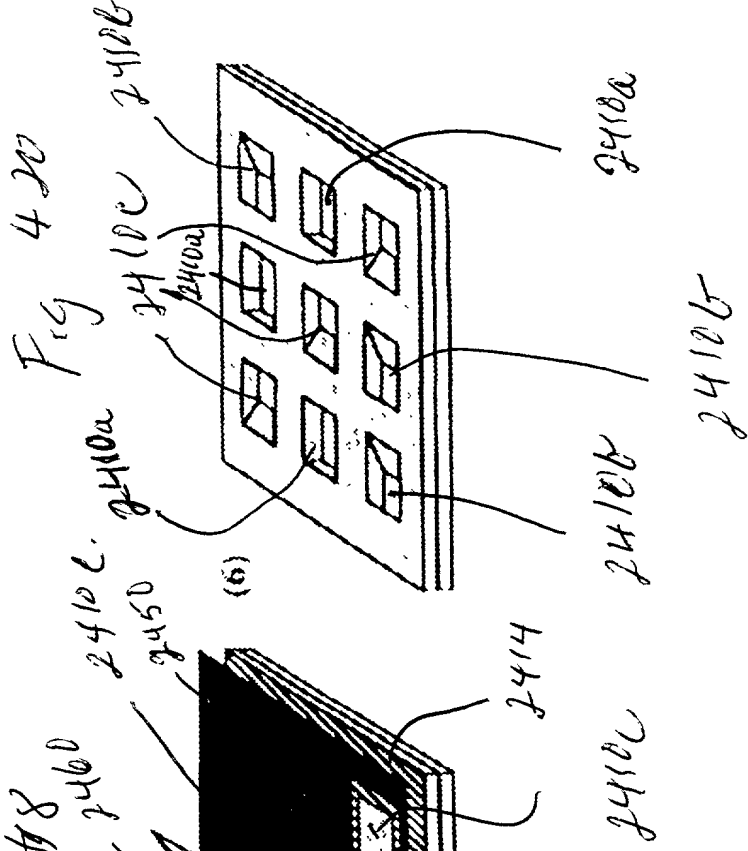
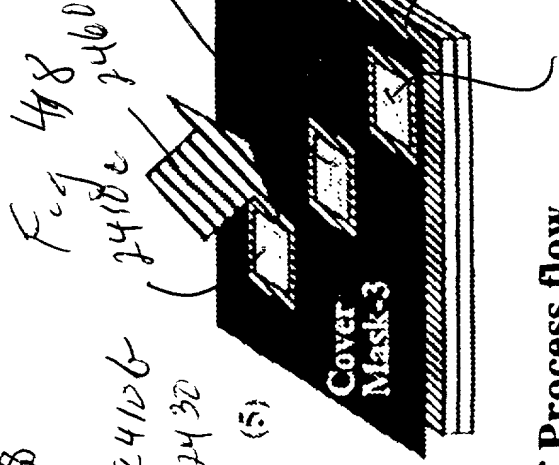
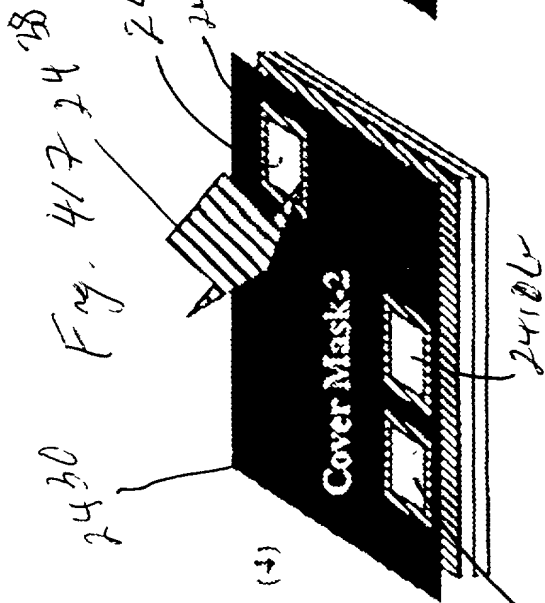


2365 2366

In the case of multi layer (a1, a5-a8) or (a5-a8) process is repeated on the (a8).

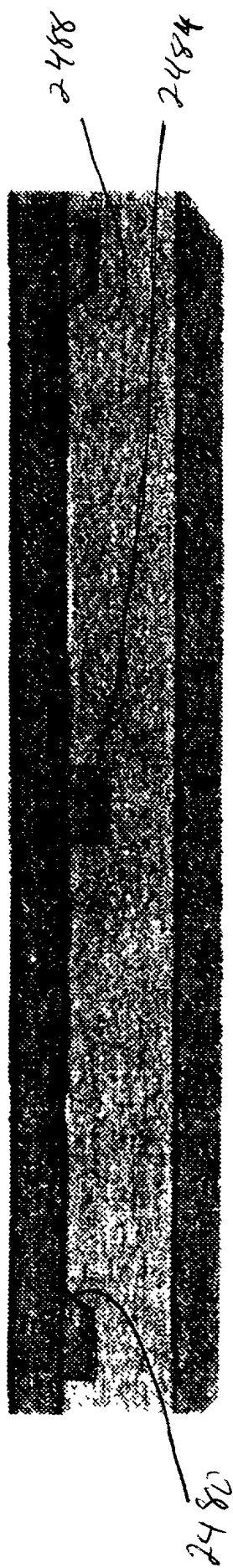
Fig. 17-2





(a) Conceptual illustration of Process flow

Fig. 4d1



(b) Trench wall formation of three different angles